

applied surface science

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and chemistry of surfaces and interfaces

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Master Index to Volumes 91-101



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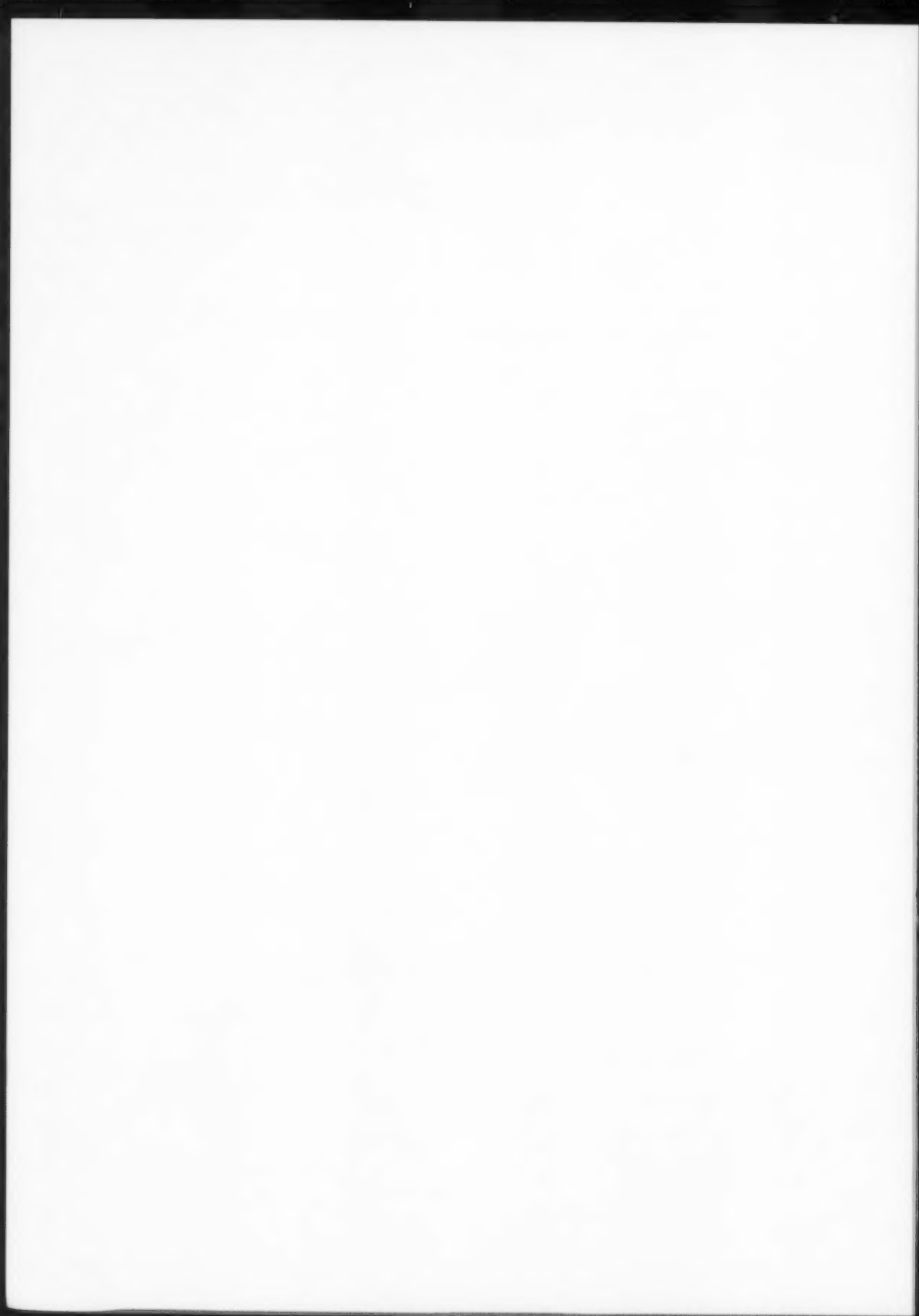
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MASTER INDEX

Volumes 91-101

Author index	1
Subject index	39
List of terms used in the subject index	134





ELSEVIER

Applied Surface Science 91–101 (1996) 1–38



Author index to volumes 91–101

- Abe, S., see Yea, B. 100/101 (1996) 365
Abend, G., see Hess, T.R. 94/95 (1996) 238
Abert, A., J.P. Contour, A. Défosses, D. Ravelosona, W. Schwegle and P. Ziemann, Critical thickness of YBaCuO (123) strained thin films and superlattices grown by pulsed laser deposition 96–98 (1996) 703
Acquaviva, S., see Berling, D. 96–98 (1996) 739
Adachi, H., see Endo, M. 94/95 (1996) 113
Adachi, H., see Satoh, H. 94/95 (1996) 247
Adachi, H., see Satoh, H. 100/101 (1996) 216
Adachi, H., see Endo, M. 100/101 (1996) 378
Adachi, M., see Uchida, H. 100/101 (1996) 399
Adamiec, M., see Zaborowski, M. 91 (1995) 246
Adamik, M., see Manaila, R. 91 (1995) 295
Aden, M. and E.W. Kreutz, Material removal and plasmadynamics during pulsed laser deposition by excimer and CO₂ laser radiation 96–98 (1996) 39
Aden, M., see Alunovic, M. 96–98 (1996) 222
Adsool, A.D., see Sharma, R.B. 94/95 (1996) 177
Affronte, M., see Gottlieb, U. 91 (1995) 82
Affronte, M., O. Laborde, U. Gottlieb, O. Thomas and R. Madar, Angular dependence of the magnetoresistance of TiSi₂ single crystals 91 (1995) 98
Afif, M., J.P. Girardeau-Montaut, C. Tomas, M. Romand, M. Charbonnier, N.S. Prakash, A. Perez, G. Marest and J.M. Frigerio, In situ surface cleaning of pure and implanted tungsten photocathodes by pulsed laser irradiation 96–98 (1996) 469
Afonso, C.N., see Gonzalo, J. 96–98 (1996) 693
Afonso, C.N., J.M. Ballesteros, J. Gonzalo, G.C. Righini and S. Pelli, Rare-earth doped glass waveguides prepared by pulsed laser deposition 96–98 (1996) 760
Aguar, R., F. Sánchez and M. Varela, Single crystal laser patterning for selective YBa₂Cu₃O_{7-x} growth 96–98 (1996) 405
Aguar, R., see Polo, M.C. 96–98 (1996) 870
Ahrens, C., D. Depta, F. Schithelm and S. Wilhelm, Electrical characterization of conductive and non-conductive barrier layers for Cu-metallization 91 (1995) 285
Aizawa, T., see Oyoshi, K. 100/101 (1996) 374
Akhsakhalyan, A.D., see Gorbunov, A.A. 96–98 (1996) 649
Akiya, S., see Homma, T. 100/101 (1996) 189
Al-Kassab, T., M.-P. Macht, V. Naundorf, H. Wollenberger, S. Chambrelaud, F. Danoix and D. Blavette, Characterization of sputter-deposited multilayers of Ni and Zr with APFIM/TAP 94/95 (1996) 306
Al-Wazzan, R.A., see Hendron, J.M. 96–98 (1996) 112
Al-Wazzan, R.A., J.M. Hendron and T. Morrow, Spatially and temporally resolved emission intensities and number densities in low temperature laser-induced plasmas in vacuum and in ambient gases 96–98 (1996) 170
Al-Wazzan, R.A., J.M. Hendron and T. Morrow, Line shape study of Ba ions in laser produced plasmas 99 (1996) 345
Alexandrescu, R., see Leggieri, G. 96–98 (1996) 866
Alfonso, J.E., M.J. Martín, J. Mendiola, K. Polgár and C. Zaldo, Pulsed laser deposition of sillenite films intended for photorefractive damage free waveguides 96–98 (1996) 791
Ali, S.T., S. Ghosh and D.N. Bose, Ruthenium and sulphide passivation of GaAs 93 (1996) 37
Aliouchouche, A., see Débarre, D. 96–98 (1996) 453
Allegrini, M., see Fuso, F. 96–98 (1996) 181
Allen, G.C. and K.R. Hallam, Characterisation of the spinels M₂Co_{1-x}Fe₂O₄ (M = Mn, Fe or Ni) using X-ray photoelectron spectroscopy 93 (1996) 25
Alnot, M., see Fusy, J. 93 (1996) 211
Altman, M.S., see Luo, E.Z. 92 (1996) 331
Alunovic, M., H. Stamm, M. Aden and E.W. Kreutz, Optical and particle properties of PLD vapour/plasmas of ceramics 96–98 (1996) 222
Ambri, M., see Ramos, S.M.M. 93 (1996) 191
Amodéo, A., see Chiarello, G. 99 (1996) 15
Amodéo, A., see Amoroso, S. 96–98 (1996) 175
Amoroso, S., A. Amodéo, V. Berardi, R. Bruzzese, N. Spinelli and R. Velotta, Laser produced plasmas in high fluence ablation of metallic surfaces probed by time-of-flight mass spectrometry 96–98 (1996) 175

- An, C.W., see Mertin, M. 96-98 (1996) 842
- Anderson, I.M., see Miller, M.K. 94/95 (1996) 288
- Anderson, I.M., see Miller, M.K. 94/95 (1996) 391
- Anderson, J., see Boardman, A.D. 96-98 (1996) 55
- Anderson, J.R., see Lu, C.R. 92 (1996) 404
- Anderson, J.R., see Lu, C.R. 92 (1996) 543
- Anderson, J.R., see Jen, J.Y. 92 (1996) 547
- Anderson, W.A., see Chang, L.H. 92 (1996) 52
- Ando, Y., see Yamada, T. 100/101 (1996) 287
- Andrei, A., see Verardi, P. 96-98 (1996) 827
- Andr  n, H.-O., see Ivchenko, V.A. 94/95 (1996) 267
- Andr  n, H.-O., see Lundin, L. 94/95 (1996) 320
- Andr  n, H.-O., see Zackrisson, J. 94/95 (1996) 351
- Andr  n, H.-O., see Kvist, A. 94/95 (1996) 356
- Angleraud, B., C. Girault, C. Champeaux, F. Garrelie, C. Germain and A. Cathelinot, Study of the expansion of the laser ablation plume above a boron nitride target 96-98 (1996) 117
- Anisimov, S.I., B.S. Luk'yanchuk and A. Luches, An analytical model for three-dimensional laser plume expansion into vacuum in hydrodynamic regime 96-98 (1996) 24
- Antoni, F., C. Fuchs and E. Fogarassy, Analytical description of the film thickness distribution obtained by the pulsed laser ablation of a monoatomic target: application to silicon and germanium 96-98 (1996) 50
- Aochi, H., see K  cher, P. 91 (1995) 359
- Aoki, K., see Togashi, H. 96-98 (1996) 267
- Aoki, T., M. Morita, S. Wickramanayaka, Y. Nakanishi and Y. Hatanaka, Growth of ZnSe thin films by radical assisted MOCVD method 92 (1996) 132
- Aoki, T., see Hatanaka, Y. 100/101 (1996) 621
- Aoki, Y., see Maruyama, K. 96-98 (1996) 764
- Aouadi, M.S., P.C. Wong and K.A.R. Mitchell, XPS study of carbon/inconel bilayers as a function of substrate bias 99 (1996) 319
- Aoyama, T., M. Tanemura and F. Okuyama, Angular distribution of particles sputtered from GaAs by Ar⁺ and Xe⁺ ion bombardment 100/101 (1996) 351
- Arafune, R., see Sakamoto, K. 100/101 (1996) 124
- Arai, M., M. Fukushima and Y. Nishiyama, Interrupted-temperature programmed desorption of hydrogen over silica-supported platinum catalysts: the distribution of activation energy of desorption and the phenomena of spillover and reverse spillover of hydrogen 99 (1996) 145
- Arakawa, T., see Iwaso, M. 100/101 (1996) 147
- Arimondo, E., see Fusco, F. 96-98 (1996) 181
- Arnold, N., see Kirichenko, N. 93 (1996) 359
- Arnold, W., see Hoffmann, A. 96-98 (1996) 71
- Asada, H., see Kawano, H. 100/101 (1996) 174
- Asahi, H., see Kim, J.H. 92 (1996) 566
- Asakura, K., see Chun, W.-J. 100/101 (1996) 143
- Asami, K., see Kim, J.H. 92 (1996) 566
- Asikainen, T., M. Ritala, M. Leskel  , T. Prohaska, G. Friedbacher and M. Grasserbauer, AFM and STM studies on In₂O₃ and ITO thin films deposited by atomic layer epitaxy 99 (1996) 91
- Asskali, A., see Reniers, F. 92 (1996) 35
- Atamny, F., see Grunwaldt, J.-D. 99 (1996) 353
- Athenstaedt, W. and M. Leisch, The segregation behaviour of a Pt₉₀Rh₁₀ alloy studied with a three-dimensional atom-probe 94/95 (1996) 403
- Aubel, D., L. Kubler, J.L. Bischoff, L. Simon and D. Bolmont, X-ray photoelectron diffraction investigation of Ge segregation and film morphology during first stage heteroepitaxy of Si on Ge(001) 99 (1996) 169
- Auger, P., see Bigot, A. 94/95 (1996) 261
- Augereau, F., B. Cros and J.P. Marco, Surface study of cross-linking gradients in photopolymers by acoustic microscopy 99 (1996) 293
- Augur, R.A., see Kordic, S. 91 (1995) 197
- Auriel, C., see Martinez, H. 93 (1996) 231
- Autric, M., see Grangeon, F. 96-98 (1996) 186
- Autric, M., see Movtchan, I.A. 96-98 (1996) 251
- Autric, M., see Nicolas, G. 96-98 (1996) 296
- Awaji, N., see Sugita, Y. 100/101 (1996) 268
- Ayame, A., see Tomizuka, H. 100/101 (1996) 243
- Baba, Y., see Yamamoto, H. 100/101 (1996) 333
- Babu, S.S., S.A. David and M.K. Miller, Microstructural development in PWA-1480 electron beam welds - an atom probe field ion microscopy study 94/95 (1996) 280
- Bacchetta, M., C. Zeccherini and L. Zanotti, Inter-metal dielectric planarization process for 0.35 µm multilevel interconnection devices 91 (1995) 367
- Bachli, A., see Dutron, A.-M. 91 (1995) 277
- Badaye, M., see Pindoria, G. 100/101 (1996) 347
- Baeri, P., see Reitano, R. 96-98 (1996) 302
- Baiker, A., see Grunwaldt, J.-D. 99 (1996) 353
- Bajikar, S.S., T.F. Kelly and P.P. Camus, Electrostatic analysis of local-electrode atom probes 94/95 (1996) 464
- Bakhtizin, R.Z., J. Kishimoto, T. Hashizume and T. Sakurai, STM study of Sr adsorption on Si(100) surface 94/95 (1996) 478
- Ballesteros, J.M., see Afonso, C.N. 96-98 (1996) 760
- Bancroft, G.M., see Kasrai, M. 99 (1996) 303
- Banerjee, S., M.K. Sanyal and A. Datta, A simulation study of multi-atom tips and estimation of resolution in atomic force microscopy 99 (1996) 255
- Baptista, J.L., see Gomes, M.J.M. 96-98 (1996) 779
- B  r, E. and J. Lorenz, 3D simulation of tungsten low-pressure chemical vapor deposition in contact holes 91 (1995) 321

- Baraldi, A., L. Gregoratti, G. Comelli, V.R. Dhanak, M. Kiskinova and R. Rosei, CO adsorption and CO oxidation on Rh(100) 99 (1996) 1
- Baranauskas, V., see Kathia de-Mesquita Braga, A. 93 (1996) 197
- Barbashev, E.A., see Skurat, V.E. 92 (1996) 441
- Barberi, R., see Chiarello, G. 99 (1996) 15
- Barborica, A., see Leggieri, G. 96-98 (1996) 866
- Barcz, A., see Zaborowski, M. 91 (1995) 239
- Barcz, A., see Zaborowski, M. 91 (1995) 246
- Bardwell, J.A., see Kasrai, M. 99 (1996) 303
- Barna, P.B., see Manaila, R. 91 (1995) 295
- Barrett, J., see Patterson, J.C. 91 (1995) 124
- Barthe, F., see Moison, J.M. 92 (1996) 526
- Barthe, M.F., see Vivet, L. 96-98 (1996) 238
- Barthe, M.F., C. Perrin, L. Vivet, B. Dubreuil and T. Gibert, Laser induced nitridation of Ga on GaAs surfaces 96-98 (1996) 359
- Barthés-Labrousse, M.G., see Marsh, J. 99 (1996) 335
- Bartoš, J., see Pinčík, E. 93 (1996) 119
- Bas, P., A. Bostel, G. Grancher, B. Deconihout and D. Blavette, Analytic treatment of charge cloud overlaps: an improvement of the tomographic atom probe efficiency 94/95 (1996) 442
- Battaglia, S., Surface phases analysis by grazing incidence of X-rays in a Bragg-Brentano diffractometer 93 (1996) 349
- Bauer, E., LEEM studies of the early stages of epitaxial growth 92 (1996) 20
- Bäuerle, D., see Proyer, S. 96-98 (1996) 668
- Bäuerle, D., see Li, S.T. 96-98 (1996) 713
- Bäuerle, D., see Ritzler, A. 96-98 (1996) 721
- Bäuerle, D., see Stangl, E. 96-98 (1996) 731
- Baumann, J., see Kaufmann, C. 91 (1995) 291
- Bayrachny, B.I., see Skatkov, L.I. 99 (1996) 367
- Beauvois, S., see Viville, P. 96-98 (1996) 558
- Beben, J., see Suchorski, Yu. 94/95 (1996) 207
- Beche, E., see Berger, F. 93 (1996) 9
- Becker, W., see Geiger, M. 96-98 (1996) 309
- Beechinor, J.T., see O'Reilly, M. 91 (1995) 152
- Behner, H. and R. Rupp, Surface composition of CVD-grown α -SiC layers - an XPS and LEED study 99 (1996) 27
- Belevsky, V.P., see Gusev, I.V. 91 (1995) 182
- Beloglazov, A.A., see Ksenevich, T.I. 92 (1996) 426
- Beloglazov, A.A., see Uglov, S.A. 92 (1996) 656
- Belouet, C., Thin film growth by the pulsed laser assisted deposition technique 96-98 (1996) 630
- Belu-Marian, A., M.D. Serbanescu, R. Manaila and A. Devenyi, Ni silicides formation and properties in RF sputtered $\text{Ni}_{100-x}\text{Si}_x$ thin films 91 (1995) 63
- Belyavsky, B.A., see Zhirnov, V.V. 94/95 (1996) 144
- Bender, H., see Donaton, R.A. 91 (1995) 77
- Bennett, L.S., see Lippert, T. 96-98 (1996) 601
- Bentley, J., see Miller, M.K. 94/95 (1996) 391
- Berardi, V., see Amoroso, S. 96-98 (1996) 175
- Berbezier, I., see Derrien, J. 92 (1996) 311
- Berger, F., E. Beche, R. Berjoan, D. Klein and A. Chambaudet, An XPS and FTIR study of SO_2 adsorption on SnO_2 surfaces 93 (1996) 9
- Bergmann, H.W., Excimer laser induced surface modifications and matter interaction using double-pulse-technique (DPT) 96-98 (1996) 287
- Bergt, M., see Götz, T. 96-98 (1996) 280
- Berjoan, R., see Berger, F. 93 (1996) 9
- Berling, D., A. Del Vecchio, S. Acquaviva, D. Bolmont, G. Leggieri, B. Loegel, M. Luisa De Giorgi, A. Luches, A. Mehdaoui and L. Tapfer, Reactive laser deposition of high quality YBaCuO and ErBaCuO films 96-98 (1996) 739
- Bernard, C., see Pons, M. 91 (1995) 34
- Bernard, C., see Bourhila, N. 91 (1995) 175
- Bernard, C., see Dutron, A.-M. 91 (1995) 277
- Bertóti, I., see Szőrényi, T. 96-98 (1996) 363
- Bertrand, P., see Weng, L.T. 99 (1996) 185
- Bertz, A., T. Werner, N. Hille and T. Gessner, Effects of the biasing frequency on RIE of Cu in a Cl_2 -based discharge 91 (1995) 147
- Beserman, R., see Chergui, A. 96-98 (1996) 874
- Betz, G., see Seifert, N. 96-98 (1996) 33
- Beyer, C., see Stegemann, K.-H. 91 (1995) 308
- Bhatnagar, M.C., see Sharma, R.K. 92 (1996) 647
- Bigl, F., see Zimmer, K. 96-98 (1996) 425
- Bigot, A., F. Danoix, P. Auger, D. Blavette and A. Menand, 3D reconstruction and analysis of GP zones in Al-1.7Cu (at%): a tomographic atom probe investigation 94/95 (1996) 261
- Bijkerk, F., see Voorma, H.-J. 93 (1996) 221
- Bilger, G., see Wanka, H.N. 93 (1996) 339
- Binau, K., see Guo, Q. 92 (1996) 513
- Biro, D., see Manaila, R. 91 (1995) 295
- Bischoff, J.L., see Aubel, D. 99 (1996) 169
- Bischoff, L., see Teichert, J. 91 (1995) 44
- Björkqvist, M., see Janin, E. 99 (1996) 371
- Bjormander, C., see Tyunina, M. 96-98 (1996) 831
- Blank, D.H.A., A.J.H.M. Rijnders, F.J.G. Roesthuis, G. den Ouden and H. Rogalla, Improved properties of Pulsed Laser Deposited YBaCuO on NdGaO_3 using CeO_2 template layers 96-98 (1996) 685
- Blanquet, E., see Dutron, A.-M. 91 (1995) 277
- Blaschke, H., see Welsch, E. 96-98 (1996) 393
- Blatter, A., see Pimenov, S.M. 92 (1996) 106
- Blavette, D., see Bigot, A. 94/95 (1996) 261
- Blavette, D., see Schmuck, C. 94/95 (1996) 273
- Blavette, D., see Al-Kassab, T. 94/95 (1996) 306
- Blavette, D., see Thuvander, M. 94/95 (1996) 343
- Blavette, D., see Bas, P. 94/95 (1996) 442
- Block, J.H., see Reckzügel, M.C. 94/95 (1996) 194
- Block, J.H., see Medvedev, V.K. 94/95 (1996) 200

- Block, J.H., see Suchorski, Yu. 94/95 (1996) 207
 Block, J.H., see Reckzügel, M.C. 94/95 (1996) 212
 Block, J.H., see Suchorski, Yu. 94/95 (1996) 217
 Block, J.H., see Hess, T.R. 94/95 (1996) 238
 Block, J.H., see Kawada, H. 100/101 (1996) 587
 Blom, P.W.M., see Cillessen, J.F.M. 96-98 (1996) 744
 Boardman, A.D., B. Cresswell and J. Anderson, An analytical model for the laser ablation of materials 96-98 (1996) 55
 Bocelli, S., G. Guizzetti, F. Marabelli, G. Thungström and C.S. Petersson, Experimental identification of the optical phonon of CoSi_2 in the infrared 91 (1995) 30
 Bodnar, S., see Regolini, J.L. 100/101 (1996) 566
 Bögli, U., see Pimenov, S.M. 92 (1996) 106
 Bogonin, I.A., A.L. Karuzskii, N.N. Melnik, Yu.A. Mityagin, V.N. Murzin, A.A. Orlikovsky, A.V. Perestoronin, P.P. Sverbil, S.D. Tkachenko, A.V. Tsikunov, N.A. Volchkov and B.G. Zhurkin, Diamond-like coating prepared by pulsed laser sputtering of graphite in a high-vacuum environment 92 (1996) 43
 Boher, P., J.L. Stehle, M. Stehle and B. Godard, Single shot excimer laser annealing of amorphous silicon for AMLCD 96-98 (1996) 376
 Bohnke, O., G. Frand, M. Fromm, J. Weber and O. Greim, Depth profiling of W, O and H in tungsten trioxide thin films using RBS and ERDA techniques 93 (1996) 45
 Bohr, M.T., Technology development strategies for the 21st century 100/101 (1996) 534
 Bolmont, D., see Berling, D. 96-98 (1996) 739
 Bolmont, D., see Aubel, D. 99 (1996) 169
 Bonardi, N., see Ramos, S.M.M. 93 (1996) 191
 Bonin, B., see Maïssa, S. 94/95 (1996) 136
 Boquillon, J.P., see Oltra, R. 96-98 (1996) 484
 Bor, Zs., see Hopp, B. 96-98 (1996) 611
 Borkowska, R., M. Siekierski and J. Przyłuski, An electrochemical impedance spectroscopy study of thin polymeric films 92 (1996) 447
 Bormatova, L., see Zhimov, V.V. 94/95 (1996) 144
 Borsella, E., see Giorgi, R. 93 (1996) 101
 Borz, M., see Proyer, S. 96-98 (1996) 668
 Bose, D.N., see Ali, S.T. 93 (1996) 37
 Bostel, A., see Stiller, K. 94/95 (1996) 326
 Bostel, A., see Deconihout, B. 94/95 (1996) 422
 Bostel, A., see Bas, P. 94/95 (1996) 442
 Botti, S., see Giorgi, R. 93 (1996) 101
 Bouet, M., see Deconihout, B. 94/95 (1996) 422
 Boulmer, J., see Débarre, D. 96-98 (1996) 453
 Bourguignon, B., see Débarre, D. 96-98 (1996) 453
 Bourhila, N., N. Thomas, J. Palleau, J. Torres, C. Bernard and R. Madar, Thermodynamic and experimental study of Cu-LPCVD by reduction of copper chloride 91 (1995) 175
 Bouziane, K., see Mamor, M. 91 (1995) 342
 Boyd, I.W., see Tyrrell, G.C. 96-98 (1996) 227
 Boyd, I.W., see Zhang, J.-Y. 96-98 (1996) 399
 Boyd, I.W., see Tyrrell, G.C. 96-98 (1996) 769
 Boyd, I.W., see Coccia, L.G. 96-98 (1996) 795
 Boyd, I.W., see King, S.L. 96-98 (1996) 811
 Boyen, H.-G., see Kilper, R. 91 (1995) 93
 Bradley, R.A., see Hess, W.P. 96-98 (1996) 321
 Braud, F., see Mouche, M.-J. 91 (1995) 129
 Braud, F., J. Torres, J. Palleau, J.-L. Mermet and M.-J. Mouche, Ti-diffusion barrier in Cu-based metallization 91 (1995) 251
 Brédas, J.L., see Viville, P. 96-98 (1996) 558
 Brenier, R., see Ramos, S.M.M. 93 (1996) 191
 Breternitz, V., see Nennewitz, O. 91 (1995) 347
 Breza, J., see Liday, J. 99 (1996) 9
 Brijis, B., see Donaton, R.A. 91 (1995) 77
 Broulik, U., see Reisse, G. 96-98 (1996) 752
 Brown, J.R., see Sastri, V.S. 93 (1996) 31
 Brown, N.M.D. and Z.H. Liu, The etching of natural alpha-recoil tracks in mica with an argon RF-plasma discharge and their imaging via atomic force microscopy 93 (1996) 89
 Brown, W.L., see Weber, A. 91 (1995) 314
 Bruckbauer, A., see Futamata, M. 100/101 (1996) 60
 Brunel, M., see Ramos, S.M.M. 93 (1996) 191
 Brunner, R., see Pinčik, E. 93 (1996) 119
 Brunner, R.W., see Kasrai, M. 99 (1996) 303
 Bruzzese, R., see Amoroso, S. 96-98 (1996) 175
 Bryantseva, T.A., D.V. Lioubtchenko and V.V. Lopatin, Ga migration process in Au film on (100) GaAs under temperature treatment in vacuum 100/101 (1996) 169
 Budai, J.D., see Norton, D.P. 96-98 (1996) 672
 Budin, J.P., see Débarre, D. 96-98 (1996) 453
 Bugiel, E., see Zeindl, H.P. 92 (1996) 552
 Bulgakov, A.V., M.R. Predtechensky and A.P. Mayorov, Transport of neutral atoms, monoxides and clusters in the plume produced by laser ablation of $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ in oxygen environment 96-98 (1996) 159
 Burger, J., see Pimenov, S.M. 92 (1996) 106
 Burmester, S., see Metev, S. 96-98 (1996) 122
 Busch, E., see Haneman, D. 92 (1996) 484
 Butcher, K.S.A., see Zhou, B. 100/101 (1996) 643
 Caetano, M., see Mao, X. 96-98 (1996) 126
 Caetano, M., see Russo, R.E. 96-98 (1996) 144
 Cagan, V., see Lisfi, A. 96-98 (1996) 66
 Cagan, V., see Guyot, M. 96-98 (1996) 802
 Cai, Q., see Luo, E.Z. 92 (1996) 331
 Calegari, C., see Sanguinetti, S. 91 (1995) 103
 Calvo, B., see Gobernado-Mitre, I. 96-98 (1996) 474
 Campbell, E.E.B., see Rosenfeld, A. 96-98 (1996) 439
 Camus, P.P., see Larson, D.J. 94/95 (1996) 434

- Camus, P.P., see Bajikar, S.S. 94/95 (1996) 464
- Canut, B., see Ramos, S.M.M. 93 (1996) 191
- Caputi, L.S., see Chiarello, G. 99 (1996) 15
- Caron, M., see Lecours, A. 96-98 (1996) 341
- Caron, P., see Schmuck, C. 94/95 (1996) 273
- Cassuto, A., The adsorption and condensation of $\text{Hg}(\text{CH}_3)_2$ on Pt(111) at 95 and 310 K: an UPS study 93 (1996) 17
- Cassuto, A., see Colin, L. 99 (1996) 245
- Catherinot, A., see Angleraud, B. 96-98 (1996) 117
- Catherinot, A., see Champeaux, C. 96-98 (1996) 775
- Catherinot, A., see Garapon, C. 96-98 (1996) 836
- Caudano, R., see Girardeaux, C. 96-98 (1996) 586
- Cauich, W., see Quintana, P. 99 (1996) 325
- Caymax, M., see Donaton, R.A. 91 (1995) 77
- Cerezo, A., see Sijbrandij, S.J. 94/95 (1996) 428
- Cerezo, A., J.M. Hyde, S.J. Sijbrandij and G.D.W. Smith, Data analysis in the optical PoSAP 94/95 (1996) 457
- Cerofolini, G.F., G. La Bruna and L. Meda, Gas-phase room-temperature oxidation of (100) silicon 93 (1996) 255
- Cesile, M.C., see Giorgi, R. 93 (1996) 101
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- Chakoumakos, B.C., see Norton, D.P. 96-98 (1996) 672
- Chambaudet, A., see Berger, F. 93 (1996) 9
- Chambrelaud, S., see Al-Kassab, T. 94/95 (1996) 306
- Chambrelaud, S., see Duval, S. 94/95 (1996) 449
- Champeaux, C., see Angleraud, B. 96-98 (1996) 117
- Champeaux, C., P. Marchet and A. Catherinot, Epitaxial ferroelectric PZT and BST thin films by pulsed UV laser deposition 96-98 (1996) 775
- Champeaux, C., see Garapon, C. 96-98 (1996) 836
- Chan, D.K., D.N. Seidman and K.L. Merkle, The chemistry and structure of {222} CdO/Ag heterophase interfaces on an atomic scale 94/95 (1996) 409
- Chan, W.-T., see Mao, X. 96-98 (1996) 126
- Chang, C.-Y., see Chang, T.-C. 92 (1996) 119
- Chang, C.-Y., see Chang, T.-C. 92 (1996) 571
- Chang, C.L., see Lu, C.R. 92 (1996) 404
- Chang, C.P., see Huang, J.C.A. 92 (1996) 480
- Chang, C.S., see Tsong, T.T. 94/95 (1996) 472
- Chang, G.-W., see Tseng, B.-H. 92 (1996) 227
- Chang, L.H. and W.A. Anderson, Stability of BaTiO_3 thin films on Si 92 (1996) 52
- Chang, S.-Z., T.-C. Chang and S.-C. Lee, A method to tune the island size and improve the uniformity for the in situ formation of InGaAs quantum dots on GaAs 92 (1996) 70
- Chang, S.J., see Lin, C.T. 92 (1996) 193
- Chang, T.-C., see Chang, S.-Z. 92 (1996) 70
- Chang, T.-C., W.-K. Yeh, C.-Y. Chang, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei, Disordered Si/SiGe superlattices grown by ultrahigh vacuum chemical vapor deposition 92 (1996) 119
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- Chang, W.-D., see Ching, K.-M. 92 (1996) 471
- Chapljuk, V.I., see Gusev, I.V. 91 (1995) 182
- Charatan, R.M., see Weber, A. 91 (1995) 314
- Charbonnier, F., Developing and using the field emitter as a high intensity electron source 94/95 (1996) 26
- Charbonnier, M., see Afif, M. 96-98 (1996) 469
- Chater, R.J., see Coccia, L.G. 96-98 (1996) 795
- Chen, B. and D. Haneman, Theory of dipole generation at cleaved semiconductor surfaces 92 (1996) 345
- Chen, B.-Y., J.-R. Chen, F.-L. Jenq and C.-S. Hong, A theoretical analysis of temperature dependence on hydrogenated amorphous silicon thin-film transistors with the consideration of resistance of the a-Si:H film layer as a function of temperature 100/101 (1996) 601
- Chen, C.H., see Chen, W.D. 100/101 (1996) 530
- Chen, C.L., T.T. Tsong and T.E. Mitchell, Surface diffusion and surface atomic roughness on Ir(001) surface and terraces 94/95 (1996) 224
- Chen, C.R. and L.J. Chen, Structural evolution and atomic structure of ultrahigh vacuum deposited Au thin films on silicon at low temperatures 92 (1996) 507
- Chen, C.S., see Young, T.F. 92 (1996) 57
- Chen, C.T., see Lee, C.H. 92 (1996) 124
- Chen, F., see Horng, R.H. 92 (1996) 387
- Chen, J.-R., see Chen, B.-Y. 100/101 (1996) 601
- Chen, K.R., see Leboeuf, J.N. 96-98 (1996) 14
- Chen, K.R., J.N. Leboeuf, R.F. Wood, D.B. Geohegan, J.M. Donato, C.L. Liu and A.A. Puretzky, Laser-solid interaction and dynamics of laser-ablated materials 96-98 (1996) 45
- Chen, L.J., see Liu, C.S. 92 (1996) 84
- Chen, L.J., see Lin, J.H. 92 (1996) 340
- Chen, L.J., see Chen, C.R. 92 (1996) 507
- Chen, P.-C., see Hwang, H.-L. 92 (1996) 180
- Chen, P.-L., M.-Y. Tsai and J.-S. Kao, Low

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- Chen, Q., D. Gu, F. Gan, L. Xu and M. Li, Scanning tunneling microscopy observations of recorded organic thin films 93 (1996) 151
- Chen, W.D. and Y.D. Cui, Determination of $\text{Al}_2\text{Ga}_{1-x}\text{As}$ Auger sensitivity factors 100/101 (1996) 156
- Chen, W.D., X.L. Xie, Y.D. Cui, C.H. Chen and C.C. Hsu, Microstructure studies of PdGe/Ge ohmic contacts to n-type GaAs formed by rapid thermal annealing 100/101 (1996) 530
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- Chen, W.S., see Lin, C.C. 92 (1996) 660
- Chen, Y., see Ding, D. 96-98 (1996) 581
- Chen, Y., see Ji, W. 99 (1996) 151
- Chen Chen-Jia, see Geddo, M. 93 (1996) 267
- Cheng, C. and K. Kunc, First-principles calculations of Ga adatom structures for Ge(111) and Si(111) surfaces 92 (1996) 496
- Cheng, H.-C., see Wang, F.-S. 92 (1996) 372
- Cheng, H.-F., Structural and electrical properties of excimer laser deposited PLZT thin films 92 (1996) 378
- Cheng, H.F., see Chuang, F.Y. 92 (1996) 452
- Cheng, H.F., see Huang, C.S. 96-98 (1996) 735
- Cheremskoy, P.G., see Skatkov, L.I. 99 (1996) 367
- Chergui, A., J.L. Deiss, J.B. Grun, J.L. Loison, M. Robino and R. Beserman, Structural and optical characteristics of pulsed laser deposited ZnSe epilayers 96-98 (1996) 874
- Chew, A., see Sykes, D.E. 100/101 (1996) 77
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- Chin, T.-S., see Ching, K.-M. 92 (1996) 471
- Chin, T.-S., see Chang, W.-D. 92 (1996) 475
- Ching, K.-M., W.-D. Chang and T.-S. Chin, Effect of substrate-film interface on magnetic properties of Mn_xN films 92 (1996) 471
- Chiou, B.-S., see Wu, W.-F. 99 (1996) 237
- Chiwaki, M., see Ohdaira, T. 100/101 (1996) 73
- Chiwaki, M., see Suzuki, R. 100/101 (1996) 297
- Cho, H.-C., Ge deposition from digermane on the $\text{Si}(100)-(2 \times 1)$ surface 92 (1996) 128
- Choi, J.-G. and L.T. Thompson, XPS study of as-prepared and reduced molybdenum oxides 93 (1996) 143
- Choi, W.B., see Zhimov, V.V. 94/95 (1996) 123
- Chuang, F.Y., C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin, Electrical properties of laser deposited $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ films on silicon wafers 92 (1996) 452
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- Chung, B.C., see Huang, C.S. 96-98 (1996) 735
- Chung, W.F., see Luo, E.Z. 92 (1996) 331
- Chyi, J.-I., see Lee, W.C. 92 (1996) 66
- Cillessen, J.F.M., R.M. Wolf, J.B. Giesbers, P.W.M. Blom, K.-O. Grosse-Holz and E. Pastoor, Growth, structuring and characterisation of all-oxide thin film devices prepared by pulsed laser deposition 96-98 (1996) 744
- Cillessen, J.F.M., see Grosse-Holz, K.-O. 96-98 (1996) 784
- Ciureanu, P., see Lecours, A. 96-98 (1996) 341
- Clères, L., see Serra, P. 96-98 (1996) 216
- Clères, L., see Polo, M.C. 96-98 (1996) 870
- Coccia, L.G., see Tyrrell, G.C. 96-98 (1996) 227
- Coccia, L.G., see Tyrrell, G.C. 96-98 (1996) 769
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- Cocke, D.L., see Hess, T.R. 94/95 (1996) 238
- Colavita, E., see Chiarello, G. 99 (1996) 15
- Colin, L., A. Cassuto, J.J. Ehrhardt, M.F. Ruiz-Lopez and D. Jamois, Adsorption and decomposition of hexamethyldisiloxane on platinum: an XPS, UPS and TDS study 99 (1996) 245
- Coluzza, C., Ultra accurate measurements of interface parameters with free-electron laser 92 (1996) 267
- Comelli, G., see Baraldi, A. 99 (1996) 1
- Contour, J.P., see Abert, A. 96-98 (1996) 703
- Cordier, P., see Dauscher, A. 96-98 (1996) 410
- Corni, F., C. Nobili, G. Ottaviani, R. Tonini, B. Grignaffini Gregorio and G. Queirolo, Metallurgical and electrical investigation of $\text{Pt}_5\text{Ni}_{95}$ /silicon interactions 91 (1995) 107
- Cossy-Favre, A., see Kilper, R. 91 (1995) 93
- Cox, N., see Numajiri, K. 100/101 (1996) 541
- Craciun, S., see Manaila, R. 91 (1995) 295
- Cranton, W.M., P.H. Key, D. Sands, C.B. Thomas and F.X. Wagner, XeCl laser ablation of thin film ZnS 96-98 (1996) 501
- Crean, G.M., see Patterson, J.C. 91 (1995) 124

- Crean, G.M., see O'Reilly, M. 91 (1995) 152
- Crecelius, G., K. Radermacher, Ch. Dieker and S. Mesters, Beam induced phase transformations and self annealing in as-implanted iron silicides 91 (1995) 50
- Cresswell, B., see Boardman, A.D. 96-98 (1996) 55
- Crisafulli, C., see Scirè, S. 93 (1996) 309
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- Cros, B., see Augereau, F. 99 (1996) 293
- Cruz, F., see Oltra, R. 96-98 (1996) 484
- Csete, M., see Hopp, B. 96-98 (1996) 611
- Cui, Y.D., see Chen, W.D. 100/101 (1996) 156
- Cui, Y.D., see Chen, W.D. 100/101 (1996) 530
- Cui, Y.D., see Chen, W.D. 100/101 (1996) 592
- Cuomo, J.J., see Zhimov, V.V. 94/95 (1996) 123
- Currie, J.F., see Lecours, A. 96-98 (1996) 341
- Currie, J.F., see Izquierdo, R. 96-98 (1996) 855
- Cuthbertson, A., see Stevens, R. 91 (1995) 208
- Czanderna, A.W., see Jung, D.R. 99 (1996) 161
- Czuba, P., see Szymonski, M. 100/101 (1996) 102
- Dacal, L.C.O., see Mollicone, M.M. 94/95 (1996) 68
- Dai, B.-T., see Liu, C.-W. 92 (1996) 176
- Dam, B., J.H. Rector, J. Johansson, S. Kars and R. Griessen, Stoichiometric transfer of complex oxides by pulsed laser deposition 96-98 (1996) 679
- Damen, E.P.N., see Fransen, M.J. 94/95 (1996) 107
- Danoix, F., see Bigot, A. 94/95 (1996) 261
- Danoix, F., see Schmuck, C. 94/95 (1996) 273
- Danoix, F., see Al-Kassab, T. 94/95 (1996) 306
- Danoix, F., see Stiller, K. 94/95 (1996) 326
- Datta, A., see Banerjee, S. 99 (1996) 255
- Dauscher, A., V. Fereggotto, P. Cordier and A. Thomy, Laser induced periodic surface structures on iron 96-98 (1996) 410
- David, S.A., see Babu, S.S. 94/95 (1996) 280
- De Castilho, C.M.C., see Mollicone, M.M. 94/95 (1996) 68
- De Frutos, A.M., see Gobernado-Mitre, I. 96-98 (1996) 474
- De Matos Gomes, E., see Gomes, M.J.M. 96-98 (1996) 779
- De Wit, L., see Geurtsen, A.J.M. 96-98 (1996) 887
- Débarre, D., A. Aliouchouche, J. Boulmer, B. Bourguignon and J.P. Budin, The role of gas-phase in the laser etching of Cu by CCl₄ 96-98 (1996) 453
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- Deconihout, B., see Bas, P. 94/95 (1996) 442
- Deconihout, B., see Duval, S. 94/95 (1996) 449
- Défossez, A., see Abert, A. 96-98 (1996) 703
- Degroote, S., see Vantomme, A. 91 (1995) 24
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- Deiss, J.L., see Chergui, A. 96-98 (1996) 874
- Dekoster, J., see Vantomme, A. 91 (1995) 24
- Dekoster, J., see Degroote, S. 91 (1995) 72
- Del Vecchio, A., see Berling, D. 96-98 (1996) 739
- Delplancke, M.P., see Reniers, F. 92 (1996) 35
- Den Ouden, G., see Blank, D.H.A. 96-98 (1996) 685
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- Depta, D., see Kähler, J.D. 91 (1995) 339
- Derrien, J., I. Berbezier, A. Ronda and J.Y. Natoli, Interface phase transition as observed in ultra thin FeSi₂ epilayers 92 (1996) 311
- Deslandes, Y., see Spevack, P. 99 (1996) 41
- Devenyi, A., see Belu-Marian, A. 91 (1995) 63
- Devenyi, A., see Manaila, R. 91 (1995) 295
- Devillers, M., see Weng, L.T. 99 (1996) 185
- Deweerd, B., see Lauwers, A. 91 (1995) 12
- Deweerd, B., see Jonckx, F. 91 (1995) 378
- Dhanak, V.R., see Baraldi, A. 99 (1996) 1
- Di Lernia, S., see Geddo, M. 93 (1996) 267
- Diaci, J., D. Hurley, J.W. Wagner and J. Možina, Simultaneous monitoring of ablative shocks in air by high-speed cinematography and multiple-pass beam deflection probe 96-98 (1996) 154
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- Dickinson, J.T., see Norton, M.G. 96-98 (1996) 617
- Dieker, Ch., see Crecelius, G. 91 (1995) 50
- Dietsch, R., see Panzner, M. 96-98 (1996) 643
- Dietsch, R., see Gorbunov, A.A. 96-98 (1996) 649
- Dietzsch, Ch., see Driesel, W. 93 (1996) 179
- Dimova-Malinovska, D., M. Tzolov, N. Malinowski, Ts. Marinova and V. Krastev, Laser-induced formation of visible light emitting silicon 96-98 (1996) 457
- Dinescu, M., see Verardi, P. 96-98 (1996) 827
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- Ding, Z.-J., R. Shimizu and K. Goto, Intrinsic Auger signal profiles derived by Monte Carlo analysis 100/101 (1996) 15
- Dirks, A.G., see Kordic, S. 91 (1995) 197
- Doi, K., see Kim, J.H. 92 (1996) 566
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- Dolin, D.E., see Suvorov, A.L. 94/95 (1996) 384
- Donato, J.M., see Leboeuf, J.N. 96-98 (1996) 14
- Donato, J.M., see Chen, K.R. 96-98 (1996) 45
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- Dorofeev, Yu.I., see Skurat, V.E. 92 (1996) 441
- Drescher, K., see Stavreva, Z. 91 (1995) 192
- Drescher, K., see Stavrev, M. 91 (1995) 257
- Drescher, K., see Vogt, M. 91 (1995) 303
- Dreyfus, R.W., see Le, H.C. 96-98 (1996) 76
- Dreyfus, R.W., see Le, H.C. 96-98 (1996) 164
- Dreyfus, R.W., see Movtchan, I.A. 96-98 (1996) 251
- Driesel, W. and Ch. Dietzsch, In situ HVTEM observation of the tip shape of tin liquid metal ion sources 93 (1996) 179
- Drilhole, D., see Lazare, S. 96-98 (1996) 605
- Du, S.K., see Lu, C.R. 92 (1996) 543
- Du Plessis, J. and E.C. Viljoen, Sn segregation to the low index surfaces of a copper single crystal 100/101 (1996) 222
- Duan, L.H., see Chen, W.D. 100/101 (1996) 592
- Dubreuil, B., see Vivet, L. 96-98 (1996) 238
- Dubreuil, B., see Barthe, M.F. 96-98 (1996) 359
- Dufour-Gergam, E., see Mamor, M. 91 (1995) 342
- Duś, R., see Nowicka, E. 93 (1996) 53
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- Dutta, V., see Paulson, P.D. 92 (1996) 295
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- Ebina, A., see Takeuchi, T. 100/101 (1996) 596
- Eddrief, M., see Reqqass, H. 92 (1996) 357
- Egawa, T., see Uchida, H. 100/101 (1996) 399
- Egawa, T., see Hasegawa, Y. 100/101 (1996) 482
- Ehrhardt, J.J., see Fusy, J. 93 (1996) 211
- Ehrhardt, J.J., see Colin, L. 99 (1996) 245
- Ehring, H. and B.U.R. Sundqvist, Excited state relaxation processes of MALDI-matrices studied by luminescence spectroscopy 96-98 (1996) 577
- Elboujdaini, M., see Sastri, V.S. 93 (1996) 31
- Ellegaard, O., see Svendsen, W. 96-98 (1996) 518
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- Engel, Th., see Stauter, C. 96-98 (1996) 522
- Enta, Y., Y. Takegawa, M. Suemitsu and N. Miyamoto, Growth kinetics of thermal oxidation process on Si(100) by real time ultraviolet photoelectron spectroscopy 100/101 (1996) 449
- Erben, J., see Teichert, St. 91 (1995) 56
- Esrom, H., see Zhang, J.-Y. 96-98 (1996) 399
- Esteve, J., see Polo, M.C. 96-98 (1996) 870
- Ettrich, K., see Welsch, E. 96-98 (1996) 393
- Fähler, S. and H.-U. Krebs, Calculations and experiments of material removal and kinetic energy during pulsed laser ablation of metals 96-98 (1996) 61
- Falkner, B., see Ritzler, A. 96-98 (1996) 721
- Farley, R.J., see Dyer, P.E. 96-98 (1996) 537
- Feng, Z.C., see Li, K. 99 (1996) 59
- Ferregotto, V., see Dauscher, A. 96-98 (1996) 410
- Ferretti, R., see Köhler, J.D. 91 (1995) 339
- Ferrón, J., see Vaquila, I. 93 (1996) 247
- Fiedler, O., see Schulz, S.E. 91 (1995) 326
- Filip, V., see Nicolaescu, D. 94/95 (1996) 79
- Filip, V., see Nicolaescu, D. 94/95 (1996) 87
- Finkman, L., see Mamor, M. 91 (1995) 342
- Flamant, G., see Mazhukin, V.I. 96-98 (1996) 82
- Flamant, G., see Mazhukin, V.I. 96-98 (1996) 89
- Flamant, G., see Gnedovets, A.G. 96-98 (1996) 272

- Flamant, G., see Ignatiev, M.B. 96-98 (1996) 505
- Flodström, A.S., see Hirschauer, B. 99 (1996) 285
- Flores, F., see Rincón, R. 92 (1996) 216
- Flores, F., see Saiz-Pardo, R. 92 (1996) 362
- Fogarassy, E., see Antoni, F. 96-98 (1996) 50
- Fontaine, G., see Stegemann, K.-H. 91 (1995) 308
- Fontaine, J., see Stauter, C. 96-98 (1996) 522
- Forbes, R.G., Field-ion imaging old and new 94/95 (1996) 1
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- Forbes, R.G., Some comments on the simultaneous desorption of ^3He and ^4He 94/95 (1996) 73
- Fouaidy, M., see Maïssa, S. 94/95 (1996) 136
- Franchy, R., J. Masuch and P. Gassmann, The oxidation of the NiAl(111) surface 93 (1996) 317
- Fränd, G., see Bohnke, O. 93 (1996) 45
- Franke, Th., see Teichert, St. 91 (1995) 56
- Franke, Th., see Kilper, R. 91 (1995) 93
- Fransen, M.J., E.P.N. Damen, C. Schiller, T.L. van Rooy, H.B. Groen and P. Kruit, Characterization of ultrasharp field emitters by projection microscopy 94/95 (1996) 107
- Friedbacher, G., see Asikainen, T. 99 (1996) 91
- Frigerio, J.M., see Afif, M. 96-98 (1996) 469
- Fromm, M., see Bohnke, O. 93 (1996) 45
- Frösche, B., see Ruhl, G. 91 (1995) 382
- Fu, G.H., see Young, T.F. 92 (1996) 57
- Fu, T., see Shern, C.S. 92 (1996) 74
- Fuchs, C., see Antoni, F. 96-98 (1996) 50
- Fuentes-Cabrera, M., see Rodríguez-Hernández, P. 92 (1996) 408
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- Fujimoto, R., see Inoue, N. 96-98 (1996) 656
- Fujiwara, S., see Deno, H. 96-98 (1996) 563
- Fujiyasu, H., see Tatsuoka, H. 92 (1996) 382
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- Fukushima, M., see Arai, M. 99 (1996) 145
- Fursey, G., Early field emission studies of semiconductors 94/95 (1996) 44
- Furukawa, T., see Inanaga, K. 100/101 (1996) 421
- Furukawa, Y., see Kayama, H. 92 (1996) 142
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- Gaidarova, V., see Takeichi, Y. 100/101 (1996) 25
- Galdetsky, A.V., see Zhirnov, V.V. 94/95 (1996) 144
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- Galvagno, S., see Scirè, S. 93 (1996) 309
- Galvagno, S., see Crisafulli, C. 99 (1996) 401
- Gambino, J., see Kücher, P. 91 (1995) 359
- Gan, F., see Chen, Q. 93 (1996) 151
- Ganjoo, A., see Yoshida, A. 100/101 (1996) 491
- Gaponov, S.V., see Gorbunov, A.A. 96-98 (1996) 649
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- García-Vidal, F.J., see Rincón, R. 92 (1996) 216
- Gardeniers, J.G.E., see King, S.L. 96-98 (1996) 811
- Garrelie, F., see Angleraud, B. 96-98 (1996) 117
- Gassmann, P., see Franchy, R. 93 (1996) 317
- Gatz, P. and O.F. Hagena, Cluster beams for metallization of microstructured surfaces 91 (1995) 169
- Gawlik, G., see Zaborowski, M. 91 (1995) 239
- Geddo, M., S. Di Lernia and Chen Chen-Jia, Photoreflexance analysis of MQWs in intermediate electric field regime 93 (1996) 267

- Geertsens, C., see García, C. 96-98 (1996) 370
- Geiger, M., W. Becker, T. Rebhan, J. Hutfless and N. Lutz, Increase of efficiency for the XeCl excimer laser ablation of ceramics 96-98 (1996) 309
- Genet, F., see Chaix-Pluchery, O. 91 (1995) 68
- Geohegan, D.B., see Leboeuf, J.N. 96-98 (1996) 14
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- Geohegan, D.B. and A.A. Puztzyk, Laser ablation plume thermalization dynamics in background gases: combined imaging, optical absorption and emission spectroscopy, and ion probe measurements 96-98 (1996) 131
- Geohegan, D.B., see Puztzyk, A.A. 96-98 (1996) 859
- Gérard, J.M., see Moison, J.M. 92 (1996) 526
- Gerard, P., see Deconihout, B. 94/95 (1996) 422
- Geretovszky, Zs., see Szörényi, T. 96-98 (1996) 363
- Gerlach, J.W., see Wengenmair, H. 99 (1996) 313
- Germain, C., see Angleraud, B. 96-98 (1996) 117
- German, K.A.H., see Hess, W.P. 96-98 (1996) 321
- Gessner, T., see Teichert, J. 91 (1995) 44
- Gessner, T., see Röber, J. 91 (1995) 134
- Gessner, T., see Bertz, A. 91 (1995) 147
- Gessner, T., see Kaufmann, C. 91 (1995) 291
- Gessner, T., see Schulz, S.E. 91 (1995) 326
- Gessner, T., see Wolf, H. 91 (1995) 332
- Geurtsen, A.J.M., J.C.S. Kools, L. de Wit and J.C. Lodder, Pulsed Laser Deposition of permanent magnetic $\text{Nd}_2\text{Fe}_{14}\text{B}$ thin films 96-98 (1996) 887
- Geus, J.W., see Van Wijk, R. 93 (1996) 237
- Geus, J.W., see Van Wijk, R. 99 (1996) 127
- Geus, J.W., see Van Wijk, R. 99 (1996) 197
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- Gheysa, S.I., S. Hirano, M. Nishio and H. Ogawa, Growth of high-quality ZnTe layers by MOVPE 100/101 (1996) 647
- Ghosh, S., see Ali, S.T. 93 (1996) 37
- Giardini Guidoni, A., see Mele, A. 96-98 (1996) 102
- Gibert-Légrand, T., see Vivet, L. 96-98 (1996) 238
- Gibert, T., see Barthe, M.F. 96-98 (1996) 359
- Giedl, R., see Dyer, P.E. 96-98 (1996) 537
- Giesbers, J.B., see Cillessen, J.F.M. 96-98 (1996) 744
- Gijzeman, O.L.J., see Van Wijk, R. 93 (1996) 237
- Gijzeman, O.L.J., see Van Wijk, R. 99 (1996) 127
- Gijzeman, O.L.J., see Mens, A.J.M. 99 (1996) 133
- Gijzeman, O.L.J., see Van Wijk, R. 99 (1996) 197
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- Girault, C., see Angleraud, B. 96-98 (1996) 117
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- Givargizov, E.I., see Zhimov, V.V. 94/95 (1996) 144
- Gmucová, K., see Pinčik, E. 93 (1996) 119
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- Gnedovets, A.G., E.B. Kul'batskii, I. Smurov and G. Flamant, Particles synthesis in erosive laser plasma in a high pressure atmosphere 96-98 (1996) 272
- Göbel, U., see Grunwaldt, J.-D. 99 (1996) 353
- Gobernado-Mitre, I., J. Medina, B. Calvo, A.C. Prieto, L.A. Leal, B. Pérez, F. Marcos and A.M. de Frutos, Laser cleaning in art restoration 96-98 (1996) 474
- Godard, B., see Boher, P. 96-98 (1996) 376
- Godfrey, T.J., see Sijbrandij, S.J. 94/95 (1996) 428
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- Goldmann, A., see Kürpick, U. 99 (1996) 221
- Gomes, M.J.M., E. de Matos Gomes, P.L.Q. Mantas and J.L. Baptista, Growth and characterization of PLZT films 96-98 (1996) 779
- Gómez San Roman, R., see Gonzalo, J. 96-98 (1996) 693
- Gómez San Román, R., see Pérez Casero, R. 96-98 (1996) 697
- Gomozov, V.P., see Skatkov, L.I. 99 (1996) 367
- Gonbeau, D., see Martinez, H. 93 (1996) 231
- Gonda, S., see Kim, J.H. 92 (1996) 566
- Gong, Y.S., J.-C. Lin and C. Lee, Interdiffusion and reactions in the Cu/TiN/Si thin film system 92 (1996) 335
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- Gonzalo, J., see Afonso, C.N. 96-98 (1996) 760

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- Gorelova, M.M., see Skurat, V.E. 92 (1996) 441
- Gordetskii, V., see Reckzügel, M.C. 94/95 (1996) 194
- Gorse, D., see Marsh, J. 99 (1996) 335
- Gorshkov, V.N., see Vladimirov, V.V. 94/95 (1996) 171
- Gorska, M., see Jen, J.Y. 92 (1996) 547
- Görts, P.C., see Van Wijk, R. 99 (1996) 127
- Göthelid, M., see Janin, E. 99 (1996) 371
- Goto, K., see Ding, Z.-J. 100/101 (1996) 15
- Goto, K., see Takeichi, Y. 100/101 (1996) 25
- Gotoh, Y., see Tsuji, H. 100/101 (1996) 342
- Gotoh, Y., see Toyota, Y. 100/101 (1996) 360
- Gotoh, Y., see Ishikawa, J. 100/101 (1996) 370
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- Götz, T., M. Bergt, W. Hoheisel, F. Träger and M. Stuke, Laser ablation of metals: the transition from non-thermal processes to thermal evaporation 96-98 (1996) 280
- Goya, T., see Numajiri, K. 100/101 (1996) 541
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- Grad, L. and J. Mořina, Optodynamic studies of Er:YAG laser induced microexplosions in dentin 96-98 (1996) 591
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- Graham, W.G., see Hendron, J.M. 96-98 (1996) 112
- Grancher, G., see Bas, P. 94/95 (1996) 442
- Grangeon, F., H. Sassoli, W. Marine and M. Autric, Time-of-flight characterization of laser ablation plume from NbTe_2 target in He atmosphere 96-98 (1996) 186
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- Granse, G., see Lenk, A. 96-98 (1996) 195
- Grasserbauer, M., see Asikainen, T. 99 (1996) 91
- Grätz, M., C. Tillman, I. Mercer and S. Svanberg, X-ray generation for medical applications from a laser-produced plasma 96-98 (1996) 443
- Gregoratti, L., see Baraldi, A. 99 (1996) 1
- Grehk, T.M., see Janin, E. 99 (1996) 371
- Greim, O., see Bohnke, O. 93 (1996) 45
- Gries, W.H., A general procedure for extracting quantitative depth information from take-off-angle-resolved XPS and AES 100/101 (1996) 41
- Griessen, R., see Dam, B. 96-98 (1996) 679
- Grignaffini Gregorio, B., see Corni, F. 91 (1995) 107
- Grigorenko, A.N. and P.I. Nikitin, Magnetostochastic resonance as a new method for investigations of surface and thin film magnetism 92 (1996) 466
- Groen, H.B., see Fransen, M.J. 94/95 (1996) 107
- Gross, M.E., see Weber, A. 91 (1995) 314
- Grosse-Holz, K.-O., see Cillessen, J.F.M. 96-98 (1996) 744
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- Grun, J.B., see Chergui, A. 96-98 (1996) 874
- Grünewald, W., see Schulz, S.E. 91 (1995) 326
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- Gruyters, M., see Mitrelias, T. 100/101 (1996) 305
- Gu, D., see Chen, Q. 93 (1996) 151
- Gu, G.-L., see Tseng, B.-H. 92 (1996) 227
- Gu, G.-L., see Tseng, B.-H. 92 (1996) 412
- Guan, W., see Lazare, S. 96-98 (1996) 605
- Gui, L., see Guo, Q. 92 (1996) 513
- Gui, L., see Guo, Q. 99 (1996) 229
- Guizzetti, G., see Bocelli, S. 91 (1995) 30
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- Gupta, V.K., see John, G. 93 (1996) 329
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- Gusev, I.V., see Mazhukin, V.I. 96-98 (1996) 82
- Gutleben, C.D., see Kita, A. 100/101 (1996) 652

- Guyot, M., see Lisfi, A. 96-98 (1996) 66
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- Gyorgy, E., see Leggieri, G. 96-98 (1996) 866
- Habermann, T., see Pupeter, N. 94/95 (1996) 94
- Habermeier, H.-U., N. Jisrawi and G. Jäger-Waldau, Giant laser-induced voltages at room temperature in Pr doped Y-Ba-Cu-O thin films 96-98 (1996) 689
- Habraken, F.H.P.M., see Marée, C.H.M. 93 (1996) 291
- Habraken, F.H.P.M., see Van Wijk, R. 99 (1996) 127
- Habraken, F.H.P.M., see Van Wijk, R. 99 (1996) 197
- Hagena, O.F., see Gatz, P. 91 (1995) 169
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- Hasegawa, M., see Fukada, T. 91 (1995) 227
- Hasegawa, M., see Ohdaira, T. 100/101 (1996) 73
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- Hashimoto, Y., see Horio, Y. 100/101 (1996) 292
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- Hashizume, T., see Jeon, D. 94/95 (1996) 493
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- Hatanaka, Y., see Jayatissa, A.H. 92 (1996) 300
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- Häussler, P., see Teichert, St. 91 (1995) 56
- Häussler, P., see Kilper, R. 91 (1995) 93
- Hayashi, K., see Nakamura, T. 92 (1996) 291
- Hayashi, K., see Iwano, H. 100/101 (1996) 487
- Hayashi, N., see Kobayashi, N. 100/101 (1996) 498
- Heck, C., see Jikimoto, T. 100/101 (1996) 513
- Heilmann, A., see Grünewald, W. 93 (1996) 157
- Heimann, R.B., see Kokai, F. 96-98 (1996) 261
- Heinen, R., see Gräfe, A. 91 (1995) 187
- Heinig, V., see Stegmann, K.-H. 91 (1995) 308
- Hellebrand, B., see Stangl, E. 96-98 (1996) 731
- Hems, J., see Sykes, D.E. 100/101 (1996) 77
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- Hille, N., see Bertz, A. 91 (1995) 147
- Hintermann, H.E., see Pimenov, S.M. 92 (1996) 106
- Hintze, B., see Schulz, S.E. 91 (1995) 326
- Hipps, K.W., see Norton, M.G. 96-98 (1996) 617
- Hirai, M., see Jikimoto, T. 100/101 (1996) 513
- Hirai, M., see Yamauchi, S. 100/101 (1996) 522
- Hiraki, A., see Tachiwaki, T. 100/101 (1996) 272
- Hirano, S., see Gheyas, S.I. 100/101 (1996) 634
- Hirano, S., see Gheyas, S.I. 100/101 (1996) 647
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- Holloway, P.H., see Viljoen, P.E. 100/101 (1996) 612
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- Holz, Th., see Panzner, M. 96-98 (1996) 643
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- Hong, Y., see Wei, Y. 92 (1996) 491
- Hono, K., see Ringer, S.P. 94/95 (1996) 253
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- Hoshi, T., see Kudo, M. 100/101 (1996) 129
- Hosokawa, N., see Numajiri, K. 100/101 (1996) 541
- Hosokawa, N., see Kim, S.W. 100/101 (1996) 546
- Hotta, K., see Ikeda, H. 100/101 (1996) 431
- Houzay, F., see Moison, J.M. 92 (1996) 526
- Hren, J.J., see Zhimov, V.V. 94/95 (1996) 123
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- Hsu, K.Y.J., see Hwang, H.-L. 92 (1996) 180
- Hsu, K.Y.J., see Lee, C.H. 92 (1996) 621
- Hsu, K.Y.J., see Lin, C.C. 92 (1996) 660
- Hsu, M.-Y., see Chang, T.-C. 92 (1996) 571
- Hsu, S.S., see Chung, B.C. 96-98 (1996) 233
- Hsu, T.M., see Lee, W.C. 92 (1996) 66
- Hu, C.C., see Lee, M.K. 92 (1996) 159
- Hua, T.H., see Ogawa, Y. 92 (1996) 232
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- Hurley, D., see Diaci, J. 96-98 (1996) 154
- Husinsky, W., see Seifert, N. 96-98 (1996) 33
- Hutless, J., see Geiger, M. 96-98 (1996) 309
- Hwang, C.Z., see Lee, M.K. 92 (1996) 159
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- Hwang, H.L., see Lin, C.C. 92 (1996) 660
- Hwu, J.-G., see Lee, K.-C. 92 (1996) 204
- Hwu, J.-G., see Jeng, M.-J. 92 (1996) 208
- Hwu, Y., see Margaritondo, G. 92 (1996) 273
- Hyde, J.M., see Cerezo, A. 94/95 (1996) 457
- Ichiki, K., see Hatakeyama, M. 100/101 (1996) 277
- Ichimiya, A., see Horio, Y. 100/101 (1996) 292
- Ichimiya, A., see Emoto, T. 100/101 (1996) 355
- Ichimura, S., see Tanuma, S. 100/101 (1996) 47
- Ichimura, S., see Kurokawa, A. 100/101 (1996) 436
- Ichimura, S., see Nakamura, K. 100/101 (1996) 444
- Ichino, K., see Lee, S.T. 100/101 (1996) 656
- Ichinohe, T., see Shimasaki, M. 92 (1996) 617
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- Ignatiev, M., see Titov, V. 96-98 (1996) 387
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- Imada, H., see Tumiran, 100/101 (1996) 238
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- Ishikawa, J., see Tsuji, H. 100/101 (1996) 342
- Ishikawa, J., see Toyota, Y. 100/101 (1996) 360
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- Ito, K., see Nakayama, N. 92 (1996) 171
- Ito, K., see Ogawa, Y. 92 (1996) 232
- Ito, M., see Ito, H. 100/101 (1996) 152
- Ito, T., see Tachiwaki, T. 100/101 (1996) 272
- Itoga, T., see Yano, F. 100/101 (1996) 138
- Itoh, H., see Tsuji, H. 100/101 (1996) 342
- Itoh, N., see Szymonski, M. 100/101 (1996) 102
- Itoh, Y., see Suzuki, Y. 100/101 (1996) 165
- Itoh, Y., see Homma, T. 100/101 (1996) 189
- Ivanov, D., see Lecours, A. 96-98 (1996) 341
- Ivanov, D., see Izquierdo, R. 96-98 (1996) 855
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- Izumi, Y., see Katoh, M. 100/101 (1996) 226

- Jablonski, A., see Tilinin, I.S. 100/101 (1996) 20
- Jackson, S.R., see Dyer, P.E. 96-98 (1996) 849
- Jacquier, B., see Garapon, C. 96-98 (1996) 836
- Jadin, A., see Hanus, F. 96-98 (1996) 807
- Jagdish, C., see Li, G. 92 (1996) 138
- Jäger-Waldau, A., see Ogawa, Y. 92 (1996) 232
- Jäger-Waldau, G., see Habermeyer, H.-U. 96-98 (1996) 689
- Jamais, D., see Colin, L. 99 (1996) 245
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- Jergel, M., see Pinčik, E. 93 (1996) 119
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- Jia, W.J., see Wang, S.L. 93 (1996) 205
- Jiang, W., see Norton, M.G. 96-98 (1996) 617
- Jiang, X., see Patterson, J.C. 91 (1995) 124
- Jiang, X., see O'Reilly, M. 91 (1995) 152
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- Jimbo, T., see Hasegawa, Y. 100/101 (1996) 482
- Jimbo, T., see Yu, G. 100/101 (1996) 617
- Jiménez, J., see García, C. 96-98 (1996) 370
- Jisrawi, N., see Habermeyer, H.-U. 96-98 (1996) 689
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- Joag, D.S., see Sharma, R.B. 94/95 (1996) 177
- Johansen, H., see Gogoll, S. 96-98 (1996) 332
- Johansson, J., see Dam, B. 96-98 (1996) 679
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- Jung, T.-G., see Chang, T.-C. 92 (1996) 119
- Jung, T.-G., see Chang, T.-C. 92 (1996) 571
- Junquera, T., see Maissa, S. 94/95 (1996) 136
- Kaalund, C., see Haneman, D. 92 (1996) 484
- Käämbre, T., see Ding, D. 96-98 (1996) 581
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- Kaibara, M., see Nakao, A. 100/101 (1996) 112
- Kaiser, N., see Welsch, E. 96-98 (1996) 393
- Kakudate, Y., see Deno, H. 96-98 (1996) 563
- Kalabina, N.A., see Ksenevich, T.I. 92 (1996) 426
- Kamei, K., see Katsuki, F. 94/95 (1996) 485
- Kameyama, K., see Ishikawa, J. 100/101 (1996) 370
- Kameyama, T., see Togashi, H. 96-98 (1996) 267
- Kamidoi, S., see Kawano, H. 100/101 (1996) 174
- Kamiura, Y., see Ying, W.B. 100/101 (1996) 556
- Kamiura, Y., see Mizokawa, Y. 100/101 (1996) 561
- Kanehori, K., see Yano, F. 100/101 (1996) 138
- Kanemitsu, Y., see Mimura, H. 92 (1996) 396
- Kanemitsu, Y., see Mimura, H. 92 (1996) 598
- Kang, H.J., see Lee, J.C. 100/101 (1996) 97
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- Kántor, Z., see Szörényi, T. 96-98 (1996) 363
- Kao, J.-S., see Chen, P.-L. 92 (1996) 30
- Karlsson, U.O., see Janin, E. 99 (1996) 371
- Karnakis, D.M., see Dyer, P.E. 96-98 (1996) 415
- Karnakis, D.M., see Dyer, P.E. 96-98 (1996) 537
- Karnakis, D.M., see Dyer, P.E. 96-98 (1996) 596
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- Kawakami, E., see Oku, T. 99 (1996) 265
- Kawakyu, Y., see Nishibe, T. 99 (1996) 35
- Kawamoto, K., see Ying, W.B. 100/101 (1996) 556
- Kawamoto, K., see Mizokawa, Y. 100/101 (1996) 561
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- Keller, B.A., see Osman, M.A. 99 (1996) 261
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- Key, P.H., see Dyer, P.E. 96-98 (1996) 596
- Key, P.H., see Dyer, P.E. 96-98 (1996) 849
- Khavin, Y., see Kirichenko, N. 93 (1996) 359
- Kikuma, I., see Morisawa, Y. 92 (1996) 147
- Kikuma, I., see Satoh, M. 92 (1996) 635
- Kilner, J.A., see Coccia, L.G. 96-98 (1996) 795
- Kilper, R., see Teichert, St. 91 (1995) 56
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- Kim, C.O., see Yoon, Y.S. 93 (1996) 285
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- Kimura, H., see Katoh, M. 100/101 (1996) 226
- King, D.A., see Mitrelias, T. 100/101 (1996) 305
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- Kirschner, A., see Pupeter, N. 94/95 (1996) 94
- Kishimoto, J., see Bakhtizin, R.Z. 94/95 (1996) 478
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- Kitagawa, Y., see Takemura, S. 100/101 (1996) 107
- Kitayama, Y., see Kawano, H. 100/101 (1996) 193
- Klages, C.-P., see Weber, A. 91 (1995) 314
- Klein, D., see Berger, F. 93 (1996) 9
- Klein, F., see Gräfe, A. 91 (1995) 187
- Klyenkov, E.B., see Gorbunov, A.A. 96-98 (1996) 649
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- Kobayashi, H., see Lee, S.T. 100/101 (1996) 656
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- Kobayashi, N., see Makimoto, T. 100/101 (1996) 403
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- Koga, Y., see Togashi, H. 96-98 (1996) 267
- Kohji, Y., see Fukumura, H. 96-98 (1996) 569
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- Kojima, A., see Katoh, M. 100/101 (1996) 226
- Kojima, A., see Iwano, H. 100/101 (1996) 487
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- Kolodinski, S., see Donaton, R.A. 91 (1995) 77
- Kolodziej, J., see Szymonski, M. 100/101 (1996) 102
- Komatsu, K., see Emoto, T. 100/101 (1996) 355
- Komiya, S., see Sugita, Y. 100/101 (1996) 268
- Komoku, K., see Jikimoto, T. 100/101 (1996) 513
- Konishi, R., see Yea, B. 100/101 (1996) 365
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- Korecki, P., see Szymonski, M. 100/101 (1996) 102
- Körner, H., see Hain, M. 91 (1995) 374
- Kosaka, M., see Shinoda, H. 100/101 (1996) 526
- Koshizuka, N., see Saito, S. 100/101 (1996) 260
- Koster, N.B., see Voorma, H.-J. 93 (1996) 221

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- Kozlov, R.I., see Givargizov, E.I. 94/95 (1996) 117
- Krabbe, A., see Streller, U. 96-98 (1996) 448
- Krastev, V., see Dimova-Malinovska, D. 96-98 (1996) 457
- Krastev, V., see Marinova, Ts. 99 (1996) 119
- Krebs, H.-U., see Fähler, S. 96-98 (1996) 61
- Kreutz, E.W., see Aden, M. 96-98 (1996) 39
- Kreutz, E.W., see Alunovic, M. 96-98 (1996) 222
- Kreutz, E.W., see Wesner, D.A. 96-98 (1996) 479
- Kreutz, E.W., see Pflöging, W. 96-98 (1996) 496
- Kreutz, E.W., see Mertin, M. 96-98 (1996) 842
- Kreuzer, H.J., see Forbes, R.G. 94/95 (1996) 60
- Kriman, A.M., see Jou, H. 92 (1996) 585
- Krishnan, R., see Lisi, A. 96-98 (1996) 66
- Krishnan, R., see Guyot, M. 96-98 (1996) 802
- Kruck, Th., see Gräfe, A. 91 (1995) 187
- Krüger, J. and W. Kautek, Femtosecond-pulse visible laser processing of transparent materials 96-98 (1996) 430
- Kruit, P., see Fransen, M.J. 94/95 (1996) 107
- Kruse, N., see Voss, C. 94/95 (1996) 186
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- Kudo, M., see Yamada, T. 100/101 (1996) 287
- Kukushkin, S.A., see Sakalo, T.V. 92 (1996) 261
- Kukushkin, S.A., see Sakalo, T.V. 92 (1996) 350
- Kul'batskii, E.B., see Gnedovets, A.G. 96-98 (1996) 272
- Kunc, K., see Cheng, C. 92 (1996) 496
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- Kusaka, M., see Yamauchi, S. 100/101 (1996) 522
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- Kusunoki, T. and M. Suzuki, Quantitative relationship between the work function and transfer ratio of a potassium-adsorbed MIM cathode 100/101 (1996) 207
- Kuwabara, H., see Tatsuoaka, H. 92 (1996) 382
- Kuwabara, H., see Nakanishi, Y. 100/101 (1996) 639
- Kuźma, M., see Gorbach, T.Ya. 96-98 (1996) 881
- Kuznetsov, V.S., see Zimin, S.P. 91 (1995) 355
- Kvist, A., see Ivchenko, V.A. 94/95 (1996) 267
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- Kwok, R.W.M., see Yan, H. 92 (1996) 61
- Kyotani, T., see Mochizuki, K. 92 (1996) 79
- La Bruna, G., see Cerofolini, G.F. 93 (1996) 255
- La Via, F., see Ravesi, S. 91 (1995) 19
- Laajalehto, K., see Kartio, I. 93 (1996) 167
- Laborde, O., see Gottlieb, U. 91 (1995) 82
- Laborde, O., see Affronte, M. 91 (1995) 98
- Lacharme, J.-P., see Reqqass, H. 92 (1996) 357
- Lacour, J.L., see García, C. 96-98 (1996) 370
- Lahaye, J., see Schoderböck, P. 93 (1996) 109
- Lai, W.-K., see Wang, F.-S. 92 (1996) 372
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- Lang, Th., see Izquierdo, R. 96-98 (1996) 855
- Lange, H., see Teichert, St. 91 (1995) 56
- Langford, S.C., see Dickinson, J.T. 96-98 (1996) 316

- Langford, S.C., see Dickinson, J.T. 96-98 (1996) 326
- Langouche, G., see Vantomme, A. 91 (1995) 24
- Langouche, G., see Degroote, S. 91 (1995) 72
- Larson, D.J., P.P. Camus and T.F. Kelly, Optimal field pulsing for atom probes with counter electrodes 94/95 (1996) 434
- Larson, P.E., see Iwai, H. 100/101 (1996) 283
- Laude, L., see Viville, P. 96-98 (1996) 558
- Laude, L., see Izquierdo, R. 96-98 (1996) 855
- Laude, L.D., see Szörényi, T. 96-98 (1996) 363
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- Le Goff, A., see Maïssa, S. 94/95 (1996) 136
- Le Thanh, V., see Reqqass, H. 92 (1996) 357
- Leal, L.A., see Gobernado-Mitre, I. 96-98 (1996) 474
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- Lennard, W.N., see Kasrai, M. 99 (1996) 303
- Leprince, L., see Moison, J.M. 92 (1996) 526
- Lesiak-Orlowska, B., see Tilinin, I.S. 100/101 (1996) 20
- Leskelä, M., see Asikainen, T. 99 (1996) 91
- Letokhov, V.S., see Konopsky, V.N. 94/95 (1996) 148
- Leusink, G.J., see Jongste, J.F. 91 (1995) 162
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- Li, S.T., see Ritzer, A. 96-98 (1996) 721
- Li, W.-H., see Lee, W.C. 92 (1996) 66
- Li, X., see Zhou, B. 100/101 (1996) 643
- Li, X.Q., see Chen, W.D. 100/101 (1996) 592
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- Lin, C.T., see Chuang, F.Y. 92 (1996) 452
- Lin, H.-S., see Jeng, M.-J. 92 (1996) 208
- Lin, I.N., see Chuang, F.Y. 92 (1996) 452
- Lin, I.N., see Chung, B.C. 96-98 (1996) 233
- Lin, I.N., see Huang, C.S. 96-98 (1996) 735
- Lin, J., see Li, K. 99 (1996) 59
- Lin, J.-C., see Gong, Y.S. 92 (1996) 335
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- Lin, S.-B., see Tseng, B.-H. 92 (1996) 412
- Lin, T.Y., see Horng, R.H. 92 (1996) 387
- Lin, T.Y., see Wu, D.S. 92 (1996) 626
- Linares-Solano, A., see Muñoz-Guillena, M.J. 99 (1996) 111
- Lindahl, P., see Zackrisson, J. 94/95 (1996) 351
- Ling, Y.-C., see Kuo, W.-K. 92 (1996) 155
- Liou, C.H., see Lu, C.R. 92 (1996) 404
- Liou, H.K., see Lin, C.C. 92 (1996) 660
- Liou, Y., Textured diamond growth by microwave plasma chemical vapor deposition 92 (1996) 115
- Liou, Y., see Huang, J.C.A. 92 (1996) 480
- Lioubitchenko, D.V., see Bryantseva, T.A. 100/101 (1996) 169
- Lippert, T., L.S. Bennett, T. Nakamura, H. Niino and A. Yabe, Single pulse threshold and transmission behaviour of a triazeno-polymer during pulsed UV-laser irradiation 96-98 (1996) 601
- Lisfi, A., M. Guyot, R. Krishnan and V. Cagan, Measurement and calculation of the Fe_2O_3 ablation depth 96-98 (1996) 66
- Lisfi, A., see Guyot, M. 96-98 (1996) 802
- Lisowski, W., see Nowicka, E. 93 (1996) 53
- Liu, C.-W., B.-T. Dai and C.-F. Yeh, Post cleaning of chemical mechanical polishing process 92 (1996) 176
- Liu, C.L., see Leboeuf, J.N. 96-98 (1996) 14
- Liu, C.L., see Chen, K.R. 96-98 (1996) 45
- Liu, C.S. and L.J. Chen, Effects of substrate cleaning and film thickness on the epitaxial growth of ultrahigh vacuum deposited Cu thin films on (001)Si 92 (1996) 84
- Liu, D.-C., see Lee, C.-P. 92 (1996) 519
- Liu, J.F., see Young, T.F. 92 (1996) 57
- Liu, J.M., Z.G. Liu, S.N. Zhu, Y.Y. Zhu and N.B. Ming, Excimer laser ablating preparation of $\text{Ba}_2\text{NaNb}_2\text{O}_{15}$ thin films on KTiOPO_4 substrate and its guide wave property 96-98 (1996) 819
- Liu, Z.G., see Liu, J.M. 96-98 (1996) 819
- Liu, Z.H., see Brown, N.M.D. 93 (1996) 89
- Ljungström, S., see Ding, D. 96-98 (1996) 581
- Lübner, B., see Teichert, J. 91 (1995) 44
- Lodder, J.C., see Geurtsen, A.J.M. 96-98 (1996) 887
- Loegel, B., see Berling, D. 96-98 (1996) 739
- Loison, J.L., see Chergui, A. 96-98 (1996) 874
- Lokhande, C.D., see Mohite, U.K. 92 (1996) 151
- Lokker, J.P., see Leusink, G.J. 91 (1995) 215
- Lopatin, V.V., see Bryantseva, T.A. 100/101 (1996) 169
- Lorenz, J., see Bär, E. 91 (1995) 321
- Lorenzi, G., see Fuso, F. 96-98 (1996) 181
- Loubnin, E.N., see Pimenov, S.M. 92 (1996) 106
- Loudet, M., see Martinez, H. 93 (1996) 231
- Louis, E., see Voorma, H.-J. 93 (1996) 221
- Lowndes, D.H., see Norton, D.P. 96-98 (1996) 672
- Lu, C.R., C.L. Chang, C.H. Liou, J.R. Anderson, D.R. Stone and R.A. Wilson,

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- Lucazeau, G., see Chaix-Pluchery, O. 91 (1995) 68
- Luches, A., see Anisimov, S.I. 96-98 (1996) 24
- Luches, A., see Berling, D. 96-98 (1996) 739
- Luches, A., see Leggieri, G. 96-98 (1996) 866
- Luedtke, W.D., see Landman, U. 92 (1996) 237
- Luisa De Giorgi, M., see Berling, D. 96-98 (1996) 739
- Luk'yanchuk, B.S., see Anisimov, S.I. 96-98 (1996) 24
- Lundin, L. and H.-O. Andrén, Observation of molybdenum-nitrogen clustering in highly alloyed martensite 94/95 (1996) 320
- Lundin, L., see Kvist, A. 94/95 (1996) 356
- Lundström, I., see Holmberg, M. 93 (1996) 67
- Luo, E.Z., Q. Cai, W.F. Chung and M.S. Altman, Interface effects in melting of Pb clusters on the Cu(111) surface 92 (1996) 331
- Luong, M., see Maïssa, S. 94/95 (1996) 136
- Lupp, F., see Wesner, D.A. 96-98 (1996) 479
- Lusby, T.A. and A.J. Melmed, Nanocrystallization of a Co-Nb-B-C metallic glass 94/95 (1996) 300
- Lüthy, W., see Tosin, P. 96-98 (1996) 384
- Lutz, N., see Geiger, M. 96-98 (1996) 309
- Lyalin, A.A., see Dolgaev, S.I. 96-98 (1996) 491
- Lynch, S., see O'Reilly, M. 91 (1995) 152
- MacDonald, R., see Kang, H.J. 100/101 (1996) 329
- Macht, M.-P., see Al-Kassab, T. 94/95 (1996) 306
- Maciel, H.S., see Mansano, R.D. 100/101 (1996) 583
- Madar, R., see Pons, M. 91 (1995) 34
- Madar, R., see Chaix-Pluchery, O. 91 (1995) 68
- Madar, R., see Gottlieb, U. 91 (1995) 82
- Madar, R., see Affronte, M. 91 (1995) 98
- Madar, R., see Bourhila, N. 91 (1995) 175
- Madiar, R., see Dutron, A.-M. 91 (1995) 277
- Maeda, T., see Saito, S. 100/101 (1996) 260
- Maex, K., see Lauwers, A. 91 (1995) 12
- Maex, K., see Donaton, R.A. 91 (1995) 77
- Maex, K., see Stevens, R. 91 (1995) 208
- Maex, K., see Jonckx, F. 91 (1995) 378
- Macyama, M., see Tumiran, 100/101 (1996) 238
- Magatani, Y., see Ito, H. 100/101 (1996) 152
- Maggiore, R., see Scirè, S. 93 (1996) 309
- Maggiore, R., see Crisafulli, C. 99 (1996) 401
- Mahner, E., see Pupeter, N. 94/95 (1996) 94
- Mahony, C., see Hendron, J.M. 96-98 (1996) 112
- Mai, H., see Panzner, M. 96-98 (1996) 643
- Mai, H., see Gorbunov, A.A. 96-98 (1996) 649
- Maillat, M., see Pimenov, S.M. 92 (1996) 106
- Maïssa, S., T. Junquera, M. Fouaidy, A. Le Goff, B. Bonin, M. Luong, H. Safa and J. Tan, Study of luminous phenomena observed on contaminated metallic surfaces submitted to high RF fields 94/95 (1996) 136
- Maiwa, Y., see Wadayama, T. 100/101 (1996) 575
- Majni, G., see Leggieri, G. 96-98 (1996) 866
- Makimura, T. and K. Murakami, Dynamics of silicon plume generated by laser ablation and its chemical reaction 96-98 (1996) 242
- Makimoto, T. and N. Kobayashi, Nitridation of GaAs surfaces using nitrogen molecules cracked by a hot tungsten filament 100/101 (1996) 403
- Makita, Y., see Kobayashi, N. 100/101 (1996) 498
- Malinowski, N., see Dimova-Malinovska, D. 96-98 (1996) 457
- Mamor, M., E. Dufour-Gergam, L. Finkman, G. Tremblay, F. Meyer and K. Bouziane, W/Si Schottky diodes: effect of sputtering deposition conditions on the barrier height 91 (1995) 342
- Manaila, R., see Belu-Marian, A. 91 (1995) 63
- Manaila, R., D. Biro, P.B. Barna, M. Adamik, F. Zavaliche, S. Craciun and A. Devenyi, Ti nitride phases in thin films deposited by DC magnetron sputtering 91 (1995) 295
- Mann, K., B. Wolff-Rottke and F. Müller, Cleaning of optical surfaces by excimer laser radiation 96-98 (1996) 463
- Mansano, R.D., P. Verdonck and H.S. Maciel, Deep trench etching in silicon with fluorine containing plasmas 100/101 (1996) 583
- Mantas, P.L.Q., see Gomes, M.J.M. 96-98 (1996) 779
- Mao, X., W.-T. Chan, M. Caetano, M.A. Shannon and R.E. Russo, Preferential vaporization and plasma shielding during nano-second laser ablation 96-98 (1996) 126
- Mao, X.L., see Russo, R.E. 96-98 (1996) 144
- Maquin, Ph., see Puech, M. 100/101 (1996) 579
- Marabelli, F., see Bocelli, S. 91 (1995) 30
- Marangon, M.S., G. Queirolo and C. Savoia, Nucleation and growth of CVD-W on TiN studied by X-ray fluorescence spectrometry 91 (1995) 157
- Marchet, P., see Champeaux, C. 96-98 (1996) 775
- Marchet, P., see Garapon, C. 96-98 (1996) 836
- Marco, J.P., see Augereau, F. 99 (1996) 293
- Marcos, F., see Gobernado-Mitre, I. 96-98 (1996) 474
- Maréchal, C., see Pérez Casero, R. 96-98 (1996) 697
- Marée, C.H.M., T.J. Savenije, T.J. Schaafsma and F.H.P.M. Habraken, Ion beam studies of porphyrin adsorption on and leaching of soda lime glass 93 (1996) 291
- Marée, C.H.M., see Van Wijk, R. 99 (1996) 127
- Marée, C.H.M., see Van Wijk, R. 99 (1996) 197
- Marest, G., see Afif, M. 96-98 (1996) 469
- Margail, J., see Regolini, J.L. 100/101 (1996) 566
- Margaritondo, G. and Y. Hwu, Photoemission spectromicroscopy and free elec-

- tron laser spectroscopy of surfaces and interfaces 92 (1996) 273
- Marine, W., see Le, H.C. 96-98 (1996) 76
- Marine, W., see Kabashin, A.V. 96-98 (1996) 139
- Marine, W., see Le, H.C. 96-98 (1996) 164
- Marine, W., see Grangeon, F. 96-98 (1996) 186
- Marine, W., see Movtchan, I.A. 96-98 (1996) 251
- Marino, N., see Reitano, R. 96-98 (1996) 302
- Marinova, Ts., see Dimova-Malinskova, D. 96-98 (1996) 457
- Marinova, Ts., V. Krastev, C. Hallin, R. Yakimova and E. Janzén, Interface chemistry and electric characterisation of nickel metallisation on 6H-SiC 99 (1996) 119
- Marsh, J., L. Minel, M.G. Barthès-Labrousse and D. Gorse, The nature of the surface acidity of anodised titanium: an XPS study using 1,2-diaminoethane 99 (1996) 335
- Martelli, S., see Giorgi, R. 93 (1996) 101
- Martín, M.J., see Alfonso, J.E. 96-98 (1996) 791
- Martín, M.J., C. Zaldo and J. Mendiola, $Pb_{1-x}Ca_xTiO_3$ thin films prepared by laser ablation of ceramic targets 96-98 (1996) 823
- Martinez, H., C. Aurier, D. Gonbeau, M. Loudet and G. Pfister-Guillouzo, Studies of IT TiS_2 by STM, AFM and XPS: the mechanism of hydrolysis in air 93 (1996) 231
- Martino, M., see Leggeri, G. 96-98 (1996) 866
- Maruyama, K., Y. Aoki, M. Matsumoto, Y. Hiroshima and H. Ohta, Preparation of SiO_2/N_y films by reactive KrF laser ablation 96-98 (1996) 764
- Marzin, J.Y., see Moison, J.M. 92 (1996) 526
- Mascia, L. and Z. Zhang, Internal surface interactions in the plasma treatment of fine bore fluoropolymer tubings 93 (1996) 1
- Masuch, J., see Franchy, R. 93 (1996) 317
- Masuhara, H., see Fukumura, H. 96-98 (1996) 569
- Masui, M., T. Ogawa and M. Takeuchi, Electrochromic behavior of amorphous cobaltphthalocyanine thin films 92 (1996) 421
- Masui, M., M. Sasahara, T. Wada and M. Takeuchi, Gas sensitive properties of copperphthalocyanine thin films 92 (1996) 634
- Matsubayashi, N., see Shimada, H. 100/101 (1996) 56
- Matsuda, M., see Satoh, M. 92 (1996) 635
- Matsuda, T., see Kücher, P. 91 (1995) 359
- Matsui, S., see Kawano, H. 100/101 (1996) 193
- Matsumoto, M., see Maruyama, K. 96-98 (1996) 764
- Matsumoto, N., see Fujii, T. 96-98 (1996) 625
- Matsumoto, S., see Satoh, M. 92 (1996) 635
- Matsumoto, T., see Mimura, H. 92 (1996) 396
- Matsumoto, T., see Mimura, H. 92 (1996) 598
- Matsuo, Y. and K. Oishi, Oxide thickness dependence of photocurrent for the GeO_2/Ge film system 100/101 (1996) 248
- Matsushige, K., see Ishida, K. 100/101 (1996) 116
- Matsuura, Y., see Nishibe, T. 99 (1996) 35
- Matthias, E., see Petzoldt, S. 96-98 (1996) 199
- Matthias, E., see Gogoll, S. 96-98 (1996) 332
- Mauch, R.H., Electroluminescence in thin films 92 (1996) 589
- Mauchien, P., see García, C. 96-98 (1996) 370
- Maury, D., see Regolini, J.L. 100/101 (1996) 566
- Mayorov, A.P., see Bulgakov, A.V. 96-98 (1996) 159
- Mazhukin, V.I., I.V. Gusev, I. Smurov and G. Flamant, The influence of the electron structure of atoms shells on characteristics of optical breakdown in metal vapour 96-98 (1996) 82
- Mazhukin, V.I., I. Smurov and G. Flamant, 2D-simulation of the system: laser beam + laser plasma + target 96-98 (1996) 89
- McAleese, J., see Chadwick, D. 99 (1996) 417
- McAlpine, N.S., see Haneman, D. 92 (1996) 484
- McAuley, B., see Hajto, J. 92 (1996) 579
- McCarthy, M.I., see Hess, W.P. 96-98 (1996) 321
- McElnea, A.E., see Morris, G.C. 92 (1996) 167
- McGibbon, M.M., see Poretzky, A.A. 96-98 (1996) 859
- Meda, L., see Cerofolini, G.F. 93 (1996) 255
- Medina, J., see Gobernado-Mitre, I. 96-98 (1996) 474
- Medvedev, V.K., Yu. Suchorski and J.H. Block, Li-mediated feedback mechanism of oscillations in CO oxidation on a Rh field emitter tip 94/95 (1996) 200
- Medvedev, V.K., see Suchorski, Yu. 94/95 (1996) 207
- Medvedev, V.K., see Suchorski, Yu. 94/95 (1996) 217
- Mehdaoui, A., see Berling, D. 96-98 (1996) 739
- Mei, Y.-J., see Chang, T.-C. 92 (1996) 119
- Mei, Y.-J., see Chang, T.-C. 92 (1996) 571
- Meister, G., see Kürpick, U. 99 (1996) 221
- Mele, A., A. Giardini Guidoni, R. Kelly, A. Miotello, S. Orlando and R. Teghil, Spatial distribution of laser-ablated material by probing a plasma plume in three dimensions 96-98 (1996) 102
- Melmed, A.J., Recollections of Erwin Müller's laboratory: the development of FIM (1951-1956) 94/95 (1996) 17
- Melmed, A.J., see Lusby, T.A. 94/95 (1996) 300
- Melnik, N.N., see Bogonin, I.A. 92 (1996) 43
- Melnik, N.N., see Karuzskii, A.L. 92 (1996) 457
- Menand, A., see Bigot, A. 94/95 (1996) 261
- Menand, A., see Thuvander, M. 94/95 (1996) 343
- Menaucourt, J., see Fusy, J. 93 (1996) 211
- Mendiola, J., see Alfonso, J.E. 96-98 (1996) 791
- Mendiola, J., see Martín, M.J. 96-98 (1996) 823
- Meneve, J.L., J.F. Smith, N.M. Jennett and S.R.J. Saunders, Surface mechanical property testing by depth sensing indentation 100/101 (1996) 64
- Mengucci, P., see Leggeri, G. 96-98 (1996) 866
- Mens, A.J.M. and O.L.J. Gijzeman, AES study of electron beam induced damage on TiO_2 surfaces 99 (1996) 133

- Mercer, I., see Grätz, M. 96-98 (1996) 443
- Merkle, K.L., see Chan, D.K. 94/95 (1996) 409
- Merk, U., see Goerke, F. 96-98 (1996) 708
- Mermet, J.-L., see Mouche, M.-J. 91 (1995) 129
- Mermet, J.-L., see Braud, F. 91 (1995) 251
- Mertin, M., see Wesner, D.A. 96-98 (1996) 479
- Mertin, M., D. Offenberg, C.W. An, D.A. Wesner and E.W. Kreutz, Pulsed laser deposition of electroceramic thin films 96-98 (1996) 842
- Mesters, S., see Crecelius, G. 91 (1995) 50
- Metev, S., M. Ozegowski, G. Sepold and S. Burmester, Plasma parameters in pulsed laser-plasma deposition of thin films 96-98 (1996) 122
- Metheringham, W.J., see Dyer, P.E. 96-98 (1996) 849
- Meunier, M., see Izquierdo, R. 96-98 (1996) 855
- Meyer, F., see Mamor, M. 91 (1995) 342
- Meynen, H., see Stevens, R. 91 (1995) 208
- Miglio, L., see Sanguinetti, S. 91 (1995) 103
- Mihailescu, I.N., see Leggeri, G. 96-98 (1996) 866
- Mikado, T., see Ohdaira, T. 100/101 (1996) 73
- Mikado, T., see Suzuki, R. 100/101 (1996) 297
- Milburn, G.H.W., see Hajto, J. 92 (1996) 579
- Miller, M.K., see Babu, S.S. 94/95 (1996) 280
- Miller, M.K., I.M. Anderson and K.F. Russell, Precipitation and grain boundary segregation in molybdenum-doped NiAl 94/95 (1996) 288
- Miller, M.K., see Thomson, R.C. 94/95 (1996) 313
- Miller, M.K., see Pareige, P.J. 94/95 (1996) 362
- Miller, M.K., see Pareige, P. 94/95 (1996) 370
- Miller, M.K. and K.F. Russell, APFIM characterization of a high phosphorus Russian RPV weld 94/95 (1996) 378
- Miller, M.K., I.M. Anderson, J. Bentley and K.F. Russell, Phase separation in the Fe-Cr-Ni system 94/95 (1996) 391
- Miller, M.K. and K.F. Russell, Comparison of the rate of decomposition in Fe-45%Cr, Fe-45%Cr-5%Ni and duplex stainless steels 94/95 (1996) 398
- Mimura, H., see Nakamura, T. 92 (1996) 291
- Mimura, H., T. Matsumoto and Y. Kanemitsu, PL properties of porous Si anodized with various light illuminations 92 (1996) 396
- Mimura, H., T. Matsumoto and Y. Kanemitsu, Si-based optical devices using porous materials 92 (1996) 598
- Minato, M., see Suzuki, Y. 100/101 (1996) 165
- Minato, M., see Homma, T. 100/101 (1996) 189
- Minel, L., see Marsh, J. 99 (1996) 335
- Minemura, J., see Uchida, Y. 100/101 (1996) 478
- Ming, N.B., see Liu, J.M. 96-98 (1996) 819
- Minicò, S., see Scirè, S. 93 (1996) 309
- Minicò, S., see Crisafulli, C. 99 (1996) 401
- Miotello, A., see Mele, A. 96-98 (1996) 102
- Miotello, A., see Kelly, R. 96-98 (1996) 205
- Miotello, A., see Laidani, N. 99 (1996) 273
- Mitchell, K.A.R., see Aouadi, M.S. 99 (1996) 319
- Mitchell, T.E., see Chen, C.L. 94/95 (1996) 224
- Mitrelias, T., V.P. Ostanin, M. Gruyters and D.A. King, Design of an ultrahigh vacuum compatible system for studying the influence of acoustic waves on surface chemical processes 100/101 (1996) 305
- Mitsuhashi, H., see Nishibe, T. 99 (1996) 35
- Mitsui, T., N. Yamamoto, J. Yoshino, T. Tadokoro, S. Ohta, K. Yanashima and K. Inoue, Correlation between cathodoluminescence and structural defects in ZnS/GaAs(100) and ZnSe/GaAs(100) studied by transmission electron microscopy 100/101 (1996) 625
- Mitsui, Y., see Yano, F. 100/101 (1996) 138
- Mitterauer, J., Field emission from thin liquid metal films 95/96 (1996) 161
- Mityagin, Yu.A., see Bogonin, I.A. 92 (1996) 43
- Miura, T., M. Niwano, D. Shoji and N. Miyamoto, Initial stages of oxidation of hydrogen-terminated Si surface stored in air 100/101 (1996) 454
- Miura, T., see Niwano, M. 100/101 (1996) 607
- Miyamoto, N., see Enta, Y. 100/101 (1996) 449
- Miyamoto, N., see Miura, T. 100/101 (1996) 454
- Miyamoto, N., see Niwano, M. 100/101 (1996) 607
- Mizokawa, Y., see Ying, W.B. 100/101 (1996) 556
- Mizokawa, Y., W.B. Ying, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto, Phosphorus redistribution in the surface region of heavily phosphorus doped silicon 100/101 (1996) 561
- Mochizuki, K., H. Oguri, T. Kyotani and M. Isshiki, Epitaxial growth of ZnSe_{1-x}Te_x by the VPE method and its photoluminescence 92 (1996) 79
- Mogi, K., see Suzuki, M. 100/101 (1996) 51
- Mohite, U.K. and C.D. Lokhande, Electrosynthesis of yttrium chalcogenides from a non-aqueous bath 92 (1996) 151
- Mohnjuk, A.A., see Gusev, I.V. 91 (1995) 182
- Moison, J.M., L. Leprince, F. Barthe, F. Houzay, N. Lebouché, J.M. Gérard and J.Y. Marzin, Self-organized growth of InAs/GaAs quantum boxes 92 (1996) 526
- Möller, A., see Stavrev, M. 91 (1995) 257
- Møller, P.J., see Guo, Q. 92 (1996) 513
- Mollicone, M.M., L.C.O. Dacal and C.M.C. de Castilho, Local field and potential barrier in tunneling processes 94/95 (1996) 68
- Momose, Y., see Satoh, M. 92 (1996) 635
- Mönch, W., Chemical trends of barrier heights in metal-semiconductor contacts: on the theory of the slope parameter 92 (1996) 367
- Monk, P., see Dyer, P.E. 96-98 (1996) 415
- Moon, D.W., see Lee, J.C. 100/101 (1996) 97

- Morawski, A., see Pohoryles, B. 92 (1996) 417
- Morenza, J.L., see Serra, P. 96-98 (1996) 216
- Mori, T., see Fukada, T. 91 (1995) 227
- Morin, C., see Regolini, J.L. 100/101 (1996) 566
- Morisaki, H., see Shimasaki, M. 92 (1996) 617
- Morisawa, Y., I. Kikuma, N. Takayama and M. Takeuchi, Mirror polishing of InP wafer surfaces with NaOCl-citric acid 92 (1996) 147
- Morishita, T., see Pindoria, G. 100/101 (1996) 347
- Morita, M., see Aoki, T. 92 (1996) 132
- Morita, M., see Hatanaka, Y. 100/101 (1996) 621
- Morita, Y. and H. Tokumoto, STM analysis of wet-chemically prepared H-Si(001) surface 100/101 (1996) 440
- Morohashi, T., T. Hoshi, H. Nikaido and M. Kudo, Determination of the interface region in multilayer Si/Mo by Auger depth profile and factor analysis 100/101 (1996) 84
- Morohashi, T., see Kudo, M. 100/101 (1996) 134
- Morokawa, S., see Sakamoto, K. 100/101 (1996) 124
- Morozov, A.P., see Gorbunov, A.A. 96-98 (1996) 649
- Morris, G.C. and A.E. McElnea, Fluorine doped tin oxide films from spray pyrolysis of stannous fluoride solutions 92 (1996) 167
- Morris, G.C. and R.J. Vanderveen, Solar cells from thin films prepared by periodic pulse electrodeposition 92 (1996) 630
- Morrow, T., see Hendron, J.M. 96-98 (1996) 112
- Morrow, T., see Al-Wazzan, R.A. 96-98 (1996) 170
- Morrow, T., see Al-Wazzan, R.A. 99 (1996) 345
- Mouche, M.-J., J.-L. Mermet, F. Pires, E. Richard, J. Torres, J. Palteau and F. Braud, Process optimization of copper MOCVD using modeling experimental design 91 (1995) 129
- Mouche, M.-J., see Braud, F. 91 (1995) 251
- Mousa, M.S., Electron emission from carbon fibre tips 94/95 (1996) 129
- Movtchan, I.A., see Le, H.C. 96-98 (1996) 164
- Movtchan, I.A., W. Marine, R.W. Dreyfus, H.C. Le, M. Sentis and M. Autric, Optical spectroscopy of emission from Si-SiO_x nanoclusters formed by laser ablation 96-98 (1996) 251
- Možina, J., see Diaci, J. 96-98 (1996) 154
- Možina, J., see Kopač, S. 96-98 (1996) 420
- Možina, J., see Grad, L. 96-98 (1996) 591
- Mozysky, D.V., see Vladimirov, V.V. 94/95 (1996) 171
- Mu, C., see Numajiri, K. 100/101 (1996) 541
- Mugnier, J., see Garapon, C. 96-98 (1996) 836
- Mujica, A., see Rodríguez-Hernández, P. 92 (1996) 408
- Mukaida, M., see Togashi, H. 96-98 (1996) 267
- Mukhtar, E., see Ding, D. 96-98 (1996) 581
- Müller, F., see Mann, K. 96-98 (1996) 463
- Müller, G., see Pupeter, N. 94/95 (1996) 94
- Muñoz, A., see Rodríguez-Hernández, P. 92 (1996) 408
- Muñoz-Guillena, M.J., A. Linares-Solano and C. Salinas-Martínez de Lecea, High temperature SO₂ retention by CaO 99 (1996) 111
- Murakami, H., see Read, H.G. 94/95 (1996) 334
- Murakami, K., see Makimura, T. 96-98 (1996) 242
- Murakami, M., see Oku, T. 99 (1996) 265
- Muranoi, T., see Satoh, M. 92 (1996) 635
- Murata, J., T. Takeuchi, Y. Suzuki, N. Sanada and Y. Fukuda, Decomposition of triethylindium (TEI) on GaP(001) surface studied by TPD, XPS and RHEED 100/101 (1996) 417
- Murzin, V.N., see Bogonin, I.A. 92 (1996) 43
- Murzin, V.N., see Karuzskii, A.L. 92 (1996) 457
- Nagahama, I., see Hatakeyama, M. 100/101 (1996) 277
- Nagasawa, Y., see Sekine, T. 100/101 (1996) 30
- Nagumo, S., see Toyota, Y. 100/101 (1996) 360
- Naito, S., see Nakanishi, Y. 92 (1996) 400
- Nakahata, T., see Inanaga, K. 100/101 (1996) 421
- Nakai, H., see Qiu, H. 92 (1996) 47
- Nakajima, Y., see Takemura, S. 100/101 (1996) 107
- Nakamura, A., see Sugioka, K. 96-98 (1996) 347
- Nakamura, K., S. Ichimura and H. Shimizu, Oxygen adsorption on hydrogen-preadsorbed Si(111)7 × 7 observed by second harmonic generation (SHG) 100/101 (1996) 444
- Nakamura, T., K. Sasaki, K. Hayashi, H. Mimura and J. Kobayashi, Electron paramagnetic resonance measurements on porous silicon 92 (1996) 291
- Nakamura, T., see Tatsuoka, H. 92 (1996) 382
- Nakamura, T., see Nakanishi, Y. 92 (1996) 400
- Nakamura, T., see Lippert, T. 96-98 (1996) 601
- Nakamura, T., see Nakanishi, Y. 100/101 (1996) 639
- Nakane, H., see Endo, M. 94/95 (1996) 113
- Nakane, H., see Satoh, H. 94/95 (1996) 247
- Nakane, H., see Satoh, H. 100/101 (1996) 216
- Nakane, H., see Endo, M. 100/101 (1996) 378
- Nakanishi, Y., see Aoki, T. 92 (1996) 132
- Nakanishi, Y., see Jayatissa, A.H. 92 (1996) 300
- Nakanishi, Y., see Tatsuoka, H. 92 (1996) 382
- Nakanishi, Y., S. Naito, T. Nakamura, Y. Hatanaka and G. Shimaoka, The influence of residual O₂ gas in vacuum on the structural and luminescent properties of ZnF₂:Mn thin films 92 (1996) 400
- Nakanishi, Y., see Hatanaka, Y. 100/101 (1996) 621
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- Nakao, A., M. Kaibara, M. Iwaki, Y. Suzuki and M. Kusakabe, Surface characterization of cell adhesion controlled polymer modified by ion bombardment 100/101 (1996) 112
- Nakao, M., see Hatakeyama, M. 100/101 (1996) 277
- Nakata, R., see Tanaka, K. 100/101 (1996) 264
- Nakayama, F., see Hata, K. 94/95 (1996) 156

- Nakayama, N. and K. Ito, Sprayed films of stannite $\text{Cu}_2\text{ZnSnS}_4$ 92 (1996) 171
- Namba, K., see Fukada, T. 91 (1995) 227
- Natoli, J.Y., see Derrien, J. 92 (1996) 311
- Naundorf, V., see Al-Kassab, T. 94/95 (1996) 306
- Nava, F., see Gottlieb, U. 91 (1995) 82
- Nayak, D.K., see Lin, C.T. 92 (1996) 193
- Nennewitz, O., L. Spiess and V. Breternitz, Ohmic contacts to p-type 6H-silicon carbide 91 (1995) 347
- Neureither, B., see Hain, M. 91 (1995) 374
- Nguyen, S., see Kücher, P. 91 (1995) 359
- Ni Dheasuna, C., see Patterson, J.C. 91 (1995) 124
- Ni Dheasuna, C., see O'Reilly, M. 91 (1995) 152
- Nicolaescu, D., V. Filip and P.R. Wilshaw, Modelling of the field emission microtriode with emitter covered with porous silicon 94/95 (1996) 79
- Nicolaescu, D. and V. Filip, Modelling of a magnetic sensor based on vacuum field emission 94/95 (1996) 87
- Nicolas, G. and M. Autric, Excimer laser-induced hydrodynamical effects and surface modifications on silicon carbide 96-98 (1996) 296
- Nicolet, M.-A., Ternary amorphous metallic thin films as diffusion barriers for Cu metallization 91 (1995) 269
- Niino, H. and A. Yabe, Chemical surface modification of fluorocarbon polymers by excimer laser processing 96-98 (1996) 550
- Niino, H. and A. Yabe, Surface chemical reaction of polymer film with reactive intermediates produced by laser ablation of azido compound 96-98 (1996) 572
- Niino, H., see Lippert, T. 96-98 (1996) 601
- Nikaido, H., see Morohashi, T. 100/101 (1996) 84
- Nikiforov, A.P., see Skurat, V.E. 92 (1996) 441
- Nikitin, P.I., see Ksenevich, T.I. 92 (1996) 426
- Nikitin, P.I., see Grigorenko, A.N. 92 (1996) 466
- Nikitin, P.I., see Kabashin, A.V. 96-98 (1996) 139
- Nikulski, R., see Weber, A. 91 (1995) 314
- Nilsson, S., see Zeindl, H.P. 92 (1996) 552
- Ninomiya, K., T. Kure, Y. Sudo, K. Kuroda and H. Todokoro, A nondestructive analysis technique for residual thin films in deep-submicron contact holes 100/101 (1996) 551
- Ninomiya, S., see Emoto, T. 100/101 (1996) 355
- Nishibe, T., H. Mitsuhashi, Y. Matsuura and Y. Kawakyu, Approach to in situ characterization of polysilicon surfaces annealed by XeCl excimer laser 99 (1996) 35
- Nishigaki, S., see Yamada, K. 99 (1996) 21
- Nishijima, A., see Shimada, H. 100/101 (1996) 56
- Nishikawa, H., see Uchida, H. 100/101 (1996) 399
- Nishikawa, K., T. Nishiuchi, M. Yamamoto and O. Nishikawa, Observation of both Ni and Mo atom images by FIM with imaging plates 94/95 (1996) 295
- Nishikawa, O., see Nishikawa, K. 94/95 (1996) 295
- Nishio, M., see Gheyas, S.I. 100/101 (1996) 211
- Nishio, M., see Gheyas, S.I. 100/101 (1996) 634
- Nishio, M., see Gheyas, S.I. 100/101 (1996) 647
- Nishioka, T., see Sumitomo, K. 100/101 (1996) 503
- Nishiuchi, T., see Nishikawa, K. 94/95 (1996) 295
- Nishiyama, Y., see Arai, M. 99 (1996) 145
- Nishizawa, J., H. Sakuraba and T. Kurabayashi, Surface reaction mechanism in MOCVD 92 (1996) 89
- Niwa, M., K. Okada and R. Sinclair, Atomically flat, ultra thin-SiO₂/Si(001) interface formation by UHV heating 100/101 (1996) 425
- Niwa, M., see Idota, K. 100/101 (1996) 311
- Niwano, M., T. Miura, R. Tajima and N. Miyamoto, Infrared study of chemistry of Si surfaces in etching solution 100/101 (1996) 607
- Niwano, M., see Miura, T. 100/101 (1996) 454
- Nobili, C., see Corni, F. 91 (1995) 107
- Noda, Y., see Kayama, H. 92 (1996) 142
- Nomura, S., see Sato, K. 92 (1996) 639
- Nonaka, H., see Hattori, M. 100/101 (1996) 301
- Norton, D.P., B.C. Chakoumakos, D.H. Lowndes and J.D. Budai, Formation of artificially-layered high-temperature superconductors using pulsed-laser deposition 96-98 (1996) 672
- Norton, M.G., W. Jiang, J.T. Dickinson and K.W. Hipps, Pulsed laser ablation and deposition of fluorocarbon polymers 96-98 (1996) 617
- Norton, P.R., see Zhdanov, V.P. 99 (1996) 205
- Nowicka, E., Z. Wolfram, W. Lisowski and R. Duś, Investigation of atomic deuterium (hydrogen) emission from the surface of some transition metal deuterides (hydrides) 93 (1996) 53
- Nozaki, S., see Shimasaki, M. 92 (1996) 617
- Nozdrin, V.S., see Karuzskii, A.L. 92 (1996) 457
- Nukui, A., see Suehara, S. 100/101 (1996) 252
- Numajiri, K., T. Goya, R. Tobe, O. Okada, N. Hosokawa, C. Mu, N. Cox, C. Scott and J. Yu, High-rate deposition of high-quality Cu film with LPCVD 100/101 (1996) 541
- Obraztsova, E.D., see Pimenov, S.M. 92 (1996) 106
- O'Connor, D.J., see Kang, H.J. 100/101 (1996) 329
- Oelhafen, P., see Kilper, R. 91 (1995) 93
- Offenberg, D., see Mertin, M. 96-98 (1996) 842
- Ogata, K., see Fukada, T. 91 (1995) 227
- Ogawa, H., see Gheyas, S.I. 100/101 (1996) 211
- Ogawa, H., see Gheyas, S.I. 100/101 (1996) 634
- Ogawa, H., see Gheyas, S.I. 100/101 (1996) 647
- Ogawa, T., see Masui, M. 92 (1996) 421
- Ogawa, Y., A. Jäger-Waldau, T.H. Hua, Y. Hashimoto and K. Ito, Influence of KCN treatment on CuInS_2 thin films 92 (1996) 232
- Ogino, T., see Kobayashi, Y. 100/101 (1996) 407

- Ogino, T., see Sumitomo, K. 100/101 (1996) 503
 Ogino, T., see Prabhakaran, K. 100/101 (1996) 518
 Ogura, T., see Kim, J.H. 92 (1996) 566
 Oguri, H., see Mochizuki, K. 92 (1996) 79
 Ohba, T., Advanced multilevel metallization technology 91 (1995) 1
 Ohbuchi, T., see Qiu, H. 92 (1996) 47
 Ohdaira, T., R. Suzuki, T. Mikado, H. Ohgaki, M. Chiwaki, T. Yamazaki and M. Hasegawa, High sensitivity of positron-annihilation induced Auger-electron spectroscopy to surface impurities 100/101 (1996) 73
 Ohdaira, T., see Suzuki, R. 100/101 (1996) 297
 Ohgaki, H., see Ohdaira, T. 100/101 (1996) 73
 Ohgaki, H., see Suzuki, R. 100/101 (1996) 297
 Ohgami, K., see Kawano, H. 100/101 (1996) 193
 Ohgami, K., see Kawano, H. 100/101 (1996) 199
 Ohno, S., see Sakka, Y. 100/101 (1996) 232
 Ohnuma, H., see Watanabe, K. 99 (1996) 411
 Ohnuma, Y., see Sugioka, K. 96-98 (1996) 347
 Ohshima, H., see Yamauchi, S. 100/101 (1996) 522
 Ohshita, A., see Hata, K. 94/95 (1996) 156
 Ohta, H., see Maruyama, K. 96-98 (1996) 764
 Ohta, S., see Mitsui, T. 100/101 (1996) 625
 Ohtani, S., see Izumi, Y. 100/101 (1996) 179
 Ohtani, S., see Katoh, M. 100/101 (1996) 226
 Ohte, T., see Izumi, Y. 100/101 (1996) 179
 Ohte, T., see Katoh, M. 100/101 (1996) 226
 Ohya, K., see Kawata, J. 100/101 (1996) 338
 Oishi, K., see Matsuo, Y. 100/101 (1996) 248
 Oiwa, R., see Iwai, H. 100/101 (1996) 283
 Oka, Y., see Jen, J.Y. 92 (1996) 547
 Okada, K., see Niwa, M. 100/101 (1996) 425
 Okada, O., see Numajiri, K. 100/101 (1996) 541
 Okada, O., see Kim, S.W. 100/101 (1996) 546
 Okazaki, M., see Kücher, P. 91 (1995) 359
 Oku, T., E. Kawakami, M. Uekubo, K. Takahiro, S. Yamaguchi and M. Murakami, Diffusion barrier property of TaN between Si and Cu 99 (1996) 265
 Okubo, S., see Shibata, N. 100/101 (1996) 69
 Okuyama, F., see Aoyama, T. 100/101 (1996) 351
 Oltra, R., O. Yavaş, F. Cruz, J.P. Boquillon and C. Sartori, Modelling and diagnostic of pulsed laser cleaning of oxidized metallic surfaces 96-98 (1996) 484
 Ono, K., see Inanaga, K. 100/101 (1996) 421
 Ooie, T., see Hattori, M. 100/101 (1996) 301
 Oosterlaken, T.G.M., see Jongste, J.F. 91 (1995) 162
 Oosterlaken, T.G.M., see Leusink, G.J. 91 (1995) 215
 Opilan, R.L., see Weber, A. 91 (1995) 314
 O'Reilly, M., see Patterson, J.C. 91 (1995) 124
 O'Reilly, M., X. Jiang, J.T. Beechinor, S. Lynch, C. Ni Dheasuna, J.C. Patterson and G.M. Crean, Investigation of the oxidation behaviour of thin film and bulk copper 91 (1995) 152
 Orlando, S., see Mele, A. 96-98 (1996) 102
 Orlikovsky, A.A., see Bogonin, I.A. 92 (1996) 43
 Osaki, T., see Yea, B. 100/101 (1996) 365
 Oshita, M., see Tatsuoka, H. 92 (1996) 382
 Osman, M.A. and B.A. Keller, Wettability of native silver surfaces 99 (1996) 261
 Ostanin, V.P., see Mitrelias, T. 100/101 (1996) 305
 Ottaviani, G., see Corni, F. 91 (1995) 107
 Otto, A., see Futamata, M. 100/101 (1996) 60
 Owen, A.E., see Hajto, J. 92 (1996) 579
 Oyoshi, K., S. Hishita, K. Wada, S. Suehara and T. Aizawa, Roughness study of ion-irradiated silica glass surface 100/101 (1996) 374
 Ozawa, M., see Kita, A. 100/101 (1996) 652
 Ozegowski, M., see Metev, S. 96-98 (1996) 122
 Palteau, J., see Mouche, M.-J. 91 (1995) 129
 Palteau, J., see Bourhila, N. 91 (1995) 175
 Palteau, J., see Braud, F. 91 (1995) 251
 Palm, H., see Kücher, P. 91 (1995) 359
 Palorec, J., see Stegemann, K.-H. 91 (1995) 308
 Pamler, W., see Ruhl, G. 91 (1995) 382
 Panczer, G., see Garapon, C. 96-98 (1996) 836
 Panjan, P., see Zalar, A. 100/101 (1996) 92
 Panknin, D., see Teichert, J. 91 (1995) 44
 Panknin, D., see Teichert, St. 91 (1995) 56
 Panzner, M., R. Dietsch, Th. Holz, H. Mai and S. Völlmar, Scale-up of pulsed laser deposition (PLD) for 4"-wafer coating 96-98 (1996) 643
 Pareige, P.J., K.F. Russell and M.K. Miller, APFIM studies of the phase transformations in thermally aged ferritic FeCuNi alloys: comparison with aging under neutron irradiation 94/95 (1996) 362
 Pareige, P. and M.K. Miller, Characterization of neutron-induced copper-enriched clusters in pressure vessel steel weld: an APFIM study 94/95 (1996) 370
 Park, N.S., see Kang, H.J. 100/101 (1996) 160
 Park, N.S., see Kang, H.J. 100/101 (1996) 329
 Passeggi, Jr., M.C.G., see Vaquira, I. 93 (1996) 247
 Pastoor, E., see Cillessen, J.F.M. 96-98 (1996) 744
 Pastuszka, S., A.S. Terekhov and A. Wolf, 'Stable to unstable' transition in the (Cs, O) activation layer on GaAs (100) surfaces with negative electron affinity in extremely high vacuum 99 (1996) 361
 Paterson, P.J.K., see Hoffman, A. 93 (1996) 301
 Patterson, J.C., C. Ni Dheasuna, J. Barrett, T.R. Spalding, M. O'Reilly, X. Jiang and G.M. Crean, Electroless copper metallisation of titanium nitride 91 (1995) 124
 Patterson, J.C., see O'Reilly, M. 91 (1995) 152
 Paul, J., see Hirschauer, B. 99 (1996) 285
 Paulson, P.D. and V. Dutta, Photoellipsometric studies on CdTe thin films 92 (1996) 295
 Pedraza, F., see Vázquez, A. 99 (1996) 213

- Peled, A., see Kathia de-Mesquita Braga, A. 93 (1996) 197
- Pelleg, J., see Sade, G. 91 (1995) 263
- Pelli, S., see Afonso, C.N. 96-98 (1996) 760
- Peña, J.L., see Quintana, P. 99 (1996) 325
- Pere, J., see Valden, M. 99 (1996) 83
- Perestoronin, A.V., see Bogonin, I.A. 92 (1996) 43
- Perestoronin, A.V., see Karuzskii, A.L. 92 (1996) 457
- Perez, A., see Afif, M. 96-98 (1996) 469
- Pérez, B., see Gobernado-Mitre, I. 96-98 (1996) 474
- Pérez Casero, R., R. Gómez San Román, C. Maréchal, J.P. Enard and J. Perrière, Laser ablation of oxides: study of the oxygen incorporation by ^{18}O isotopic tracing techniques 96-98 (1996) 697
- Perrière, J., see Gonzalo, J. 96-98 (1996) 693
- Perrière, J., see Pérez Casero, R. 96-98 (1996) 697
- Perrière, J., see Laidani, N. 99 (1996) 273
- Perrin, C., see Barthe, M.F. 96-98 (1996) 359
- Perrone, A., see Leggieri, G. 96-98 (1996) 866
- Pertsyn, A.I., see Skurat, V.E. 92 (1996) 441
- Perumareddi, J.R., see Sastri, V.S. 93 (1996) 31
- Pessa, M., see Valden, M. 99 (1996) 83
- Petersson, C.S., see Bocelli, S. 91 (1995) 30
- Petzoldt, S., J. Reif and E. Matthias, Laser plasma threshold of metals 96-98 (1996) 199
- Pfister-Guillouzo, G., see Martinez, H. 93 (1996) 231
- Pfleging, W., D.A. Wesner and E.W. Kreutz, CCl_4 -assisted CF_4 etching of silicon in a microwave-assisted LDE (laser dry etching)-process 96-98 (1996) 496
- Piatkowski, P., see Szymonski, M. 100/101 (1996) 102
- Piel, H., see Pupeter, N. 94/95 (1996) 94
- Pimenov, S.M., A.A. Smolin, E.D. Obratsova, V.I. Konov, U. Bögli, A. Blatter, E.N. Loubnin, M. Maillat, A. Leijala, J. Burger and H.E. Hintermann, Tribological properties of smooth diamond films 92 (1996) 106
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- Pireaux, J.J., see Girardeaux, C. 96-98 (1996) 586
- Pires, F., see Mouche, M.-J. 91 (1995) 129
- Pirš, J., see Kopač, S. 96-98 (1996) 420
- Pitaval, M., see Ramos, S.M.M. 93 (1996) 191
- Plekhanov, P.S., see Givargizov, E.I. 94/95 (1996) 117
- Plekhanov, P.S., see Zhirmov, V.V. 94/95 (1996) 144
- Plötner, M., see Stavreva, Z. 91 (1995) 192
- Pohoryles, B. and A. Morawski, Surface charge transfer in plastically deformed Si 92 (1996) 417
- Polgár, K., see Alfonso, J.E. 96-98 (1996) 791
- Polmear, I.J., see Ringer, S.P. 94/95 (1996) 253
- Polo, M.C., R. Aguiar, P. Serra, L. Clèries, M. Varela and J. Esteve, Carbon nitride thin films obtained by laser ablation of graphite in a nitrogen plasma 96-98 (1996) 870
- Pomes, R., see Quintana, P. 99 (1996) 325
- Pompe, W., see Gorbunov, A.A. 96-98 (1996) 649
- Pons, M., C. Bernard, H. Rouch and R. Madar, The modelling routes for the chemical vapour deposition process: application to $\text{Si}_{1-x}\text{Ge}_x$ deposition 91 (1995) 34
- Popovych, D.I., see Kotlyarchuk, B.K. 96-98 (1996) 192
- Porte, M., see Guyot, M. 96-98 (1996) 802
- Postawa, Z., see Szymonski, M. 100/101 (1996) 102
- Powalla, M., see Herz, K. 91 (1995) 87
- Prabhakaran, K. and T. Ogino, Behavior of ultrathin layers of Co on Si and Ge systems 100/101 (1996) 518
- Pradeep, N., see Sharma, R.B. 94/95 (1996) 177
- Pradier, C.-M., see Janin, E. 99 (1996) 371
- Prakash, N.S., see Afif, M. 96-98 (1996) 469
- Preckwinkel, U., see Wengenmair, H. 99 (1996) 313
- Predtechensky, M.R., see Bulgakov, A.V. 96-98 (1996) 159
- Predtechensky, M.R., O.M. Tukhto, A.N. Smal' and S.A. Vasil'eva, Substrate size effect at off-axis laser deposition of multicomponent films 96-98 (1996) 717
- Prieto, A.C., see García, C. 96-98 (1996) 370
- Prieto, A.C., see Gobernado-Mitre, I. 96-98 (1996) 474
- Prohaska, T., see Asikainen, T. 99 (1996) 91
- Prokashnikov, A.V., see Zimin, S.P. 91 (1995) 355
- Proyer, S., E. Stangl, M. Borz and D. Bäuerle, Classification of particulates on pulsed-laser deposited Y-Ba-Cu-O films 96-98 (1996) 668
- Proyer, S., see Li, S.T. 96-98 (1996) 713
- Proyer, S., see Stangl, E. 96-98 (1996) 731
- Przyłuski, J., see Borkowska, R. 92 (1996) 447
- Puech, M. and Ph. Maquin, Low temperature etching of Si and PR in high density plasmas 100/101 (1996) 579
- Pupeter, N., T. Habermann, A. Kirschner, E. Mahner, G. Müller and H. Piel, Comparative studies on enhanced field emission from mechanically and chemically polished broad-area Nb, Cu, and Al cathodes 94/95 (1996) 94
- Puretzky, A.A., see Leboeuf, J.N. 96-98 (1996) 14
- Puretzky, A.A., see Chen, K.R. 96-98 (1996) 45
- Puretzky, A.A., see Geohagan, D.B. 96-98 (1996) 131
- Puretzky, A.A., D.B. Geohagan, G.E. Jellison Jr. and M.M. McGibbon, Comparative diagnostics of ArF- and KrF-laser generated carbon plumes used for amorphous diamond-like carbon film deposition 96-98 (1996) 859

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- Qiu, H., T. Ohbuchi, H. Nakai and M. Hashimoto, Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on MgO(001) 92 (1996) 47
- Qiu, S.N., C.X. Qiu and I. Shih, Diffusion length measurements on electrodeposited CuInSe_2 cells 92 (1996) 306
- Queirolo, G., see Corni, F. 91 (1995) 107
- Queirolo, G., see Marangon, M.S. 91 (1995) 157
- Quintana, P., L. Veleza, W. Cauich, R. Pomes and J.L. Peña, Study of the composition and morphology of initial stages of corrosion products formed on Zn plates exposed to the atmosphere of southeast Mexico 99 (1996) 325
- Raen, S., see Torkelsen, N.G. 93 (1996) 199
- Radelaar, S., see Jongste, J.F. 91 (1995) 162
- Radelaar, S., see Leusink, G.J. 91 (1995) 215
- Radermacher, K., see Crecelius, G. 91 (1995) 50
- Raineri, V., see Ravesi, S. 91 (1995) 19
- Ramm, P., see Ruhl, G. 91 (1995) 382
- Ramos, J., see García, C. 96-98 (1996) 370
- Ramos, S.M.M., B. Canut, M. Ambri, N. Bonardi, R. Brenier, M. Pitaval, P. Thevenard and M. Brunel, Formation of polycrystalline BaTi_2O_7 compounds in barium implanted TiO_2 93 (1996) 191
- Rangelow, I.W., see Zaborowski, M. 91 (1995) 239
- Rao, C.N.R., see Hari Kumar, K.R. 93 (1996) 135
- Rao, K.V., see Tyunina, M. 96-98 (1996) 831
- Raschke, T., see Kaufmann, C. 91 (1995) 291
- Rauschenbach, B., see Wengenmair, H. 99 (1996) 313
- Ravelosona, D., see Abert, A. 96-98 (1996) 703
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- Read, H.G. and H. Murakami, Microstructural influences on the decomposition of an Al-containing ferritic stainless steel 94/95 (1996) 334
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- Rebhan, T., see Geiger, M. 96-98 (1996) 309
- Reckzügel, M.C., V. Gorodetskii and J.H. Block, Digitizing chemical oscillations: analyzing experimental data of the CO oxidation on a Pt-tip 94/95 (1996) 194
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- Rector, J.H., see Dam, B. 96-98 (1996) 679
- Regolini, J.L., J. Margail, S. Bodnar, D. Maury and C. Morin, Selective epitaxial Si based layers and TiSi_2 deposition by integrated chemical vapor deposition 100/101 (1996) 566
- Reichling, M., see Gogoll, S. 96-98 (1996) 332
- Reif, J., see Petzoldt, S. 96-98 (1996) 199
- Reiff, S., see Kawada, H. 100/101 (1996) 587
- Reinhardt, C., see Grünewald, W. 93 (1996) 157
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- Richard, E., see Mouche, M.-J. 91 (1995) 129
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- Rogalla, H., see Blank, D.H.A. 96-98 (1996) 685
- Röhl, S., see Hain, M. 91 (1995) 374
- Rohr, K., see Granse, G. 96-98 (1996) 97
- Romand, M., see Afif, M. 96-98 (1996) 469
- Ronay, M., see Kücher, P. 91 (1995) 359
- Ronda, A., see Derrien, J. 92 (1996) 311
- Rooryck, V., see Reniers, F. 92 (1996) 35
- Roos, W.D., see Viljoen, P.E. 100/101 (1996) 612
- Roose, N., see Reniers, F. 99 (1996) 379
- Roper, M.D., see Voorma, H.-J. 93 (1996) 221
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- Rouch, H., see Pons, M. 91 (1995) 34
- Rougier, P., see Guyot, M. 96-98 (1996) 802
- Roussel, Ph.J., see Donat, R.A. 91 (1995) 77
- Roussel, Ph.J., see Stevens, R. 91 (1995) 208
- Rowan, C., see Watson, T.A. 96-98 (1996) 532
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- Rupp, A., see Granse, G. 96-98 (1996) 97
- Rupp, R., see Behner, H. 99 (1996) 27
- Russell, K.F., see Miller, M.K. 94/95 (1996) 288
- Russell, K.F., see Pareige, P.J. 94/95 (1996) 362
- Russell, K.F., see Miller, M.K. 94/95 (1996) 378
- Russell, K.F., see Miller, M.K. 94/95 (1996) 391
- Russell, K.F., see Miller, M.K. 94/95 (1996) 398
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- Sabet-Dariani, R., see Crisp, R.S. 92 (1996) 198
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- Saito, Y., see Hata, K. 94/95 (1996) 156
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- Sakurai, T., see Ringer, S.P. 94/95 (1996) 253
- Sakurai, T., see Bakhtizin, R.Z. 94/95 (1996) 478
- Sakurai, T., see Jeon, D. 94/95 (1996) 493
- Salaschenko, N.N., see Gorbunov, A.A. 96-98 (1996) 649
- Salinas-Martínez de Lecea, C., see Muñoz-Guillena, M.J. 99 (1996) 111
- Sameshima, T., Laser beam application to thin film transistors 96-98 (1996) 352
- Sanada, N., see Fukuda, Y. 92 (1996) 212
- Sanada, N., see Murata, J. 100/101 (1996) 417
- Sánchez, F., see Aguiar, R. 96-98 (1996) 405
- Sands, D., see Cranton, W.M. 96-98 (1996) 501
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- Sanyal, M.K., see Banerjee, S. 99 (1996) 255
- Sartori, C., see Oltra, R. 96-98 (1996) 484
- Sasahara, M., see Masui, M. 92 (1996) 634
- Sasaki, K., see Nakamura, T. 92 (1996) 291
- Sasaki, M., see Yoshida, S. 100/101 (1996) 184
- Sasaki, T.A., see Yamamoto, H. 100/101 (1996) 333
- Sassoli, H., see Grangeon, F. 96-98 (1996) 186
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- Sato, T., see Shimada, H. 100/101 (1996) 56
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- Savchuk, V.K., see Kotlyarchuk, B.K. 96-98 (1996) 192
- Savenije, T.J., see Marée, C.H.M. 93 (1996) 291
- Savitsky, V.G., see Kotlyarchuk, B.K. 96-98 (1996) 192
- Savoia, C., see Marangon, M.S. 91 (1995) 157
- Schaafsma, T.J., see Marée, C.H.M. 93 (1996) 291
- Scherer, M., see Gräfe, A. 91 (1995) 187
- Schiller, C., see Fransen, M.J. 94/95 (1996) 107
- Schittelm, F., see Ahrens, C. 91 (1995) 285
- Schmid, P.E., see Wu, W.T. 92 (1996) 391
- Schmidt, M.J.J., see Dyer, P.E. 96-98 (1996) 849
- Schmidt, N.M., see Remenyuk, A.D. 91 (1995) 352
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- Schubert, M.B., see Wanka, H.N. 93 (1996) 339
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- Schumacher, D., see Futamata, M. 100/101 (1996) 60
- Schwegle, W., see Abert, A. 96-98 (1996) 703
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- Scott, C., see Numajiri, K. 100/101 (1996) 541
- Seah, M.P., see Gilmore, I.S. 93 (1996) 273
- Sébenne, C.A., see Reqqass, H. 92 (1996) 357
- Seibt, E.W., see Zalar, A. 100/101 (1996) 92
- Seidman, D.N., see Chan, D.K. 94/95 (1996) 409
- Seidman, D.N., see Shashkov, D.A. 94/95 (1996) 416
- Seifert, N., G. Betz and W. Husinsky, Hydrodynamic phenomena during laser irradiation: a finite difference approach 96-98 (1996) 33
- Sekatskii, S.K., see Konopsky, V.N. 94/95 (1996) 148
- Sekiguchi, A., see Kim, S.W. 100/101 (1996) 546
- Sekiguchi, M., see Emoto, T. 100/101 (1996) 355
- Sekine, S., see Hattori, M. 100/101 (1996) 301
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- Senkiw, K., see Chadwick, D. 99 (1996) 417
- Sentis, M., see Le, H.C. 96-98 (1996) 76
- Sentis, M., see Kabashin, A.V. 96-98 (1996) 139
- Sentis, M., see Le, H.C. 96-98 (1996) 164
- Sentis, M., see Movtchan, I.A. 96-98 (1996) 251
- Sepold, G., see Metev, S. 96-98 (1996) 122
- Serbanescu, M.D., see Belu-Marian, A. 91 (1995) 63
- Serizawa, N., see Kawano, H. 100/101 (1996) 199
- Serra, P., L. Clères and J.L. Morenza, Analysis of the expansion of hydroxyapatite laser ablation plumes 96-98 (1996) 216
- Serra, P., see Polo, M.C. 96-98 (1996) 870
- Sewing, A., see Gorbunov, A.A. 96-98 (1996) 649
- Shafeev, G.A., see Dolgaev, S.I. 96-98 (1996) 491
- Shannon, M.A., see Mao, X. 96-98 (1996) 126
- Shannon, M.A., see Russo, R.E. 96-98 (1996) 144
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- Shih, K.L., see Tsong, T.T. 94/95 (1996) 472
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- Shimizu, H., see Nakamura, K. 100/101 (1996) 444
- Shimizu, R., see Ding, Z.-J. 100/101 (1996) 15
- Shin, J.-J., see Dickinson, J.T. 96-98 (1996) 316
- Shin, J.J., see Dickinson, J.T. 96-98 (1996) 326
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- Shiraki, Y., see Lin, C.T. 92 (1996) 193
- Shoji, D., see Miura, T. 100/101 (1996) 454
- Show, Y., see Shimasaki, M. 92 (1996) 617
- Shub, V.E., see Uglov, S.A. 92 (1996) 656
- Shuttleworth, S., Optimisation of laser wavelength in the ablation sampling of glass materials 96-98 (1996) 513
- Siegbahn, K., see Ding, D. 96-98 (1996) 581
- Siekierski, M., see Borkowska, R. 92 (1996) 447
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- Silberberg, E., see Reniers, F. 99 (1996) 379
- Simakin, A.V., see Dolgaev, S.I. 96-98 (1996) 491
- Simon, L., see Aubel, D. 99 (1996) 169
- Sinclair, R., see Niwa, M. 100/101 (1996) 425
- Singhal, R.P., see Wang, S.L. 93 (1996) 205
- Skatkov, L.I., P.G. Cheremskoy, V.P. Gomozev and B.I. Bayrachny, Investigation of the solid surface structural inhomogeneities by the 'combined' small-angle X-ray scattering and Hg porosimetry methods 99 (1996) 367
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- Smertenko, P.S., see Gorbach, T.Ya. 96-98 (1996) 881
- Smith, A.D., see Voorma, H.-J. 93 (1996) 221
- Smith, G.D.W., see Sijbrandij, S.J. 94/95 (1996) 428
- Smith, G.D.W., see Cerezo, A. 94/95 (1996) 457
- Smith, J.F., see Meneve, J.L. 100/101 (1996) 64
- Smolin, A.A., see Pimenov, S.M. 92 (1996) 106
- Smurov, I., see Mazhukin, V.I. 96-98 (1996) 82
- Smurov, I., see Mazhukin, V.I. 96-98 (1996) 89
- Smurov, I., see Gnedomets, A.G. 96-98 (1996) 272
- Smurov, I., see Titov, V. 96-98 (1996) 387
- Smurov, I.Yu., see Ignatiev, M.B. 96-98 (1996) 505
- Snell, A.J., see Hajto, J. 92 (1996) 579
- Söderholm, S., see Hirschauer, B. 99 (1996) 285
- Soeda, F., see Ito, H. 100/101 (1996) 152
- Soga, M., see Furuya, M. 100/101 (1996) 508
- Soga, T., see Yu, G. 100/101 (1996) 617
- Somers, M.A.J., see Graat, P.C.J. 100/101 (1996) 36
- Son, U.T., see Zhironov, V.V. 94/95 (1996) 144
- Song, J.H., see Lie, D.Y.C. 92 (1996) 557
- Soukiasian, P., see Spiess, L. 92 (1996) 501
- Souma, I., see Jen, J.Y. 92 (1996) 547
- Sowa, K., see Nakanishi, Y. 100/101 (1996) 639
- Spalding, T.R., see Patterson, J.C. 91 (1995) 124
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- Spinelli, N., see Amoroso, S. 96-98 (1996) 175
- Sreenivas, K., see Tyunina, M. 96-98 (1996) 831
- Stamm, H., see Alunovic, M. 96-98 (1996) 222
- Stangl, E., see Proyer, S. 96-98 (1996) 668
- Stangl, E., see Li, S.T. 96-98 (1996) 713
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- Stehle, M., see Boher, P. 96-98 (1996) 376
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- Stepanova, A.N., see Givargizov, E.I. 94/95 (1996) 117
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- Stiller, K., see Thuvander, M. 94/95 (1996) 343
- Stone, D.R., see Lu, C.R. 92 (1996) 404
- Stone, D.R., see Lu, C.R. 92 (1996) 543
- Streiter, R., see Wolf, H. 91 (1995) 332
- Streller, U., B. Li, A. Krabbe and N. Schwentner, Photon-induced dry etching of Si(100) in the VUV 96-98 (1996) 448
- Stribley, K., see Sykes, D.E. 100/101 (1996) 77
- Stritzker, B., see Wengenmair, H. 99 (1996) 313
- Stuke, M., see Götz, T. 96-98 (1996) 280
- Su, W.B., see Tsong, T.T. 94/95 (1996) 472
- Suchorski, Yu., see Medvedev, V.K. 94/95 (1996) 200
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- Suehara, S., see Oyoshi, K. 100/101 (1996) 374
- Suemitsu, M., see Enta, Y. 100/101 (1996) 449
- Sugahara, K., see Yea, B. 100/101 (1996) 365
- Sugihara, T., see Kuba, K. 96-98 (1996) 659
- Sugimoto, J., see Tachiwaki, T. 100/101 (1996) 272
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- Sugiyama, S., see Deno, H. 96-98 (1996) 563
- Sulpice, A., see Gottlieb, U. 91 (1995) 82
- Sumita, I., see Idota, K. 100/101 (1996) 311
- Sumitomo, K., T. Nishioka and T. Ogino, Atomic structure analysis of the interfaces in Si/Ge superlattices 100/101 (1996) 503
- Sun, C.Y., see Chuang, F.Y. 92 (1996) 452
- Sun, C.Y., see Li, D.C. 92 (1996) 665
- Sundqvist, B.U.R., see Ehring, H. 96-98 (1996) 577
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- Suoninen, E., see Kartio, I. 93 (1996) 167
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- Suzuki, M., see Kusunoki, T. 100/101 (1996) 207
- Suzuki, R., see Ohdaira, T. 100/101 (1996) 73

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- Suzuki, T., see Homma, T. 100/101 (1996) 189
- Suzuki, Y., see Fukuda, Y. 92 (1996) 212
- Suzuki, Y., see Nakao, A. 100/101 (1996) 112
- Suzuki, Y., see Sakamoto, K. 100/101 (1996) 124
- Suzuki, Y., T. Homma, M. Minato and Y. Itoh, Effect of different surface treatments on the precipitation of boron nitride for stainless steel SUS304 100/101 (1996) 165
- Suzuki, Y., see Murata, J. 100/101 (1996) 417
- Svanberg, S., see Grütz, M. 96-98 (1996) 443
- Svechnikov, S.V., see Gorbach, T.Ya. 96-98 (1996) 881
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- Sverbil, P.P., see Bogonin, I.A. 92 (1996) 43
- Swart, H.C., see Viljoen, P.E. 100/101 (1996) 612
- Swenson, P., see Ding, D. 96-98 (1996) 581
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- Sytkin, N.N., see Ivchenko, V.A. 94/95 (1996) 267
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- Tadokoro, T., see Mitsui, T. 100/101 (1996) 625
- Tait, J.P., see Dyer, P.E. 96-98 (1996) 596
- Tajima, R., see Niwano, M. 100/101 (1996) 607
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- Takahagi, T., see Shingubara, S. 91 (1995) 220
- Takahashi, Y., see Iijima, M. 100/101 (1996) 120
- Takahiro, K., see Oku, T. 99 (1996) 265
- Takano, H., see Furuya, M. 100/101 (1996) 508
- Takaoka, T., see Takagaki, T. 92 (1996) 287
- Takayama, N., see Morisawa, Y. 92 (1996) 147
- Takegawa, Y., see Enta, Y. 100/101 (1996) 449
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- Takenaka, H., see Suzuki, M. 100/101 (1996) 51
- Takeuchi, M., see Morisawa, Y. 92 (1996) 147
- Takeuchi, M., see Masui, M. 92 (1996) 421
- Takeuchi, M., see Masui, M. 92 (1996) 634
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- Takeuchi, T., see Murata, J. 100/101 (1996) 417
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- Tan, J., see Maïssa, S. 94/95 (1996) 136
- Tan, K.H., see Kasrai, M. 99 (1996) 303
- Tan, K.L., see Li, K. 99 (1996) 59
- Tanaka, A., see Jo, M. 100/101 (1996) 11
- Tanaka, K., N. Yokota, N. Shirai, Q. Zhuang and R. Nakata, Angular resolved EPMA analysis of thin films prepared by pulsed laser ablation of CdWO₄(010) 100/101 (1996) 264
- Tanemura, M., see Aoyama, T. 100/101 (1996) 351
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- Tani, T., see Saito, S. 100/101 (1996) 260
- Tanioka, H., see Yea, B. 100/101 (1996) 365
- Tansley, T.L., see Zhou, B. 100/101 (1996) 643
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- Tanuma, S., see Kitada, T. 100/101 (1996) 89
- Tapfer, L., see Berling, D. 96-98 (1996) 739
- Tashiro, H., see Sugioka, K. 96-98 (1996) 347
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- Teixeira Rabelo, J.N., see Zubov, V.I. 92 (1996) 436

- Terekhov, A.S., see Pastuszka, S. 99 (1996) 361
- Theodore, N.D., see Lie, D.Y.C. 92 (1996) 557
- Thestrup, B., see Svendsen, W. 96-98 (1996) 518
- Thevenard, P., see Ramos, S.M.M. 93 (1996) 191
- Thomas, C.B., see Cranton, W.M. 96-98 (1996) 501
- Thomas, N., see Bourhila, N. 91 (1995) 175
- Thomas, O., see Affronte, M. 91 (1995) 98
- Thompson, L.T., see Choi, J.-G. 93 (1996) 143
- Thomson, R.C. and M.K. Miller, An atom probe study of cementite precipitation in autotempered martensite in an Fe-Mn-C alloy 94/95 (1996) 313
- Thomy, A., see Dauscher, A. 96-98 (1996) 410
- Thorns, A., see Goerke, F. 96-98 (1996) 708
- Thungström, G., see Bocelli, S. 91 (1995) 30
- Thuvander, M., K. Stiller, D. Blavette and A. Menand, Grain boundary precipitation and segregation in Ni-16Cr-9Fe model materials 94/95 (1996) 343
- Thuvander, M., see Zackrisson, J. 94/95 (1996) 351
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- Tillman, C., see Grätz, M. 96-98 (1996) 443
- Tirions, O., see Weng, L.T. 99 (1996) 185
- Titov, V., I. Smurov and M. Ignatiev, Erosion plume dynamics during pulsed laser alloying 96-98 (1996) 387
- Tkachenko, S.D., see Bogonin, I.A. 92 (1996) 43
- Tobe, R., see Numajiri, K. 100/101 (1996) 541
- Todokoro, H., see Ninomiya, K. 100/101 (1996) 551
- Togashi, H., K. Saito, Y. Koga, H. Yamawaki, K. Aoki, M. Mukaida and T. Kameyama, Formation of large carbon cluster ions at graphite (HOPG) surfaces by laser irradiation 96-98 (1996) 267
- Tokumoto, H., see Morita, Y. 100/101 (1996) 440
- Tomas, C., see Afif, M. 96-98 (1996) 469
- Tomek, S., see Liday, J. 99 (1996) 9
- Tomellini, M., Modelling of the particle size distribution function in the nucleation and early stages of thin film growth 99 (1996) 67
- Tomizuka, H. and A. Ayame, Charge-up and charge compensation on monochromatized X-ray photoelectron spectroscopic measurements of alumina and glass 100/101 (1996) 243
- Tong, L., see Wang, B.P. 94/95 (1996) 101
- Tonini, R., see Corni, F. 91 (1995) 107
- Tontegode, A.Ya., see Gall, N.R. 93 (1996) 353
- Torkelsen, N.G. and S. Raen, Work function variations and oxygen conduction in a $\text{Pt}(\text{ZrO}_2(\text{Y}_2\text{O}_3))\text{Pt}$ solid electrolyte cell 93 (1996) 199
- Torres, J., Advanced copper interconnections for silicon CMOS technologies 91 (1995) 112
- Torres, J., see Mouche, M.-J. 91 (1995) 129
- Torres, J., see Bourhila, N. 91 (1995) 175
- Torres, J., see Braud, F. 91 (1995) 251
- Toshima, S., see Inoue, N. 96-98 (1996) 656
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- Toyoda, K., see Sugioka, K. 96-98 (1996) 347
- Toyoda, Y., see Fukada, T. 91 (1995) 227
- Toyota, Y., see Tsuji, H. 100/101 (1996) 342
- Toyota, Y., H. Tsuji, S. Nagumo, Y. Gotoh and J. Ishikawa, Charging phenomenon of insulators in negative-ion implantation 100/101 (1996) 360
- Träger, F., see Götz, T. 96-98 (1996) 280
- Tremblay, G., see Mamor, M. 91 (1995) 342
- Tretiakov, N.P., see Zubov, V.I. 92 (1996) 436
- Tsai, C.H., see Chung, B.C. 96-98 (1996) 233
- Tsai, C.H., see Huang, C.S. 96-98 (1996) 735
- Tsai, M.-J., see Wang, F.-S. 92 (1996) 372
- Tsai, M.-Y., see Chen, P.-L. 92 (1996) 30
- Tsai, W.-C., see Chang, T.-C. 92 (1996) 119
- Tsai, W.-C., see Chang, T.-C. 92 (1996) 571
- Tsang, W., see Jou, H. 92 (1996) 585
- Tsay, J.S., see Shern, C.S. 92 (1996) 74
- Tseng, B.-H., G.-W. Chang and G.-L. Gu, Surfactant modified growth of CuInSe_2 thin films 92 (1996) 227
- Tseng, B.-H., S.-B. Lin, G.-L. Gu and H.-Z. Hsu, Interface of $\text{CuIn}_{1-x}\text{Ga}_x\text{Se}_2/\text{GaAs}$ heterostructure 92 (1996) 412
- Tseng, S.-Y., see Lee, C.-H. 92 (1996) 282
- Tseng, T.Y., see Chung, B.C. 96-98 (1996) 233
- Tseng, T.Y., see Huang, C.S. 96-98 (1996) 735
- Teikunov, A.V., see Bogonin, I.A. 92 (1996) 43
- Tsong, I.S.T., see Wei, Y. 92 (1996) 491
- Tsong, T.T., see Chen, C.L. 94/95 (1996) 224
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- Tsuji, H., see Toyota, Y. 100/101 (1996) 360
- Tsuji, H., see Ishikawa, J. 100/101 (1996) 370
- Tsutsumi, T., see Jen, J.Y. 92 (1996) 547
- Tu, K.N., see Lin, C.C. 92 (1996) 660
- Tukhto, O.M., see Predtechensky, M.R. 96-98 (1996) 717
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- Turcotte, G., see Lecours, A. 96-98 (1996) 341
- Turtù, S., see Giorgi, R. 93 (1996) 101
- Tyrrell, G.C., L.G. Coccia, T.H. York and I.W. Boyd, Energy-dispersive mass spectrometry of high energy ions generated during KrF excimer and frequency-doubled Nd:YAG laser ablation of metals 96-98 (1996) 227
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- Uekusa, S., see Kobayashi, N. 100/101 (1996) 498
- Uetsuka, H., see Watanabe, K. 99 (1996) 411
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- Umeno, M., see Uchida, H. 100/101 (1996) 399
- Umeno, M., see Hasegawa, Y. 100/101 (1996) 482
- Umeno, M., see Yu, G. 100/101 (1996) 617
- Urisu, T., see Gheys, S.I. 100/101 (1996) 211
- Ushimaru, K., see Kawano, H. 100/101 (1996) 174
- Ushioda, S., see Sakamoto, K. 100/101 (1996) 124
- Usufov, M.M., see Gall, N.R. 93 (1996) 353
- Utsumi, K., see Yoshida, A. 100/101 (1996) 491
- Utsunomiya, I., see Shingubara, S. 91 (1995) 220
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- Van den Homberg, M.J.C., see Leusink, G.J. 91 (1995) 215
- Van der Jeugd, C.A., see Jongste, J.F. 91 (1995) 162
- Vanderveen, R.J., see Morris, G.C. 92 (1996) 630
- Van Dorssen, G.E., see Voorma, H.-J. 93 (1996) 221
- Van Rooy, T.L., see Fransen, M.J. 94/95 (1996) 107
- Van Sinay, O., see Reniers, F. 92 (1996) 35
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- Vaquila, I., M.C.G. Passeggi, Jr. and J. Ferrón, Temperature effects in the early stages of titanium oxidation 93 (1996) 247
- Varela, M., see Aguiar, R. 96-98 (1996) 405
- Varela, M., see Polo, M.C. 96-98 (1996) 870
- Vasil'eva, S.A., see Predtechensky, M.R. 96-98 (1996) 717
- Vázquez, A. and F. Pedraza, High resolution electron microscopy characterization of small Pt-Pd/SiO₂ particles in oxide-reducing cycles 99 (1996) 213
- Veleva, L., see Quintana, P. 99 (1996) 325
- Velotta, R., see Amoroso, S. 96-98 (1996) 175
- Verardi, P., M. Dinescu and A. Andrei, Characterization of ZnO thin films deposited by laser ablation in reactive atmosphere 96-98 (1996) 827
- Verbeeck, R., see Jonckx, F. 91 (1995) 378
- Verdonck, P., see Mansano, R.D. 100/101 (1996) 583
- Vereecken, J., see Reniers, F. 99 (1996) 379
- Vidali, G. and H. Zeng, Recent advances in island and multilayer growth of metals on metals far from equilibrium 92 (1996) 11
- Viljoen, E.C., see du Plessis, J. 100/101 (1996) 222
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- Vinkó, J., see Hopp, B. 96-98 (1996) 611
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- Vivet, L., see Barthe, M.F. 96-98 (1996) 359
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- Volchkov, N.A., see Bogonin, I.A. 92 (1996) 43
- Volchkov, N.A., see Karuzskii, A.L. 92 (1996) 457
- Völlmar, S., see Granse, G. 96-98 (1996) 97
- Völlmar, S., see Panzner, M. 96-98 (1996) 643
- Völlmar, S., see Gorbunov, A.A. 96-98 (1996) 649
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- Vuillon, J., see Le, H.C. 96-98 (1996) 76
- Vyacheslavov, L.N., see Fuso, F. 96-98 (1996) 181
- Wada, K., see Oyoshi, K. 100/101 (1996) 374
- Wada, S., see Sugioka, K. 96-98 (1996) 347
- Wada, T., see Masui, M. 92 (1996) 634
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- Wagner, J.W., see Diaci, J. 96-98 (1996) 154
- Waller, D., see Coccia, L.G. 96-98 (1996) 795
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- Wang, F., see Pindoria, G. 100/101 (1996) 347
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- Wang, H., see Ji, W. 99 (1996) 151
- Wang, J.-P., see Kuo, W.-K. 92 (1996) 155
- Wang, K.C., T.R. Yew and H.L. Hwang, Very low temperature polycrystalline silicon films with very large grains deposited for thin film transistor applications 92 (1996) 99
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- Wang, R.L.C., see Forbes, R.G. 94/95 (1996) 60
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- Warabisako, T., see Uchida, Y. 100/101 (1996) 478
- Waser, R., see Grosse-Holz, K.-O. 96-98 (1996) 784
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- Watanabe, K., see Hirayama, H. 100/101 (1996) 460
- Watanabe, N., see Saito, S. 100/101 (1996) 260
- Watanabe, S., see Sugita, Y. 100/101 (1996) 268
- Watanabe, T., see Kudo, M. 100/101 (1996) 129
- Watson, T.A. and C. Rowan, Industrial excimer laser beam properties 96-98 (1996) 532
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- Weber, J., see Bohnke, O. 93 (1996) 45
- Wee, A.T.S., see Li, K. 99 (1996) 59
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- Wei, Y., see Wang, G. 93 (1996) 281
- Weide, K., J. Ullmann and W. Hasse, Model calculations on a bipolar transistor emitter interconnection with different contact shapes 91 (1995) 234
- Weissmantel, S., see Reisse, G. 96-98 (1996) 752
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- Wenzel, C., see Stavrev, M. 91 (1995) 257
- Werner, T., see Bertz, A. 91 (1995) 147
- Wesner, D.A., M. Martin, F. Lupp and E.W. Kreutz, Cleaning of copper traces on circuit boards with excimer laser radiation 96-98 (1996) 479
- Wesner, D.A., see Pflöging, W. 96-98 (1996) 496

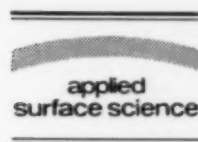
- Wesner, D.A., see Martin, M.
 Wickramanayaka, S., see Aoki, T.
 Wiczorek, P., see Lewowski, T.
 Wilhelm, S., see Ahrens, C.
 Wilshaw, P.R., see Nicolaescu, D.
 Wilson, R.A., see Lu, C.R.
 Wilson, R.A., see Lu, C.R.
 Wimmer, E., see Spiess, L.
 Wistus, E., see Ding, D.
 Wisz, G., see Gorbach, T.Ya.
 Witke, Th., see Lenk, A.
 Wittborn, J., see Tyunina, M.
 Witvrouw, A., see Stevens, R.
 Wolf, A., see Pastuszka, S.
 Wolf, H., R. Streiter, S.E. Schulz and T. Gessner, Growth rate modeling for selective tungsten LPCVD 91 (1995) 332
 Wolf, R.M., see Cillessen, J.F.M.
 Wolff-Rottke, B., see Mann, K.
 Wolfram, Z., see Nowicka, E.
 Wollenberger, H., see Al-Kassab, T.
 Wolters, R.A.M., see Kordic, S.
 Wong, P.C., see Aouadi, M.S.
 Wong, S.P., see Yan, H.
 Wood, R.F., see Leboeuf, J.N.
 Wood, R.F., see Chen, K.R.
 Wu, C.C., see Young, T.F.
 Wu, N., see Guo, Q.
 Wu, W.-F. and B.-S. Chiou, Properties of radio frequency magnetron sputtered silicon dioxide films 99 (1996) 237
 Wu, W.T., P.E. Schmid and F. Lévy, Structural and optical properties of $\text{Pd}_{1-x}\text{In}_x$ thin films 92 (1996) 391
 Wu, D.S., see Horng, R.H.
 Wu, D.S., M.L. Lee and T.Y. Lin, Properties of multilayered thin films for thermal ink-jet printing devices 92 (1996) 626
 Xiang, N., see Valden, M.
 Xie, X.L., see Chen, W.D.
 Xie, X.L., see Chen, W.D.
 Xu, L., see Chen, Q.
 Yabe, A., see Niino, H.
 Yabe, A., see Niino, H.
 Yabe, A., see Lippert, T.
 Yakimova, R., see Marinova, Ts.
 Yamada, K. and S. Nishigaki, Oxidation of a Si(001) surface mediated by repetitive adsorption/desorption cycles of Cs: a metastable deexcitation spectroscopy study 99 (1996) 21
 Yamada, S., see Kudo, M.
 Yamada, T., M. Kudo, Y. Ando, T. Sekine and Y. Sakai, Development of high spatial resolution Auger microscope as applied to semiconductor analysis 100/101 (1996) 287
 Yamada, T., see Ikeda, H.
 Yamaguchi, S., see Oku, T.
 Yamamoto, H., Y. Baba and T.A. Sasaki, Dissociative scattering of low-energy SiF_3^+ and SiF^+ ions (5-200 eV) on Cu(100) surface 100/101 (1996) 333
 Yamamoto, M., see Nishikawa, K.
 Yamamoto, N., see Mitsui, T.
 Yamamoto, Y., see Iwatsuki, M.
 Yamauchi, S., Y. Hasebe, H. Ohshima, T. Hattori, M. Hirai, M. Kusaka and M. Iwami, Valence band structure of metal silicides modified by argon ion implantation 100/101 (1996) 522
 Yamauchi, Y., see Uwai, K.
 Yamawaki, H., see Togashi, H.
 Yamazaki, T., see Ohdaira, T.
 Yamazaki, T., see Suzuki, R.
 Yan, H., R.W.M. Kwok and S.P. Wong, XPS studies on SiC thin layers formed by ion implantation with a metal vapor vacuum arc ion source 92 (1996) 61
 Yanagisawa, Y., NO interaction with thermally activated CaO and SrO surfaces 100/101 (1996) 256
 Yanashima, K., see Mitsui, T.
 Yang, W.T., see Huang, J.C.A.
 Yano, F., A. Hiraoka, T. Itoga, H. Kojima, K. Kanehori and Y. Mitsui, Influence of ion-implantation on native oxidation of Si in a clean-room atmosphere 100/101 (1996) 138
 Yao, Y.D., see Huang, J.C.A.
 Yasuda, Y., see Ikeda, H.
 Yasuda, Y., see Iwano, H.
 Yasuda, Y., see Shinoda, H.
 Yavaş, O., see Oltra, R.
 Yazawa, Y., see Uchida, Y.
 Yea, B., R. Konishi, T. Osaki, S. Abe, H. Tanioka and K. Sugahara, Analysis of the sensing mechanism of tin dioxide thin film gas sensors using the change of work function in flammable gas atmosphere 100/101 (1996) 365
 Yeh, C.-F., see Liu, C.-W.
 Yeh, C.C., see Lee, C.H.
 Yeh, W.-K., see Chang, T.-C.
 Yeh, W.-K., see Chang, T.-C.
 Yelon, A., see Lecours, A.
 Yelon, A., see Izquierdo, R.
 Yew, T.R., see Wang, K.C.
 Ying, W.B., Y. Mizokawa, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto, Annealing behavior of phosphorus in native oxide films on heavily phosphorus doped silicon 100/101 (1996) 556
 Ying, W.B., see Mizokawa, Y.
 Yokota, N., see Tanaka, K.
 Yoon, S.S., see Yoon, Y.S.
 Yonemitsu, K., see Shibata, N.

- Yoo, C.S., see Li, D.C. 92 (1996) 665
- Yoon, Y.S., S.S. Yom, T.W. Kim, D.U. Lee and C.O. Kim, Improvement of the crystallinity in PbTiO₃ films grown on indium tin oxide-coated glass by metalorganic chemical vapor deposition using the continuous cooling process 93 (1996) 285
- York, T.H., see Tyrrell, G.C. 96-98 (1996) 227
- York, T.H., see Tyrrell, G.C. 96-98 (1996) 769
- Yoshida, A., K. Utsumi and A. Ganjoo, Si epitaxial growth at low temperatures using remote plasma process 100/101 (1996) 491
- Yoshida, M., see Deno, H. 96-98 (1996) 563
- Yoshida, S., see Kudo, M. 100/101 (1996) 129
- Yoshida, S., M. Sasaki and T. Ishikawa, The effect of EB irradiation with and without hot-jet Cl₂ on an ultra-thin GaN layer for selective etching 100/101 (1996) 184
- Yoshihara, K., see Tanuma, S. 100/101 (1996) 47
- Yoshihara, K., see Yoshitake, M. 100/101 (1996) 203
- Yoshikawa, K., see Iwano, H. 100/101 (1996) 487
- Yoshino, J., see Mitsui, T. 100/101 (1996) 625
- Yoshitake, M. and K. Yoshihara, Effect of gas adsorption on the segregation behavior of substrate Cu on Ti film 100/101 (1996) 203
- Young, T.F., J.F. Liu, C.C. Wu, G.H. Fu and C.S. Chen, Study of Ag thin films deposited on porous silicon 92 (1996) 57
- Yu, G., T. Soga, T. Jimbo and M. Umeno, Characterization of MOCVD-grown GaAs on Si by spectroscopic ellipsometry 100/101 (1996) 617
- Yu, J., see Numajiri, K. 100/101 (1996) 541
- Yu, Y.B., see Ying, W.B. 100/101 (1996) 556
- Yu, Y.B., see Mizokawa, Y. 100/101 (1996) 561
- Zabinski, J.S., see John, G. 93 (1996) 329
- Zaborowski, M., A. Barcz, G. Gawlik and I.W. Rangelow, The effect of ion implantation on the properties of Al films 91 (1995) 239
- Zaborowski, M., M. Adamiec and A. Barcz, Hillock recognition by digital image processing 91 (1995) 246
- Zabrodin, I.G., see Gorbunov, A.A. 96-98 (1996) 649
- Zaccherini, C., see Bacchetta, M. 91 (1995) 367
- Zackrisson, J., M. Thuvander, P. Lindahl and H.-O. Andr n, Atom probe analysis of carbonitride grains in (Ti, W, Ta, Mo)(C, N)(Co/Ni) cermets with different carbon content 94/95 (1996) 351
- Zaima, S., see Ikeda, H. 100/101 (1996) 431
- Zaima, S., see Iwano, H. 100/101 (1996) 487
- Zaima, S., see Shinoda, H. 100/101 (1996) 526
- Zaitsev, S.Yu., see Ksenevich, T.I. 92 (1996) 426
- Zalar, A., E.W. Seibt and P. Panjan, Oxide thin films formed during rotational AES sputter depth profiling of Ni/Cr multilayers using oxygen ions 100/101 (1996) 92
- Zaldo, C., see Alfonso, J.E. 96-98 (1996) 791
- Zaldo, C., see Mart n, M.J. 96-98 (1996) 823
- Zanotti, L., see Bacchetta, M. 91 (1995) 367
- Zappa, G., see Giorgi, R. 93 (1996) 101
- Zavaliche, F., see Manaila, R. 91 (1995) 295
- Zeidler, D., see Stavreva, Z. 91 (1995) 192
- Zeindl, H.P., S. Nilsson and E. Bugiel, Diffusion phenomena in MBE grown Si/SiGe single quantum wells studied by PL and TEM measurements 92 (1996) 552
- Zeitoun, D., see Le, H.C. 96-98 (1996) 76
- Zeng, H., see Vidali, G. 92 (1996) 11
- Zettler, J.-T., see Richter, W. 100/101 (1996) 465
- Zhang, J.-Y., H. Esrom and I.W. Boyd, Decomposition mechanisms of thin palladium acetate film with excimer UV radiation 96-98 (1996) 399
- Zhang, Z., see Mascia, L. 93 (1996) 1
- Zhdanov, V.P. and P.R. Norton, Growth of oxide films on metal surfaces: transition from parabolic to linear kinetics 99 (1996) 205
- Zheleznykh, I.M., see Sadygov, Z.Y. 92 (1996) 575
- Zhirnov, V.V., W.B. Choi, J.J. Cuomo and J.J. Hren, Diamond coated Si and Mo field emitters: diamond thickness effect 94/95 (1996) 123
- Zhirnov, V.V., see Givargizov, E.I. 94/95 (1996) 117
- Zhirnov, V.V., L. Bormatova, E.I. Givargizov, P.S. Plekhanov, U.T. Son, A.V. Galdetsky and B.A. Belyavsky, Field emission properties of Au-Si eutectic 94/95 (1996) 144
- Zhou, B., X. Li, T.L. Tansley and K.S.A. Butcher, Microwave plasma assisted LCVD growth and characterization of GaN 100/101 (1996) 643
- Zhu, S.N., see Liu, J.M. 96-98 (1996) 819
- Zhu, Y.Y., see Liu, J.M. 96-98 (1996) 819
- Zhuang, Q., see Tanaka, K. 100/101 (1996) 264
- Zhurkin, B.G., see Bogonin, I.A. 92 (1996) 43
- Zhurkin, B.G., see Karuzskii, A.L. 92 (1996) 457
- Zichner, N., see Teichert, J. 91 (1995) 44
- Zichner, N., see Kaufmann, C. 91 (1995) 291
- Ziemann, P., see Abert, A. 96-98 (1996) 703
- Ziemann, P., see Koch, T. 99 (1996) 51
- Zimin, S.P., V.S. Kuznetsov and A.V. Prokaznikov, Electrical characteristics of aluminum contacts to porous silicon 91 (1995) 355
- Zimmer, K., D. Hirsch and F. Bigl, Excimer laser machining for the fabrication of analogous microstructures 96-98 (1996) 425
- Zubov, V.I., N.P. Tretiakov and J.N. Teixeira Rabelo, Microscopic theory of atomic properties of the surfaces of anharmonic crystals. Singular faces of fullerite C₆₀ 92 (1996) 436



ELSEVIER

Applied Surface Science 91-101 (1996) 39-133



Subject index to volumes 91-101

Ablation

- Diamond-like coating prepared by pulsed laser sputtering of graphite in a high-vacuum environment, I.A. Bogonin, A.L. Karuzskii, N.N. Melnik, Yu.A. Mityagin, V.N. Murzin, A.A. Orlikovsky, A.V. Perestoronin, P.P. Sverbil, S.D. Tkachenko, A.V. Tsikunov, N.A. Volchikov and B.G. Zhurkin 92 (1996) 43
- Structural and electrical properties of excimer laser deposited PLZT thin films, H.-F. Cheng 92 (1996) 378
- Electrical properties of laser deposited $\text{YBa}_2\text{Cu}_3\text{O}_{7-\delta}$ films on silicon wafers, F.Y. Chuang, C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin 92 (1996) 452
- Pulsed-laser deposition of "diamond-like" carbon coating on $\text{YBa}_2\text{Cu}_3\text{O}_7$ high- T_c superconductor films, A.L. Karuzskii, N.N. Melnik, V.N. Murzin, V.S. Nozdrin, A.V. Perestoronin, N.A. Volchikov and B.G. Zhurkin 92 (1996) 457
- Carbon nitride - prospects for ultimate performance of superhard materials, S.A. Uglov, V.E. Shub, A.A. Beloglazov and V.I. Konov 92 (1996) 656
- Studies of silicon-nitride (Si_3N_4) using laser ablation mass spectrometry, S.L. Wang, K.W.D. Ledingham, W.J. Jia and R.P. Singhal 93 (1996) 205
- Microscopic and mesoscopic aspects of laser-induced desorption and ablation, R.F. Haglund, Jr. 96-98 (1996) 1
- Modeling of dynamical processes in laser ablation, J.N. Leboeuf, K.R. Chen, J.M. Donato, D.B. Geohegan, C.L. Liu, A.A. Poretzky and R.F. Wood 96-98 (1996) 14
- An analytical model for three-dimensional laser plume expansion into vacuum in hydrodynamic regime, S.I. Anisimov, B.S. Luk'yanchuk and A. Luches 96-98 (1996) 24
- Laser-solid interaction and dynamics of laser-ablated materials, K.R. Chen, J.N. Leboeuf, R.F. Wood, D.B. Geohegan, J.M. Donato, C.L. Liu and A.A. Poretzky 96-98 (1996) 45
- Analytical description of the film thickness distribution obtained by the pulsed laser ablation of a monoatomic target: application to silicon and germanium, F. Antoni, C. Fuchs and E. Fogarassy 96-98 (1996) 50
- An analytical model for the laser ablation of materials, A.D. Boardman, B. Cresswell and J. Anderson 96-98 (1996) 55
- Calculations and experiments of material removal and kinetic energy during pulsed laser ablation of metals, S. Fähler and H.-U. Krebs 96-98 (1996) 61
- Measurement and calculation of the Fe_2O_3 ablation depth, A. Lisfi, M. Guyot, R. Krishnan and V. Cagan 96-98 (1996) 66
- Calculation and measurement of the ultrasonic signals generated by ablating material with a Q-switched pulse laser, A. Hoffmann and W. Arnold 96-98 (1996) 71
- 2D modeling of laser-induced plume expansion near the plasma ignition threshold, H.C. Le, J. Vuillon, D. Zeitoun, W. Marine, M. Sentis and R.W. Dreyfus 96-98 (1996) 76
- Spatial distribution of laser-ablated material by probing a plasma plume in three dimensions, A. Mele, A. Giardini Guidoni, R. Kelly, A. Miotello, S. Orlando and R. Teghil 96-98 (1996) 102
- Electrostatic probe and optical spectroscopy studies of low temperature laser produced plasmas, J.M. Hendron, R.A. Al-Wazzan, C. Mahony, T. Morrow and W.G. Graham 96-98 (1996) 112
- Study of the expansion of the laser ablation plume above a boron nitride target, B. Angleraud, C. Girault, C. Champeaux, F. Garrelie, C. Germain and A. Catherinot 96-98 (1996) 117

- Preferential vaporization and plasma shielding during nano-second laser ablation, X. Mao, W.-T. Chan, M. Caetano, M.A. Shannon and R.E. Russo 96-98 (1996) 126
- Laser ablation plume thermalization dynamics in background gases: combined imaging, optical absorption and emission spectroscopy, and ion probe measurements, D.B. Geohegan and A.A. Puretzky 96-98 (1996) 131
- Fundamental characteristics of laser-material interactions (ablation) in noble gases at atmospheric pressure using inductively coupled plasma-atomic emission spectroscopy, R.E. Russo, X.L. Mao, M. Caetano and M.A. Shannon 96-98 (1996) 144
- Simultaneous monitoring of ablative shocks in air by high-speed cinchology and multiple-pass beam deflection probe, J. Diaci, D. Hurley, J.W. Wagner and J. Možina 96-98 (1996) 154
- Transport of neutral atoms, monoxides and clusters in the plume produced by laser ablation of $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ in oxygen environment, A.V. Bulgakov, M.R. Predtechensky and A.P. Mayorov 96-98 (1996) 159
- Temperature measurements during laser ablation of Si into He, Ar and O_2 , H.C. Le, R.W. Dreyfus, W. Marine, M. Sentis and I.A. Movtchan 96-98 (1996) 164
- Spatially and temporally resolved emission intensities and number densities in low temperature laser-induced plasmas in vacuum and in ambient gases, R.A. Al-Wazzan, J.M. Hendron and T. Morrow 96-98 (1996) 170
- Laser produced plasmas in high fluence ablation of metallic surfaces probed by time-of-flight mass spectrometry, S. Amoruso, A. Amodeo, V. Berardi, R. Bruzzese, N. Spinelli and R. Velotta 96-98 (1996) 175
- Optical diagnostics of the laser-target and laser-plume interaction in pulsed laser ablation, F. Fuso, L.N. Vyacheslavov, G. Lorenzi, M. Allegrini and E. Arimondo 96-98 (1996) 181
- Time-of-flight characterization of laser ablation plume from NbTe_2 target in He atmosphere, F. Grangeon, H. Sassoli, W. Marine and M. Autric 96-98 (1996) 186
- Laser plasma threshold of metals, S. Petzoldt, J. Reif and E. Matthias 96-98 (1996) 199
- Comments on explosive mechanisms of laser sputtering, R. Kelly and A. Miotello 96-98 (1996) 205
- Optical and particle properties of PLD vapour/plasmas of ceramics, M. Alunovic, H. Stamm, M. Aden and E.W. Kreutz 96-98 (1996) 222
- Energy-dispersive mass spectrometry of high energy ions generated during KrF excimer and frequency-doubled Nd:YAG laser ablation of metals, G.C. Tyrrell, L.G. Coccia, T.H. York and I.W. Boyd 96-98 (1996) 227
- Soft laser sputtering of the GaAlAs (100) surface, L. Vivet, B. Dubreuil, T. Gibert-Legrand and M.F. Barthe 96-98 (1996) 238
- Dynamics of silicon plume generated by laser ablation and its chemical reaction, T. Makimura and K. Murakami 96-98 (1996) 242
- Optical spectroscopy of emission from Si-SiO_2 nanoclusters formed by laser ablation, I.A. Movtchan, W. Marine, R.W. Dreyfus, H.C. Le, M. Sentis and M. Autric 96-98 (1996) 251
- Magnetic field enhanced growth of carbon cluster ions in the laser ablation plume of graphite, F. Kokai, Y. Koga and R.B. Heimann 96-98 (1996) 261
- Particles synthesis in erosive laser plasma in a high pressure atmosphere, A.G. Gnedovets, E.B. Kul'batskii, I. Smurov and G. Flamant 96-98 (1996) 272
- Laser ablation of metals: the transition from non-thermal processes to thermal evaporation, T. Götz, M. Bergt, W. Hoheisel, F. Träger and M. Stuke 96-98 (1996) 280
- Excimer laser induced thermal evaporation and ablation of silicon carbide, R. Reitano, P. Baeri and N. Marino 96-98 (1996) 302
- Increase of efficiency for the XeCl excimer laser ablation of ceramics, M. Geiger, W. Becker, T. Rebhan, J. Hutfless and N. Lutz 96-98 (1996) 309
- Laser ablation of sodium nitrate: NO desorption following excitation of the $\pi-\pi^*$ band of the nitrate anion, W.P. Hess, K.A.H. German, R.A. Bradley and M.I. McCarthy 96-98 (1996) 321
- Laser patterning of thin-film electrochemical gas sensors, A. Lecours, M. Caron, P. Ciureanu, G. Turcotte, D. Ivanov, A. Yelon and J.F. Currie 96-98 (1996) 341
- Multiwavelength irradiation effect in fused quartz ablation using vacuum-ultraviolet Raman laser, K. Sugioaka, S. Wada, Y. Ohnuma, A. Nakamura, H. Tashiro and K. Toyoda 96-98 (1996) 347
- Micro-Raman study of UV laser ablation of GaAs and Si substrates, C. García, J. Ramos, A.C. Prieto, J. Jiménez, C. Geertsen, J.L. Lacour and P. Mauchien 96-98 (1996) 370
- Erosion plume dynamics during pulsed laser alloying, V. Titov, I. Smurov and M. Ignatiev 96-98 (1996) 387

- Excimer laser ablation for micro-machining: geometric effects, P.E. Dyer, D.M. Karnakis, P.H. Key and P. Monk 96-98 (1996) 415
- Optodynamics of laser ablation of graduation lines in chromium thin film on glass, S. Kopač, J. Pirš and J. Možina 96-98 (1996) 420
- Picosecond UV-laser ablation of Au and Ni films, A. Rosenfeld and E.E.B. Campbell 96-98 (1996) 439
- XeCl laser ablation of thin film ZnS, W.M. Cranton, P.H. Key, D. Sands, C.B. Thomas and F.X. Wagner 96-98 (1996) 501
- Optimisation of laser wavelength in the ablation sampling of glass materials, S. Shuttleworth 96-98 (1996) 513
- Ablation from metals induced by visible and UV laser irradiation, W. Svendsen, J. Schou, B. Thestrup and O. Ellegaard 96-98 (1996) 518
- Real-time determination of the amount of removed material during short pulses laser micromachining, C. Stauter, J. Fontaine and Th. Engel 96-98 (1996) 522
- Excimer laser ablation of polymers and glasses for grating fabrication, P.E. Dyer, R.J. Farley, R. Giedl and D.M. Karnakis 96-98 (1996) 537
- VUV ablation of polymers by emission from gas-puff Z-pinch plasmas, H. Deno, S. Sugiyama, Y. Kakudate, M. Yoshida and S. Fujiwara 96-98 (1996) 563
- Surface chemical reaction of polymer film with reactive intermediates produced by laser ablation of azido compound, H. Niino and A. Yabe 96-98 (1996) 572
- Excimer laser ablation of low and high absorption index polymers, P.E. Dyer, D.M. Karnakis, P.H. Key and J.P. Tait 96-98 (1996) 596
- High sensitivity quadrupole mass spectrometry of neutrals sputtered by UV-laser ablation of polymers, S. Lazare, W. Guan and D. Drillhole 96-98 (1996) 605
- Formation of the surface structure of polyethylene-terephthalate (PET) due to ArF excimer laser ablation, B. Hopp, M. Csete, K. Révész, J. Vinkó and Zs. Bor 96-98 (1996) 611
- Pulsed laser ablation and deposition of fluorocarbon polymers, M.G. Norton, W. Jiang, J.T. Dickinson and K.W. Hipps 96-98 (1996) 617
- Deposition of fluoropolymer thin films containing semiconductor microcrystallites by VUV laser ablation, T. Fujii, S. Inoue and F. Kannari 96-98 (1996) 621
- Thin film growth by the pulsed laser assisted deposition technique, C. Belouet 96-98 (1996) 630
- Ultrathin film deposition by pulsed laser ablation using crossed beams, A.A. Gorbunov, W. Pompe, A. Sewing, S.V. Gaponov, A.D. Akhsakhalyan, I.G. Zabrodin, I.A. Kas'kov, E.B. Klyenkov, A.P. Morozov, N.N. Salaschenko, R. Dietsch, H. Mai and S. Völlmar 96-98 (1996) 649
- Selection of kinetic energy of laser ablated particles, K. Kuba and T. Sugihara 96-98 (1996) 659
- Aspects of particulate production from metals exposed to pulsed laser radiation, I. Weaver and C.L.S. Lewis 96-98 (1996) 663
- Formation of artificially-layered high-temperature superconductors using pulsed-laser deposition, D.P. Norton, B.C. Chakoumakos, D.H. Lowndes and J.D. Budai 96-98 (1996) 672
- The importance of gas scattering processes on the stoichiometry deviations of laser deposited films, J. Gonzalo, C.N. Afonso, J. Perrière and R. Gómez San Roman 96-98 (1996) 693
- Laser ablation of oxides: study of the oxygen incorporation by ^{18}O isotopic tracing techniques, R. Pérez Casero, R. Gómez San Román, C. Maréchal, J.P. Enard and J. Perrière 96-98 (1996) 697
- Substrate size effect at off-axis laser deposition of multicomponent films, M.R. Predtechensky, O.M. Tukhto, A.N. Smal' and S.A. Vasil'eva 96-98 (1996) 717
- Deposition of optical coatings by pulsed laser ablation, G. Reisse, S. Weissmantel, B. Keiper and U. Broulik 96-98 (1996) 752
- Preparation of SiO_2N_x films by reactive KrF laser ablation, K. Maruyama, Y. Aoki, M. Matsumoto, Y. Hiroshima and H. Ohta 96-98 (1996) 764
- Kinetic energy distributions of ions ejected during laser ablation of lead zirconate titanate and their correlation to deposition of ferroelectric thin films, G.C. Tyrrell, T.H. York, L.G. Coccia and I.W. Boyd 96-98 (1996) 769
- Excimer laser ablating preparation of $\text{Ba}_2\text{NaNb}_2\text{O}_{15}$ thin films on KTiOPO_4 substrate and its guide wave property, J.M. Liu, Z.G. Liu, S.N. Zhu, Y.Y. Zhu and N.B. Ming 96-98 (1996) 819
- $\text{Pb}_{1-x}\text{Ca}_x\text{TiO}_3$ thin films prepared by laser ablation of ceramic targets, M.J. Martín, C. Zaldo and J. Mendiola 96-98 (1996) 823
- Excimer laser ablation and film deposition of Ti:sapphire, P.E. Dyer, S.R. Jackson, P.H. Key, W.J. Metheringham and M.J.J. Schmidt 96-98 (1996) 849
- Laser reactive ablation deposition of silicon carbide films, G. Leggieri, A. Luches, M. Martino, A. Perrone, R. Alexandrescu, A. Barborica, E. Gyorgy, I.N. Mihailescu, G. Majni and P. Mengucci 96-98 (1996) 866
- Carbon nitride thin films obtained by laser

- ablation of graphite in a nitrogen plasma, M.C. Polo, R. Aguiar, P. Serra, L. Clèries, M. Varela and J. Esteve 96-98 (1996) 870
- Large area synthesis of thin alumina films by laser ablation, B. Hirschauer, S. Söderholm, J. Paul and A.S. Flodström 99 (1996) 285
- Time-resolved detection of laser-ablated particles based on intensity decrease of cw probe laser beam, M. Hattori, S. Sekine, T. Ooie and H. Nonaka 100/101 (1996) 301
- Acoustic effects*
- Design of an ultrahigh vacuum compatible system for studying the influence of acoustic waves on surface chemical processes, T. Mitrelias, V.P. Ostanin, M. Gruyters and D.A. King 100/101 (1996) 305
- Alkali halides*
- Thickness dependent electron stimulated desorption of thin epitaxial films of alkali halides, M. Szymonski, J. Kolodziej, P. Czuba, P. Piatkowski, P. Korecki, Z. Postawa and N. Itoh 100/101 (1996) 102
- Temperature-programmed desorption of positive ions and neutral molecules from alkali halide layers deposited on a metal surface, H. Kawano, S. Kamidoi, H. Shimizu, K. Ushimaru and H. Asada 100/101 (1996) 174
- Empirical formulae of the threshold temperature range for dissociative positive ionization of alkali halides on heated metal surfaces, H. Kawano, K. Ohgami, S. Matsui and Y. Kitayama 100/101 (1996) 193
- Alkali metals*
- Structural properties of Na adsorbed on a Ge(100)2×1 surface: all electron, ab initio, density functional, cluster calculations, L. Spiess, E. Wimmer and P. Soukiasian 92 (1996) 501
- Electrocatalytic activities of proton-exchanged layered oxides for the anodic oxidation on the solid oxide fuel cell, K. Sato, S. Nomura and Y. Inoue 92 (1996) 639
- Formation of polycrystalline BaTi₄O₉ compounds in barium implanted TiO₂, S.M.M. Ramos, B. Canut, M. Ambri, N. Bonardi, R. Brenier, M. Pitaval, P. Thevenard and M. Brunel 93 (1996) 191
- FT-IR characterization of alkali-doped Pd catalysts for the selective hydrogenation of phenol to cyclohexanone, S. Scirè, C. Crisafulli, R. Maggiore, S. Minicò and S. Galvagno 93 (1996) 309
- Li-mediated feedback mechanism of oscillations in CO oxidation on a Rh field emitter tip, V.K. Medvedev, Yu. Suchorski and J.H. Block 94/95 (1996) 200
- Scanning tunneling microscopy of charge transfer on the Si(111)7×7 surface, D. Jeon, T. Hashizume and T. Sakurai 94/95 (1996) 493
- Laser-induced emission of neutral atoms and molecules from electron-irradiated NaNO₃, J.T. Dickinson, J.J. Shin and S.C. Langford 96-98 (1996) 326
- Pulsed laser deposition of nasicon thin films, R. Izquierdo, F. Hanus, Th. Lang, D. Ivanov, M. Meunier, L. Laude, J.F. Currie and A. Yelon 96-98 (1996) 855
- Oxidation of a Si(001) surface mediated by repetitive adsorption/desorption cycles of Cs: a metastable deexcitation spectroscopy study, K. Yamada and S. Nishigaki 99 (1996) 21
- Quantitative relationship between the work function and transfer ratio of a potassium-adsorbed MIM cathode, T. Kusunoki and M. Suzuki 100/101 (1996) 207
- Alloys*
- Metallurgical and electrical investigation of Pt₃Ni₉₅/silicon interactions, F. Corni, C. Nobili, G. Ottaviani, R. Tonini, B. Grignaffini Gregorio and G. Queirolo 91 (1995) 107
- Stress voiding and electromigration phenomena in aluminum alloys, S. Kordic, R.A. Augur, A.G. Dirks and R.A.M. Wolters 91 (1995) 197
- Stress in Al, AlSiCu, and AlVPd films on oxidized Si substrates, G.J. Leusink, J.P. Lokker, M.J.C. van den Homberg, J.F. Jongste, T.G.M. Oosterlaan, G.C.A.M. Janssen and S. Radelaar 91 (1995) 215
- Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
- Pulsed field desorption mass spectrometric study of the oxidation of hydrogen-doped Ni₃Zr, T.R. Hess, D.L. Cocke, G. Abend and J.H. Block 94/95 (1996) 238
- Precipitation processes during the early stages of ageing in Al-Cu-Mg alloys, S.P. Ringer, K. Hono, I.J. Polmear and T. Sakurai 94/95 (1996) 253

- AP-FIM analysis of ordered Cu_3Au -(4 at% Pt) alloy, V.A. Ivchenko, A. Kvist, H.-O. Andr  n, N.N. Syutkin and K. Stiller 94/95 (1996) 267
- Precipitation and grain boundary segregation in molybdenum-doped NiAl, M.K. Miller, I.M. Anderson and K.F. Russell 94/95 (1996) 288
- Observation of both Ni and Mo atom images by FIM with imaging plates, K. Nishikawa, T. Nishiuchi, M. Yamamoto and O. Nishikawa 94/95 (1996) 295
- Observation of molybdenum-nitrogen clustering in highly alloyed martensite, L. Lundin and H.-O. Andr  n 94/95 (1996) 320
- Grain boundary precipitation and segregation in Ni-16Cr-9Fe model materials, M. Thuvander, K. Stiller, D. Blavette and A. Menand 94/95 (1996) 343
- The segregation behaviour of a $\text{Pt}_{90}\text{Rh}_{10}$ alloy studied with a three-dimensional atom-probe, W. Athenstaedt and M. Leisch 94/95 (1996) 403
- Erosion plume dynamics during pulsed laser alloying, V. Titov, I. Smurov and M. Ignatiev 96-98 (1996) 387
- XPS study of carbon/inconel bilayers as a function of substrate bias, M.S. Aouadi, P.C. Wong and K.A.R. Mitchell 99 (1996) 319
- Hydrogen adsorption on the $\text{Pt}(111)\sqrt{3}\times\sqrt{3}\text{R}30^\circ\text{-Sn}$ surface alloy studied by high resolution core level photoelectron spectroscopy, E. Janin, M. Bj  rkqvist, T.M. Grehk, M. G  thelid, C.-M. Pradier, U.O. Karlsson and A. Rosengren 99 (1996) 371
- Preferential sputtering and surface segregation of CuZr alloys, H.J. Kang, C.H. Kim, N.S. Park, D.J. O'Connor and R. MacDonald 100/101 (1996) 329
- Synthesis of metastable group-IV alloy semiconductors by ion implantation and ion-beam-induced epitaxial crystallization, N. Kobayashi, M. Hasegawa, N. Hayashi, H. Katsumata, Y. Makita, H. Shibata and S. Uekusa 100/101 (1996) 498
- Aluminium**
- Some particular features of the condensation process, structure and properties of thin metal films caused by self-ion bombardment, I.V. Gusev, A.A. Mohnjuk, V.I. Chapljuk and V.P. Belevsky 91 (1995) 182
- Precursor development for the chemical vapor deposition of aluminium, copper and palladium, A. Gr  fe, R. Heinen, F. Klein, Th. Kruck, M. Scherer and M. Schober 91 (1995) 187
- Stress voiding and electromigration phenomena in aluminum alloys, S. Kordic, R.A. Augur, A.G. Dirks and R.A.M. Wolters 91 (1995) 197
- Stress in Al, AlSiCu, and AlVPd films on oxidized Si substrates, G.J. Leusink, J.P. Lokker, M.J.C. van den Homberg, J.F. Jongste, T.G.M. Oosterlaken, G.C.A.M. Janssen and S. Radelaar 91 (1995) 215
- Electromigration resistance of TiWN/Cu/TiWN interconnections, T. Fukada, T. Mori, Y. Toyoda, M. Hasegawa, K. Namba and K. Ogata 91 (1995) 227
- The effect of ion implantation on the properties of Al films, M. Zaborowski, A. Barcz, G. Gawlik and I.W. Rangelow 91 (1995) 239
- Hillock recognition by digital image processing, M. Zaborowski, M. Adamiec and A. Barcz 91 (1995) 246
- Evaluation of selective tungsten plugs on TiN, W and AlSi by analytical and electrical measurements, S.E. Schulz, B. Hintze, W. Gr  newald, O. Fiedler and T. Gessner 91 (1995) 326
- Ohmic contacts to p-type 6H-silicon carbide, O. Nennewitz, L. Spiess and V. Breternitz 91 (1995) 347
- Electrical characteristics of aluminum contacts to porous silicon, S.P. Zimin, V.S. Kuznetsov and A.V. Prokashnikov 91 (1995) 355
- Growth of Zn δ -doped $\text{Al}_x\text{Ga}_{1-x}\text{As}$ ($x=0-0.65$) by low pressure metal organic vapour phase epitaxy, G. Li and C. Jagadish 92 (1996) 138
- Ultra accurate measurements of interface parameters with free-electron laser, C. Coluzza 92 (1996) 267
- In situ X-ray reflectivity measurement of thin film growth during vacuum deposition, C.-H. Lee and S.-Y. Tseng 92 (1996) 282
- Photoreflectance study of $\text{GaAs}/\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}$ resonant asymmetric double quantum wells with Si δ -doping in side barriers, C.R. Lu, S.K. Du, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 543
- Improvement of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, T. Ogura, K. Doi and S. Gon  da 92 (1996) 566
- Properties of multilayered thin films for thermal ink-jet printing devices, D.S. Wu, M.L. Lee and T.Y. Lin 92 (1996) 626
- Determination of the subband carrier densities in a strained $\text{GaAs}/\text{In}_{0.15}\text{Ga}_{0.85}\text{As}/\text{Al}_{0.23}\text{Ga}_{0.77}\text{As}$ single quantum well using photoluminescence, T.W. Kim, M. Jung and D.U. Lee 93 (1996) 131

- Photoreflectance analysis of MQWs in intermediate electric field regime, M. Geddo, S. Di Lernia and Chen Chen-Jia 93 (1996) 267
- The oxidation of the NiAl(111) surface, R. Franchy, J. Masuch and P. Gassmann 93 (1996) 317
- Comparative studies on enhanced field emission from mechanically and chemically polished broad-area Nb, Cu, and Al cathodes, N. Pupeter, T. Habermann, A. Kirschner, E. Mahner, G. Müller and H. Piel 94/95 (1996) 94
- Precipitation processes during the early stages of ageing in Al-Cu-Mg alloys, S.P. Ringer, K. Hono, I.J. Polmear and T. Sakurai 94/95 (1996) 253
- 3D reconstruction and analysis of GP zones in Al-1.7Cu (at%): a tomographic atom probe investigation, A. Bigot, F. Danoix, P. Auger, D. Blavette and A. Menand 94/95 (1996) 261
- Atomic scale investigation of ordering and precipitation processes in a model Ni-Cr-Al alloy, C. Schmuck, F. Danoix, P. Caron, A. Hauet and D. Blavette 94/95 (1996) 273
- Precipitation and grain boundary segregation in molybdenum-doped NiAl, M.K. Miller, I.M. Anderson and K.F. Russell 94/95 (1996) 288
- Microstructural influences on the decomposition of an Al-containing ferritic stainless steel, H.G. Read and H. Murakami 94/95 (1996) 334
- Soft laser sputtering of the GaAlAs (100) surface, L. Vivet, B. Dubreuil, T. Gibert-Legrand and M.F. Barthe 96-98 (1996) 238
- Aspects of particulate production from metals exposed to pulsed laser radiation, I. Weaver and C.L.S. Lewis 96-98 (1996) 663
- Determination of Al_xGa_{1-x}As Auger sensitivity factors, W.D. Chen and Y.D. Cui 100/101 (1996) 156
- Molecular beam epitaxy of GaAs/Al_xGa_{1-x}As/In_yGa_{1-y}As heterostructures for opto-electronic devices: control of growth parameters, K. Köhler 100/101 (1996) 383
- Comparison of MOCVD and MBE semiconductor superlattices for the evaluation of depth resolution in AES and SIMS, M. Furuya, M. Soga and H. Takano 100/101 (1996) 508
- In-situ IR and mass spectroscopic study of the Al(CH₃)₂H/a-Si:H reaction processes, T. Wadayama, Y. Maiwa, H. Shibata and A. Hata 100/101 (1996) 575
- CHF₃ adsorption and decomposition on clean and oxygen covered Al(111), H. Kawada, S. Reiff and J.H. Block 100/101 (1996) 587
- Aluminum doping of ZnTe grown by MOVPE, S.I. Gheysa, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 634
- Aluminium oxide*
- Electrical and optical properties of thin β -FeSi₂ films on Al₂O₃ substrates, K. Herz and M. Powalla 91 (1995) 87
- Surface and subsurface 1 keV electron stimulated reduction of sapphire studied by electron spectroscopy, A. Hoffman and P.J.K. Paterson 93 (1996) 301
- Fast etching of sapphire by a visible range quasi-cw laser radiation, S.I. Dolgaev, A.A. Lyalin, A.V. Simakin and G.A. Shafeev 96-98 (1996) 491
- Excimer laser ablation and film deposition of Ti:sapphire, P.E. Dyer, S.R. Jackson, P.H. Key, W.J. Metheringham and M.J.J. Schmidt 96-98 (1996) 849
- Modelling of the particle size distribution function in the nucleation and early stages of thin film growth, M. Tomellini 99 (1996) 67
- FTIR study of adsorption of CO, NO and C₂H₄ and reaction of CO + H₂ on the well-dispersed FeOx/ γ -Al₂O₃ and FeOx/TiO₂(a) catalysts, W. Ji, Y. Chen, S. Shen, S. Li and H. Wang 99 (1996) 151
- Large area synthesis of thin alumina films by laser ablation, B. Hirschauer, S. Söderholm, J. Paul and A.S. Flodström 99 (1996) 285
- Surface structure analysis of dispersed metal sites on single crystal metal oxides by means of polarization-dependent total-reflection fluorescent EXAFS, W.-J. Chun, K. Asakura and Y. Iwasawa 100/101 (1996) 143
- The surface and interface reaction of metal thin film on sapphire substrate, H.J. Kang, C.H. Kim, N.S. Park and M.W. Kim 100/101 (1996) 160
- The correlation between surface charge distribution and flashover properties of alumina surface in vacuum, Tumiran, S. Kobayashi, M. Maceyama, H. Imada and Y. Saito 100/101 (1996) 238
- Charge-up and charge compensation on monochromatized X-ray photoelectron spectroscopic measurements of alumina and glass, H. Tomizuka and A. Ayame 100/101 (1996) 243
- Ammonia*
- Laser induced nitridation of Ga on GaAs surfaces, M.F. Barthe, C. Perrin, L. Vivet, B. Dubreuil and T. Gibert 96-98 (1996) 359
- Amorphous materials*
- Ternary amorphous metallic thin films as diffusion barriers for Cu metallization, M.-A. Nicolet 91 (1995) 269

Annealing

- Metallurgical and electrical investigation of Pt₅Ni₉₅/silicon interactions, F. Corni, C. Nobili, G. Ottaviani, R. Tonini, B. Grignaffini Gregorio and G. Queirolo 91 (1995) 107
- Integration of a TiN barrier layer formed by rapid thermal annealing in a 1 µm CMOS process, K.-H. Stegemann, V. Heinig, G. Fontaine, J. Palorec and C. Beyer 91 (1995) 308
- Rapid thermal post-metallization annealing effect on thin gate oxides, M.-J. Jeng, H.-S. Lin and J.-G. Hwu 92 (1996) 208
- Ellipsometric study of thermal and laser annealed amorphous and microcrystalline silicon films, A.H. Jayatissa, M. Suzuki, Y. Nakanishi and Y. Hatanaka 92 (1996) 300
- Single shot excimer laser annealing of amorphous silicon for AMLCD, P. Boher, J.L. Stehle, M. Stehle and B. Goudard 96-98 (1996) 376
- Approach to in situ characterization of polysilicon surfaces annealed by XeCl excimer laser, T. Nishibe, H. Mitsuhashi, Y. Matsuura and Y. Kawakyu 99 (1996) 35
- Microstructure studies of PdGe/Ge ohmic contacts to n-type GaAs formed by rapid thermal annealing, W.D. Chen, X.L. Xie, Y.D. Cui, C.H. Chen and C.C. Hsu 100/101 (1996) 530
- Annealing behavior of phosphorus in native oxide films on heavily phosphorus doped silicon, W.B. Ying, Y. Mizokawa, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto 100/101 (1996) 556
- Photoluminescence enhancement of (NH₄)₂S_x passivated InP surface by rapid thermal annealing, W.D. Chen, X.Q. Li, L.H. Duan, X.L. Xie and Y.D. Cui 100/101 (1996) 592

Antimony

- Surfactant modified growth of CuInSe₂ thin films, B.-H. Tseng, G.-W. Chang and G.-L. Gu 92 (1996) 227
- Structural characterization of epitaxial ferromagnetic MnSb layers grown by hot-wall epitaxy, H. Tatsuoka, H. Kuwabara, M. Oshita, Y. Nakanishi, T. Nakamura and H. Fujiyasu 92 (1996) 382
- Surfactant effect of Sb on the growth of Ag films on a sapphire substrate, T. Lewowski and P. Wiczorek 93 (1996) 85

Arc evaporation

- Low temperature growth of diamond-like films by cathodic arc plasma deposition, P.-L. Chen, M.-Y. Tsai and J.-S. Kao 92 (1996) 30
- XPS studies on SiC thin layers formed by ion implantation with a metal vapor vacuum arc ion source, H. Yan, R.W.M. Kwok and S.P. Wong 92 (1996) 61

Argon

- Damage profiling of Ar⁺ sputtered Si(100) surface by medium energy ion scattering spectroscopy, J.C. Lee, C.S. Jeong, H.J. Kang, H.K. Kim and D.W. Moon 100/101 (1996) 97
- Ion induced alteration at Pb-Sn alloy surface investigated by Auger electron spectroscopy and X-ray photoelectron spectroscopy, M. Kudo, A. Ishijima and T. Morohashi 100/101 (1996) 134
- Angular distribution of particles sputtered from GaAs by Ar⁺ and Xe⁺ ion bombardment, T. Aoyama, M. Tanemura and F. Okuyama 100/101 (1996) 351
- Valence band structure of metal silicides modified by argon ion implantation, S. Yamauchi, Y. Hasebe, H. Ohshima, T. Hattori, M. Hirai, M. Kusaka and M. Iwami 100/101 (1996) 522

Arsenic

- Growth of the thin film Cd-Si-As system by metalorganic chemical vapor deposition, H. Kayama, Y. Noda and Y. Furukawa 92 (1996) 142
- Investigation of the dosage effect on the activation of arsenic- and boron-implanted low-pressure chemical vapor deposition (LPCVD) amorphous-silicon films, F.-S. Wang, M.-J. Tsai, W.-K. Lai and H.-C. Cheng 92 (1996) 372
- Study of the internal electric fields across the interfaces in the GaAs/(Al,Ga)As microstructures, C.R. Lu, C.L. Chang, C.H. Liou, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 404
- Soft laser sputtering of the GaAlAs (100) surface, L. Vivet, B. Dubreuil, T. Gibert-Legrand and M.F. Barthe 96-98 (1996) 238

Atomic force microscopy

- Improved thermal stability of cobalt silicide formed by ion beam assisted deposition

- on polysilicon, S. Ravesi, F. La Via, V. Raineri and C. Spinella 91 (1995) 19
- Electroless copper metallisation of titanium nitride, J.C. Patterson, C. Ni Dheasuna, J. Barrett, T.R. Spalding, M. O'Reilly, X. Jiang and G.M. Crean 91 (1995) 124
- Sputtering of tantalum-based diffusion barriers in Si/Cu metallization: effects of gas pressure and composition, M. Stavrev, C. Wenzel, A. Möller and K. Drescher 91 (1995) 257
- The etching of natural alpha-recoil tracks in mica with an argon RF-plasma discharge and their imaging via atomic force microscopy, N.M.D. Brown and Z.H. Liu 93 (1996) 89
- Studies of 1T TiS₂ by STM, AFM and XPS: the mechanism of hydrolysis in air, H. Martinez, C. Auriel, D. Gonbeau, M. Loudet and G. Pfister-Guillouzo 93 (1996) 231
- Relationship between organic thin film uniformity and its electroluminescence, G. Wang, Y. Ding and Y. Wei 93 (1996) 281
- Excimer laser machining for the fabrication of analogous microstructures, K. Zimmer, D. Hirsch and F. Bigl 96-98 (1996) 425
- Picosecond UV-laser ablation of Au and Ni films, A. Rosenfeld and E.E.B. Campbell 96-98 (1996) 439
- Formation of the surface structure of polyethylene-terephthalate (PET) due to ArF excimer laser ablation, B. Hopp, M. Csete, K. Révész, J. Vinkó and Zs. Bor 96-98 (1996) 611
- Improved properties of Pulsed Laser Deposited YBaCuO on NdGaO₃ using CeO₂ template layers, D.H.A. Blank, A.J.H.M. Rijnders, F.J.G. Roesthuis, G. den Ouden and H. Rogalla 96-98 (1996) 685
- Mirror-smooth YBa₂Cu₃O_{7-x} superconducting films deposited by plasma-enhanced pulsed laser deposition technique, C.S. Huang, T.Y. Tseng, B.C. Chung, C.H. Tsai, H.F. Cheng and I.N. Lin 96-98 (1996) 735
- Ferrimagnetic thin films prepared by pulsed laser deposition, M. Guyot, A. Lisfi, R. Krishnan, M. Porte, P. Rougier and V. Cagan 96-98 (1996) 802
- Structural and optical characteristics of pulsed laser deposited ZnSe epilayers, A. Chergui, J.L. Deiss, J.B. Grun, J.L. Loison, M. Robino and R. Beserman 96-98 (1996) 874
- XPS and AFM characterization of a vanadium oxide film on TiO₂(100) surface, G. Chiarello, R. Barberi, A. Amoddeo, L.S. Caputi and E. Colavita 99 (1996) 15
- Approach to in situ characterization of polysilicon surfaces annealed by XeCl excimer laser, T. Nishibe, H. Mitsuhashi, Y. Matsuura and Y. Kawakyu 99 (1996) 35
- AFM and STM studies on In₂O₃ and ITO thin films deposited by atomic layer epitaxy, T. Asikainen, M. Ritala, M. Leskelä, T. Prohaska, G. Friedbacher and M. Grasserbauer 99 (1996) 91
- A simulation study of multi-atom tips and estimation of resolution in atomic force microscopy, S. Banerjee, M.K. Sanyal and A. Datta 99 (1996) 255
- Preparation of thin silver films on mica studied by XRD and AFM, J.-D. Grunwaldt, F. Atamny, U. Göbel and A. Baiker 99 (1996) 353
- Investigation of the physical and chemical interaction of a low energy oxygen ion beam with oxide superconducting films, G. Pindoria, M. Badaye, F. Wang, K. Kawaguchi and T. Morishita 100/101 (1996) 347
- Roughness study of ion-irradiated silica glass surface, K. Oyoshi, S. Hishita, K. Wada, S. Suchara and T. Aizawa 100/101 (1996) 374
- CBE-grown high-quality GaAs on Si substrate, H. Uchida, M. Adachi, H. Nishikawa, T. Egawa, T. Jimbo and M. Umeno 100/101 (1996) 399
- Initial stage of oxidation of Si(100) surfaces in dry oxygen, K. Inanaga, T. Nakahata, T. Furukawa and K. Ono 100/101 (1996) 421
- Surface barriers formation mechanism of the chemically etched CdTe(111) polar surfaces and gold interfaces, T. Takeuchi, T. Kore-eda and A. Ebina 100/101 (1996) 596

Atomic probe analysis

- Precipitation processes during the early stages of ageing in Al-Cu-Mg alloys, S.P. Ringer, K. Hono, I.J. Polmear and T. Sakurai 94/95 (1996) 253
- 3D reconstruction and analysis of GP zones in Al-1.7Cu (at%): a tomographic atom probe investigation, A. Bigot, F. Danoix, P. Auger, D. Blavette and A. Menand 94/95 (1996) 261
- AP-FIM analysis of ordered Cu₃Au-(4 at% Pt) alloy, V.A. Ivchenko, A. Kvist, H.-O. André, N.N. Syutkin and K. Stiller 94/95 (1996) 267
- Atomic scale investigation of ordering and precipitation processes in a model Ni-Cr-Al alloy, C. Schmuck, F. Danoix, P. Caron, A. Hauet and D. Blavette 94/95 (1996) 273
- Microstructural development in PWA-1480 electron beam welds - an atom probe field ion microscopy study, S.S. Babu, S.A. David and M.K. Miller 94/95 (1996) 280
- Precipitation and grain boundary segrega-

- tion in molybdenum-doped NiAl, M.K. Miller, I.M. Anderson and K.F. Russell 94/95 (1996) 288
- Nanocrystallization of a Co-Nb-B-C metallic glass, T.A. Lusby and A.J. Melmed 94/95 (1996) 300
- Characterization of sputter-deposited multi-layers of Ni and Zr with APFIM/TAP, T. Al-Kassab, M.-P. Macht, V. Naundorf, H. Wollenberger, S. Chambrelaud, F. Danoix and D. Blavette 94/95 (1996) 306
- An atom probe study of cementite precipitation in autotempered martensite in an Fe-Mn-C alloy, R.C. Thomson and M.K. Miller 94/95 (1996) 313
- Observation of molybdenum-nitrogen clustering in highly alloyed martensite, L. Lundin and H.-O. Andr  n 94/95 (1996) 320
- Investigation of precipitation in a new maraging stainless steel, K. Stiller, F. Danoix and A. Bostel 94/95 (1996) 326
- Microstructural influences on the decomposition of an Al-containing ferritic stainless steel, H.G. Read and H. Murakami 94/95 (1996) 334
- Grain boundary precipitation and segregation in Ni-16Cr-9Fe model materials, M. Thuvander, K. Stiller, D. Blavette and A. Menand 94/95 (1996) 343
- Atom probe analysis of carbonitride grains in (Ti, W, Ta, Mo)(C, N)(Co/Ni) cermets with different carbon content, J. Zackrisson, M. Thuvander, P. Lindahl and H.-O. Andr  n 94/95 (1996) 351
- A specimen preparation technique for atom probe analysis of the near-surface region of cemented carbides, A. Kvist, H.-O. Andr  n and L. Lundin 94/95 (1996) 356
- APFIM studies of the phase transformations in thermally aged ferritic FeCuNi alloys: comparison with aging under neutron irradiation, P.J. Pareige, K.F. Russell and M.K. Miller 94/95 (1996) 362
- Characterization of neutron-induced copper-enriched clusters in pressure vessel steel weld: an APFIM study, P. Pareige and M.K. Miller 94/95 (1996) 370
- APFIM characterization of a high phosphorus Russian RPV weld, M.K. Miller and K.F. Russell 94/95 (1996) 378
- Phase separation in the Fe-Cr-Ni system, M.K. Miller, I.M. Anderson, J. Bentley and K.F. Russell 94/95 (1996) 391
- The segregation behaviour of a Pt₉₀Rh₁₀ alloy studied with a three-dimensional atom-probe, W. Athenstaedt and M. Leisch 94/95 (1996) 403
- The chemistry and structure of (222) CdO/Ag heterophase interfaces on an atomic scale, D.K. Chan, D.N. Seidman and K.L. Merkle 94/95 (1996) 409
- Atomic-scale studies of silver segregation at MgO/Cu heterophase interfaces, D.A. Shashkov and D.N. Seidman 94/95 (1996) 416
- Improvement of the detection efficiency of channel plate electron multiplier for atom probe application, B. Deconihout, P. Gerard, M. Bouet and A. Bostel 94/95 (1996) 422
- Improvements in the mass resolution of the three-dimensional atom probe, S.J. Sijbrandij, A. Cerezo, T.J. Godfrey and G.D.W. Smith 94/95 (1996) 428
- Optimal field pulsing for atom probes with counter electrodes, D.J. Larson, P.P. Camus and T.F. Kelly 94/95 (1996) 434
- Analytic treatment of charge cloud overlaps: an improvement of the tomographic atom probe efficiency, P. Bas, A. Bostel, G. Granicher, B. Deconihout and D. Blavette 94/95 (1996) 442
- Contribution of 3D atom probe to the understanding of plane-by-plane AP analyses data: application to the study of ordering in Cu₃Au, S. Duval, S. Chambrelaud and B. Deconihout 94/95 (1996) 449
- Data analysis in the optical PoSAP, A. Cerezo, J.M. Hyde, S.J. Sijbrandij and G.D.W. Smith 94/95 (1996) 457
- Electrostatic analysis of local-electrode atom probes, S.S. Bajkar, T.F. Kelly and P.P. Camus 94/95 (1996) 464
- ### Auger electron spectroscopy
- Metallurgical and electrical investigation of Pt₅Ni₉₅/silicon interactions, F. Corni, C. Nobili, G. Ottaviani, R. Tonini, B. Grignaffini Gregorio and G. Queirolo 91 (1995) 107
- Structure and electrical properties of thin copper films deposited by MOCVD, J. R  ber, C. Kaufmann and T. Gessner 91 (1995) 134
- Stress voiding and electromigration phenomena in aluminum alloys, S. Kordic, R.A. Augur, A.G. Dirks and R.A.M. Wolters 91 (1995) 197
- Influence of the anti reflective coating on the electromigration resistance of 0.5 µm technology metal-2 line structures, R. Stevens, A. Witvrouw, Ph.J. Roussel, K. Maex, H. Meynen and A. Cuthbertson 91 (1995) 208
- Sputtering of tantalum-based diffusion barriers in Si/Cu metallization: effects of gas pressure and composition, M. Stavrev, C. Wenzel, A. M  ller and K. Drescher 91 (1995) 257

- Co-sputtered TiB_2 as a diffusion barrier for advanced microelectronics with Cu metallization, G. Sade and J. Pelleg 91 (1995) 263
- LPCVD $\text{Re}_x\text{Si}_y\text{N}_z$ diffusion barriers in $\text{Si}/\text{SiO}_2/\text{Cu}$ metallizations, A.-M. Dutron, E. Blanquet, C. Bernard, A. Bachli and R. Madar 91 (1995) 277
- Electrical characterization of reactively sputtered TiN diffusion barrier layers for copper metallization, C. Kaufmann, J. Baumann, T. Gessner, T. Raschke, M. Rennau and N. Zichner 91 (1995) 291
- Barrier behaviour of plasma deposited silicon oxide and nitride against Cu diffusion, M. Vogt and K. Drescher 91 (1995) 303
- Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delpiancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
- Growth mechanism of Ni on Pt(110) at low temperature, C.S. Shern, J.S. Tsay and T. Fu 92 (1996) 74
- Effects of substrate cleaning and film thickness on the epitaxial growth of ultrahigh vacuum deposited Cu thin films on (001)Si, C.S. Liu and L.J. Chen 92 (1996) 84
- Characteristics of PECVD GaN thin films, C.H. Lee and C.T. Chen 92 (1996) 124
- Ge deposition from digermane on the $\text{Si}(100)-(2 \times 1)$ surface, H.-C. Cho 92 (1996) 128
- The properties of SiO_2 films using direct photo-chemical vapor deposition on strained SiGe layers, C.T. Lin, S.J. Chang, D.K. Nayak and Y. Shiraki 92 (1996) 193
- Adsorption of H_2S on GaP(001) surface and passivation effects studied by AES, LEED and XPS, Y. Fukuda, N. Sanada, M. Kuroda and Y. Suzuki 92 (1996) 212
- AES and SRUPS studies on surface passivation of GaAs by $(\text{NH}_4)_2\text{S}_x$ sulfurization techniques, J.T. Hsieh and H.L. Hwang 92 (1996) 222
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- Savitzky and Golay differentiation in AES, I.S. Gilmore and M.P. Seah 93 (1996) 273
- Improvement of the crystallinity in PbTiO_3 films grown on indium tin oxide-coated glass by metalorganic chemical vapor deposition using the continuous cooling process, Y.S. Yoon, S.S. Yom, T.W. Kim, D.U. Lee and C.O. Kim 93 (1996) 285
- Surface and subsurface 1 keV electron stimulated reduction of sapphire studied by electron spectroscopy, A. Hoffman and P.J.K. Paterson 93 (1996) 301
- The oxidation of the NiAl(111) surface, R. Franchy, J. Masuch and P. Gassmann 93 (1996) 317
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- Excimer laser-induced hydrodynamical effects and surface modifications on silicon carbide, G. Nicolas and M. Autric 96-98 (1996) 296
- Laser induced nitridation of Ga on GaAs surfaces, M.F. Barthe, C. Perrin, L. Vivet, B. Dubreuil and T. Gibert 96-98 (1996) 359
- Modelling and diagnostic of pulsed laser cleaning of oxidized metallic surfaces, R. Oltra, O. Yavaş, F. Cruz, J.P. Boquillon and C. Sartori 96-98 (1996) 484
- Pulsed laser deposition of high quality ITO thin films, F. Hanus, A. Jadin and L.D. Laude 96-98 (1996) 807
- AES of semi-insulating polycrystalline silicon layers, J. Liday, S. Tomek and J. Breza 99 (1996) 9
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- Study of the chemical bonding in tungsten carbide and chromium films by application of factor analysis on AES depth profiles, F. Reniers, E. Silberberg, N. Roose and J. Vereecken 99 (1996) 379
- Oxidation of ultrathin iron layers grown on Cu(111), C. Ruby and J. Fusy 99 (1996) 393
- Auger electron peaks of Cu in XPS, M. Jo and A. Tanaka 100/101 (1996) 11
- Intrinsic Auger signal profiles derived by Monte Carlo analysis, Z.-J. Ding, R. Shimizu and K. Goto 100/101 (1996) 15
- True Auger spectral shapes (standards), Y. Takeichi, K. Goto and V. Gaidarova 100/101 (1996) 25
- Comparison of AES chemical shifts with XPS chemical shifts, T. Sekine, N. Ikeo and Y. Nagasawa 100/101 (1996) 30
- A general procedure for extracting quantitative depth information from take-off-angle-resolved XPS and AES, W.H. Gries 100/101 (1996) 41
- Auger electron spectroscopy measurement of electron attenuation lengths using multilayer systems, M. Suzuki, K. Mogi and H. Takenaka 100/101 (1996) 51
- High sensitivity of positron-annihilation induced Auger-electron spectroscopy to surface impurities, T. Ohdaira, R. Suzuki, T. Mikado, H. Ohgaki, M. Chiwaki, T. Yamazaki and M. Hasegawa 100/101 (1996) 73
- Determination of the interface region in multilayer Si/Mo by Auger depth profile and factor analysis, T. Morohashi, T. Hoshi, H. Nikaido and M. Kudo 100/101 (1996) 84
- Analysis of Auger sputter depth profiles with a resolution function, T. Kitada, T. Harada and S. Tanuma 100/101 (1996) 89
- Oxide thin films formed during rotational AES sputter depth profiling of Ni/Cr multilayers using oxygen ions, A. Zalar, E.W. Seibt and P. Panjan 100/101 (1996) 92
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- Submicron particle analysis by the Auger microprobe (FE-SAM), H. Ito, M. Ito, Y. Magatani and F. Soeda 100/101 (1996) 152
- Determination of Al₂Ga_{1-x}As Auger sensitivity factors, W.D. Chen and Y.D. Cui 100/101 (1996) 156
- Ga migration process in Au film on (100) GaAs under temperature treatment in vacuum, T.A. Bryantseva, D.V. Lioubchenko and V.V. Lopatin 100/101 (1996) 169
- The effect of EB irradiation with and without hot-jet Cl₂ on an ultra-thin GaN layer for selective etching, S. Yoshida, M. Sasaki and T. Ishikawa 100/101 (1996) 184
- Effect of gas adsorption on the segregation behavior of substrate Cu on Ti film, M. Yoshitake and K. Yoshihara 100/101 (1996) 203
- Sn segregation to the low index surfaces of a copper single crystal, J. du Plessis and E.C. Viljoen 100/101 (1996) 222
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Barium

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Bismuth

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Borides

- Co-sputtered TiB_2 as a diffusion barrier for advanced microelectronics with Cu metallization, G. Sade and J. Pelleg 91 (1995) 263
- Properties of multilayered thin films for thermal ink-jet printing devices, D.S. Wu, M.L. Lee and T.Y. Lin 92 (1996) 626

Boron

- Investigation of the dosage effect on the activation of arsenic- and boron-implanted low-pressure chemical vapor deposition (LPCVD) amorphous-silicon films, F.-S. Wang, M.-J. Tsai, W.-K. Lai and H.-C. Cheng 92 (1996) 372
- Refractive index behavior of boron-doped silica films by plasma-enhanced chemical vapor deposition, R.H. Horng, F. Chen, D.S. Wu and T.Y. Lin 92 (1996) 387
- Nanocrystallization of a Co-Nb-B-C metallic glass, T.A. Lusby and A.J. Melmed 94/95 (1996) 300

Boron nitride

- Study of the expansion of the laser ablation plume above a boron nitride target, B. Angleraud, C. Girault, C. Champeaux, F. Garrelie, C. Germain and A. Catherinot 96-98 (1996) 117
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Cadmium

- Growth of the thin film Cd-Si-As system by metalorganic chemical vapor deposition, H. Kayama, Y. Noda and Y. Furukawa 92 (1996) 142
- Stimulated blue emission processes in $\text{Zn}_{1-x}\text{Cd}_x\text{Se}/\text{ZnSe}$ multi-quantum wells, J.Y. Jen, T. Tsutsumi, I. Souma, Y. Oka, J.R. Anderson and M. Gorska 92 (1996) 547
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Cadmium sulphide

- Solar cells from thin films prepared by periodic pulse electrodeposition, G.C. Morris and R.J. Vanderveen 92 (1996) 630

Cadmium telluride

- Photoellipsometric studies on CdTe thin films, P.D. Paulson and V. Dutta 92 (1996) 295
- Thin film photovoltaics, H.W. Schock 92 (1996) 606
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- NO interaction with thermally activated CaO and SrO surfaces, Y. Yanagisawa 100/101 (1996) 256
- Calcium fluoride**
- Laser damage of CaF₂(111) surfaces at 248 nm, S. Gogoll, E. Stenzel, M. Reichling, H. Johansen and E. Matthias 96-98 (1996) 332
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- XPS study of the reaction of the Si(100) surface with a C₂H₄ beam, T. Takagaki, Y. Igari, T. Takaoka and I. Kusunoki 92 (1996) 287
- Microstructural properties of laser synthesized Si/C/N nanoparticles, R. Giorgi, S. Turtù, G. Zappa, E. Borsella, S. Botti, M.C. Cesile and S. Martelli 93 (1996) 101
- A specimen preparation technique for atom probe analysis of the near-surface region of cemented carbides, A. Kvist, H.-O. Andrén and L. Lundin 94/95 (1996) 356
- Study of the chemical bonding in tungsten carbide and chromium films by application of factor analysis on AES depth profiles, F. Reniers, E. Silberberg, N. Roose and J. Vereecken 99 (1996) 379
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- Electron emission from carbon fibre tips, M.S. Mousa 94/95 (1996) 129
- Nanocrystallization of a Co-Nb-B-C metallic glass, T.A. Lusby and A.J. Melmed 94/95 (1996) 300
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- XPS study of carbon/inconel bilayers as a function of substrate bias, M.S. Aouadi, P.C. Wong and K.A.R. Mitchell 99 (1996) 319
- Heating effects on modifying carbon surface by reactive plasma, Y. Izumi, M. Katoh, T. Ohte, S. Ohtani, A. Kojima and N. Saitoh 100/101 (1996) 179
- Investigation of characteristics of carbon materials with various structures modified by plasmas using plasma diagnostics and material-surface analysis, M. Katoh, Y. Izumi, H. Kimura, T. Ohte, A. Kojima and S. Ohtani 100/101 (1996) 226
- Carbon monoxide**
- The influence of impurities contained in quartz sand on the catalytic reduction of nitric oxide by carbon monoxide, P. Schoderböck and J. Lahaye 93 (1996) 109
- Growth and reactivity of evaporated platinum films on Cu(111): a study by AES, RHEED and adsorption of carbon monoxide and xenon, J. Fusy, J. Menaucourt, M. Alnot, C. Huguet and J.J. Ehrhardt 93 (1996) 211

FT-IR characterization of alkali-doped Pd catalysts for the selective hydrogenation of phenol to cyclohexanone, S. Scirè, C. Crisafulli, R. Maggiore, S. Minicò and S. Galvagno

93 (1996) 309

Digitizing chemical oscillations: analyzing experimental data of the CO oxidation on a Pt-tip, M.C. Reckzúgel, V. Gorodetskii and J.H. Block

94/95 (1996) 194

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94/95 (1996) 200

Study of CO surface diffusion on CO/W(111) by analysis of CO⁺ field ion rate fluctuations, Yu. Suchorski, J. Bèben, V.K. Medvedev and J.H. Block
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94/95 (1996) 207

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99 (1996) 151

Ru-Cu/ZSM5 catalysts: Characterization by FT-IR spectroscopy, C. Crisafulli, S. Scirè, S. Minicò, R. Maggiore and S. Galvagno

99 (1996) 401

Infrared chemiluminescence study of the dynamics of catalytic oxidation of CO and HCOOH on Pd(111) and polycrystalline Pd surfaces, K. Watanabe, H. Uetsuka, H. Ohnuma and K. Kunimori

99 (1996) 411

Catalysis

The influence of impurities contained in quartz sand on the catalytic reduction of nitric oxide by carbon monoxide, P. Schoderböck and J. Lahaye

93 (1996) 109

Oscillatory behavior in the catalytic reduction of NO and NO₂ with hydrogen on Pt field emitter tips, C. Voss and N. Kruse

94/95 (1996) 186

High resolution electron microscopy characterization of small Pt-Pd/SiO₂ particles in oxide-reducing cycles, A. Vázquez and F. Pedraza

99 (1996) 213

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99 (1996) 411

Ceramics

Optical diagnostics of the laser-target and laser-plume interaction in pulsed laser ablation, F. Fuso, L.N. Vyacheslavov, G. Lorenzi, M. Allegrini and E. Arimondo

96-98 (1996) 181

Optical and particle properties of PLD vapour/plasmas of ceramics, M. Alunovic, H. Stamm, M. Aden and E.W. Kreutz

96-98 (1996) 222

Increase of efficiency for the XeCl excimer laser ablation of ceramics, M. Geiger, W. Becker, T. Rebhan, J. Hutfless and N. Lutz

96-98 (1996) 309

Surface temperature measurements during pulsed laser action on metallic and ceramic materials, M.B. Ignatiev, I.Yu. Smurov, G. Flamant and V.N. Senchenko

96-98 (1996) 505

Pb_{1-x}Ca_xTiO₃ thin films prepared by laser ablation of ceramic targets, M.J. Martín, C. Zaldo and J. Mendiola

96-98 (1996) 823

Pulsed laser deposition of electroceramic thin films, M. Mertin, D. Offenberg, C.W. An, D.A. Wesner and E.W. Kreutz

96-98 (1996) 842

Cerium

Preparation of blue-emitting SrGa₂Se₄:Ce thin films by multi-source deposition, Y. Nakanishi, F. Shiba, K. Sowa, H. Tatsuoka, H. Kuwabara, T. Nakamura and Y. Hatanaka

100/101 (1996) 639

Chalcogenides

Studies of 1T TiS₂ by STM, AFM and XPS: the mechanism of hydrolysis in air, H. Martinez, C. Auriel, D. Gonbeau, M. Loudet and G. Pfister-Guillouzo

93 (1996) 231

Chemical vapour deposition

Advanced multilevel metallization technology, T. Ohba

91 (1995) 1

The modelling routes for the chemical vapour deposition process: application to Si_{1-x}Ge_x deposition, M. Pons, C. Bernard, H. Rouch and R. Madar

91 (1995) 34

Formation of CoSi₂ on strained Si_{0.8}Ge_{0.2} using a sacrificial Si layer, R.A. Donaton, S. Kolodinski, M. Caymax, Ph.J. Roussel, H. Bender, B. Brijs and K. Maex

91 (1995) 77

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- Nucleation and growth of CVD-W on TiN studied by X-ray fluorescence spectrometry, M.S. Marangon, G. Queirolo and C. Savoia 91 (1995) 157
- Influence of mixed reductants on the growth rate of WF_6 -based W-CVD, J.F. Jongste, T.G.M. Oosterlaken, G.J. Leusink, C.A. van der Jeugd, G.C.A.M. Janssen and S. Radelaar 91 (1995) 162
- Thermodynamic and experimental study of Cu-LPCVD by reduction of copper chloride, N. Bourhila, N. Thomas, J. Palleau, J. Torres, C. Bernard and R. Madar 91 (1995) 175
- Precursor development for the chemical vapor deposition of aluminium, copper and palladium, A. Gräfe, R. Heinen, F. Klein, Th. Kruck, M. Scherer and M. Schober 91 (1995) 187
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- A highly reliable, low cost 0.5 μ m three level tungsten metallization, M. Hain, H. Körner, B. Neureither and S. Röhl 91 (1995) 374
- Deposition of titanium nitride/tungsten layers for application in vertically integrated circuits technology, G. Ruhl, B. Fröschle, P. Ramm, A. Intemann and W. Pamler 91 (1995) 382
- Surface reaction mechanism in MOCVD, J. Nishizawa, H. Sakuraba and T. Kurabayashi 92 (1996) 89
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- Characteristics of PECVD GaN thin films, C.H. Lee and C.T. Chen 92 (1996) 124
- Ge deposition from digermene on the Si(100)-(2 \times 1) surface, H.-C. Cho 92 (1996) 128
- Growth of ZnSe thin films by radical assisted MOCVD method, T. Aoki, M. Morita, S. Wickramanayaka, Y. Nakanishi and Y. Hatanaka 92 (1996) 132
- The electrical and optical characteristics of GaAs on Si by modified flow rate modulation epitaxy, M.K. Lee, C.C. Hu, and C.Z. Hwang 92 (1996) 159
- Ultra-thin gate dielectrics grown by low-temperature processes for applications to ULSI devices, H.-L. Hwang, P.-C. Chen and K.Y.J. Hsu 92 (1996) 180
- The properties of SiO₂ films using direct photo-chemical vapor deposition on strained SiGe layers, C.T. Lin, S.J. Chang, D.K. Nayak and Y. Shiraki 92 (1996) 193
- Investigation of the dosage effect on the activation of arsenic- and boron-implanted low-pressure chemical vapor deposition (LPCVD) amorphous-silicon films, F.-S. Wang, M.-J. Tsai, W.-K. Lai and H.-C. Cheng 92 (1996) 372
- Refractive index behavior of boron-doped silica films by plasma-enhanced chemical vapor deposition, R.H. Horng, F. Chen, D.S. Wu and T.Y. Lin 92 (1996) 387
- Tungsten absorber on indium tin oxide membrane, D.C. Li, C.S. Yoo and C.Y. Sun 92 (1996) 665
- Improvement of the crystallinity in PbTiO₃ films grown on indium tin oxide-coated glass by metalorganic chemical vapor deposition using the continuous cooling process, Y.S. Yoon, S.S. Yom, T.W. Kim, D.U. Lee and C.O. Kim 93 (1996) 285

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- Decomposition mechanisms of thin palladium acetate film with excimer UV radiation, J.-Y. Zhang, H. Esrom and I.W. Boyd 96-98 (1996) 399
- Surface composition of CVD-grown α -SiC layers - an XPS and LEED study, H. Behner and R. Rupp 99 (1996) 27
- Application and properties of sub-monomolecular layers of silicon dioxide deposited under mild conditions, D.M. Knotter 99 (1996) 99
- On the application of XPS to ceria films grown by MOCVD using a fluorinated precursor, D. Chadwick, J. McAleese, K. Senkiw and B.C.H. Steele 99 (1996) 417
- GaAs-based LED on Si substrate with GaAs islands active region by droplet-epitaxy, Y. Hasegawa, T. Egawa, T. Jimbo and M. Umeno 100/101 (1996) 482
- Si epitaxial growth at low temperatures using remote plasma process, A. Yoshida, K. Utsumi and A. Ganjoo 100/101 (1996) 491
- Comparison of MOCVD and MBE semiconductor superlattices for the evaluation of depth resolution in AES and SIMS, M. Furuya, M. Soga and H. Takano 100/101 (1996) 508
- High-rate deposition of high-quality Cu film with LPCVD, K. Numajiri, T. Goya, R. Tobe, O. Okada, N. Hosokawa, C. Mu, N. Cox, C. Scott and J. Yu 100/101 (1996) 541
- Low pressure MOCVD of TiN thin films, S.W. Kim, H. Jimba, A. Sekiguchi, O. Okada and N. Hosokawa 100/101 (1996) 546
- Selective epitaxial Si based layers and TiSi_2 deposition by integrated chemical vapor deposition, J.L. Regolini, J. Margail, S. Bodnar, D. Maury and C. Morin 100/101 (1996) 566
- In-situ IR and mass spectroscopic study of the $\text{Al}(\text{CH}_3)_2\text{H}/\alpha\text{-Si:H}$ reaction processes, T. Wadayama, Y. Maiwa, H. Shibata and A. Hatta 100/101 (1996) 575
- Characterization of MOCVD-grown GaAs on Si by spectroscopic ellipsometry, G. Yu, T. Soga, T. Jimbo and M. Umeno 100/101 (1996) 617
- ZnSe crystal growth by radical assisted MOCVD, Y. Hatanaka, T. Aoki, M. Morita and Y. Nakanishi 100/101 (1996) 621
- Aluminum doping of ZnTe grown by MOVPE, S.I. Gheys, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 634
- Microwave plasma assisted LCDVD growth and characterization of GaN, B. Zhou, X. Li, T.L. Tansley and K.S.A. Butcher 100/101 (1996) 643

Chromium

- Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asksali, V. Rooryck and O. Van Sinay 92 (1996) 35
- Novel epitaxial growth and magnetotransport characterization of single crystal $\text{Co}(1\bar{1}20)/\text{Cr}(100)$ superlattices on Mo buffer layers, J.C.A. Huang, Y.D. Yao, Y. Liou, S.F. Lee, W.T. Yang, C.P. Chang, S.Y. Liao and C.H. Lee 92 (1996) 480
- XPS, AES and LEED studies of Cu deposited on $\text{Cr}_2\text{O}_3(0001)$ surfaces, Q. Guo, L. Gui, P.J. Möller and K. Binau 92 (1996) 513
- Atomic scale investigation of ordering and precipitation processes in a model Ni-Cr-Al alloy, C. Schmuck, F. Danoix, P. Caron, A. Hauet and D. Blavette 94/95 (1996) 273
- Grain boundary precipitation and segregation in Ni-16Cr-9Fe model materials, M. Thuvander, K. Stiller, D. Blavette and A. Menand 94/95 (1996) 343
- Comparison of the rate of decomposition in Fe-45%Cr, Fe-45%Cr-5%Ni and duplex stainless steels, M.K. Miller and K.F. Russell 94/95 (1996) 398
- Optodynamics of laser ablation of graduation lines in chromium thin film on glass, S. Kopač, J. Pirš and J. Možina 96-98 (1996) 420
- X-ray photoelectron spectroscopy of Cr/COOCH_3 interfaces on self-assembled monolayers of 16-mercaptohexadecanoate, D.R. Jung and A.W. Czanderna 99 (1996) 161
- Study of the chemical bonding in tungsten carbide and chromium films by application of factor analysis on AES depth profiles, F. Reniers, E. Silberberg, N. Roose and J. Vereecken 99 (1996) 379
- Oxide thin films formed during rotational AES sputter depth profiling of Ni/Cr multilayers using oxygen ions, A. Zalar, E.W. Seibt and P. Panjan 100/101 (1996) 92

Clusters

- Cluster beams for metallization of microstructured surfaces, P. Gatz and O.F. Hagena 91 (1995) 169

Cobalt

- Ti/Co bilayers in salicide technology: elec-

- trical evaluation, A. Lauwers, Q.F. Wang, B. Deweerdt and K. Maex
Improved thermal stability of cobalt silicide formed by ion beam assisted deposition on polysilicon, S. Ravesi, F. La Via, V. Raineri and C. Spinella
Epitaxy of $\text{CoSi}_2/\text{Si}(100)$: from $\text{Co/Ti/Si}(100)$ to reactive deposition epitaxy, A. Vantomme, S. Degroote, J. Dekoster and G. Langouche
Experimental identification of the optical phonon of CoSi_2 in the infrared, S. Bocelli, G. Guizzetti, F. Marabelli, G. Thungström and C.S. Petersson
Comparison of CoSi_2 interconnection lines on crystalline and noncrystalline silicon fabricated by writing focused ion beam implantation, J. Teichert, L. Bischoff, J. Hesse, P. Schneider, D. Panknin, T. Gessner, B. Löbner and N. Zichner
Electrical and optical properties of thin $\text{Fe}_{1-x}\text{Co}_x\text{Si}_2$ films, St. Teichert, R. Kilper, Th. Franke, J. Erben, P. Häusler, W. Henrion, H. Lange and D. Panknin
Formation of CoSi_2 on strained $\text{Si}_{0.8}\text{Ge}_{0.2}$ using a sacrificial Si layer, R.A. Donaton, S. Kolodinski, M. Caymax, Ph.J. Roussel, H. Bender, B. Brijs and K. Maex
Phonon dispersion relations of metallic NiSi_2 and CoSi_2 by semi-empirical tight-binding calculation, S. Sanguinetti, C. Calegari and L. Miglio
Selective deposition of tungsten on ITM-CoSi_2 , J.D. Köhler, D. Depta and R. Ferretti
On the formation of silicides on poly runners with topography by a two-step silydation process, F. Jonckx, R. Verbeeck, B. Deweerdt and K. Maex
Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on $\text{MgO}(001)$, H. Qiu, T. Ohbuchi, H. Nakai and M. Hashimoto
Coercivity of $\gamma\text{-(Fe}_{0.74}\text{Mn}_{0.15}\text{Co}_{0.11})_2\text{O}_3$ thin films by dc reactive magnetron sputtering, W.-D. Chang and T.-S. Chin
Novel epitaxial growth and magnetotransport characterization of single crystal $\text{Co}(11\bar{2}0)/\text{Cr}(100)$ superlattices on Mo buffer layers, J.C.A. Huang, Y.D. Yao, Y. Liou, S.F. Lee, W.T. Yang, C.P. Chang, S.Y. Liao and C.H. Lee
Characterisation of the spinels $\text{M}_x\text{Co}_{1-x}\text{Fe}_2\text{O}_4$ ($\text{M} = \text{Mn, Fe or Ni}$) using X-ray photoelectron spectroscopy, G.C. Allen and K.R. Hallam
Adsorption studies of cobalt on tungsten (110), (100) and (111) planes by probe-hole field emission microscopy, R.B. Sharma, A.D. Adsool, N. Pradeep and D.S. Joag
Nanocrystallization of a Co-Nb-B-C metallic glass, T.A. Luszby and A.J. Meled
Atom probe analysis of carbonitride grains in (Ti, W, Ta, Mo)C, N(Co/Ni) cermets with different carbon content, J. Zackrisson, M. Thuvander, P. Lindahl and H.-O. André
Hydrogen desorption characteristics of composite Co-TiN nanoparticles, Y. Sakka and S. Ohno
Co overlayer formation process on $\text{Si}(100)2 \times 1$ studied by SR-PES, T. Jikimoto, C. Heck, K. Komoku, M. Hirai, M. Kusaka and M. Iwami
Behavior of ultrathin layers of Co on Si and Ge systems, K. Prabhakaran and T. Ogino
Computer simulations
3D simulation of tungsten low-pressure chemical vapor deposition in contact holes, E. Bär and J. Lorenz
A study of the optimum field emitter shape for vacuum electronics applications, B.P. Wang and L. Tong
An analytical model for the laser ablation of materials, A.D. Boardman, B. Cresswell and J. Anderson
Copper
Advanced copper interconnections for silicon CMOS technologies, J. Torres
Electroless copper metallisation of titanium nitride, J.C. Patterson, C. Ni Dheasuna, J. Barrett, T.R. Spalding, M. O'Reilly, X. Jiang and G.M. Crean
Process optimization of copper MOCVD using modeling experimental design, M.-J. Mouche, J.-L. Mermet, F. Pires, E. Richard, J. Torres, J. Palleau and F. Braud
Structure and electrical properties of thin copper films deposited by MOCVD, J. Röber, C. Kaufmann and T. Gessner
Patterning of copper for multilevel metallization: reactive ion etching and chemical-mechanical polishing, C. Steinbrüchel

- Effects of the biasing frequency on RIE of Cu in a Cl_2 -based discharge, A. Bertz, T. Werner, N. Hille and T. Gessner 91 (1995) 147
- Investigation of the oxidation behaviour of thin film and bulk copper, M. O'Reilly, X. Jiang, J.T. Beechinor, S. Lynch, C. Ni Dheasuna, J.C. Patterson and G.M. Crean 91 (1995) 152
- Thermodynamic and experimental study of Cu-LPCVD by reduction of copper chloride, N. Bourhila, N. Thomas, J. Palleau, J. Torres, C. Bernard and R. Madar 91 (1995) 175
- Precursor development for the chemical vapor deposition of aluminium, copper and palladium, A. Gräfe, R. Heinen, F. Klein, Th. Kruck, M. Scherer and M. Schober 91 (1995) 187
- Chemical mechanical polishing of copper for multilevel metallization, Z. Stavreva, D. Zeidler, M. Plömer and K. Drescher 91 (1995) 192
- Stress in Al, AlSiCu, and AlVPd films on oxidized Si substrates, G.J. Leusink, J.P. Lokker, M.J.C. van den Homberg, J.F. Jongste, T.G.M. Oosterlaken, G.C.A.M. Janssen and S. Radelaar 91 (1995) 215
- Electromigration resistance of TiWN/Cu/TiWN interconnections, T. Fukada, T. Mori, Y. Toyoda, M. Hasegawa, K. Namba and K. Ogata 91 (1995) 227
- Model calculations on a bipolar transistor emitter interconnection with different contact shapes, K. Weide, J. Ullmann and W. Hasse 91 (1995) 234
- Ti-diffusion barrier in Cu-based metallization, F. Braud, J. Torres, J. Palleau, J.-L. Mermet and M.-J. Mouche 91 (1995) 251
- Sputtering of tantalum-based diffusion barriers in Si/Cu metallization: effects of gas pressure and composition, M. Stavrev, C. Wenzel, A. Möller and K. Drescher 91 (1995) 257
- Co-sputtered TiB_2 as a diffusion barrier for advanced microelectronics with Cu metallization, G. Sade and J. Pelleg 91 (1995) 263
- Ternary amorphous metallic thin films as diffusion barriers for Cu metallization, M.-A. Nicolet 91 (1995) 269
- LPCVD $\text{Re}_x\text{Si}_y\text{N}_z$ diffusion barriers in Si/ SiO_2 /Cu metallizations, A.-M. Dutron, E. Blanquet, C. Bernard, A. Bachli and R. Madar 91 (1995) 277
- Electrical characterization of conductive and non-conductive barrier layers for Cu-metallization, C. Ahrens, D. Depta, F. Schitthelm and S. Wilhelm 91 (1995) 285
- Barrier behaviour of plasma deposited silicon oxide and nitride against Cu diffusion, M. Vogt and K. Drescher 91 (1995) 303
- Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
- Effects of substrate cleaning and film thickness on the epitaxial growth of ultrahigh vacuum deposited Cu thin films on (001)Si, C.S. Liu and L.J. Chen 92 (1996) 84
- Sprayed films of stannite $\text{Cu}_2\text{ZnSnS}_4$, N. Nakayama and K. Ito 92 (1996) 171
- Surfactant modified growth of CuInSe_2 thin films, B.-H. Tseng, G.-W. Chang and G.-L. Gu 92 (1996) 227
- Influence of KCN treatment on CuInS_2 thin films, Y. Ogawa, A. Jäger-Waldau, T.H. Hua, Y. Hashimoto and K. Ito 92 (1996) 232
- Diffusion length measurements on electrodeposited CuInSe_2 cells, S.N. Qiu, C.X. Qiu and I. Shih 92 (1996) 306
- Interface effects in melting of Pb clusters on the Cu(111) surface, E.Z. Luo, Q. Cai, W.F. Chung and M.S. Altman 92 (1996) 331
- Interdiffusion and reactions in the Cu/TiN/Si thin film system, Y.S. Gong, J.-C. Lin and C. Lee 92 (1996) 335
- Interface of $\text{CuIn}_{1-x}\text{Ga}_x\text{Se}_2$ /GaAs heterostructure, B.-H. Tseng, S.-B. Lin, G.-L. Gu and H.-Z. Hsu 92 (1996) 412
- XPS, AES and LEED studies of Cu deposited on Cr_2O_3 (0001) surfaces, Q. Guo, L. Gui, P.J. Möller and K. Binau 92 (1996) 513
- Thin film photovoltaics, H.W. Schock 92 (1996) 606
- Gas sensitive properties of copperphthalocyanine thin films, M. Masui, M. Sasahara, T. Wada and M. Takeuchi 92 (1996) 634
- An investigation of the Cu/ZnO/Zn system: evidence for the formation of Cu-Zn alloys by the inward diffusion of Cu, K.R. Harikumar, A.K. Santra and C.N.R. Rao 93 (1996) 135
- Growth and reactivity of evaporated platinum films on Cu(111): a study by AES, RHEED and adsorption of carbon monoxide and xenon, J. Fusy, J. Menau-court, M. Alnot, C. Huguet and J.J. Ehrhardt 93 (1996) 211
- Ellipsometric studies of the oxidation kinetics of Cu particles supported on oxidised Si(100), R. van Wijk, O.L.J. Gijzeman and J.W. Geus 93 (1996) 237
- Comparative studies on enhanced field emission from mechanically and chemically polished broad-area Nb, Cu, and

- Al cathodes, N. Puper, T. Habermann, A. Kirschner, E. Mahner, G. Müller and H. Piel 94/95 (1996) 94
- Precipitation processes during the early stages of ageing in Al-Cu-Mg alloys, S.P. Ringer, K. Hono, I.J. Polmear and T. Sakurai 94/95 (1996) 253
- 3D reconstruction and analysis of GP zones in Al-1.7Cu (at%): a tomographic atom probe investigation, A. Bigot, F. Danoix, P. Auger, D. Blavette and A. Menand 94/95 (1996) 261
- AP-FIM analysis of ordered Cu₃Au-(4 at% Pt) alloy, V.A. Ivchenko, A. Kvist, H.-O. André, N.N. Syutkin and K. Stiller 94/95 (1996) 267
- Atomic-scale studies of silver segregation at MgO/Cu heterophase interfaces, D.A. Shashkov and D.N. Seidman 94/95 (1996) 416
- Contribution of 3D atom probe to the understanding of plane-by-plane AP analyses data: application to the study of ordering in Cu₃Au, S. Duval, S. Chambréland and B. Deconihout 94/95 (1996) 449
- Preferential vaporization and plasma shielding during nano-second laser ablation, X. Mao, W.-T. Chan, M. Caetano, M.A. Shannon and R.E. Russo 96-98 (1996) 126
- Electromagnetic diagnostics during pulsed laser deposition, A.V. Kabashin, W. Marine, P.I. Nikitin and M. Sentis 96-98 (1996) 139
- The role of gas-phase in the laser etching of Cu by CCl₄, D. Débarre, A. Aliouchouche, J. Boulmer, B. Bourguignon and J.P. Budin 96-98 (1996) 453
- Aspects of particulate production from metals exposed to pulsed laser radiation, I. Weaver and C.L.S. Lewis 96-98 (1996) 663
- The oxidation of Cu particles supported on oxidised Si(100) as studied by nuclear reaction analysis and ellipsometry, R. van Wijk, P.C. Görts, C.H.M. Marée, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 99 (1996) 127
- ¹⁸O-exchange with the substrate during ¹⁸O oxidation of Cu particles supported on ¹⁶O-oxidised Si(100), R. van Wijk, C.H.M. Marée, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 99 (1996) 197
- Influence of oxygen on the mass diffusion of Ag on Cu(110): a laterally resolved photoemission study, U. Kürpick, G. Meister and A. Goldmann 99 (1996) 221
- CuCl growth on the reconstructed surface of (0001) haematite, Q. Guo, L. Gui and N. Wu 99 (1996) 229
- Diffusion barrier property of TaN between Si and Cu, T. Oku, E. Kawakami, M. Uekubo, K. Takahiro, S. Yamaguchi and M. Murakami 99 (1996) 265
- Oxidation of ultrathin iron layers grown on Cu(111), C. Ruby and J. Fusy 99 (1996) 393
- Ru-Cu/ZSM5 catalysts: Characterization by FT-IR spectroscopy, C. Crisafulli, S. Scire, S. Minicò, R. Maggiore and S. Galvagno 99 (1996) 401
- Effect of gas adsorption on the segregation behavior of substrate Cu on Ti film, M. Yoshitake and K. Yoshihara 100/101 (1996) 203
- Sn segregation to the low index surfaces of a copper single crystal, J. du Plessis and E.C. Viljoen 100/101 (1996) 222
- Preferential sputtering and surface segregation of CuZr alloys, H.J. Kang, C.H. Kim, N.S. Park, D.J. O'Connor and R. MacDonald 100/101 (1996) 329
- Dissociative scattering of low-energy SiF₃⁺ and SiF⁺ ions (5-200 eV) on Cu(100) surface, H. Yamamoto, Y. Baba and T.A. Sasaki 100/101 (1996) 333
- High-rate deposition of high-quality Cu film with LPCVD, K. Numajiri, T. Goya, R. Tobe, O. Okada, N. Hosokawa, C. Mu, N. Cox, C. Scott and J. Yu 100/101 (1996) 541
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- Electrical properties of laser deposited YBa₂Cu₃O_{7-x} films on silicon wafers, F.Y. Chuang, C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin 92 (1996) 452
- Corrosion inhibition of iron in 1M HCl by 1-phenyl-5-mercapto-1,2,3,4-tetrazole, S. Kertit and B. Hammouti 93 (1996) 59
- Corrosion of iron by a perfluoropolyalkyl-ether identified by Mössbauer spectroscopy, G. John, J.S. Zabinski and V.K. Gupta 93 (1996) 329
- Study of the composition and morphology of initial stages of corrosion products formed on Zn plates exposed to the atmosphere of southeast Mexico, P. Quintana, L. Veleza, W. Cauich, R. Pomes and J.L. Peña 99 (1996) 325
- ### Depth profiling
- Influence of the anti reflective coating on the electromigration resistance of 0.5 µm technology metal-2 line structures, R. Stevens, A. Witvrouw, Ph.J. Roussel, K. Maex, H. Meynen and A. Cuthbertson 91 (1995) 208
- Depth profiling of W, O and H in tungsten trioxide thin films using RBS and ERDA techniques, O. Bohnke, G. Frand, M. Fromm, J. Weber and O. Greim 93 (1996) 45

- CO₂ plasma treatment of tin oxides, H.N. Wanka, G. Bilger and M.B. Schubert 93 (1996) 339
- Excimer laser-induced hydrodynamical effects and surface modifications on silicon carbide, G. Nicolas and M. Autric 96-98 (1996) 296
- Study of the chemical bonding in tungsten carbide and chromium films by application of factor analysis on AES depth profiles, F. Reniers, E. Silberberg, N. Roose and J. Vereecken 99 (1996) 379
- XPS depth profiling by changing incident X-ray energy, H. Shimada, N. Matsubayashi, M. Imamura, T. Sato and A. Nishijima 100/101 (1996) 56
- Depth-dependent non-destructive analysis of thin overlayers using total-reflection-angle X-ray spectroscopy, N. Shibata, S. Okubo and K. Yonemitsu 100/101 (1996) 69
- High depth resolution depth profiling of metal films using SIMS and sample rotation, D.E. Sykes, A. Chew, J. Hems and K. Stribley 100/101 (1996) 77
- Determination of the interface region in multilayer Si/Mo by Auger depth profile and factor analysis, T. Morohashi, T. Hoshi, H. Nikaido and M. Kudo 100/101 (1996) 84
- Analysis of Auger sputter depth profiles with a resolution function, T. Kitada, T. Harada and S. Tanuma 100/101 (1996) 89
- Oxide thin films formed during rotational AES sputter depth profiling of Ni/Cr multilayers using oxygen ions, A. Zalar, E.W. Seibt and P. Panjan 100/101 (1996) 92
- Novel method of strain-relaxed Si_{1-x}Ge_x growth on Si(100) by MBE, H. Iwano, K. Yoshikawa, A. Kojima, K. Hayashi, S. Zaima and Y. Yasuda 100/101 (1996) 487
- Comparison of MOCVD and MBE semiconductor superlattices for the evaluation of depth resolution in AES and SIMS, M. Furuya, M. Soga and H. Takano 100/101 (1996) 508
- Deuterium**
- Ge deposition from digermane on the Si(100)-(2 × 1) surface, H.-C. Cho 92 (1996) 128
- Investigation of atomic deuterium (hydrogen) emission from the surface of some transition metal deuterides (hydrides), E. Nowicka, Z. Wolfram, W. Lisowski and R. Dufé 93 (1996) 53
- Diamond**
- Low temperature growth of diamond-like films by cathodic arc plasma deposition, P.-L. Chen, M.-Y. Tsai and J.-S. Kao 92 (1996) 30
- Diamond-like coating prepared by pulsed laser sputtering of graphite in a high-vacuum environment, I.A. Bagonin, A.L. Karuzskii, N.N. Melnik, Yu.A. Mityagin, V.N. Murzin, A.A. Orlikovsky, A.V. Perestoronin, P.P. Sverbil, S.D. Tkachenko, A.V. Tsikunov, N.A. Volchkov and B.G. Zhurkin 92 (1996) 43
- Tribological properties of smooth diamond films, S.M. Pimenov, A.A. Smolin, E.D. Obraztsova, V.I. Konov, U. Bögli, A. Blatter, E.N. Loubnin, M. Maillat, A. Leijala, J. Burger and H.E. Hintermann 92 (1996) 106
- Textured diamond growth by microwave plasma chemical vapor deposition, Y. Liou 92 (1996) 115
- Pulsed-laser deposition of "diamond-like" carbon coating on YBa₂Cu₃O₇ high-T_c superconductor films, A.L. Karuzskii, N.N. Melnik, V.N. Murzin, V.S. Nozdrin, A.V. Perestoronin, N.A. Volchkov and B.G. Zhurkin 92 (1996) 457
- Field emission characteristics of polycrystalline and single-crystalline diamond grown on Si tips, E.I. Givargizov, V.V. Zhirnov, A.N. Stepanova, P.S. Plekhanov and R.I. Kozlov 94/95 (1996) 117
- Diamond coated Si and Mo field emitters: diamond thickness effect, V.V. Zhirnov, W.B. Choi, J.J. Cuomo and J.J. Hren 94/95 (1996) 123
- Liquid carbon observed with reflection measurements on CVD-diamond under UV pulsed-laser irradiation, P. Tosin, W. Lüthy and H.P. Weber 96-98 (1996) 384
- Comparative diagnostics of ArF- and KrF-laser generated carbon plumes used for amorphous diamond-like carbon film deposition, A.A. Puretzky, D.B. Geohegan, G.E. Jellison Jr. and M.M. McGibbon 96-98 (1996) 859
- Carbon Auger peak shape measurements in the characterization of reactions on (001) diamond, P.E. Viljoen, W.D. Roos, H.C. Swart and P.H. Holloway 100/101 (1996) 612
- Doping effects**
- Growth of Zn δ-doped Al_xGa_{1-x}As (x = 0-0.65) by low pressure metal organic vapour phase epitaxy, G. Li and C. Jagadish 92 (1996) 138
- Fluorine doped tin oxide films from spray pyrolysis of stannous fluoride solutions, G.C. Morris and A.E. McElnea 92 (1996) 167
- Investigation of the dosage effect on the activation of arsenic- and boron-implanted low-pressure chemical vapor deposition (LPCVD) amorphous-silicon

- films, F.-S. Wang, M.-J. Tsai, W.-K. Lai and H.-C. Cheng 92 (1996) 372
- Refractive index behavior of boron-doped silica films by plasma-enhanced chemical vapor deposition, R.H. Horng, F. Chen, D.S. Wu and T.Y. Lin 92 (1996) 387
- Dopant activation and strain relaxation in P-implanted metastable pseudomorphic $\text{Ge}_{0.12}\text{Si}_{0.88}$ grown on Si(100), D.Y.C. Lie, N.D. Theodore and J.H. Song 92 (1996) 557
- Light emission from the porous boron δ -doped Si superlattice, T.-C. Chang, W.-K. Yeh, M.-Y. Hsu, C.-Y. Chang, C.-P. Lee, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 571
- Effect of Nb metal ion in TiO_2 oxygen gas sensor, R.K. Sharma, M.C. Bhatnagar and G.L. Sharma 92 (1996) 647
- UPS studies of conducting polymers: dopant effect on conjugated polymer systems sensitive to conductivity, S. Takemura, Y. Kitagawa, H. Kato and Y. Nakajima 100/101 (1996) 107
- Doping dependence of second harmonic generation from native oxide/Si(111) interfaces, H. Hirayama, K. Watanabe and M. Kawada 100/101 (1996) 460
- Aluminum doping of ZnTe grown by MOVPE, S.I. Gheys, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 634
- Electrical properties**
- Ti/Co bilayers in salicide technology: electrical evaluation, A. Lauwers, Q.F. Wang, B. Dewerd and K. Maex 91 (1995) 12
- Improved thermal stability of cobalt silicide formed by ion beam assisted deposition on polysilicon, S. Ravesi, F. La Via, V. Raineri and C. Spinella 91 (1995) 19
- Comparison of CoSi_2 interconnection lines on crystalline and noncrystalline silicon fabricated by writing focused ion beam implantation, J. Teichert, L. Bischoff, E. Hesse, P. Schneider, D. Panknin, T. Gessner, B. Löbner and N. Zichner 91 (1995) 44
- Electrical and optical properties of thin $\text{Fe}_{1-x}\text{Co}_x\text{Si}_2$ films, St. Teichert, R. Kilper, Th. Franke, J. Erben, P. Häussler, W. Henrion, H. Lange and D. Panknin 91 (1995) 56
- Ni silicides formation and properties in RF sputtered $\text{Ni}_{100-x}\text{Si}_x$ thin films, A. Belu-Marian, M.D. Serbanescu, R. Manaila and A. Devenyi 91 (1995) 63
- Formation of CoSi_2 on strained $\text{Si}_{0.8}\text{Ge}_{0.2}$ using a sacrificial Si layer, R.A. Donatton, S. Kolodinski, M. Caymax, Ph.J. Roussel, H. Bender, B. Brijs and K. Maex 91 (1995) 77
- Some physical properties of $\text{ReSi}_{1.75}$ single crystals, U. Gottlieb, M. Affronte, F. Nava, O. Laborde, A. Sulpice and R. Madar 91 (1995) 82
- Electrical and optical properties of thin β - FeSi_2 films on Al_2O_3 substrates, K. Herz and M. Powalla 91 (1995) 87
- Metallurgical and electrical investigation of $\text{Pt}_{50}\text{Ni}_{50}$ /silicon interactions, F. Corni, C. Nobili, G. Ottaviani, R. Tonini, B. Grignaffini Gregorio and G. Queirolo 91 (1995) 107
- Process optimization of copper MOCVD using modeling experimental design, M.-J. Mouche, J.-L. Mermet, F. Pires, E. Richard, J. Torres, J. Palleau and F. Braud 91 (1995) 129
- Influence of the anti reflective coating on the electromigration resistance of $0.5\text{ }\mu\text{m}$ technology metal-2 line structures, R. Stevens, A. Witvrouw, Ph.J. Roussel, K. Maex, H. Meynen and A. Cuthbertson 91 (1995) 208
- Electromigration resistance of TiWN/Cu/TiWN interconnections, T. Fukada, T. Mori, Y. Toyoda, M. Hasegawa, K. Namba and K. Ogata 91 (1995) 227
- Model calculations on a bipolar transistor emitter interconnection with different contact shapes, K. Weide, J. Ullmann and W. Hasse 91 (1995) 234
- Sputtering of tantalum-based diffusion barriers in Si/Cu metallization: effects of gas pressure and composition, M. Stavrev, C. Wenzel, A. Möller and K. Drescher 91 (1995) 257
- Electrical characterization of conductive and non-conductive barrier layers for Cu-metallization, C. Ahrens, D. Depta, F. Schithelm and S. Wilhelm 91 (1995) 285
- Electrical characterization of reactively sputtered TiN diffusion barrier layers for copper metallization, C. Kaufmann, J. Baumann, T. Gessner, T. Raschke, M. Rennau and N. Zichner 91 (1995) 291
- Barrier behaviour of plasma deposited silicon oxide and nitride against Cu diffusion, M. Vogt and K. Drescher 91 (1995) 303
- Evaluation of selective tungsten plugs on TiN, W and AlSi by analytical and electrical measurements, S.E. Schulz, B. Hintze, W. Grünwald, O. Fiedler and T. Gessner 91 (1995) 326
- Selective deposition of tungsten on ITM- CoSi_2 , J.D. Köhler, D. Depta and R. Ferretti 91 (1995) 339

- W/Si Schottky diodes: effect of sputtering deposition conditions on the barrier height, M. Mamor, E. Dufour-Gergam, L. Finkman, G. Tremblay, F. Meyer and K. Bouziane 91 (1995) 342
- Ohmic contacts to p-type 6H-silicon carbide, O. Nennewitz, L. Spiess and V. Breternitz 91 (1995) 347
- The ohmic contact to the silicon Schottky barrier using vanadium silicide and gold or silver metallization, A.D. Remenyuk and N.M. Schmidt 91 (1995) 352
- Electrical characteristics of aluminum contacts to porous silicon, S.P. Zimin, V.S. Kuznetsov and A.V. Prokashnikov 91 (1995) 355
- On the formation of silicides on poly runners with topography by a two-step silicidation process, F. Jonckx, R. Verbeeck, B. Dewerdit and K. Maex 91 (1995) 378
- Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on MgO(001), H. Qiu, T. Ohbuchi, H. Nakai and M. Hashimoto 92 (1996) 47
- Stability of BaTiO₃ thin films on Si, L.H. Chang and W.A. Anderson 92 (1996) 52
- Study of Ag thin films deposited on porous silicon, T.F. Young, J.F. Liu, C.C. Wu, G.H. Fu and C.S. Chen 92 (1996) 57
- The electrical and optical characteristics of GaAs on Si by modified flow rate modulation epitaxy, M.K. Lee, C.C. Hu, and C.Z. Hwang 92 (1996) 159
- The properties of SiO₂ films using direct photo-chemical vapor deposition on strained SiGe layers, C.T. Lin, S.J. Chang, D.K. Nayak and Y. Shiraki 92 (1996) 193
- Diffusion length measurements on electrodeposited CuInSe₂ cells, S.N. Qiu, C.X. Qiu and I. Shih 92 (1996) 306
- Investigation of the dosage effect on the activation of arsenic- and boron-implanted low-pressure chemical vapor deposition (LPCVD) amorphous-silicon films, F.-S. Wang, M.-J. Tsai, W.-K. Lai and H.-C. Cheng 92 (1996) 372
- Structural and electrical properties of excimer laser deposited PLZT thin films, H.-F. Cheng 92 (1996) 378
- An electrochemical impedance spectroscopy study of thin polymeric films, R. Borkowska, M. Siekierski and J. Przyhuski 92 (1996) 447
- Electrical properties of laser deposited YBa₂Cu₃O_{7- δ} films on silicon wafers, F.Y. Chuang, C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin 92 (1996) 452
- Noise characteristics of an infrared hot-electron transistor, C.H. Kuan 92 (1996) 532
- Effect of Nb metal ion in TiO₂ oxygen gas sensor, R.K. Sharma, M.C. Bhatnagar and G.L. Sharma 92 (1996) 647
- A new method for the detection of hydrogen spillover, M. Holmberg and I. Lundström 93 (1996) 67
- Plasma anodic oxidation of semiinsulating GaAs, E. Pinčík, K. Gmucová, J. Bartoš, M. Kučera, M. Jergel and R. Brunner 93 (1996) 119
- Work function variations and oxygen conduction in a Pt(ZrO₂(Y₂O₃)/Pt solid electrolyte cell, N.G. Torkelsen and S. Raaen 93 (1996) 199
- Improvement of the crystallinity in PbTiO₃ films grown on indium tin oxide-coated glass by metalorganic chemical vapor deposition using the continuous cooling process, Y.S. Yoon, S.S. Yom, T.W. Kim, D.U. Lee and C.O. Kim 93 (1996) 285
- Electrical and optical characteristics of organic thin films fabricated by laser ablation, T. Fujii, H. Shima, N. Matsumoto and F. Kannari 96-98 (1996) 625
- Giant laser-induced voltages at room temperature in Pr doped Y-Ba-Cu-O thin films, H.-U. Habermeier, N. Jisrawi and G. Jäger-Waldau 96-98 (1996) 689
- Electrical characterization of semiconducting La doped SrTiO₃ thin films prepared by pulsed laser deposition, K.-O. Grosse-Holz, J.F.M. Cillessen and R. Waser 96-98 (1996) 784
- Pulsed laser deposition of nasicon thin films, R. Izquierdo, F. Hanus, Th. Lang, D. Ivanov, M. Meunier, L. Laude, J.F. Currie and A. Yelon 96-98 (1996) 855
- Interface chemistry and electric characterization of nickel metallisation on 6H-SiC, Ts. Marinova, V. Krastev, C. Hallin, R. Yakimova and E. Jazén 99 (1996) 119
- 'Stable to unstable' transition in the (Cs, O) activation layer on GaAs (100) surfaces with negative electron affinity in extremely high vacuum, S. Pastuszka, A.S. Terekhov and A. Wolf 99 (1996) 361
- The correlation between surface charge distribution and flashover properties of alumina surface in vacuum, Tumiran, S. Kobayashi, M. Maeyama, H. Imada and Y. Saito 100/101 (1996) 238
- Water vapor effects on the TeO₂/Te thin film conductance, S. Suchara, T. Hatano and A. Nukui 100/101 (1996) 252
- Analysis of the sensing mechanism of tin

- dioxide thin film gas sensors using the change of work function in flammable gas atmosphere, B. Yea, R. Konishi, T. Osaki, S. Abe, H. Tanioka and K. Sugahara 100/101 (1996) 365
- Electrical properties of metal/Si_{1-x}Ge_x/Si(100) heterojunctions, H. Shinoda, M. Kosaka, J. Kojima, H. Ikeda, S. Zaima and Y. Yasuda 100/101 (1996) 526
- Surface barriers formation mechanism of the chemically etched CdTe(111) polar surfaces and gold interfaces, T. Takeuchi, T. Kore-eda and A. Ebina 100/101 (1996) 596
- A theoretical analysis of temperature dependence on hydrogenated amorphous silicon thin-film transistors with the consideration of resistance of the a-Si:H film layer as a function of temperature, B.-Y. Chen, J.-R. Chen, F.-L. Jenq and C.-S. Hong 100/101 (1996) 601
- ZnSe crystal growth by radical assisted MOCVD, Y. Hatanaka, T. Aoki, M. Morita and Y. Nakanishi 100/101 (1996) 621
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- Beam induced phase transformations and self annealing in as-implanted iron silicides, G. Creclius, K. Radermacher, Ch. Dieker and S. Mesters 91 (1995) 50
- Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
- Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on MgO(001), H. Qiu, T. Ohbuchi, H. Nakai and M. Hashimoto 92 (1996) 47
- Structural characterization of epitaxial ferromagnetic MnSb layers grown by hot-wall epitaxy, H. Tatsuoka, H. Kuwabara, M. Oshita, Y. Nakanishi, T. Nakamura and H. Fujiyasu 92 (1996) 382
- Novel epitaxial growth and magnetotransport characterization of single crystal Co(11 $\bar{2}$ 0)/Cr(100) superlattices on Mo buffer layers, J.C.A. Huang, Y.D. Yao, Y. Liou, S.F. Lee, W.T. Yang, C.P. Chang, S.Y. Liao and C.H. Lee 92 (1996) 480
- Structural evolution and atomic structure of ultrahigh vacuum deposited Au thin films on silicon at low temperatures, C.R. Chen and L.J. Chen 92 (1996) 507
- Growth and reactivity of evaporated platinum films on Cu(111): a study by AES, RHEED and adsorption of carbon monoxide and xenon, J. Fusy, J. Menau-court, M. Alnot, C. Huguet and J.J. Ehrhardt 93 (1996) 211
- Oxidation of ultrathin iron layers grown on Cu(111), C. Ruby and J. Fusy 99 (1996) 393
- Thickness dependent electron stimulated desorption of thin epitaxial films of alkali halides, M. Szymonski, J. Kolodziej, P. Czuba, P. Piatkowski, P. Korecki, Z. Postawa and N. Itoh 100/101 (1996) 102
- A new type of RHEED apparatus equipped with an energy filter, Y. Horio, Y. Hashimoto and A. Ichimiya 100/101 (1996) 292
- Ultrahigh vacuum system for atomic-scale planarization of 6 inch Si(001) substrate, K. Idota, M. Niwa and I. Sumita 100/101 (1996) 311
- Molecular beam epitaxy of GaAs/Al_xGa_{1-x}As/In_yGa_{1-y}As heterostructures for opto-electronic devices: control of growth parameters, K. Köhler 100/101 (1996) 383
- Nitridation of GaAs surfaces using nitrogen molecules cracked by a hot tungsten filament, T. Makimoto and N. Kobayashi 100/101 (1996) 403
- In situ observation of nitridation of GaAs (001) surfaces by infrared reflectance spectroscopy, K. Uwai, Y. Yamauchi and N. Kobayashi 100/101 (1996) 412
- Decomposition of triethylindium (TEI) on GaP(001) surface studied by TPD, XPS and RHEED, J. Murata, T. Takeuchi, Y. Suzuki, N. Sanada and Y. Fukuda 100/101 (1996) 417
- Epitaxial growth of GaAs on HF-treated Si substrates, Y. Uchida, J. Minemura, Y. Yazawa and T. Warabisako 100/101 (1996) 478
- Si epitaxial growth at low temperatures using remote plasma process, A. Yoshida, K. Utsumi and A. Ganjoo 100/101 (1996) 491
- Routine measurement of the absolute As₄ flux in a molecular beam epitaxy system with conventional RHEED equipment, Ch. Heyn and M. Hansdorff 100/101 (1996) 494
- ### Electron emission
- Electron emission from carbon fibre tips, M.S. Mousa 94/95 (1996) 129
- Quantitative relationship between the work function and transfer ratio of a potassium-adsorbed MIM cathode, T. Kusunoki and M. Suzuki 100/101 (1996) 207
- Monte Carlo simulation of ion-induced kinetic electron emission from a metal surface, J. Kawata and K. Ohya 100/101 (1996) 338

Electron energy loss spectroscopy

- Beam induced phase transformations and self annealing in as-implanted iron silicides, G. Crecelius, K. Radermacher, Ch. Dieker and S. Mesters 91 (1995) 50
- The oxidation of the NiAl(111) surface, R. Franchy, J. Masuch and P. Gassmann 93 (1996) 317
- CuCl growth on the reconstructed surface of (0001) haematite, Q. Guo, L. Gui and N. Wu 99 (1996) 229
- Thickness dependent electron stimulated desorption of thin epitaxial films of alkali halides, M. Szymonski, J. Kolodziej, P. Czuba, P. Piatkowski, P. Korecki, Z. Postawa and N. Itoh 100/101 (1996) 102
- Initial oxidation of Si(311) surfaces studied by high-resolution electron energy loss spectroscopy, H. Ikeda, T. Yamada, K. Hotta, S. Zaima and Y. Yasuda 100/101 (1996) 431
- CHF₃ adsorption and decomposition on clean and oxygen covered Al(111), H. Kawada, S. Reiff and J.H. Block 100/101 (1996) 587

Electron microscopy

- Ti/Co bilayers in salicide technology: electrical evaluation, A. Lauwers, Q.F. Wang, B. Dewerdet and K. Maex 91 (1995) 12
- Improved thermal stability of cobalt silicide formed by ion beam assisted deposition on polysilicon, S. Ravesi, F. La Via, V. Raineri and C. Spinella 91 (1995) 19
- Comparison of CoSi₂ interconnection lines on crystalline and noncrystalline silicon fabricated by writing focused ion beam implantation, J. Teichert, L. Bischoff, E. Hesse, P. Schneider, D. Panknin, T. Gessner, B. Löbner and N. Zichner 91 (1995) 44
- Beam induced phase transformations and self annealing in as-implanted iron silicides, G. Crecelius, K. Radermacher, Ch. Dieker and S. Mesters 91 (1995) 50
- Formation of CoSi₂ on strained Si_{0.8}Ge_{0.2} using a sacrificial Si layer, R.A. Donaton, S. Kolodinski, M. Caymax, Ph.J. Roussel, H. Bender, B. Brijs and K. Maex 91 (1995) 77
- Metallurgical and electrical investigation of Pt₅Ni₉₅/silicon interactions, F. Corni, C. Nobili, G. Ottaviani, R. Tonini, B. Grignaffini Gregorio and G. Queirolo 91 (1995) 107
- Electroless copper metallisation of titanium nitride, J.C. Patterson, C. Ni Dheasuna, J. Barrett, T.R. Spalding, M. O'Reilly, X. Jiang and G.M. Crean 91 (1995) 124
- Process optimization of copper MOCVD using modeling experimental design,

- M.-J. Mouche, J.-L. Mermet, F. Pires, E. Richard, J. Torres, J. Palleau and F. Braud 91 (1995) 129
- Structure and electrical properties of thin copper films deposited by MOCVD, J. Röber, C. Kaufmann and T. Gessner 91 (1995) 134
- Stress voiding and electromigration phenomena in aluminum alloys, S. Kordic, R.A. Augur, A.G. Dirks and R.A.M. Wolters 91 (1995) 197
- Influence of the anti reflective coating on the electromigration resistance of 0.5 µm technology metal-2 line structures, R. Stevens, A. Witvrouw, Ph.J. Roussel, K. Maex, H. Meynen and A. Cuthbertson 91 (1995) 208
- Electromigration resistance of TiWN/Cu/TiWN interconnections, T. Fukada, T. Mori, Y. Toyoda, M. Hasegawa, K. Namba and K. Ogata 91 (1995) 227
- The effect of ion implantation on the properties of Al films, M. Zaborowski, A. Barcz, G. Gawlik and I.W. Rangelow 91 (1995) 239
- Hillock recognition by digital image processing, M. Zaborowski, M. Adamiec and A. Barcz 91 (1995) 246
- Sputtering of tantalum-based diffusion barriers in Si/Cu metallization: effects of gas pressure and composition, M. Stavrev, C. Wenzel, A. Möller and K. Drescher 91 (1995) 257
- Co-sputtered TiB₂ as a diffusion barrier for advanced microelectronics with Cu metallization, G. Sade and J. Pelleg 91 (1995) 263
- LPCVD Re₂Si₂N₂ diffusion barriers in Si/SiO₂/Cu metallizations, A.-M. Dutron, E. Blanquet, C. Bernard, A. Bachli and R. Madar 91 (1995) 277
- Electrical characterization of reactively sputtered TiN diffusion barrier layers for copper metallization, C. Kaufmann, J. Baumann, T. Gessner, T. Raschke, M. Rennau and N. Zichner 91 (1995) 291
- Ti nitride phases in thin films deposited by DC magnetron sputtering, R. Manaila, D. Biro, P.B. Barna, M. Adamik, F. Zavaliche, S. Craciun and A. Devenyi 91 (1995) 295
- Evaluation of selective tungsten plugs on TiN, W and AISi by analytical and electrical measurements, S.E. Schulz, B. Hintze, W. Grünewald, O. Fiedler and T. Gessner 91 (1995) 326
- Growth rate modeling for selective tungsten LPCVD, H. Wolf, R. Streiter, S.E. Schulz and T. Gessner 91 (1995) 332
- Advanced metallization technology for 256M DRAM, P. Kücher, H. Aochi, J. Gambino, T. Licata, T. Matsuda, S. Nguyen, M. Okazaki, H. Palm and M. Ronay 91 (1995) 359

- Inter-metal dielectric planarization process for 0.35 μm multilevel interconnection devices, M. Bacchetta, C. Zaccherini and L. Zanotti 91 (1995) 367
- On the formation of silicides on poly runners with topography by a two-step silicidation process, F. Jonckx, R. Verbeeck, B. Deweerdt and K. Maex 91 (1995) 378
- LEEM studies of the early stages of epitaxial growth, E. Bauer 92 (1996) 20
- Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
- Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on MgO(001), H. Qiu, T. Ohbuchi, H. Nakai and M. Hashimoto 92 (1996) 47
- Study of Ag thin films deposited on porous silicon, T.F. Young, J.F. Liu, C.C. Wu, G.H. Fu and C.S. Chen 92 (1996) 57
- A method to tune the island size and improve the uniformity for the in situ formation of InGaAs quantum dots on GaAs, S.-Z. Chang, T.-C. Chang and S.-C. Lee 92 (1996) 70
- Effects of substrate cleaning and film thickness on the epitaxial growth of ultrahigh vacuum deposited Cu thin films on (001)Si, C.S. Liu and L.J. Chen 92 (1996) 84
- Very low temperature polycrystalline silicon films with very large grains deposited for thin film transistor applications, K.C. Wang, T.R. Yew and H.L. Hwang 92 (1996) 99
- Textured diamond growth by microwave plasma chemical vapor deposition, Y. Liou 92 (1996) 115
- Disordered Si/SiGe superlattices grown by ultrahigh vacuum chemical vapor deposition, T.-C. Chang, W.-K. Yeh, C.-Y. Chang, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 119
- Electrosynthesis of yttrium chalcogenides from a non-aqueous bath, U.K. Mohite and C.D. Lokhande 92 (1996) 151
- Characteristics of spray pyrolytic ZnO thin films, C.H. Lee and L.Y. Lin 92 (1996) 163
- Interface phase transition as observed in ultra thin FeSi₂ epilayers, J. Derrien, I. Berbezier, A. Ronda and J.Y. Natoli 92 (1996) 311
- Interface effects in melting of Pb clusters on the Cu(111) surface, E.Z. Luo, Q. Cai, W.F. Chung and M.S. Altman 92 (1996) 331
- The determination of the average compositions of amorphous interlayers in the V/Si system using a buried ultrathin oxide layer and a capping Mo layer to define the reference planes for interdiffusion, J.H. Lin and L.J. Chen 92 (1996) 340
- Investigation of the dosage effect on the activation of arsenic- and boron-implanted low-pressure chemical vapor deposition (LPCVD) amorphous-silicon films, F.-S. Wang, M.-J. Tsai, W.-K. Lai and H.-C. Cheng 92 (1996) 372
- Structural characterization of epitaxial ferromagnetic MnSb layers grown by hot-wall epitaxy, H. Tatsuoka, H. Kuwabara, M. Oshita, Y. Nakanishi, T. Nakamura and H. Fujiyasu 92 (1996) 382
- Interface of CuIn_{1-x}Ga_xSe₂/GaAs heterostructure, B.-H. Tseng, S.-B. Lin, A.G.-L. Gu and H.-Z. Hsu 92 (1996) 412
- Effect of substrate-film interface on magnetic properties of Mn₄N films, K.-M. Ching, W.-D. Chang and T.-S. Chin 92 (1996) 471
- Structural evolution and atomic structure of ultrahigh vacuum deposited Au thin films on silicon at low temperatures, C.R. Chen and L.J. Chen 92 (1996) 507
- Diffusion phenomena in MBE grown Si/SiGe single quantum wells studied by PL and TEM measurements, H.P. Zeindl, S. Nilsson and E. Bugiel 92 (1996) 552
- Dopant activation and strain relaxation in P-implanted metastable pseudomorphic Ge_{0.12}Si_{0.88} grown on Si(100), D.Y.C. Lie, N.D. Theodore and J.H. Song 92 (1996) 557
- Light emission from the porous boron δ -doped Si superlattice, T.-C. Chang, W.-K. Yeh, M.-Y. Hsu, C.-Y. Chang, C.-P. Lee, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 571
- Tribochemical characterization of the lubrication film at the Si₃N₄/Si₃N₄ interface sliding in aqueous solutions, F. Honda and T. Saito 92 (1996) 651
- Cross-sectional TEM investigations of plasmopolymer-metal composite films, W. Grünwald, A. Heilmann and C. Reinhardt 93 (1996) 157
- In situ HVTEM observation of the tip shape of tin liquid metal ion sources, W. Driesel and Ch. Dietzsch 93 (1996) 179
- Formation of polycrystalline BaTi₄O₉ compounds in barium implanted TiO₂, S.M.M. Ramos, B. Canut, M. Ambri, N. Bonardi, R. Brenier, M. Pitaval, P. Thevenard and M. Brunel 93 (1996) 191
- Diamond coated Si and Mo field emitters: diamond thickness effect, V.V. Zhimov, W.B. Choi, J.J. Cuomo and J.J. Hren 94/95 (1996) 123
- Precipitation processes during the early

- stages of ageing in Al-Cu-Mg alloys, S.P. Ringer, K. Hono, I.J. Polmear and T. Sakurai 94/95 (1996) 253
- AP-FIM analysis of ordered Cu_3Au -(4 at% Pt) alloy, V.A. Ivchenko, A. Kvist, H.-O. Andr  n, N.N. Syutkin and K. Stiller 94/95 (1996) 267
- Nanocrystallization of a Co-Nb-B-C metallic glass, T.A. Lusby and A.J. Melmed 94/95 (1996) 300
- Investigation of precipitation in a new maraging stainless steel, K. Stiller, F. Danoix and A. Bostel 94/95 (1996) 326
- Grain boundary precipitation and segregation in Ni-16Cr-9Fe model materials, M. Thuvander, K. Stiller, D. Blavette and A. Menand 94/95 (1996) 343
- Atom probe analysis of carbonitride grains in (Ti, W, Ta, Mo)C, N(Co/Ni) cermets with different carbon content, J. Zackrisson, M. Thuvander, P. Lindahl and H.-O. Andr  n 94/95 (1996) 351
- The chemistry and structure of {222} CdO/Ag heterophase interfaces on an atomic scale, D.K. Chan, D.N. Seidman and K.L. Merkle 94/95 (1996) 409
- Soft laser sputtering of the GaAlAs (100) surface, L. Vivet, B. Dubreuil, T. Gibert-Legrand and M.F. Barthe 96-98 (1996) 238
- Formation of large carbon cluster ions at graphite (HOPG) surfaces by laser irradiation, H. Togashi, K. Saito, Y. Koga, H. Yamawaki, K. Aoki, M. Mukaida and T. Kameyama 96-98 (1996) 267
- Particles synthesis in erosive laser plasma in a high pressure atmosphere, A.G. Gnedovets, E.B. Kul'batskii, I. Smurov and G. Flamant 96-98 (1996) 272
- Laser induced periodic surface structures on iron, A. Dauscher, V. Feregotto, P. Cordier and A. Thom  y 96-98 (1996) 410
- Laser cleaning in art restoration, I. Gobernado-Mitre, J. Medina, B. Calvo, A.C. Prieto, L.A. Leal, B. P  rez, F. Marcos and A.M. de Frutos 96-98 (1996) 474
- Modelling and diagnostic of pulsed laser cleaning of oxidized metallic surfaces, R. Oltra, O. Yava  , F. Cruz, J.P. Boquillon and C. Sartori 96-98 (1996) 484
- Fast etching of sapphire by a visible range quasi-cw laser radiation, S.I. Dolgaev, A.A. Lyalin, A.V. Simakin and G.A. Shafeev 96-98 (1996) 491
- Selection of kinetic energy of laser ablated particles, K. Kuba and T. Sugihara 96-98 (1996) 659
- Classification of particulates on pulsed-laser deposited Y-Ba-Cu-O films, S. Proyer, E. Stangl, M. Borz and D. B  uerle 96-98 (1996) 668
- Stoichiometric transfer of complex oxides by pulsed laser deposition, B. Dam, J.H. Rector, J. Johansson, S. Kars and R. Griessen 96-98 (1996) 679
- Improved properties of Pulsed Laser Deposited YBaCuO on NdGaO₃ using CeO₂ template layers, D.H.A. Blank, A.J.H.M. Rijnders, F.J.G. Roesthuis, G. den Ouden and H. Rogalla 96-98 (1996) 685
- Laser deposition of YBa₂Cu₃O₇ films on MgO(100) at 100 mm target-substrate distance and oxygen pressures below 0.1 mbar, F. Goerke, A. Thorns and U. Merkt 96-98 (1996) 708
- Anisotropic resistivity in pulsed-laser deposited Bi₂Sr₂CaCu₂O_{8+x} films, S.T. Li, A. Ritzer, S. Proyer, E. Stangl, D. B  uerle and N. Reschauer 96-98 (1996) 713
- Preparation of SiO₂N_y films by reactive KrF laser ablation, K. Maruyama, Y. Aoki, M. Matsumoto, Y. Hiroshima and H. Ohia 96-98 (1996) 764
- Excimer laser ablating preparation of Ba₂NaNb₃O₁₅ thin films on KTiOPO₄ substrate and its guide wave property, J.M. Liu, Z.G. Liu, S.N. Zhu, Y.Y. Zhu and N.B. Ming 96-98 (1996) 819
- Characterization of ZnO thin films deposited by laser ablation in reactive atmosphere, P. Verardi, M. Dinescu and A. Andrei 96-98 (1996) 827
- Deposition of HgCdTe epitaxial layers on anisotropically etched silicon surfaces by laser evaporation, T.Ya. Gorbach, M. Ku  ma, E. Shergii, P.S. Smertenko, S.V. Svechnikov and G. W  sz 96-98 (1996) 881
- Application and properties of sub-monomolecular layers of silicon dioxide deposited under mild conditions, D.M. Knotter 99 (1996) 99
- High resolution electron microscopy characterization of small Pt-Pd/SiO₂ particles in oxide-reducing cycles, A. V  zquez and F. Pedraza 99 (1996) 213
- Properties of radio frequency magnetron sputtered silicon dioxide films, W.-F. Wu and B.-S. Chiou 99 (1996) 237
- Diffusion barrier property of TaN between Si and Cu, T. Oku, E. Kawakami, M. Uekubo, K. Takahiro, S. Yamaguchi and M. Murakami 99 (1996) 265
- Photon and ion beam assisted deposition of titanium nitride, H. Wengenmair, J.W. Gerlach, U. Preckwinkel, B. Stritzker and B. Rauschenbach 99 (1996) 313
- Study of the composition and morphology of initial stages of corrosion products formed on Zn plates exposed to the atmosphere of southeast Mexico, P.

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- Determination of the interface region in multilayer Si/Mo by Auger depth profile and factor analysis, T. Morohashi, T. Hoshi, H. Nikaïdo and M. Kudo 100/101 (1996) 84
- Effect of different surface treatments on the precipitation of boron nitride for stainless steel SUS304, Y. Suzuki, T. Homma, M. Minato and Y. Itoh 100/101 (1996) 165
- Investigation of characteristics of carbon materials with various structures modified by plasmas using plasma diagnostics and material-surface analysis, M. Katoh, Y. Izumi, H. Kimura, T. Ohte, A. Kojima and S. Ohtani 100/101 (1996) 226
- Hydrogen desorption characteristics of composite Co-TiN nanoparticles, Y. Sakka and S. Ohno 100/101 (1996) 232
- New-type focused fast atom beam (F-FAB) source and evaluation of emitted beam density distribution, M. Hatakeyama, I. Nagahama, K. Ichiki, M. Nakao and Y. Hatamura 100/101 (1996) 277
- Development of high spatial resolution Auger microscope as applied to semiconductor analysis, T. Yamada, M. Kudo, Y. Ando, T. Sekine and Y. Sakai 100/101 (1996) 287
- Ultrahigh vacuum system for atomic-scale planarization of 6 inch Si(001) substrate, K. Idota, M. Niwa and I. Sumita 100/101 (1996) 311
- Atomically flat, ultra thin-SiO₂/Si(001) interface formation by UHV heating, M. Niwa, K. Okada and R. Sinclair 100/101 (1996) 425
- Comparison of MOCVD and MBE semiconductor superlattices for the evaluation of depth resolution in AES and SIMS, M. Furuya, M. Soga and H. Takano 100/101 (1996) 508
- Microstructure studies of PdGe/Ge ohmic contacts to n-type GaAs formed by rapid thermal annealing, W.D. Chen, X.L. Xie, Y.D. Cui, C.H. Chen and C.C. Hsu 100/101 (1996) 530
- Low pressure MOCVD of TiN thin films, S.W. Kim, H. Jimba, A. Sekiguchi, O. Okada and N. Hosokawa 100/101 (1996) 546
- A nondestructive analysis technique for residual thin films in deep-submicron contact holes, K. Ninomiya, T. Kure, Y. Sudo, K. Kuroda and H. Todokoro 100/101 (1996) 551
- Selective epitaxial Si based layers and TiSi₂ deposition by integrated chemical vapor deposition, J.L. Regolini, J. Margail, S. Bodnar, D. Maury and C. Morin 100/101 (1996) 566
- Correlation between cathodoluminescence and structural defects in ZnS/GaAs(100) and ZnSe/GaAs(100) studied by transmission electron microscopy, T. Mitsui, N. Yamamoto, J. Yoshino, T. Tadokoro, S. Ohta, K. Yanashima and K. Inoue 100/101 (1996) 625
- ### Electron spin resonance
- Electron paramagnetic resonance measurements on porous silicon, T. Nakamura, K. Sasaki, K. Hayashi, H. Mimura and J. Kobayashi 92 (1996) 291
- ### Electron stimulated desorption
- Surface and subsurface 1 keV electron stimulated reduction of sapphire studied by electron spectroscopy, A. Hoffman and P.J.K. Paterson 93 (1996) 301
- AES study of electron beam induced damage on TiO₂ surfaces, A.J.M. Mens and O.L.J. Gijzeman 99 (1996) 133
- Thickness dependent electron stimulated desorption of thin epitaxial films of alkali halides, M. Szymonski, J. Kołodziej, P. Czuba, P. Piatkowski, P. Korecki, Z. Postawa and N. Itoh 100/101 (1996) 102
- The effect of EB irradiation with and without hot-jet Cl₂ on an ultra-thin GaN layer for selective etching, S. Yoshida, M. Sasaki and T. Ishikawa 100/101 (1996) 184
- ### Ellipsometry
- Investigation of the oxidation behaviour of thin film and bulk copper, M. O'Reilly, X. Jiang, J.T. Beechinor, S. Lynch, C. Ni Dheasuna, J.C. Patterson and G.M. Crean 91 (1995) 152
- Ellipsometric study of thermal and laser annealed amorphous and microcrystalline silicon films, A.H. Jayatissa, M. Suzuki, Y. Nakanishi and Y. Hatanaka 92 (1996) 300
- Structural and optical properties of Pd_{1-x}In_x thin films, W.T. Wu, P.E. Schmid and F. Lévy 92 (1996) 391
- Ellipsometric studies of the oxidation kinetics of Cu particles supported on oxidised Si(100), R. van Wijk, O.L.J. Gijzeman and J.W. Geus 93 (1996) 237
- CO₂ plasma treatment of tin oxides, H.N. Wanka, G. Bilger and M.B. Schubert 93 (1996) 339
- Single shot excimer laser annealing of amorphous silicon for AMLCD, P. Boher, J.L. Stehle, M. Stehle and B. Godard 96-98 (1996) 376
- Cleaning of copper traces on circuit boards with excimer laser radiation, D.A. Wesner, M. Martin, F. Lupp and E.W. Kreutz 96-98 (1996) 479

- Scale-up of pulsed laser deposition (PLD) for 4"-wafer coating, M. Panzner, R. Dietsch, Th. Holz, H. Mai and S. Völlmar 96-98 (1996) 643
- Comparative diagnostics of ArF- and KrF-laser generated carbon plumes used for amorphous diamond-like carbon film deposition, A.A. Puretzky, D.B. Geohegan, G.E. Jellison Jr. and M.M. McGibbon 96-98 (1996) 859
- The oxidation of Cu particles supported on oxidised Si(100) as studied by nuclear reaction analysis and ellipsometry, R. van Wijk, P.C. Görts, C.H.M. Marée, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 99 (1996) 127
- Real-time analysis of III-V-semiconductor epitaxial growth, W. Richter and J.-T. Zettler 100/101 (1996) 465
- Characterization of MOCVD-grown GaAs on Si by spectroscopic ellipsometry, G. Yu, T. Soga, T. Jimbo and M. Umeno 100/101 (1996) 617
- Emission*
- Photoellipsometric studies on CdTe thin films, P.D. Paulson and V. Dutta 92 (1996) 295
- Epitaxy*
- Epitaxy of CoSi₂/Si(100): from Co/Ti/Si(100) to reactive deposition epitaxy, A. Vantomme, S. Degroote, J. Dekoster and G. Langouche 91 (1995) 24
- Cubic metastable FeSi_{1-x} epitaxially grown on Si and MgO substrates, S. Degroote, A. Vantomme, J. Dekoster and G. Langouche 91 (1995) 72
- Ohmic contacts to p-type 6H-silicon carbide, O. Nennewitz, L. Spiess and V. Breternitz 91 (1995) 347
- Recent advances in island and multilayer growth of metals on metals far from equilibrium, G. Vidali and H. Zeng 92 (1996) 11
- LEEM studies of the early stages of epitaxial growth, E. Bauer 92 (1996) 20
- Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
- Characterization of low temperature GaAs grown by molecular beam epitaxy, W.C. Lee, T.M. Hsu, J.-I. Chyi, G.S. Lee, W.-H. Li and K.C. Lee 92 (1996) 66
- Epitaxial growth of ZnSe_xTe_{1-x} by the VPE method and its photoluminescence, K. Mochizuki, H. Oguri, T. Kyotani and M. Isshiki 92 (1996) 79
- Effects of substrate cleaning and film thickness on the epitaxial growth of ultrahigh vacuum deposited Cu thin films on (001)Si, C.S. Liu and L.J. Chen 92 (1996) 84
- Surface reaction mechanism in MOCVD, J. Nishizawa, H. Sakuraba and T. Kurabayashi 92 (1996) 89
- Growth of Zn δ-doped Al_xGa_{1-x}As (x = 0-0.65) by low pressure metal organic vapour phase epitaxy, G. Li and C. Jagadish 92 (1996) 138
- The electrical and optical characteristics of GaAs on Si by modified flow rate modulation epitaxy, M.K. Lee, C.C. Hu, and C.Z. Hwang 92 (1996) 159
- Surfactant modified growth of CuInSe₂ thin films, B.-H. Tseng, G.-W. Chang and G.-L. Gu 92 (1996) 227
- Interface phase transition as observed in ultra thin FeSi₂ epilayers, J. Derrien, I. Berbezier, A. Ronda and J.Y. Natoli 92 (1996) 311
- Surface electronic properties of GaSe-covered Si(111) upon UHV thermal desorption of the GaSe epitaxial layer, H. Reqqass, J.-P. Lacharme, C.A. Sébenne, M. Eddrief and V. Le Thanh 92 (1996) 357
- Structural characterization of epitaxial ferromagnetic MnSb layers grown by hot-wall epitaxy, H. Tatsuoka, H. Kuwabara, M. Oshita, Y. Nakanishi, T. Nakamura and H. Fujiyasu 92 (1996) 382
- Study of the internal electric fields across the interfaces in the GaAs/(Al,Ga)As microstructures, C.R. Lu, C.L. Chang, C.H. Liou, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 404
- Band lineup modification by Ge interlayer deposition at II-VI/III-V semiconductor heterojunctions, P. Rodríguez-Hernández, M. González-Díaz, M. Fuentes-Cabrera, A. Mujica and A. Muñoz 92 (1996) 408
- Interface of CuIn_{1-x}Ga_xSe₂/GaAs heterostructure, B.-H. Tseng, S.-B. Lin, G.-L. Gu and H.-Z. Hsu 92 (1996) 412
- Novel epitaxial growth and magnetotransport characterization of single crystal Co(11 $\bar{2}$ 0)/Cr(100) superlattices on Mo buffer layers, J.C.A. Huang, Y.D. Yao, Y. Liou, S.F. Lee, W.T. Yang, C.P. Chang, S.Y. Liao and C.H. Lee 92 (1996) 480
- High quality quantum dots fabricated by molecular beam epitaxy, C.-P. Lee and D.-C. Liu 92 (1996) 519

- Diffusion phenomena in MBE grown Si/SiGe single quantum wells studied by PL and TEM measurements, H.P. Zeindl, S. Nilsson and E. Bugiel 92 (1996) 552
- Improvement of optical properties of gas source MBE grown GaP/AIP short period superlattices, J.H. Kim, H. Asahi, K. Asami, T. Ogura, K. Doi and S. Gonda 92 (1996) 566
- Determination of the subband carrier densities in a strained GaAs/In_{0.15}-Ga_{0.85}As/Al_{0.22}Ga_{0.78}As single quantum well using photoluminescence, T.W. Kim, M. Jung and D.U. Lee 93 (1996) 131
- Photoreflectance analysis of MQWs in intermediate electric field regime, M. Geddo, S. Di Lernia and Chen Chen-Jia 93 (1996) 267
- Formation of artificially-layered high-temperature superconductors using pulsed-laser deposition, D.P. Norton, B.C. Chakoumakos, D.H. Lowndes and J.D. Budai 96-98 (1996) 672
- Reactive laser deposition of high quality YBaCuO and ErBaCuO films, D. Berling, A. Del Vecchio, S. Acquaviva, D. Bolmont, G. Leggieri, B. Loegel, M. Luisa De Giorgi, A. Luches, A. Mehdaoui and L. Tapfer 96-98 (1996) 739
- Epitaxial ferroelectric PZT and BST thin films by pulsed UV laser deposition, C. Champeaux, P. Marchet and A. Catherinot 96-98 (1996) 775
- Structural and optical characteristics of pulsed laser deposited ZnSe epilayers, A. Chergui, J.L. Deiss, J.B. Grun, J.L. Loison, M. Robino and R. Beserman 96-98 (1996) 874
- Deposition of HgCdTe epitaxial layers on anisotropically etched silicon surfaces by laser evaporation, T.Ya. Gorbach, M. Kuźma, E. Sheregii, P.S. Smertenko, S.V. Svechnikov and G. Wisz 96-98 (1996) 881
- Zr-silicide formation during the epitaxial growth of Y-stabilized zirconia films on Si(100) and its avoidance by ion beam assisted deposition at a reduced temperature, T. Koch and P. Ziemann 99 (1996) 51
- AFM and STM studies on In₂O₃ and ITO thin films deposited by atomic layer epitaxy, T. Asikainen, M. Ritala, M. Leskelä, T. Prohaska, G. Friedbacher and M. Grasserbauer 99 (1996) 91
- X-ray photoelectron diffraction investigation of Ge segregation and film morphology during first stage heteroepitaxy of Si on Ge(001), D. Aubel, L. Kubler, J.L. Bischoff, L. Simon and D. Bolmont 99 (1996) 169
- Structural properties of epitaxially grown perfluoro *n*-alkane thin films prepared by vapor deposition, K. Ishida, T. Horiuchi, S. Kai and K. Matsushige 100/101 (1996) 116
- Molecular beam epitaxy of GaAs/Al_xGa_{1-x}As/In_yGa_{1-y}As heterostructures for opto-electronic devices: control of growth parameters, K. Köhler 100/101 (1996) 383
- Surface chemistry of materials deposition at atomic layer level, T. Suntola 100/101 (1996) 391
- CBE-grown high-quality GaAs on Si substrate, H. Uchida, M. Adachi, H. Nishikawa, T. Egawa, T. Jimbo and M. Umeno 100/101 (1996) 399
- Real-time analysis of III-V-semiconductor epitaxial growth, W. Richter and J.-T. Zettler 100/101 (1996) 465
- Epitaxial growth of GaAs on HF-treated Si substrates, Y. Uchida, J. Minemura, Y. Yazawa and T. Warabisako 100/101 (1996) 478
- GaAs-based LED on Si substrate with GaAs islands active region by droplet-epitaxy, Y. Hasegawa, T. Egawa, T. Jimbo and M. Umeno 100/101 (1996) 482
- Novel method of strain-relaxed Si_{1-x}Ge_x growth on Si(100) by MBE, H. Iwano, K. Yoshikawa, A. Kojima, K. Hayashi, S. Zaima and Y. Yasuda 100/101 (1996) 487
- Si epitaxial growth at low temperatures using remote plasma process, A. Yoshida, K. Utsumi and A. Ganjoo 100/101 (1996) 491
- Synthesis of metastable group-IV alloy semiconductors by ion implantation and ion-beam-induced epitaxial crystallization, N. Kobayashi, M. Hasegawa, N. Hayashi, H. Katsumata, Y. Makita, H. Shibata and S. Uekusa 100/101 (1996) 498
- Atomic structure analysis of the interfaces in Si/Ge superlattices, K. Sumitomo, T. Nishioka and T. Ogino 100/101 (1996) 503
- Selective epitaxial Si based layers and TiSi₂ deposition by integrated chemical vapor deposition, J.L. Regolini, J. Margail, S. Bodnar, D. Maury and C. Morin 100/101 (1996) 566
- ZnSe crystal growth by radical assisted MOCVD, Y. Hatanaka, T. Aoki, M. Morita and Y. Nakanishi 100/101 (1996) 621
- Aluminum doping of ZnTe grown by MOVPE, S.I. Gheys, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 634
- Growth of high-quality ZnTe layers by MOVPE, S.I. Gheys, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 647

Etching

- Patterning of copper for multilevel metalization: reactive ion etching and chemi-

- cal-mechanical polishing, C. Steinbrüchel 91 (1995) 139
- Effects of the biasing frequency on RIE of Cu in a Cl_2 -based discharge, A. Bertz, T. Werner, N. Hille and T. Gessner 91 (1995) 147
- Oxygen etching of the Si(100)-(2 × 1) surface, Y. Wei, Y. Hong and I.S.T. Tsong 92 (1996) 491
- The etching of natural alpha-recoil tracks in mica with an argon RF-plasma discharge and their imaging via atomic force microscopy, N.M.D. Brown and Z.H. Liu 93 (1996) 89
- Photon-induced dry etching of Si(100) in the VUV, U. Streller, B. Li, A. Krabbe and N. Schwentner 96-98 (1996) 448
- The role of gas-phase in the laser etching of Cu by CCl_4 , D. Débarre, A. Aliouchouche, J. Boulmer, B. Bourguignon and J.P. Budin 96-98 (1996) 453
- Fast etching of sapphire by a visible range quasi-cw laser radiation, S.I. Dolgaev, A.A. Lyalin, A.V. Simakin and G.A. Shafeev 96-98 (1996) 491
- CCl_4 -assisted CF_4 etching of silicon in a microwave-assisted LDE (laser dry etching)-process, W. Pfleging, D.A. Wesner and E.W. Kreutz 96-98 (1996) 496
- Etching and functionalization of a fluorocarbon polymer by UV laser treatment, C. Girardeaux, Y. Idrissi, J.J. Pireaux and R. Caudano 96-98 (1996) 586
- The effect of EB irradiation with and without hot-jet Cl_2 on an ultra-thin GaN layer for selective etching, S. Yoshida, M. Sasaki and T. Ishikawa 100/101 (1996) 184
- New-type focused fast atom beam (F-FAB) source and evaluation of emitted beam density distribution, M. Hatakeyama, I. Nagahama, K. Ichiki, M. Nakao and Y. Hatamura 100/101 (1996) 277
- Low temperature etching of Si and PR in high density plasmas, M. Puech and Ph. Maquin 100/101 (1996) 579
- Deep trench etching in silicon with fluorine containing plasmas, R.D. Mansano, P. Verdonck and H.S. Maciel 100/101 (1996) 583
- Surface barriers formation mechanism of the chemically etched CdTe(111) polar surfaces and gold interfaces, T. Takeuchi, T. Kore-eda and A. Ebina 100/101 (1996) 596
- Infrared study of chemistry of Si surfaces in etching solution, M. Niwano, T. Miura, R. Tajima and N. Miyamoto 100/101 (1996) 607
- on polysilicon, S. Ravesi, F. La Via, V. Raineri and C. Spinella 91 (1995) 19
- Electrical and optical properties of thin β - FeSi_2 films on Al_2O_3 substrates, K. Herz and M. Powalla 91 (1995) 87
- Some particular features of the condensation process, structure and properties of thin metal films caused by self-ion bombardment, I.V. Gusev, A.A. Mohnjuk, V.I. Chapljuk and V.P. Belevsky 91 (1995) 182
- In situ X-ray reflectivity measurement of thin film growth during vacuum deposition, C.-H. Lee and S.-Y. Tseng 92 (1996) 282
- The influence of residual O_2 gas in vacuum on the structural and luminescent properties of ZnF_2 :Mn thin films, Y. Nakanishi, S. Naito, T. Nakamura, Y. Hatanaka and G. Shimaoka 92 (1996) 400
- Electrochromic behavior of amorphous cobaltphthalocyanine thin films, M. Masui, T. Ogawa and M. Takeuchi 92 (1996) 421
- Gas sensitive properties of copperphthalocyanine thin films, M. Masui, M. Sashihara, T. Wada and M. Takeuchi 92 (1996) 634
- Depth profiling of W, O and H in tungsten trioxide thin films using RBS and ERDA techniques, O. Bohnke, G. Frand, M. Fromm, J. Weber and O. Greim 93 (1996) 45
- Growth and reactivity of evaporated platinum films on Cu(111): a study by AES, RHEED and adsorption of carbon monoxide and xenon, J. Fusy, J. Menau-court, M. Alnot, C. Huguet and J.J. Ehrhardt 93 (1996) 211
- Excimer laser induced thermal evaporation and ablation of silicon carbide, R. Reitano, P. Baeri and N. Marino 96-98 (1996) 302
- Photon and ion beam assisted deposition of titanium nitride, H. Wengenmair, J.W. Gerlach, U. Preckwinkel, B. Stritzker and B. Rauschenbach 99 (1996) 313
- Preparation of thin silver films on mica studied by XRD and AFM, J.-D. Grunwaldt, F. Atamny, U. Göbel and A. Baiker 99 (1996) 353
- Structural properties of epitaxially grown perfluoro *n*-alkane thin films prepared by vapor deposition, K. Ishida, T. Horiuchi, S. Kai and K. Matsushige 100/101 (1996) 116
- Preparation of blue-emitting SrGa_2Se_4 :Ce thin films by multi-source deposition, Y. Nakanishi, F. Shiba, K. Sowa, H. Tatsuoka, H. Kuwabara, T. Nakamura and Y. Hatanaka 100/101 (1996) 639

Evaporation

- Improved thermal stability of cobalt silicide formed by ion beam assisted deposition

Field desorption

- Pulsed field desorption mass spectrometric study of the oxidation of hydrogen-

doped Ni₃Zr, T.R. Hess, D.L. Cocke, G. Abend and J.H. Block

94/95 (1996) 238

Field effect

On the theory of helium field adsorption, R.G. Forbes, H.J. Kreuzer and R.L.C. Wang

94/95 (1996) 60

Some comments on the simultaneous desorption of ³He and ⁴He, R.G. Forbes

94/95 (1996) 73

Noble-gas-like mechanism of localized field ionization of nitrogen as detected by field ion appearance energy spectroscopy, Yu. Suchorski, V.K. Medvedev and J.H. Block

94/95 (1996) 217

Pulsed field desorption mass spectrometric study of the oxidation of hydrogen-doped Ni₃Zr, T.R. Hess, D.L. Cocke, G. Abend and J.H. Block

94/95 (1996) 238

Field electron microscopy

Oscillatory behavior in the catalytic reduction of NO and NO₂ with hydrogen on Pt field emitter tips, C. Voss and N. Kruse

94/95 (1996) 186

Field emission

Field emission from the surface quantum well of silicon, Q.-A. Huang

93 (1996) 77

Developing and using the field emitter as a high intensity electron source, F. Charbonnier

94/95 (1996) 26

Modelling of the field emission microtriode with emitter covered with porous silicon, D. Nicolaescu, V. Filip and P.R. Wilshaw

94/95 (1996) 79

Modelling of a magnetic sensor based on vacuum field emission, D. Nicolaescu and V. Filip

94/95 (1996) 87

Comparative studies on enhanced field emission from mechanically and chemically polished broad-area Nb, Cu, and Al cathodes, N. Puper, T. Habermann, A. Kirschner, E. Mahner, G. Müller and H. Piel

94/95 (1996) 94

A study of the optimum field emitter shape for vacuum electronics applications, B.P. Wang and L. Tong

94/95 (1996) 101

Characterization of ultrasharp field emitters by projection microscopy, M.J. Fransen, E.P.N. Damen, C. Schiller, T.L. van Rooy, H.B. Groen and P. Krut

94/95 (1996) 107

Fabrication of transition metal nitride field emitters, M. Endo, H. Nakane and H. Adachi

94/95 (1996) 113

Field emission characteristics of polycrystalline and single-crystalline diamond grown on Si tips, E.I. Givargizov, V.V. Zhirnov, A.N. Stepanova, P.S. Plekhanov and R.I. Kozlov

94/95 (1996) 117

Diamond coated Si and Mo field emitters: diamond thickness effect, V.V. Zhirnov, W.B. Choi, J.J. Cuomo and J.J. Hrea

94/95 (1996) 123

Study of luminous phenomena observed on contaminated metallic surfaces submitted to high RF fields, S. Maïssa, T. Junquera, M. Fouaidy, A. Le Goff, B. Bonin, M. Luong, H. Safa and J. Tan

94/95 (1996) 136

Field emission properties of Au-Si eutectic, V.V. Zhirnov, L. Bormatova, E.I. Givargizov, P.S. Plekhanov, U.T. Son, A.V. Galdetsky and B.A. Belyavsky

94/95 (1996) 144

Laser photoelectron projection microscopy with subwavelength spatial resolution, V.N. Konopsky, S.K. Sekatskii and V.S. Letokhov

94/95 (1996) 148

Control of formation sites for liquid-Li cones on a W(100) tip by means of the remolding method, K. Hata, F. Nakayama, Y. Saito and A. Ohshita

94/95 (1996) 156

Microdroplet emission on liquid metal surface at the development of Rayleigh instabilities - applications in cosmos, V.V. Vladimirov, V.N. Gorshkov and D.V. Mozyrsky

94/95 (1996) 171

Digitizing chemical oscillations: analyzing experimental data of the CO oxidation on a Pt-tip, M.C. Reckzügel, V. Gorodetski and J.H. Block

94/95 (1996) 194

Li-mediated feedback mechanism of oscillations in CO oxidation on a Rh field emitter tip, V.K. Medvedev, Yu. Suchorski and J.H. Block

94/95 (1996) 200

Field emission from thin liquid metal films, J. Mitterauer

95/96 (1996) 161

Field emission from transition metal nitride, M. Endo, H. Nakane and H. Adachi

100/101 (1996) 378

Field emission microscopy

Investigation of the oxidation behaviour of thin film and bulk copper, M. O'Reilly, X. Jiang, J.T. Beechinor, S. Lynch, C. Ni Dheasuna, J.C. Patterson and G.M. Crean

91 (1995) 152

Early field emission studies of semiconductors, G. Fursey

94/95 (1996) 44

Adsorption studies of cobalt on tungsten (110), (100) and (111) planes by probe-hole field emission microscopy, R.B. Sharma, A.D. Adscool, N. Pradeep and D.S. Joag

94/95 (1996) 177

- The chemistry and structure of (222) CdO/Ag heterophase interfaces on an atomic scale, D.K. Chan, D.N. Seidman and K.L. Merkle 94/95 (1996) 409
- Field ion microscopy*
- Field-ion imaging old and new, R.G. Forbes 94/95 (1996) 1
- Recollections of Erwin Müller's laboratory: the development of FIM (1951-1956), A.J. Melmed 94/95 (1996) 17
- Local field and potential barrier in tunneling processes, M.M. Mollicone, L.C.O. Dacal and C.M.C. de Castilho 94/95 (1996) 68
- Oscillatory behavior in the catalytic reduction of NO and NO₂ with hydrogen on Pt field emitter tips, C. Voss and N. Kruse 94/95 (1996) 186
- Study of CO surface diffusion on CO/W(111) by analysis of CO⁺ field ion rate fluctuations, Yu. Suchorski, J. Bęben, V.K. Medvedev and J.H. Block 94/95 (1996) 207
- Surface diffusion and surface atomic roughness on Ir(001) surface and terraces, C.L. Chen, T.T. Tsong and T.E. Mitchell 94/95 (1996) 224
- Precipitation processes during the early stages of ageing in Al-Cu-Mg alloys, S.P. Ringer, K. Hono, I.J. Polmear and T. Sakurai 94/95 (1996) 253
- 3D reconstruction and analysis of GP zones in Al-1.7Cu (at%): a tomographic atom probe investigation, A. Bigot, F. Danoix, P. Auger, D. Blavette and A. Menand 94/95 (1996) 261
- AP-FIM analysis of ordered Cu₃Au-(4 at% Pt) alloy, V.A. Ivchenko, A. Kvist, H.-O. André, N.N. Syutkin and K. Stiller 94/95 (1996) 267
- Microstructural development in PWA-1480 electron beam welds - an atom probe field ion microscopy study, S.S. Babu, S.A. David and M.K. Miller 94/95 (1996) 280
- Precipitation and grain boundary segregation in molybdenum-doped NiAl, M.K. Miller, I.M. Anderson and K.F. Russell 94/95 (1996) 288
- Observation of both Ni and Mo atom images by FIM with imaging plates, K. Nishikawa, T. Nishiuchi, M. Yamamoto and O. Nishikawa 94/95 (1996) 295
- Nanocrystallization of a Co-Nb-B-C metallic glass, T.A. Lusby and A.J. Melmed 94/95 (1996) 300
- Characterization of sputter-deposited multilayers of Ni and Zr with APFIM/TAP, T. Al-Kassab, M.-P. Macht, V. Naundorf, H. Wollenberger, S. Chambrelaud, F. Danoix and D. Blavette 94/95 (1996) 306
- An atom probe study of cementite precipitation in autotempered martensite in an Fe-Mn-C alloy, R.C. Thomson and M.K. Miller 94/95 (1996) 313
- Observation of molybdenum-nitrogen clustering in highly alloyed martensite, L. Lundin and H.-O. André 94/95 (1996) 320
- Investigation of precipitation in a new maraging stainless steel, K. Stiller, F. Danoix and A. Bostel 94/95 (1996) 326
- Microstructural influences on the decomposition of an Al-containing ferritic stainless steel, H.G. Read and H. Murakami 94/95 (1996) 334
- Grain boundary precipitation and segregation in Ni-16Cr-9Fe model materials, M. Thuvander, K. Stiller, D. Blavette and A. Menand 94/95 (1996) 343
- Atom probe analysis of carbonitride grains in (Ti, W, Ta, Mo)(C, N)(Co/Ni) cermets with different carbon content, J. Zackrisson, M. Thuvander, P. Lindahl and H.-O. André 94/95 (1996) 351
- APFIM studies of the phase transformations in thermally aged ferritic FeCuNi alloys: comparison with aging under neutron irradiation, P.J. Pareige, K.F. Russell and M.K. Miller 94/95 (1996) 362
- Characterization of neutron-induced copper-enriched clusters in pressure vessel steel weld: an APFIM study, P. Pareige and M.K. Miller 94/95 (1996) 370
- APFIM characterization of a high phosphorus Russian RPV weld, M.K. Miller and K.F. Russell 94/95 (1996) 378
- Field ion microscopy study of the interactions between self interstitials and impurities in metals, A.L. Suvorov and D.E. Dolin 94/95 (1996) 384
- Phase separation in the Fe-Cr-Ni system, M.K. Miller, I.M. Anderson, J. Bentley and K.F. Russell 94/95 (1996) 391
- Comparison of the rate of decomposition in Fe-45%Cr, Fe-45%Cr-5%Ni and duplex stainless steels, M.K. Miller and K.F. Russell 94/95 (1996) 398
- Atomic-scale studies of silver segregation at MgO/Cu heterophase interfaces, D.A. Shashkov and D.N. Seidman 94/95 (1996) 416
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- Surface reaction mechanism in MOCVD, J. Nishizawa, H. Sakuraba and T. Kurabayashi 92 (1996) 89
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- Ultra accurate measurements of interface parameters with free-electron laser, C. Coluzza 92 (1996) 267
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- Ga migration process in Au film on (100) GaAs under temperature treatment in vacuum, T.A. Bryantseva, D.V. Lioubtchenko and V.V. Lopatin 100/101 (1996) 169
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- Roughness study of ion-irradiated silica glass surface, K. Oyoshi, S. Hishita, K. Wada, S. Suchara and T. Aizawa 100/101 (1996) 374
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Gold

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Hafnium

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Halides

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Hall effect

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Halogens

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Heterostructures

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Hydrocarbons

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- In situ radiotracer method for study of adsorption on semiconductor single crystal surfaces, M. Szklarczyk 92 (1996) 431
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Hydrogen

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- High purity ozone oxidation on hydrogen passivated silicon surface, A. Kurokawa and S. Ichimura 100/101 (1996) 436
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Indium

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- NO interaction with thermally activated CaO and SrO surfaces, Y. Yanagisawa 100/101 (1996) 256
- Infrared external reflection spectroscopy of self-assembled monolayer films on Si substrate with a buried metal layer (BML) structure, Y. Kobayashi and T. Ogino 100/101 (1996) 407
- In situ observation of nitridation of GaAs (001) surfaces by infrared reflectance spectroscopy, K. Uwai, Y. Yamauchi and N. Kobayashi 100/101 (1996) 412
- Initial stage of oxidation of $\text{Si}(100)$ surfaces in dry oxygen, K. Inanaga, T. Nakahata, T. Furukawa and K. Ono 100/101 (1996) 421
- Initial stages of oxidation of hydrogen-terminated Si surface stored in air, T. Miura, M. Niwano, D. Shoji and N. Miyamoto 100/101 (1996) 454
- In-situ IR and mass spectroscopic study of the $\text{Al}(\text{CH}_3)_2\text{H}/\text{a-Si:H}$ reaction processes, T. Wadayama, Y. Maiwa, H. Shibata and A. Hatta 100/101 (1996) 575
- Infrared study of chemistry of Si surfaces in etching solution, M. Niwano, T. Miura, R. Tajima and N. Miyamoto 100/101 (1996) 607
- ### Interfaces
- Ultra accurate measurements of interface parameters with free-electron laser, C. Coluzza 92 (1996) 267
- Interface effects in melting of Pb clusters on the $\text{Cu}(111)$ surface, E.Z. Luo, Q. Cai, W.F. Chung and M.S. Altman 92 (1996) 331
- Study of the internal electric fields across the interfaces in the $\text{GaAs}/(\text{Al,Ga})\text{As}$ microstructures, C.R. Lu, C.L. Chang, C.H. Liou, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 404

- Interface of $\text{CuIn}_{1-x}\text{Ga}_x\text{Se}_2/\text{GaAs}$ heterostructure, B.-H. Tseng, S.-B. Lin, G.-L. Gu and H.-Z. Hsu 92 (1996) 412
- Effect of substrate-film interface on magnetic properties of Mn_4N films, K.-M. Ching, W.-D. Chang and T.-S. Chin 92 (1996) 471
- The chemistry and structure of {222} CdO/Ag heterophase interfaces on an atomic scale, D.K. Chan, D.N. Seidman and K.L. Merkle 94/95 (1996) 409
- Surface and interface analysis of GaSb/GaAs semiconductor materials, K. Li, J. Lin, A.T.S. Wee, K.L. Tan, Z.C. Feng and J.B. Webb 99 (1996) 59
- Determination of the interface region in multilayer Si/Mo by Auger depth profile and factor analysis, T. Morohashi, T. Hoshi, H. Nikaido and M. Kudo 100/101 (1996) 84
- Structural fluctuation of SiO_2 network at the interface with Si , Y. Sugita, S. Watanabe, N. Awaji and S. Komiya 100/101 (1996) 268
- Novel method of strain-relaxed $\text{Si}_{1-x}\text{Ge}_x$ growth on $\text{Si}(100)$ by MBE, H. Iwano, K. Yoshikawa, A. Kojima, K. Hayashi, S. Zaima and Y. Yasuda 100/101 (1996) 487
- Atomic structure analysis of the interfaces in Si/Ge superlattices, K. Sumitomo, T. Nishioka and T. Ogino 100/101 (1996) 503
- ### *Ion bombardment*
- Improved thermal stability of cobalt silicide formed by ion beam assisted deposition on polysilicon, S. Ravesi, F. La Via, V. Raineri and C. Spinella 91 (1995) 19
- Patterning of copper for multilevel metalization: reactive ion etching and chemical-mechanical polishing, C. Steinbrüchel 91 (1995) 139
- Some particular features of the condensation process, structure and properties of thin metal films caused by self-ion bombardment, I.V. Gusev, A.A. Mohnjuk, V.I. Chaptjuk and V.P. Belevsky 91 (1995) 182
- Field ion microscopy study of the interactions between self interstitials and impurities in metals, A.L. Suvorov and D.E. Dolin 94/95 (1996) 384
- Ion-assisted pulsed-laser deposition for the fabrication of $\text{Y}-\text{Ba}-\text{Cu}-\text{O}$ multilayer structures using oriented intermediate layers of YSZ and CeO_2 , R.P. Reade and R.E. Russo 96-98 (1996) 726
- Photon and ion beam assisted deposition of titanium nitride, H. Wengenmair, J.W. Gerlach, U. Preckwinkel, B. Stritzker and B. Rauschenbach 99 (1996) 313
- Damage profiling of Ar^+ sputtered $\text{Si}(100)$ surface by medium energy ion scattering spectroscopy, J.C. Lee, C.S. Jeong, H.J. Kang, H.K. Kim and D.W. Moon 100/101 (1996) 97
- Surface characterization of cell adhesion controlled polymer modified by ion bombardment, A. Nakao, M. Kaibara, M. Iwaki, Y. Suzuki and M. Kusakabe 100/101 (1996) 112
- Ion induced alteration at $\text{Pb}-\text{Sn}$ alloy surface investigated by Auger electron spectroscopy and X-ray photoelectron spectroscopy, M. Kudo, A. Ishijima and T. Morohashi 100/101 (1996) 134
- Processes in low-energy ion-surface collisions: preferential sputtering, defect and adatom formation, H. Gnaser 100/101 (1996) 316
- Preferential sputtering and surface segregation of CuZr alloys, H.J. Kang, C.H. Kim, N.S. Park, D.J. O'Connor and R. MacDonald 100/101 (1996) 329
- Investigation of the physical and chemical interaction of a low energy oxygen ion beam with oxide superconducting films, G. Pindoria, M. Badaye, F. Wang, K. Kawaguchi and T. Morishita 100/101 (1996) 347
- Angular distribution of particles sputtered from GaAs by Ar^+ and Xe^+ ion bombardment, T. Aoyama, M. Tanemura and F. Okuyama 100/101 (1996) 351
- Soft X-ray emissions by highly charged ions on solid surfaces: Mo and Ta surfaces, T. Emoto, K. Komatsu, A. Ichimiya, S. Ninomiya and M. Sekiguchi 100/101 (1996) 355
- Development of ion irradiation system for in situ observation of ion irradiated semiconductor surfaces by ultra high vacuum scanning tunneling microscope, J. Ishikawa, H. Tsuji, K. Kameyama, S. Shimada and Y. Gotoh 100/101 (1996) 370
- Roughness study of ion-irradiated silica glass surface, K. Oyoshi, S. Hishita, K. Wada, S. Suehara and T. Aizawa 100/101 (1996) 374
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- Comparison of CoSi_2 interconnection lines on crystalline and noncrystalline silicon fabricated by writing focused ion beam implantation, J. Teichert, L. Bischoff, E. Hesse, P. Schneider, D. Panknin, T. Gessner, B. Löbner and N. Zichner 91 (1995) 44
- Beam induced phase transformations and self annealing in as-implanted iron silicides, G. Crecelius, K. Radermacher, Ch. Dieker and S. Mesters 91 (1995) 50
- The effect of ion implantation on the properties of Al films, M. Zaborowski, A. Barcz, G. Gawlik and I.W. Rangelow 91 (1995) 239

- Selective deposition of tungsten on ITM-
CoSi₂, J.D. Kähler, D. Depta and R.
Ferretti 91 (1995) 339
- XPS studies on SiC thin layers formed by
ion implantation with a metal vapor vac-
uum arc ion source, H. Yan, R.W.M.
Kwok and S.P. Wong 92 (1996) 61
- Dopant activation and strain relaxation in
P-implanted metastable pseudomorphic
Ge_{0.12}Si_{0.88} grown on Si(100), D.Y.C.
Lie, N.D. Theodore and J.H. Song 92 (1996) 557
- Tungsten absorber on silicon membrane,
D.C. Li, C.S. Yoo and C.Y. Sun 92 (1996) 665
- Chemical, mechanical and electrical prop-
erties of CN_x-films produced by reactive
sputtering and N⁺-implantation in car-
bon films, N. Laidani, A. Miotello and
J. Perrière 99 (1996) 273
- Influence of ion-implantation on native ox-
idation of Si in a clean-room atmosphere,
F. Yano, A. Hiraoka, T. Itoga, H. Ko-
jima, K. Kanehori and Y. Mitsui 100/101 (1996) 138
- Fundamental study on powder-scattering in
positive- and negative-ion implantation
into powder materials, H. Tsuji, J.
Ishikawa, H. Itoh, Y. Toyota and Y.
Gotoh 100/101 (1996) 342
- Charging phenomenon of insulators in nega-
tive-ion implantation, Y. Toyota, H.
Tsuji, S. Nagumo, Y. Gotoh and J.
Ishikawa 100/101 (1996) 360
- Synthesis of metastable group-IV alloy
semiconductors by ion implantation and
ion-beam-induced epitaxial crystalliza-
tion, N. Kobayashi, M. Hasegawa, N.
Hayashi, H. Katsumata, Y. Makita, H.
Shibata and S. Uekusa 100/101 (1996) 498
- Valence band structure of metal silicides
modified by argon ion implantation, S.
Yamauchi, Y. Hasebe, H. Ohshima, T.
Hattori, M. Hirai, M. Kusaka and M.
Iwami 100/101 (1996) 522
- Ion scattering*
- Epitaxy of CoSi₂/Si(100): from
Co/Ti/Si(100) to reactive deposition
epitaxy, A. Vantomme, S. Degroote, J.
Dekoster and G. Langouche 91 (1995) 24
- Beam induced phase transformations and
self annealing in as-implanted iron sili-
cides, G. Creclius, K. Radermacher,
Ch. Dieker and S. Mesters 91 (1995) 50
- Ni silicides formation and properties in RF
sputtered Ni_{100-x}-Si_x thin films, A.
Belu-Marian, M.D. Serbanescu, R.
Manaila and A. Devenyi 91 (1995) 63
- Cubic metastable FeSi_{1-x} epitaxially grown
on Si and MgO substrates, S. Degroote,
A. Vantomme, J. Dekoster and G. Lan-
gouche 91 (1995) 72
- Formation of CoSi₂ on strained Si_{0.8}Ge_{0.2}
using a sacrificial Si layer, R.A. Dona-
ton, S. Kolodinski, M. Caymax, Ph.J.
Roussel, H. Bender, B. Brijs and K.
Maex 91 (1995) 77
- Metallurgical and electrical investigation of
Pt₅Ni₉₅/silicon interactions, F. Corni,
C. Nobili, G. Ottaviani, R. Tonini, B.
Grignaffini Gregorio and G. Queirolo 91 (1995) 107
- Structure and electrical properties of thin
copper films deposited by MOCVD, J.
Röber, C. Kaufmann and T. Gessner 91 (1995) 134
- Sputtering of tantalum-based diffusion bar-
riers in Si/Cu metallization: effects of
gas pressure and composition, M.
Stavrev, C. Wenzel, A. Möller and K.
Drescher 91 (1995) 257
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Si/SiO₂/Cu metallizations, A.-M.
Dutron, E. Blanquet, C. Bernard, A.
Bachli and R. Madar 91 (1995) 277
- Barrier behaviour of plasma deposited sili-
con oxide and nitride against Cu diffu-
sion, M. Vogt and K. Drescher 91 (1995) 303
- Dopant activation and strain relaxation in
P-implanted metastable pseudomorphic
Ge_{0.12}Si_{0.88} grown on Si(100), D.Y.C.
Lie, N.D. Theodore and J.H. Song 92 (1996) 557
- Depth profiling of W, O and H in tungsten
trioxide thin films using RBS and ERDA
techniques, O. Bohnke, G. Frand, M.
Fromm, J. Weber and O. Greim 93 (1996) 45
- Formation of polycrystalline BaTi₃O₇ com-
pounds in barium implanted TiO₂,
S.M.M. Ramos, B. Canut, M. Ambri, N.
Bonardi, R. Brenier, M. Pitaval, P.
Thevenard and M. Brunel 93 (1996) 191
- Ion beam studies of porphyrin adsorption on
and leaching of soda lime glass, C.H.M.
Marée, T.J. Savenije, T.J. Schaafsma
and F.H.P.M. Habraken 93 (1996) 291
- Electrical characterization of semiconduct-
ing La doped SrTiO₃ thin films prepared
by pulsed laser deposition, K.-O.
Grosse-Holz, J.F.M. Cillessen and R.
Waser 96-98 (1996) 784
- Laser reactive ablation deposition of silicon
carbide films, G. Leggieri, A. Luches,
M. Martino, A. Perrone, R. Alexan-
drescu, A. Barborica, E. Gyorgy, I.N.
Mihailescu, G. Majni and P. Mengucci 96-98 (1996) 866

- Application and properties of sub-mono-molecular layers of silicon dioxide deposited under mild conditions, D.M. Knotter 99 (1996) 99
- ^{18}O -exchange with the substrate during ^{18}O oxidation of Cu particles supported on ^{16}O -oxidised Si(100), R. van Wijk, C.H.M. Marée, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 99 (1996) 197
- Diffusion barrier property of TaN between Si and Cu, T. Oku, E. Kawakami, M. Uekubo, K. Takahiro, S. Yamaguchi and M. Murakami 99 (1996) 265
- Photon and ion beam assisted deposition of titanium nitride, H. Wengenmair, J.W. Gerlach, U. Preckwinkel, B. Stritzker and B. Rauschenbach 99 (1996) 313
- Damage profiling of Ar^+ sputtered Si(100) surface by medium energy ion scattering spectroscopy, J.C. Lee, C.S. Jeong, H.J. Kang, H.K. Kim and D.W. Moon 100/101 (1996) 97
- Preferential sputtering and surface segregation of CuZr alloys, H.J. Kang, C.H. Kim, N.S. Park, D.J. O'Connor and R. MacDonald 100/101 (1996) 329
- Dissociative scattering of low-energy SiF_3^+ and SiF^+ ions (5-200 eV) on Cu(100) surface, H. Yamamoto, Y. Baba and T.A. Sasaki 100/101 (1996) 333
- Synthesis of metastable group-IV alloy semiconductors by ion implantation and ion-beam-induced epitaxial crystallization, N. Kobayashi, M. Hasegawa, N. Hayashi, H. Katsumata, Y. Makita, H. Shibata and S. Uekusa 100/101 (1996) 498
- Atomic structure analysis of the interfaces in Si/Ge superlattices, K. Sumitomo, T. Nishioka and T. Ogino 100/101 (1996) 503
- ### Iridium
- Surface diffusion and surface atomic roughness on Ir(001) surface and terraces, C.L. Chen, T.T. Tsong and T.E. Mitchell 94/95 (1996) 224
- ### Iron
- Beam induced phase transformations and self annealing in as-implanted iron silicides, G. Creclius, K. Radermacher, Ch. Dieker and S. Mesters 91 (1995) 50
- Electrical and optical properties of thin $\text{Fe}_{1-x}\text{Co}_x\text{Si}_2$ films, St. Teichert, R. Kilper, Th. Franke, J. Erben, P. Häussler, W. Henrion, H. Lange and D. Panknin 91 (1995) 56
- Cubic metastable FeSi_{1-x} epitaxially grown on Si and MgO substrates, S. Degroote, A. Vantomme, J. Dekoster and G. Langouche 91 (1995) 72
- Electrical and optical properties of thin $\beta\text{-FeSi}_2$ films on Al_2O_3 substrates, K. Herz and M. Powalla 91 (1995) 87
- Photoelectron spectroscopic investigations of thin $\text{Fe}_2\text{Si}_{100-x}$ films, R. Kilper, St. Teichert, Th. Franke, P. Häussler, H.-G. Boyen, A. Cossy-Favre and P. Oelhafen 91 (1995) 93
- Interface phase transition as observed in ultra thin FeSi_2 epilayers, J. Derrien, I. Berbezier, A. Ronda and J.Y. Natoli 92 (1996) 311
- Coercivity of $\gamma\text{-(Fe}_{0.74}\text{Mn}_{0.15}\text{Co}_{0.11})_2\text{O}_3$ thin films by dc reactive magnetron sputtering, W.-D. Chang and T.-S. Chin 92 (1996) 475
- Characterisation of the spinels $\text{M}_2\text{Co}_{1-x}\text{Fe}_x\text{O}_4$ (M = Mn, Fe or Ni) using X-ray photoelectron spectroscopy, G.C. Allen and K.R. Hallam 93 (1996) 25
- Corrosion inhibition of iron in 1M HCl by 1-phenyl-5-mercapto-1,2,3,4-tetrazole, S. Kertit and B. Hammouti 93 (1996) 59
- Corrosion of iron by a perfluoropolyalkyl-ether identified by Mössbauer spectroscopy, G. John, J.S. Zabinski and V.K. Gupta 93 (1996) 329
- Grain boundary precipitation and segregation in Ni-16Cr-9Fe model materials, M. Thuvander, K. Stiller, D. Blavette and A. Menand 94/95 (1996) 343
- Comparison of the rate of decomposition in Fe-45%Cr, Fe-45%Cr-5%Ni and duplex stainless steels, M.K. Miller and K.F. Russell 94/95 (1996) 398
- Measurement and calculation of the Fe_2O_3 ablation depth, A. Lisfi, M. Guyot, R. Krishnan and V. Cagan 96-98 (1996) 66
- Laser induced periodic surface structures on iron, A. Dauscher, V. Fereggoto, P. Cordier and A. Thomé 96-98 (1996) 410
- FTIR study of adsorption of CO, NO and C_2H_4 and reaction of $\text{CO} + \text{H}_2$ on the well-dispersed $\text{FeOx}/\gamma\text{-Al}_2\text{O}_3$ and $\text{FeOx}/\text{TiO}_2(\text{a})$ catalysts, W. Ji, Y. Chen, S. Shen, S. Li and H. Wang 99 (1996) 151
- CuCl growth on the reconstructed surface of (0001) haematite, Q. Guo, L. Gui and N. Wu 99 (1996) 229
- XPS study of carbon/inconel bilayers as a function of substrate bias, M.S. Aouadi, P.C. Wong and K.A.R. Mitchell 99 (1996) 319
- Oxidation of ultrathin iron layers grown on Cu(111), C. Ruby and J. Fusy 99 (1996) 393
- Simultaneous determination of composition and thickness of thin iron-oxide films from XPS Fe 2p spectra, P.C.J. Graat and M.A.J. Somers 100/101 (1996) 36

Langmuir-Blodgett structures

- Mapping of molecular C_{17} indandione-1,3 pyridinium betaine adsorbates on fused silica by surface second harmonic generation, D. Ding, T. Käämbre, S. Ljungström, Y. Chen, K. Siegbahn, E. Wistius, P. Swensson and E. Mukhtar 96-98 (1996) 581
- Secondary ion emission from Langmuir-Blodgett (LB) films investigated by time-of-flight secondary ion mass spectrometry, M. Kudo, S. Yamada, S. Yoshida, T. Watanabe and T. Hoshi 100/101 (1996) 129

Laser processing

- Diamond-like coating prepared by pulsed laser sputtering of graphite in a high-vacuum environment, I.A. Bogonin, A.L. Karuzskii, N.N. Melnik, Yu.A. Mityagin, V.N. Murzin, A.A. Orlikovsky, A.V. Perestoronin, P.P. Sverbil, S.D. Tkachenko, A.V. Tsikunov, N.A. Volchkov and B.G. Zhurkin 92 (1996) 43
- Ellipsometric study of thermal and laser annealed amorphous and microcrystalline silicon films, A.H. Jayatissa, M. Suzuki, Y. Nakanishi and Y. Hatanaka 92 (1996) 300
- Structural and electrical properties of excimer laser deposited PLZT thin films, H.-F. Cheng 92 (1996) 378
- Electrical properties of laser deposited $YBa_2Cu_3O_{7-x}$ films on silicon wafers, F.Y. Chuang, C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin 92 (1996) 452
- Pulsed-laser deposition of "diamond-like" carbon coating on $YBa_2Cu_3O_7$ high- T_c superconductor films, A.L. Karuzskii, N.N. Melnik, V.N. Murzin, V.S. Nozdrin, A.V. Perestoronin, N.A. Volchkov and B.G. Zhurkin 92 (1996) 457
- Carbon nitride - prospects for ultimate performance of superhard materials, S.A. Uglov, V.E. Shub, A.A. Beloglazov and V.I. Konov 92 (1996) 656
- Microstructural properties of laser synthesized Si/C/N nanoparticles, R. Giorgi, S. Turbù, G. Zappa, E. Borsella, S. Botti, M.C. Cesile and S. Martelli 93 (1996) 101
- Studies of silicon-nitride (Si_3N_4) using laser ablation mass spectrometry, S.L. Wang, K.W.D. Ledingham, W.J. Jia and R.P. Singhal 93 (1996) 205
- Instabilities in laser direct writing due to non-uniform cross section of stripes, N. Kirichenko, Y. Khavin and N. Arnold 93 (1996) 359
- Microscopic and mesoscopic aspects of laser-induced desorption and ablation, R.F. Haglund, Jr. 96-98 (1996) 1
- Hydrodynamic phenomena during laser irradiation: a finite difference approach, N. Seifert, G. Betz and W. Husinsky 96-98 (1996) 33
- Measurement and calculation of the Fe_2O_3 ablation depth, A. Lisfi, M. Guyot, R. Krishnan and V. Cagan 96-98 (1996) 66
- Calculation and measurement of the ultrasonic signals generated by ablating material with a Q-switched pulse laser, A. Hoffmann and W. Arnold 96-98 (1996) 71
- 2D-simulation of the system: laser beam + laser plasma + target, V.I. Mazhukin, I. Smurov and G. Flamant 96-98 (1996) 89
- Modeling of laser induced plasma, spectroscopic and time of flight experiments in pulsed laser deposition, G. Granse, S. Völlmar, A. Lenk, A. Rupp and K. Rohr 96-98 (1996) 97
- Study of the expansion of the laser ablation plume above a boron nitride target, B. Angleraud, C. Girault, C. Champeaux, F. Garrelie, C. Germain and A. Catherinot 96-98 (1996) 117
- Preferential vaporization and plasma shielding during nano-second laser ablation, X. Mao, W.-T. Chan, M. Caetano, M.A. Shannon and R.E. Russo 96-98 (1996) 126
- Laser ablation plume thermalization dynamics in background gases: combined imaging, optical absorption and emission spectroscopy, and ion probe measurements, D.B. Geohegan and A.A. Puretzky 96-98 (1996) 131
- Fundamental characteristics of laser-material interactions (ablation) in noble gases at atmospheric pressure using inductively coupled plasma-atomic emission spectroscopy, R.E. Russo, X.L. Mao, M. Caetano and M.A. Shannon 96-98 (1996) 144
- Monitoring stress power during high-power pulsed laser-material interactions, M.A. Shannon and R.E. Russo 96-98 (1996) 149
- Spatially and temporally resolved emission intensities and number densities in low temperature laser-induced plasmas in vacuum and in ambient gases, R.A. Al-Wazzan, J.M. Hendron and T. Morrow 96-98 (1996) 170
- Laser produced plasmas in high fluence ablation of metallic surfaces probed by time-of-flight mass spectrometry, S. Amoroso, A. Amodeo, V. Berardi, R. Bruzzese, N. Spinelli and R. Velotta 96-98 (1996) 175
- Optical diagnostics of the laser-target and laser-plume interaction in pulsed laser ablation, F. Fuso, L.N. Vyacheslavov,

- G. Lorenzi, M. Allegrini and E. Arimondo 96-98 (1996) 181
- Time-of-flight characterization of laser ablation plume from NbTe₂ target in He atmosphere, F. Grangeon, H. Sassoli, W. Marine and M. Autric 96-98 (1996) 186
- Investigation of vaporization and condensation processes of thin layers of CdHgTe from laser erosion plasma in Hg atmosphere, B.K. Kotlyarchuk, D.I. Popovych, V.K. Savchuk and V.G. Savitsky 96-98 (1996) 192
- Density and electron temperature of laser induced plasma - a comparison of different investigation methods, A. Lenk, Th. Witke and G. Granse 96-98 (1996) 195
- Comments on explosive mechanisms of laser sputtering, R. Kelly and A. Miotello 96-98 (1996) 205
- Analysis of the expansion of hydroxyapatite laser ablation plumes, P. Serra, L. Clères and J.L. Morenza 96-98 (1996) 216
- Dynamics of silicon plume generated by laser ablation and its chemical reaction, T. Makimura and K. Murakami 96-98 (1996) 242
- Formation of large carbon cluster ions at graphite (HOPG) surfaces by laser irradiation, H. Togashi, K. Saito, Y. Koga, H. Yamawaki, K. Aoki, M. Mukaida and T. Kameyama 96-98 (1996) 267
- Excimer laser induced surface modifications and matter interaction using double-pulse-technique (DPT), H.W. Bergmann 96-98 (1996) 287
- Excimer laser-induced hydrodynamical effects and surface modifications on silicon carbide, G. Nicolas and M. Autric 96-98 (1996) 296
- Excimer laser induced thermal evaporation and ablation of silicon carbide, R. Reitano, P. Baeri and N. Marino 96-98 (1996) 302
- Increase of efficiency for the XeCl excimer laser ablation of ceramics, M. Geiger, W. Becker, T. Rebhan, J. Hutfless and N. Lutz 96-98 (1996) 309
- The role of defects in laser induced positive ion emission from ionic crystals, J.T. Dickinson, J.-J. Shin and S.C. Langford 96-98 (1996) 316
- Laser-induced emission of neutral atoms and molecules from electron-irradiated NaNO₃, J.T. Dickinson, J.J. Shin and S.C. Langford 96-98 (1996) 326
- Laser damage of CaF₂(111) surfaces at 248 nm, S. Gogoll, E. Stenzel, M. Reichling, H. Johansen and E. Matthias 96-98 (1996) 332
- Laser patterning of thin-film electrochemical gas sensors, A. Lecours, M. Caron, P. Ciureanu, G. Turcotte, D. Ivanov, A. Yelon and J.F. Currie 96-98 (1996) 341
- Laser beam application to thin film transistors, T. Sameshima 96-98 (1996) 352
- Laser induced nitridation of Ga on GaAs surfaces, M.F. Barthe, C. Perrin, L. Vivet, B. Dubreuil and T. Gibert 96-98 (1996) 359
- Low-fluence excimer laser irradiation-induced defect formation in indium-tin oxide films, T. Szörényi, L.D. Laude, I. Bertóti, Zs. Geretovszky and Z. Kántor 96-98 (1996) 363
- Micro-Raman study of UV laser ablation of GaAs and Si substrates, C. García, J. Ramos, A.C. Prieto, J. Jiménez, C. Geertsen, J.L. Lacour and P. Mauchien 96-98 (1996) 370
- Single shot excimer laser annealing of amorphous silicon for AMLCD, P. Boher, J.L. Stehle, M. Stehle and B. Godard 96-98 (1996) 376
- Erosion plume dynamics during pulsed laser alloying, V. Titov, I. Smurov and M. Ignatiev 96-98 (1996) 387
- Excimer laser interaction with dielectric thin films, E. Welsch, K. Etrich, H. Blaschke and N. Kaiser 96-98 (1996) 393
- Decomposition mechanisms of thin palladium acetate film with excimer UV radiation, J.-Y. Zhang, H. Esrom and I.W. Boyd 96-98 (1996) 399
- Single crystal laser patterning for selective YBa₂Cu₃O_{7-x} growth, R. Aguiar, F. Sánchez and M. Varela 96-98 (1996) 405
- Laser induced periodic surface structures on iron, A. Dauscher, V. Feregotto, P. Cordier and A. Thomy 96-98 (1996) 410
- Excimer laser ablation for micro-machining: geometric effects, P.E. Dyer, D.M. Karnakis, P.H. Key and P. Monk 96-98 (1996) 415
- Optodynamics of laser ablation of graduation lines in chromium thin film on glass, S. Kopač, J. Pirš and J. Možina 96-98 (1996) 420
- Excimer laser machining for the fabrication of analogous microstructures, K. Zimmer, D. Hirsch and F. Bigl 96-98 (1996) 425
- Femtosecond-pulse visible laser processing of transparent materials, J. Krüger and W. Kautek 96-98 (1996) 430
- Picosecond UV-laser ablation of Au and Ni films, A. Rosenfeld and E.E.B. Campbell 96-98 (1996) 439
- The role of gas-phase in the laser etching of Cu by CCl₄, D. Débarre, A. Aliouchouche, J. Boulmer, B. Bourguignon and J.P. Budin 96-98 (1996) 453
- Laser-induced formation of visible light emitting silicon, D. Dimova-Malinovska, M. Tzolov, N. Malinowski, Ts. Marinova and V. Krastev 96-98 (1996) 457

- Cleaning of optical surfaces by excimer laser radiation, K. Mann, B. Wolff-Rotke and F. Müller 96-98 (1996) 463
- In situ surface cleaning of pure and implanted tungsten photocathodes by pulsed laser irradiation, M. Afif, J.P. Girardeau-Montaut, C. Tomas, M. Romand, M. Charbonnier, N.S. Prakash, A. Perez, G. Marest and J.M. Frigerio 96-98 (1996) 469
- Laser cleaning in art restoration, I. Gubernado-Mitre, J. Medina, B. Calvo, A.C. Prieto, L.A. Leal, B. Pérez, F. Marcos and A.M. de Frutos 96-98 (1996) 474
- Cleaning of copper traces on circuit boards with excimer laser radiation, D.A. Wesner, M. Mertin, F. Lupp and E.W. Kreutz 96-98 (1996) 479
- Modelling and diagnostic of pulsed laser cleaning of oxidized metallic surfaces, R. Oltra, O. Yavaş, F. Cruz, J.P. Boquillon and C. Sartori 96-98 (1996) 484
- Fast etching of sapphire by a visible range quasi-cw laser radiation, S.I. Dolgaev, A.A. Lyalin, A.V. Simakin and G.A. Shafeev 96-98 (1996) 491
- Surface temperature measurements during pulsed laser action on metallic and ceramic materials, M.B. Ignatiev, I.Yu. Smurov, G. Flamant and V.N. Senchenko 96-98 (1996) 505
- Real-time determination of the amount of removed material during short pulses laser micromachining, C. Stauter, J. Fontaine and Th. Engel 96-98 (1996) 522
- White synchrotron X-radiation-section topography of high energy density ns-pulsed (Nd:YAG) ablation damage in Si(100) wafers, J.D. Stephenson 96-98 (1996) 528
- Excimer laser ablation of polymers and glasses for grating fabrication, P.E. Dyer, R.J. Farley, R. Giedl and D.M. Karnakis 96-98 (1996) 537
- Chemical surface modification of fluorocarbon polymers by excimer laser processing, H. Niino and A. Yabe 96-98 (1996) 550
- Excimer laser-induced surface modifications of biocompatible polymer blends, P. Viville, S. Beauvois, G. Lambin, R. Lazzaroni, J.L. Brédas, K. Kolev and L. Laude 96-98 (1996) 558
- Laser implantation of fluorescent molecules into polymer films, H. Fukumura, Y. Kohji and H. Masuhara 96-98 (1996) 569
- Excited state relaxation processes of MALDI-matrices studied by luminescence spectroscopy, H. Ehring and B.U.R. Sundqvist 96-98 (1996) 577
- Etching and functionalization of a fluorocarbon polymer by UV laser treatment, C. Girardeaux, Y. Idrissi, J.J. Pireaux and R. Caudano 96-98 (1996) 586
- Optodynamic studies of Er:YAG laser induced microexplosions in dentin, L. Grad and J. Možina 96-98 (1996) 591
- Single pulse threshold and transmission behaviour of a triazeno-polymer during pulsed UV-laser irradiation, T. Lippert, L.S. Bennett, T. Nakamura, H. Niino and A. Yabe 96-98 (1996) 601
- Formation of the surface structure of polyethylene-terephthalate (PET) due to ArF excimer laser ablation, B. Hopp, M. Csete, K. Révész, J. Vinkó and Zs. Bor 96-98 (1996) 611
- Thin film growth by the pulsed laser assisted deposition technique, C. Belouet 96-98 (1996) 630
- Giant laser-induced voltages at room temperature in Pr doped Y-Ba-Cu-O thin films, H.-U. Habermeyer, N. Jisrawi and G. Jäger-Waldau 96-98 (1996) 689
- Laser ablation of oxides: study of the oxygen incorporation by ^{18}O isotopic tracing techniques, R. Pérez Casero, R. Gómez San Román, C. Maréchal, J.P. Enard and J. Perrière 96-98 (1996) 697
- Substrate size effect at off-axis laser deposition of multicomponent films, M.R. Predtechensky, O.M. Tukhto, A.N. Smal' and S.A. Vasil'eva 96-98 (1996) 717
- Reactive laser deposition of high quality YBaCuO and ErBaCuO films, D. Berling, A. Del Vecchio, S. Acquaviva, D. Bolmont, G. Leggieri, B. Loegel, M. Luisa De Giorgi, A. Luches, A. Mehdaoui and L. Tapfer 96-98 (1996) 739
- Approach to in situ characterization of polysilicon surfaces annealed by XeCl excimer laser, T. Nishibe, H. Mitsuhashi, Y. Matsuura and Y. Kawakyu 99 (1996) 35
- Line shape study of Ba ions in laser produced plasmas, R.A. Al-Wazzan, J.M. Hendron and T. Morrow 99 (1996) 345

Lead

- Interface effects in melting of Pb clusters on the Cu(111) surface, E.Z. Luo, Q. Cai, W.F. Chung and M.S. Altman 92 (1996) 331
- A study of galena (PbS) surfaces under controlled potential in pH 4.6 solution by synchrotron radiation excited photoelectron spectroscopy, I. Kartio, K. Laajalehto, T. Kaurila and E. Suominen 93 (1996) 167
- Improvement of the crystallinity in PbTiO₃ films grown on indium tin oxide-coated glass by metalorganic chemical vapor deposition using the continuous cooling

- process, Y.S. Yoon, S.S. Yom, T.W. Kim, D.U. Lee and C.O. Kim 93 (1996) 285
- Pb_{1-x}Ca_xTiO₃ thin films prepared by laser ablation of ceramic targets, M.J. Martín, C. Zaldo and J. Mendiola 96-98 (1996) 823
- Ion induced alteration at Pb-Sn alloy surface investigated by Auger electron spectroscopy and X-ray photoelectron spectroscopy, M. Kudo, A. Ishijima and T. Morohashi 100/101 (1996) 134

Low energy electron diffraction

- Growth mechanism of Ni on Pt(110) at low temperature, C.S. Shern, J.S. Tsay and T. Fu 92 (1996) 74
- Adsorption of H₂S on GaP(001) surface and passivation effects studied by AES, LEED and XPS, Y. Fukuda, N. Sanada, M. Kuroda and Y. Suzuki 92 (1996) 212
- XPS, AES and LEED studies of Cu deposited on Cr₂O₃(0001) surfaces, Q. Guo, L. Gui, P.J. Möller and K. Binau 92 (1996) 513
- The oxidation of the NiAl(111) surface, R. Franchy, J. Masuch and P. Gassmann 93 (1996) 317
- LEED and XPS studies of the ZrO/W(100) surface, H. Satoh, H. Nakane and H. Adachi 94/95 (1996) 247
- STM study of Sr adsorption on Si(100) surface, R.Z. Bakhizina, J. Kishimoto, T. Hashizume and T. Sakurai 94/95 (1996) 478
- CO adsorption and CO oxidation on Rh(100), A. Baraldi, L. Gregoratti, G. Comelli, V.R. Dhanak, M. Kiskinova and R. Rosei 99 (1996) 1
- Surface composition of CVD-grown α -SiC layers - an XPS and LEED study, H. Behner and R. Rupp 99 (1996) 27
- CuCl growth on the reconstructed surface of (0001) haematite, Q. Guo, L. Gui and N. Wu 99 (1996) 229
- Behavior of zirconium on ZrO/W(100) surface, H. Satoh, H. Nakane and H. Adachi 100/101 (1996) 216
- Sn segregation to the low index surfaces of a copper single crystal, J. du Plessis and E.C. Viljoen 100/101 (1996) 222
- Co overlayer formation process on Si(100)2 \times 1 studied by SR-PES, T. Jikimoto, C. Heck, K. Komoku, M. Hirai, M. Kusaka and M. Iwami 100/101 (1996) 513
- CHF₃ adsorption and decomposition on clean and oxygen covered Al(111), H. Kawada, S. Reiff and J.H. Block 100/101 (1996) 587

Luminescence

- Study of Ag thin films deposited on porous silicon, T.F. Young, J.F. Liu, C.C. Wu, G.H. Fu and C.S. Chen 92 (1996) 57
- Epitaxial growth of ZnSe_xTe_{1-x} by the VPE method and its photoluminescence, K. Mochizuki, H. Oguri, T. Kyotani and M. Isshiki 92 (1996) 79
- The electrical and optical characteristics of GaAs on Si by modified flow rate modulation epitaxy, M.K. Lee, C.C. Hu, and C.Z. Hwang 92 (1996) 159
- PL properties of porous Si anodized with various light illuminations, H. Mimura, T. Matsumoto and Y. Kanemitsu 92 (1996) 396
- The influence of residual O₂ gas in vacuum on the structural and luminescent properties of ZnF₂:Mn thin films, Y. Nakanishi, S. Naito, T. Nakamura, Y. Hatanaka and G. Shimaoka 92 (1996) 400
- High quality quantum dots fabricated by molecular beam epitaxy, C.-P. Lee and D.-C. Liu 92 (1996) 519
- Stimulated blue emission processes in Zn_{1-x}Cd_xSe/ZnSe multi-quantum wells, J.Y. Jen, T. Tsutsumi, I. Souma, Y. Oka, J.R. Anderson and M. Gorska 92 (1996) 547
- Diffusion phenomena in MBE grown Si/SiGe single quantum wells studied by PL and TEM measurements, H.P. Zeindl, S. Nilsson and E. Bugiel 92 (1996) 552
- Light emission from the porous boron δ -doped Si superlattice, T.-C. Chang, W.-K. Yeh, M.-Y. Hsu, C.-Y. Chang, C.-P. Lee, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 571
- Electroluminescence in thin films, R.H. Mauch 92 (1996) 589
- Si-based optical devices using porous materials, H. Mimura, T. Matsumoto and Y. Kanemitsu 92 (1996) 598
- Ruthenium and sulphide passivation of GaAs, S.T. Ali, S. Ghosh and D.N. Bose 93 (1996) 37
- Plasma anodic oxidation of semiinsulating GaAs, E. Pinčik, K. Gmucová, J. Bartoš, M. Kučera, M. Jergel and R. Brunner 93 (1996) 119
- Determination of the subband carrier densities in a strained GaAs/In_{0.15}Ga_{0.85}As/Al_{0.22}Ga_{0.78}As single quantum well using photoluminescence, T.W. Kim, M. Jung and D.U. Lee 93 (1996) 131
- Relationship between organic thin film uniformity and its electroluminescence, G. Wang, Y. Ding and Y. Wei 93 (1996) 281

- Optical spectroscopy of emission from Si-SiO_x nanoclusters formed by laser ablation, I.A. Movtchan, W. Marine, R.W. Dreyfus, H.C. Le, M. Sentis and M. Autric 96-98 (1996) 251
- Laser-induced formation of visible light emitting silicon, D. Dimova-Malinovska, M. Tzolov, N. Malinowski, Ts. Marinova and V. Krastev 96-98 (1996) 457
- Excited state relaxation processes of MALDI-matrices studied by luminescence spectroscopy, H. Ehring and B.U.R. Sundqvist 96-98 (1996) 577
- Infrared chemiluminescence study of the dynamics of catalytic oxidation of CO and HCOOH on Pd(111) and polycrystalline Pd surfaces, K. Watanabe, H. Uetsuka, H. Ohnuma and K. Kunimori 99 (1996) 411
- Luminescent properties of an anodically oxidized P-doped silicon wafer, M. Iwasa and T. Arakawa 100/101 (1996) 147
- Angular resolved EPMA analysis of thin films prepared by pulsed laser ablation of CdWO₄(010), K. Tanaka, N. Yokota, N. Shirai, Q. Zhuang and R. Nakata 100/101 (1996) 264
- Molecular beam epitaxy of GaAs/Al_xGa_{1-x}As/In_yGa_{1-y}As heterostructures for opto-electronic devices: control of growth parameters, K. Köhler 100/101 (1996) 383
- Synthesis of metastable group-IV alloy semiconductors by ion implantation and ion-beam-induced epitaxial crystallization, N. Kobayashi, M. Hasegawa, N. Hayashi, H. Katsumata, Y. Makita, H. Shibata and S. Uekusa 100/101 (1996) 498
- Photoluminescence enhancement of (NH₄)₂S_x passivated InP surface by rapid thermal annealing, W.D. Chen, X.Q. Li, L.H. Duan, X.L. Xie and Y.D. Cui 100/101 (1996) 592
- Correlation between cathodoluminescence and structural defects in ZnS/GaAs(100) and ZnSe/GaAs(100) studied by transmission electron microscopy, T. Mitsui, N. Yamamoto, J. Yoshino, T. Tadokoro, S. Ohta, K. Yanashima and K. Inoue 100/101 (1996) 625
- Aluminum doping of ZnTe grown by MOVPE, S.I. Gheyas, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 634
- Growth of high-quality ZnTe layers by MOVPE, S.I. Gheyas, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 647
- Preparation and photoluminescent characteristics of Zn_xSr_{1-x}:S:Ce thin films, S.T. Lee, M. Kitagawa, K. Ichino and H. Kobayashi 100/101 (1996) 656

Magnesium

- Precipitation processes during the early stages of ageing in Al-Cu-Mg alloys, S.P. Ringer, K. Hono, I.J. Polmear and T. Sakurai 94/95 (1996) 253

Magnesium oxide

- Cubic metastable FeSi_{1-x} epitaxially grown on Si and MgO substrates, S. Degroote, A. Vantomme, J. Dekoster and G. Langgouche 91 (1995) 72
- Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on MgO(001), H. Qiu, T. Ohbuchi, H. Nakai and M. Hashimoto 92 (1996) 47
- Atomic-scale studies of silver segregation at MgO/Cu heterophase interfaces, D.A. Shashkov and D.N. Seidman 94/95 (1996) 416
- The role of defects in laser induced positive ion emission from ionic crystals, J.T. Dickinson, J.-J. Shin and S.C. Langford 96-98 (1996) 316

Magnetic measurements

- Some physical properties of ReSi_{1.75} single crystals, U. Gottlieb, M. Affronte, F. Nava, O. Laborde, A. Sulpice and R. Madar 91 (1995) 82
- Angular dependence of the magnetoresistance of TiSi₂ single crystals, M. Affronte, O. Laborde, U. Gottlieb, O. Thomas and R. Madar 91 (1995) 98
- Coercivity of γ-(Fe_{0.74}Mn_{0.15}Co_{0.11})₂O₃ thin films by dc reactive magnetron sputtering, W.-D. Chang and T.-S. Chin 92 (1996) 475

Magnetic structures

- Ferrimagnetic thin films prepared by pulsed laser deposition, M. Guyot, A. Lisfi, R. Krishnan, M. Porte, P. Rougier and V. Cagan 96-98 (1996) 802
- Pulsed Laser Deposition of permanent magnetic Nd₂Fe₁₄B thin films, A.J.M. Geurtsen, J.C.S. Kools, L. de Wit and J.C. Lodder 96-98 (1996) 887

Manganese

- Structural characterization of epitaxial ferromagnetic MnSb layers grown by hot-wall epitaxy, H. Tatsuoka, H. Kuwabara,

- M. Oshita, Y. Nakanishi, T. Nakamura and H. Fujiyasu
The influence of residual O_2 gas in vacuum on the structural and luminescent properties of $ZnF_2:Mn$ thin films, Y. Nakanishi, S. Naito, T. Nakamura, Y. Hatanaka and G. Shimaoka 92 (1996) 382
- Effect of substrate-film interface on magnetic properties of Mn_4N films, K.-M. Ching, W.-D. Chang and T.-S. Chin 92 (1996) 400
- Coercivity of $\gamma-(Fe_{0.74}Mn_{0.15}Co_{0.11})_2O_3$ thin films by dc reactive magnetron sputtering, W.-D. Chang and T.-S. Chin 92 (1996) 471
- Characterisation of the spinels $M_xCo_{1-x}Fe_2O_4$ ($M = Mn, Fe$ or Ni) using X-ray photoelectron spectroscopy, G.C. Allen and K.R. Hallam 93 (1996) 25
- An atom probe study of cementite precipitation in autotempered martensite in an Fe-Mn-C alloy, R.C. Thomson and M.K. Miller 94/95 (1996) 313
- ### Mass spectroscopy
- Surface reaction mechanism in MOCVD, J. Nishizawa, H. Sakuraba and T. Kurabayashi 92 (1996) 89
- Investigation of atomic deuterium (hydrogen) emission from the surface of some transition metal deuterides (hydrides), E. Nowicka, Z. Wolfram, W. Lisowski and R. Duś 93 (1996) 53
- Studies of silicon-nitride (Si_3N_4) using laser ablation mass spectrometry, S.L. Wang, K.W.D. Ledingham, W.J. Jia and R.P. Singhal 93 (1996) 205
- Pulsed field desorption mass spectrometric study of the oxidation of hydrogen-doped Ni_2Zr , T.R. Hess, D.L. Cocke, G. Abend and J.H. Block 94/95 (1996) 238
- Transport of neutral atoms, monoxides and clusters in the plume produced by laser ablation of $YBa_2Cu_3O_{7-x}$ in oxygen environment, A.V. Bulgakov, M.R. Predtechensky and A.P. Mayorov 96-98 (1996) 159
- Laser produced plasmas in high fluence ablation of metallic surfaces probed by time-of-flight mass spectrometry, S. Amoruso, A. Amodio, V. Berardi, R. Bruzzese, N. Spinelli and R. Velotta 96-98 (1996) 175
- Energy-dispersive mass spectrometry of high energy ions generated during KrF excimer and frequency-doubled Nd:YAG laser ablation of metals, G.C. Tyrrell, L.G. Coccia, T.H. York and I.W. Boyd 96-98 (1996) 227
- Soft laser sputtering of the GaAlAs (100) surface, L. Vivet, B. Dubreuil, T. Gilbert-Legrand and M.F. Barthe 96-98 (1996) 238
- Magnetic field enhanced growth of carbon cluster ions in the laser ablation plume of graphite, F. Kokai, Y. Koga and R.B. Heimann 96-98 (1996) 261
- Formation of large carbon cluster ions at graphite (HOPG) surfaces by laser irradiation, H. Togashi, K. Saito, Y. Koga, H. Yamawaki, K. Aoki, M. Mukaida and T. Kameyama 96-98 (1996) 267
- The role of defects in laser induced positive ion emission from ionic crystals, J.T. Dickinson, J.-J. Shin and S.C. Langford 96-98 (1996) 316
- Laser-induced emission of neutral atoms and molecules from electron-irradiated $NaNO_3$, J.T. Dickinson, J.J. Shin and S.C. Langford 96-98 (1996) 326
- Decomposition mechanisms of thin palladium acetate film with excimer UV radiation, J.-Y. Zhang, H. Esrom and I.W. Boyd 96-98 (1996) 399
- CCl_4 -assisted CF_4 etching of silicon in a microwave-assisted LDE (laser dry etching)-process, W. Pflöging, D.A. Wesner and E.W. Kreutz 96-98 (1996) 496
- Excited state relaxation processes of MALDI-matrices studied by luminescence spectroscopy, H. Ehring and B.U.R. Sundqvist 96-98 (1996) 577
- High sensitivity quadrupole mass spectrometry of neutrals sputtered by UV-laser ablation of polymers, S. Lazare, W. Guan and D. Drillhole 96-98 (1996) 605
- In-situ IR and mass spectroscopic study of the $Al(CH_3)_3/H/a-Si:H$ reaction processes, T. Wadayama, Y. Maiwa, H. Shibata and A. Hattai 100/101 (1996) 575
- ### Mercury
- The adsorption and condensation of $Hg(CH_3)_2$ on $Pt(111)$ at 95 and 310 K: an UPS study, A. Cassuto 93 (1996) 17
- Investigation of vaporization and condensation processes of thin layers of $CdHgTe$ from laser erosion plasma in Hg atmosphere, B.K. Kotlyarchuk, D.I. Popovych, V.K. Savchuk and V.G. Savitsky 96-98 (1996) 192
- Deposition of $HgCdTe$ epitaxial layers on anisotropically etched silicon surfaces by laser evaporation, T.Ya. Gorbach, M. Kuźma, E. Sheregii, P.S. Smertenko, S.V. Svechnikov and G. Wiaz 96-98 (1996) 881

Metal-oxide-semiconductor structure (MOS)

- Advanced copper interconnections for silicon CMOS technologies, J. Torres 91 (1995) 112
- Integration of a TiN barrier layer formed by rapid thermal annealing in a 1 μm CMOS process, K.-H. Stegmann, V. Heinig, G. Fontaine, J. Palorec and C. Beyer 91 (1995) 308
- A highly reliable, low cost 0.5 μm three level tungsten metallization, M. Hain, H. Körner, B. Neureither and S. Röhl 91 (1995) 374
- Ultra-thin gate dielectrics grown by low-temperature processes for applications to ULSI devices, H.-L. Hwang, P.-C. Chen and K.Y.J. Hsu 92 (1996) 180
- Application of irradiation-then-nitridation to improve the radiation hardness in MOS gate dielectrics, K.-C. Lee and J.-G. Hwu 92 (1996) 204
- Rapid thermal post-metallization annealing effect on thin gate oxides, M.-J. Jeng, H.-S. Lin and J.-G. Hwu 92 (1996) 208

Metals

- Advanced multilevel metallization technology, T. Ohba 91 (1995) 1
- Cluster beams for metallization of microstructured surfaces, P. Gatz and O.F. Hagena 91 (1995) 169
- Some particular features of the condensation process, structure and properties of thin metal films caused by self-ion bombardment, I.V. Gusev, A.A. Mohnjuk, V.I. Chapljuk and V.P. Belevsky 91 (1995) 182
- Advanced metallization technology for 256M DRAM, P. Kücher, H. Aochi, J. Gambino, T. Licata, T. Matsuda, S. Nguyen, M. Okazaki, H. Palm and M. Ronay 91 (1995) 359
- Optical diagnostics of the laser-target and laser-plume interaction in pulsed laser ablation, F. Fuso, L.N. Vyacheslavov, G. Lorenzi, M. Allegrini and E. Arimondo 96-98 (1996) 181
- Laser ablation of metals: the transition from non-thermal processes to thermal evaporation, T. Götz, M. Bergt, W. Hoheisel, F. Träger and M. Stuke 96-98 (1996) 280
- Surface temperature measurements during pulsed laser action on metallic and ceramic materials, M.B. Ignatiev, I.Yu. Smurov, G. Flamant and V.N. Senchenko 96-98 (1996) 505
- Pulsed laser deposition of novel materials for thin film solid oxide fuel cell applications: $\text{Ce}_{0.9}\text{Gd}_{0.1}\text{O}_{1.95}$, $\text{La}_{0.7}\text{Sr}_{0.3}\text{Co}$

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- Growth of oxide films on metal surfaces: transition from parabolic to linear kinetics, V.P. Zhdanov and P.R. Norton 99 (1996) 205

Metal-semiconductor interfaces

- Chemical trends of barrier heights in metal-semiconductor contacts: on the theory of the slope parameter, W. Mönch 92 (1996) 367

Methane

- Dissociative chemisorption of methane on clean and oxygen precovered $\text{Pt}(111)$, M. Valden, N. Xiang, J. Pere and M. Pessa 99 (1996) 83
- CHF_3 adsorption and decomposition on clean and oxygen covered $\text{Al}(111)$, H. Kawada, S. Reiff and J.H. Block 100/101 (1996) 587

Mica

- The etching of natural alpha-recoil tracks in mica with an argon RF-plasma discharge and their imaging via atomic force microscopy, N.M.D. Brown and Z.H. Liu 93 (1996) 89
- Preparation of thin silver films on mica studied by XRD and AFM, J.-D. Grunwaldt, F. Atamny, U. Göbel and A. Bäiker 99 (1996) 353

Molecular beam epitaxy

- Novel method of strain-relaxed $\text{Si}_{1-x}\text{Ge}_x$ growth on $\text{Si}(100)$ by MBE, H. Iwano, K. Yoshikawa, A. Kojima, K. Hayashi, S. Zaima and Y. Yasuda 100/101 (1996) 487
- Routine measurement of the absolute As_4 flux in a molecular beam epitaxy system with conventional RHEED equipment, Ch. Heyn and M. Harsdorff 100/101 (1996) 494
- Comparison of MOCVD and MBE semiconductor superlattices for the evaluation of depth resolution in AES and SIMS, M. Furuya, M. Soga and H. Takano 100/101 (1996) 508

Molecular dynamics

- Interaction of a void and a grain boundary under a high electric current stress em-

- playing three-dimensional molecular dynamics simulation, S. Shingubara, I. Utsumiya and T. Takahagi 91 (1995) 220
- Atomistic dynamics of interfacial processes: films, junctions and nanostructures, U. Landman and W.D. Luedtke 92 (1996) 237
- ### Molybdenum
- The determination of the average compositions of amorphous interlayers in the V/Si system using a buried ultrathin oxide layer and a capping Mo layer to define the reference planes for interdiffusion, J.H. Lin and L.J. Chen 92 (1996) 340
- Novel epitaxial growth and magnetotransport characterization of single crystal Co(1120)/Cr(100) superlattices on Mo buffer layers, J.C.A. Huang, Y.D. Yao, Y. Liou, S.F. Lee, W.T. Yang, C.P. Chang, S.Y. Liao and C.H. Lee 92 (1996) 480
- XPS study of as-prepared and reduced molybdenum oxides, J.-G. Choi and L.T. Thompson 93 (1996) 143
- EXAFS measurements on the structure of Mo/Si multilayers produced using ion bombardment and increased deposition temperature, H.-J. Voorma, G.E. van Dorssen, E. Louis, N.B. Koster, A.D. Smith, M.D. Roper and F. Bijkerk 93 (1996) 221
- Diamond coated Si and Mo field emitters: diamond thickness effect, V.V. Zhimov, W.B. Choi, J.J. Cuomo and J.J. Hren 94/95 (1996) 123
- Precipitation and grain boundary segregation in molybdenum-doped NiAl, M.K. Miller, I.M. Anderson and K.F. Russell 94/95 (1996) 288
- Observation of both Ni and Mo atom images by FIM with imaging plates, K. Nishikawa, T. Nishiuchi, M. Yamamoto and O. Nishikawa 94/95 (1996) 295
- Observation of molybdenum-nitrogen clustering in highly alloyed martensite, L. Lundin and H.-O. Andr n 94/95 (1996) 320
- Atom probe analysis of carbonitride grains in (Ti, W, Ta, Mo)(C, N)(Co/Ni) cermets with different carbon content, J. Zackrisson, M. Thuvander, P. Lindahl and H.-O. Andr n 94/95 (1996) 351
- Time-of-flight SIMS study of Bi-Mo selective oxidation catalysts, L.T. Weng, P. Bertrand, O. Tirions and M. Devillers 99 (1996) 185
- High sensitivity of positron-annihilation induced Auger-electron spectroscopy to surface impurities, T. Ohdaira, R. Suzuki, T. Mikado, H. Ohgaki, M. Chiwaki, T. Yamazaki and M. Hasegawa 100/101 (1996) 73
- Determination of the interface region in multilayer Si/Mo by Auger depth profile and factor analysis, T. Morohashi, T. Hoshi, H. Nikaido and M. Kudo 100/101 (1996) 84
- Soft X-ray emissions by highly charged ions on solid surfaces: Mo and Ta surfaces, T. Emoto, K. Komatsu, A. Ichimiya, S. Ninomiya and M. Sekiguchi 100/101 (1996) 355
- ### Monte Carlo simulations
- Computer simulation of nucleation on (001) Kossel crystal surface with and without diffusion, T.B. Tang 92 (1996) 257
- Intrinsic Auger signal profiles derived by Monte Carlo analysis, Z.-J. Ding, R. Shimizu and K. Goto 100/101 (1996) 15
- The influence of elastic scattering on the concentration dependence of the photoelectron line intensity, I.S. Tilinin, A. Jablonski and B. Lesiak-Orlowska 100/101 (1996) 20
- Calculations of 'effective' inelastic mean free paths in solids, S. Tanuma, S. Ichimura and K. Yoshihara 100/101 (1996) 47
- Monte Carlo simulation of ion-induced kinetic electron emission from a metal surface, J. Kawata and K. Ohya 100/101 (1996) 338
- ### M ssbauer spectroscopy
- Corrosion of iron by a perfluoropolyalkylether identified by M ssbauer spectroscopy, G. John, J.S. Zabinski and V.K. Gupta 93 (1996) 329
- ### Multilayers
- A technological evolution from bulk crystalline age to multilayered thin film age in optoelectronic devices, Y. Hamakawa 92 (1996) 1
- Recent advances in island and multilayer growth of metals on metals far from equilibrium, G. Vidali and H. Zeng 92 (1996) 11
- Properties of multilayered thin films for thermal ink-jet printing devices, D.S. Wu, M.L. Lee and T.Y. Lin 92 (1996) 626
- EXAFS measurements on the structure of Mo/Si multilayers produced using ion bombardment and increased deposition temperature, H.-J. Voorma, G.E. van Dorssen, E. Louis, N.B. Koster, A.D. Smith, M.D. Roper and F. Bijkerk 93 (1996) 221
- Characterization of sputter-deposited multilayers of Ni and Zr with APFIM/TAP, T. Al-Kassab, M.-P. Macht, V. Naundorf, H. Wollenberger, S. Chambrelaud, F. Danoix and D. Blavette 94/95 (1996) 306

- Excimer laser interaction with dielectric thin films, E. Welsch, K. Ettrich, H. Blaschke and N. Kaiser 96-98 (1996) 393
- Ultrathin film deposition by pulsed laser ablation using crossed beams, A.A. Gorbunov, W. Pompe, A. Sewing, S.V. Gaponov, A.D. Akhsakhlyan, I.G. Zabrodin, I.A. Kas'kov, E.B. Klyenkov, A.P. Morozov, N.N. Salaschenko, R. Dietsch, H. Mai and S. Völlmar 96-98 (1996) 649
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- XPS study of carbon/inconel bilayers as a function of substrate bias, M.S. Aouadi, P.C. Wong and K.A.R. Mitchell 99 (1996) 319
- Auger electron spectroscopy measurement of electron attenuation lengths using multilayer systems, M. Suzuki, K. Mogi and H. Takenaka 100/101 (1996) 51
- Determination of the interface region in multilayer Si/Mo by Auger depth profile and factor analysis, T. Morohashi, T. Hoshi, H. Nikaïdo and M. Kudo 100/101 (1996) 84
- Oxide thin films formed during rotational AES sputter depth profiling of Ni/Cr multilayers using oxygen ions, A. Zalar, E.W. Seibt and P. Panjan 100/101 (1996) 92
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- Ni silicides formation and properties in RF sputtered $\text{Ni}_{100-x}\text{-Si}_x$ thin films, A. Belu-Marian, M.D. Serbanescu, R. Manaila and A. Devenyi 91 (1995) 63
- Phonon dispersion relations of metallic NiSi_2 and CoSi_2 by semi-empirical tight-binding calculation, S. Sanguinetti, C. Calegari and L. Miglio 91 (1995) 103
- Metallurgical and electrical investigation of $\text{Pt}_5\text{Ni}_{95}$ /silicon interactions, F. Corni, C. Nobili, G. Ottaviani, R. Tonini, B. Grignaffini Gregorio and G. Queirolo 91 (1995) 107
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- Growth mechanism of Ni on Pt(110) at low temperature, C.S. Shern, J.S. Tsay and T. Fu 92 (1996) 74
- Characterisation of the spinels $\text{M}_2\text{Co}_{1-x}\text{Fe}_2\text{O}_4$ (M = Mn, Fe or Ni) using X-ray photoelectron spectroscopy, G.C. Allen and K.R. Hallam 93 (1996) 25
- The oxidation of the NiAl(111) surface, R. Franchy, J. Masuch and P. Gassmann 93 (1996) 317
- Pulsed field desorption mass spectrometric study of the oxidation of hydrogen-doped Ni_3Zr , T.R. Hess, D.L. Cocke, G. Abend and J.H. Block 94/95 (1996) 238
- Atomic scale investigation of ordering and precipitation processes in a model Ni-Cr-Al alloy, C. Schmuck, F. Danoix, P. Caron, A. Hauet and D. Blavette 94/95 (1996) 273
- Precipitation and grain boundary segregation in molybdenum-doped NiAl, M.K. Miller, I.M. Anderson and K.F. Russell 94/95 (1996) 288
- Observation of both Ni and Mo atom images by FIM with imaging plates, K. Nishikawa, T. Nishiuchi, M. Yamamoto and O. Nishikawa 94/95 (1996) 295
- Characterization of sputter-deposited multilayers of Ni and Zr with APFIM/TAP, T. Al-Kassab, M.-P. Macht, V. Naundorf, H. Wollenberger, S. Chambrelaud, F. Danoix and D. Blavette 94/95 (1996) 306
- Grain boundary precipitation and segregation in Ni-16Cr-9Fe model materials, M. Thuvander, K. Stiller, D. Blavette and A. Menand 94/95 (1996) 343
- Atom probe analysis of carbonitride grains in (Ti, W, Ta, Mo)(C, N)(Co/Ni) cermets with different carbon content, J. Zackrisson, M. Thuvander, P. Lindahl and H.-O. Andréén 94/95 (1996) 351
- Comparison of the rate of decomposition in Fe-45%Cr, Fe-45%Cr-5%Ni and duplex stainless steels, M.K. Miller and K.F. Russell 94/95 (1996) 398
- Picosecond UV-laser ablation of Au and Ni films, A. Rosenfeld and E.E.B. Campbell 96-98 (1996) 439
- Interface chemistry and electric characterisation of nickel metallisation on 6H-SiC, Ts. Marinova, V. Krastev, C. Hallin, R. Yakimova and E. Janzén 99 (1996) 119
- XPS study of carbon/inconel bilayers as a function of substrate bias, M.S. Aouadi, P.C. Wong and K.A.R. Mitchell 99 (1996) 319
- True Auger spectral shapes (standards), Y. Takeichi, K. Goto and V. Gaidarova 100/101 (1996) 25
- Oxide thin films formed during rotational AES sputter depth profiling of Ni/Cr multilayers using oxygen ions, A. Zalar, E.W. Seibt and P. Panjan 100/101 (1996) 92
- Niobium**
- Some particular features of the condensation process, structure and properties of thin metal films caused by self-ion bombardment, I.V. Gusev, A.A. Mohnjuk, V.I. Chaptjuk and V.P. Belevsky 91 (1995) 182

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- Comparative studies on enhanced field emission from mechanically and chemically polished broad-area Nb, Cu, and Al cathodes, N. Pupeter, T. Habermann, A. Kirschner, E. Mahner, G. Müller and H. Piel 94/95 (1996) 94
- Fabrication of transition metal nitride field emitters, M. Endo, H. Nakane and H. Adachi 94/95 (1996) 113
- Nanocrystallization of a Co-Nb-B-C metallic glass, T.A. Lusby and A.J. Melmed 94/95 (1996) 300
- Time-of-flight characterization of laser ablation plume from NbTe₂ target in He atmosphere, F. Grangeon, H. Sassoli, W. Marine and M. Autric 96-98 (1996) 186

Nitric oxide

- The influence of impurities contained in quartz sand on the catalytic reduction of nitric oxide by carbon monoxide, P. Schoderböck and J. Lahaye 93 (1996) 109
- Laser-induced emission of neutral atoms and molecules from electron-irradiated NaNO₃, J.T. Dickinson, J.J. Shin and S.C. Langford 96-98 (1996) 326
- NO interaction with thermally activated CaO and SrO surfaces, Y. Yanagisawa 100/101 (1996) 256

Nitrides

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- Characteristics of PECVD GaN thin films, C.H. Lee and C.T. Chen 92 (1996) 124
- Effect of substrate-film interface on magnetic properties of Mn₄N films, K.-M. Ching, W.-D. Chang and T.-S. Chin 92 (1996) 471
- Carbon nitride - prospects for ultimate performance of superhard materials, S.A. Uglov, V.E. Shub, A.A. Beloglazov and V.I. Konov 92 (1996) 656
- Microstructural properties of laser synthesized Si/C/N nanoparticles, R. Giorgi, S. Turtù, G. Zappa, E. Borsella, S. Botti, M.C. Cesile and S. Martelli 93 (1996) 101
- Atom probe analysis of carbonitride grains in (Ti, W, Ta, Mo)(C, N)(Co/Ni) cermets with different carbon content, J.

- Zackrisson, M. Thuvander, P. Lindahl and H.-O. André 94/95 (1996) 351
- Laser induced nitridation of Ga on GaAs surfaces, M.F. Barthe, C. Perrin, L. Vivet, B. Dubreuil and T. Gibert 96-98 (1996) 359
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- Diffusion barrier property of TaN between Si and Cu, T. Oku, E. Kawakami, M. Uekubo, K. Takahiro, S. Yamaguchi and M. Murakami 99 (1996) 265
- Chemical, mechanical and electrical properties of CN_x-films produced by reactive sputtering and N⁺-implantation in carbon films, N. Laidani, A. Miotello and J. Perrière 99 (1996) 273
- The effect of EB irradiation with and without hot-jet Cl₂ on an ultra-thin GaN layer for selective etching, S. Yoshida, M. Sasaki and T. Ishikawa 100/101 (1996) 184
- In situ observation of nitridation of GaAs (001) surfaces by infrared reflectance spectroscopy, K. Uwai, Y. Yamauchi and N. Kobayashi 100/101 (1996) 412
- Microwave plasma assisted LCDVD growth and characterization of GaN, B. Zhou, X. Li, T.L. Tansley and K.S.A. Butcher 100/101 (1996) 643
- Fabrication of transition metal nitride field emitters, M. Endo, H. Nakane and H. Adachi 94/95 (1996) 113

Nitrogen

- Microstructural properties of laser synthesized Si/C/N nanoparticles, R. Giorgi, S. Turtù, G. Zappa, E. Borsella, S. Botti, M.C. Cesile and S. Martelli 93 (1996) 101
- Noble-gas-like mechanism of localized field ionization of nitrogen as detected by field ion appearance energy spectroscopy, Yu. Suchorski, V.K. Medvedev and J.H. Block 94/95 (1996) 217
- Observation of molybdenum-nitrogen clustering in highly alloyed martensite, L. Lundin and H.-O. André 94/95 (1996) 320
- Nitridation of GaAs surfaces using nitrogen molecules cracked by a hot tungsten filament, T. Makimoto and N. Kobayashi 100/101 (1996) 403

Nitrogen dioxide

- Oscillatory behavior in the catalytic reduction of NO and NO₂ with hydrogen on

- Pt field emitter tips, C. Voss and N. Kruse 94/95 (1996) 186
- Nitrous oxide*
- Oscillatory behavior in the catalytic reduction of NO and NO₂ with hydrogen on Pt field emitter tips, C. Voss and N. Kruse 94/95 (1996) 186
- Noble gases*
- Growth and reactivity of evaporated platinum films on Cu(111): a study by AES, RHEED and adsorption of carbon monoxide and xenon, J. Fusy, J. Menucourt, M. Alnot, C. Huguet and J.J. Ehrhardt 93 (1996) 211
- Nuclear reaction analysis*
- The oxidation of Cu particles supported on oxidised Si(100) as studied by nuclear reaction analysis and ellipsometry, R. van Wijk, P.C. Görts, C.H.M. Marée, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 99 (1996) 127
- ¹⁸O-exchange with the substrate during ¹⁸O oxidation of Cu particles supported on ¹⁸O-oxidised Si(100), R. van Wijk, C.H.M. Marée, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 99 (1996) 197
- Optical properties*
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- Electrical and optical properties of thin β-FeSi₂ films on Al₂O₃ substrates, K. Herz and M. Powalla 91 (1995) 87
- The electrical and optical characteristics of GaAs on Si by modified flow rate modulation epitaxy, M.K. Lee, C.C. Hu, and C.Z. Hwang 92 (1996) 159
- Diffusion length measurements on electrodeposited CuInSe₂ cells, S.N. Qiu, C.X. Qiu and I. Shih 92 (1996) 306
- Refractive index behavior of boron-doped silica films by plasma-enhanced chemical vapor deposition, R.H. Horng, F. Chen, D.S. Wu and T.Y. Lin 92 (1996) 387
- Structural and optical properties of Pd_{1-x}In_x thin films, W.T. Wu, P.E. Schmid and F. Lévy 92 (1996) 391
- Study of the internal electric fields across the interfaces in the GaAs/(Al,Ga)As microstructures, C.R. Lu, C.L. Chang, C.H. Liou, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 404
- Study of biochemical reactions in thin organic films by means of evanescent optical wave, T.I. Ksenevich, A.A. Beloglazov, P.I. Nikitin, N.A. Kalabina and S.Yu. Zaitsev 92 (1996) 426
- Photorefectance study of GaAs/Al_{0.3}Ga_{0.7}As resonant asymmetric double quantum wells with Si δ-doping in side barriers, C.R. Lu, S.K. Du, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 543
- Improvement of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, T. Ogura, K. Doi and S. Gonda 92 (1996) 566
- Electrostatic probe and optical spectroscopy studies of low temperature laser produced plasmas, J.M. Hendron, R.A. Al-Wazzan, C. Mahony, T. Morrow and W.G. Graham 96-98 (1996) 112
- Optical spectroscopy of emission from Si-SiO_x nanoclusters formed by laser ablation, I.A. Movtchan, W. Marine, R.W. Dreyfus, H.C. Le, M. Sentis and M. Autric 96-98 (1996) 251
- Excimer laser interaction with dielectric thin films, E. Welsch, K. Eitrich, H. Blaschke and N. Kaiser 96-98 (1996) 393
- Electrical and optical characteristics of organic thin films fabricated by laser ablation, T. Fujii, H. Shima, N. Matsumoto and F. Kannari 96-98 (1996) 625
- In-situ reflectivity measurements during pulsed-laser deposition of Bi₂Sr₂CaCu₂O_{8-x}, A. Ritzler, B. Falkner, S.T. Li and D. Bäuerle 96-98 (1996) 721
- Deposition of optical coatings by pulsed laser ablation, G. Reisse, S. Weissmantel, B. Keiper and U. Broulik 96-98 (1996) 752
- Molecular orientation of polyimide films determined by an optical retardation method, K. Sakamoto, R. Arafune, S. Ushioda, Y. Suzuki and S. Morokawa 100/101 (1996) 124
- Oxygen adsorption on hydrogen-preadsorbed Si(111)7 × 7 observed by second harmonic generation (SHG), K. Nakamura, S. Ichimura and H. Shimizu 100/101 (1996) 444
- Doping dependence of second harmonic generation from native oxide/Si(111)

- interfaces, H. Hirayama, K. Watanabe and M. Kawada 100/101 (1996) 460
- Organic substances*
- Corrosion inhibition of iron in 1M HCl by 1-phenyl-5-mercapto-1,2,3,4-tetrazole, S. Kertit and B. Hammouti 93 (1996) 59
- Scanning tunneling microscopy observations of recorded organic thin films, Q. Chen, D. Gu, F. Gan, L. Xu and M. Li 93 (1996) 151
- Relationship between organic thin film uniformity and its electroluminescence, G. Wang, Y. Ding and Y. Wei 93 (1996) 281
- Electrical and optical characteristics of organic thin films fabricated by laser ablation, T. Fujii, H. Shima, N. Matsumoto and F. Kannari 96-98 (1996) 625
- X-ray photoelectron spectroscopy of Cr/COOCH₃ interfaces on self-assembled monolayers of 16-mercaptohexadecanoate, D.R. Jung and A.W. Czanderma 99 (1996) 161
- Organometallic vapour deposition*
- Growth of high-quality ZnTe layers by MOVPE, S.I. Gheyas, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 647
- Oxidation*
- Investigation of the oxidation behaviour of thin film and bulk copper, M. O'Reilly, X. Jiang, J.T. Beechinor, S. Lynch, C. Ni Dheasuna, J.C. Patterson and G.M. Crean 91 (1995) 152
- Electrocatalytic activities of proton-exchanged layered oxides for the anodic oxidation on the solid oxide fuel cell, K. Sato, S. Nomura and Y. Inoue 92 (1996) 639
- Plasma anodic oxidation of seminsulating GaAs, E. Pinčík, K. Gmucová, J. Bartoš, M. Kučera, M. Jergel and R. Brunner 93 (1996) 119
- Ellipsometric studies of the oxidation kinetics of Cu particles supported on oxidised Si(100), R. van Wijk, O.L.J. Gijzeman and J.W. Geus 93 (1996) 237
- Temperature effects in the early stages of titanium oxidation, I. Vaquila, M.C.G. Passeggi, Jr. and J. Ferrón 93 (1996) 247
- Gas-phase room-temperature oxidation of (100) silicon, G.F. Cerofolini, G. La Bruna and L. Meda 93 (1996) 255
- The oxidation of the NiAl(111) surface, R. Franchy, J. Masuch and P. Gassmann 93 (1996) 317
- Pulsed field desorption mass spectrometric study of the oxidation of hydrogen-doped Ni₃Zr, T.R. Hess, D.L. Cocke, G. Abend and J.H. Block 94/95 (1996) 238
- Etching and functionalization of a fluorocarbon polymer by UV laser treatment, C. Girardeaux, Y. Idrissi, J.J. Pireaux and R. Caudano 96-98 (1996) 586
- CO adsorption and CO oxidation on Rh(100), A. Baraldi, L. Gregoratti, G. Comelli, V.R. Dhanak, M. Kiskinova and R. Rosei 99 (1996) 1
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- The oxidation of Cu particles supported on oxidised Si(100) as studied by nuclear reaction analysis and ellipsometry, R. van Wijk, P.C. Görts, C.H.M. Marée, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 99 (1996) 127
- Time-of-flight SIMS study of Bi-Mo selective oxidation catalysts, L.T. Weng, P. Bertrand, O. Tirions and M. Devillers 99 (1996) 185
- ¹⁸O-exchange with the substrate during ¹⁸O oxidation of Cu particles supported on ¹⁶O-oxidised Si(100), R. van Wijk, C.H.M. Marée, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 99 (1996) 197
- Oxidation of ultrathin iron layers grown on Cu(111), C. Ruby and J. Fusy 99 (1996) 393
- Infrared chemiluminescence study of the dynamics of catalytic oxidation of CO and HCOOH on Pd(111) and polycrystalline Pd surfaces, K. Watanabe, H. Uetsuka, H. Ohnuma and K. Kunimori 99 (1996) 411
- Influence of ion-implantation on native oxidation of Si in a clean-room atmosphere, F. Yano, A. Hiraoka, T. Itoga, H. Kojima, K. Kanehori and Y. Mitsui 100/101 (1996) 138
- Luminescent properties of an anodically oxidized P-doped silicon wafer, M. Iwano and T. Arakawa 100/101 (1996) 147
- Initial stage of oxidation of Si(100) surfaces in dry oxygen, K. Inanaga, T. Nakahata, T. Furukawa and K. Ono 100/101 (1996) 421
- Atomically flat, ultra thin-SiO₂/Si(001) interface formation by UHV heating, M. Niwa, K. Okada and R. Sinclair 100/101 (1996) 425
- Initial oxidation of Si(311) surfaces studied by high-resolution electron energy loss spectroscopy, H. Ikeda, T. Yamada, K. Hotta, S. Zaima and Y. Yasuda 100/101 (1996) 431

- High purity ozone oxidation on hydrogen passivated silicon surface, A. Kurokawa and S. Ichimura 100/101 (1996) 436
- Growth kinetics of thermal oxidation process on Si(100) by real time ultraviolet photoelectron spectroscopy, Y. Enta, Y. Takegawa, M. Suemitsu and N. Miyamoto 100/101 (1996) 449
- Initial stages of oxidation of hydrogen-terminated Si surface stored in air, T. Miura, M. Niwano, D. Shoji and N. Miyamoto 100/101 (1996) 454
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- Electrical properties of laser deposited $\text{YBa}_2\text{Cu}_3\text{O}_{7-\delta}$ films on silicon wafers, F.Y. Chuang, C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin 92 (1996) 452
- Coercivity of $\gamma\text{-(Fe}_{0.74}\text{Mn}_{0.15}\text{Co}_{0.11})_2\text{O}_3$ thin films by dc reactive magnetron sputtering, W.-D. Chang and T.-S. Chin 92 (1996) 475
- XPS, AES and LEED studies of Cu deposited on $\text{Cr}_2\text{O}_3(0001)$ surfaces, Q. Guo, L. Gui, P.J. Möller and K. Binau 92 (1996) 513
- Formation of bottom oxides in porous silicon films by anodic oxidation, C.H. Lee, C.C. Yeh, C.H. Lee and K.Y.J. Hsu 92 (1996) 621
- Characterisation of the spinels $\text{M}_2\text{Co}_{1-x}\text{Fe}_2\text{O}_4$ (M = Mn, Fe or Ni) using X-ray photoelectron spectroscopy, G.C. Allen and K.R. Hallam 93 (1996) 25
- An investigation of the Cu/ZnO/Zn system: evidence for the formation of Cu-Zn alloys by the inward diffusion of Cu, K.R. Hari Kumar, A.K. Santra and C.N.R. Rao 93 (1996) 135
- XPS study of as-prepared and reduced molybdenum oxides, J.-G. Choi and L.T. Thompson 93 (1996) 143
- Work function variations and oxygen conduction in a $\text{Pt|ZrO}_2(\text{Y}_2\text{O}_3)\text{|Pt}$ solid electrolyte cell, N.G. Torkelsen and S. Raaen 93 (1996) 199
- Improvement of the crystallinity in PbTiO_3 films grown on indium tin oxide-coated glass by metalorganic chemical vapor deposition using the continuous cooling process, Y.S. Yoon, S.S. Yom, T.W. Kim, D.U. Lee and C.O. Kim 93 (1996) 285
- The chemistry and structure of {22} CdO/Ag heterophase interfaces on an atomic scale, D.K. Chan, D.N. Seidman and K.L. Merkle 94/95 (1996) 409
- Measurement and calculation of the Fe_2O_3 ablation depth, A. Lisfi, M. Guyot, R. Krishnan and V. Cagan 96-98 (1996) 66
- Off-axis excimer laser deposition of Ta_2O_5 thin films, N. Inoue, S. Kashiwabara, S. Toshima and R. Fujimoto 96-98 (1996) 656
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- Laser ablation of oxides: study of the oxygen incorporation by ^{18}O isotopic tracing techniques, R. Pérez Casero, R. Gómez San Román, C. Maréchal, J.P. Enard and J. Perrière 96-98 (1996) 697
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- Epitaxial ferroelectric PZT and BST thin films by pulsed UV laser deposition, C. Champeaux, P. Marchet and A. Catherinot 96-98 (1996) 775
- Pulsed laser deposition of sillenite films intended for photorefractive damage free waveguides, J.E. Alfonso, M.J. Martín, J. Mendiola, K. Polgár and C. Zaldo 96-98 (1996) 791
- Pulsed laser deposition of novel materials for thin film solid oxide fuel cell applications: $\text{Ce}_{0.9}\text{Gd}_{0.1}\text{O}_{1.95}$, $\text{La}_{0.7}\text{Sr}_{0.3}\text{CoO}_y$ and $\text{La}_{0.7}\text{Sr}_{0.3}\text{Co}_{0.2}\text{Fe}_{0.8}\text{O}_y$, L.G. Coccia, G.C. Tyrrell, J.A. Kilner, D. Waller, R.J. Chater and I.W. Boyd 96-98 (1996) 795
- Excimer laser ablating preparation of $\text{Ba}_2\text{NaNb}_3\text{O}_{15}$ thin films on KTiOPO_4 substrate and its guide wave property, J.M. Liu, Z.G. Liu, S.N. Zhu, Y.Y. Zhu and N.B. Ming 96-98 (1996) 819
- $\text{Pb}_{1-x}\text{Ca}_x\text{TiO}_3$ thin films prepared by laser ablation of ceramic targets, M.J. Martín, C. Zaldo and J. Mendiola 96-98 (1996) 823
- XPS and AFM characterization of a vanadium oxide film on $\text{TiO}_2(100)$ surface, G. Chiarello, R. Barberi, A. Amoddeo, L.S. Caputi and E. Colavita 99 (1996) 15
- Growth of oxide films on metal surfaces: transition from parabolic to linear kinetics, V.P. Zhdanov and P.R. Norton 99 (1996) 205
- CuCl growth on the reconstructed surface of (0001) haematite, Q. Guo, L. Gui and N. Wu 99 (1996) 229
- Simultaneous determination of composition and thickness of thin iron-oxide films from XPS Fe 2p spectra, P.C.J. Graat and M.A.J. Somers 100/101 (1996) 36
- Oxide thin films formed during rotational AES sputter depth profiling of Ni/Cr multilayers using oxygen ions, A. Zalar, E.W. Seibt and P. Panjan 100/101 (1996) 92

- Behavior of zirconium on ZrO/W(100) surface, H. Satoh, H. Nakane and H. Adachi 100/101 (1996) 216
- Oxide thickness dependence of photocurrent for the GeO₂/Ge film system, Y. Matsuo and K. Oishi 100/101 (1996) 248
- Water vapor effects on the TeO₂/Te thin film conductance, S. Suehara, T. Hatano and A. Nukui 100/101 (1996) 252
- NO interaction with thermally activated CaO and SrO surfaces, Y. Yanagisawa 100/101 (1996) 256
- Angular resolved EPMA analysis of thin films prepared by pulsed laser ablation of CdWO₄(010), K. Tanaka, N. Yokota, N. Shirai, Q. Zhuang and R. Nakata 100/101 (1996) 264
- Characterization of freeze-dried powders prepared by alkoxide route for YBCO superconductors, T. Tachiwaki, J. Sugimoto, T. Ito and A. Hiraki 100/101 (1996) 272
- Annealing behavior of phosphorus in native oxide films on heavily phosphorus doped silicon, W.B. Ying, Y. Mizokawa, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto 100/101 (1996) 556

Oxygen

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- Oxygen etching of the Si(100)-(2×1) surface, Y. Wei, Y. Hong and I.S.T. Tsong 92 (1996) 491
- Depth profiling of W, O and H in tungsten trioxide thin films using RBS and ERDA techniques, O. Bohnke, G. Frand, M. Fromm, J. Weber and O. Greim 93 (1996) 45
- Work function variations and oxygen conduction in a Pt/ZrO₂(Y₂O₃)/Pt solid electrolyte cell, N.G. Torkelsen and S. Raen 93 (1996) 199
- Laser-induced emission of neutral atoms and molecules from electron-irradiated NaNO₃, J.T. Dickinson, J.J. Shin and S.C. Langford 96-98 (1996) 326
- Laser ablation of oxides: study of the oxygen incorporation by ¹⁸O isotopic tracing techniques, R. Pérez Casero, R. Gómez San Román, C. Maréchal, J.P. Enard and J. Perrière 96-98 (1996) 697
- Dissociative chemisorption of methane on clean and oxygen precovered Pt(111), M. Valden, N. Xiang, J. Perc and M. Pessa 99 (1996) 83
- Influence of oxygen on the mass diffusion of Ag on Cu(110): a laterally resolved

- photoemission study, U. Kürpick, G. Meister and A. Goldmann 99 (1996) 221
- 'Stable to unstable' transition in the (Cs, O) activation layer on GaAs (100) surfaces with negative electron affinity in extremely high vacuum, S. Pastuszka, A.S. Terekhov and A. Wolf 99 (1996) 361
- Surface oxygen and electrical resistance of YBa₂Cu₃O₈, S. Saito, M. Ishihara, T. Tani, T. Maeda, N. Watanabe, I. Rittaporn and N. Koshizuka 100/101 (1996) 260
- Investigation of the physical and chemical interaction of a low energy oxygen ion beam with oxide superconducting films, G. Pindoria, M. Badaye, F. Wang, K. Kawaguchi and T. Morishita 100/101 (1996) 347
- Oxygen adsorption on hydrogen-preadsorbed Si(111)7×7 observed by second harmonic generation (SHG), K. Nakamura, S. Ichimura and H. Shimizu 100/101 (1996) 444

Oxynitrides

- Application of irradiation-then-nitridation to improve the radiation hardness in MOS gate dielectrics, K.-C. Lee and J.-G. Hwu 92 (1996) 204

Ozone

- High purity ozone oxidation on hydrogen passivated silicon surface, A. Kurokawa and S. Ichimura 100/101 (1996) 436

Palladium

- Precursor development for the chemical vapor deposition of aluminium, copper and palladium, A. Gräfe, R. Heinen, F. Klein, Th. Kruck, M. Scherer and M. Schöber 91 (1995) 187
- Stress in Al, AlSiCu, and AlVPd films on oxidized Si substrates, G.J. Leusink, J.P. Lokker, M.J.C. van den Homberg, J.F. Jongste, T.G.M. Oosterlaan, G.C.A.M. Janssen and S. Radelaar 91 (1995) 215
- Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
- Structural and optical properties of Pd_{1-x}In_x thin films, W.T. Wu, P.E. Schmid and F. Lévy 92 (1996) 391

A new method for the detection of hydrogen spillover, M. Holmberg and I. Lundström

93 (1996) 67

FT-IR characterization of alkali-doped Pd catalysts for the selective hydrogenation of phenol to cyclohexanone, S. Scirè, C. Crisafulli, R. Maggiore, S. Minicò and S. Galvagno

93 (1996) 309

Atomic jump lengths in surface diffusion: experiment and theory, D.C. Senft

94/95 (1996) 231

Decomposition mechanisms of thin palladium acetate film with excimer UV radiation, J.-Y. Zhang, H. Esrom and I.W. Boyd

96-98 (1996) 399

High resolution electron microscopy characterization of small Pt-Pd/SiO₂ particles in oxide-reducing cycles, A. Vázquez and F. Pedraza

99 (1996) 213

Infrared chemiluminescence study of the dynamics of catalytic oxidation of CO and HCOOH on Pd(111) and polycrystalline Pd surfaces, K. Watanabe, H. Uetsuka, H. Ohnuma and K. Kunimori

99 (1996) 411

Microstructure studies of PdGe/Ge ohmic contacts to n-type GaAs formed by rapid thermal annealing, W.D. Chen, X.L. Xie, Y.D. Cui, C.H. Chen and C.C. Hsu

100/101 (1996) 530

Phase transitions

Phase separation in the Fe-Cr-Ni system, M.K. Miller, I.M. Anderson, J. Bentley and K.F. Russell

94/95 (1996) 391

Phosphorus

APFIM characterization of a high phosphorus Russian RPV weld, M.K. Miller and K.F. Russell

94/95 (1996) 378

Annealing behavior of phosphorus in native oxide films on heavily phosphorus doped silicon, W.B. Ying, Y. Mizokawa, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto

100/101 (1996) 556

Phosphorus redistribution in the surface region of heavily phosphorus doped silicon, Y. Mizokawa, W.B. Ying, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto

100/101 (1996) 561

Photochemistry

In-situ IR and mass spectroscopic study of the Al(CH₃)₂H/a-Si:H reaction processes, T. Wadayama, Y. Maiwa, H. Shibata and A. Hatta

100/101 (1996) 575

Photoconductivity

Oxide thickness dependence of photocurrent for the GeO₂/Ge film system, Y. Matsuo and K. Oishi

100/101 (1996) 248

Photodesorption

Microscopic and mesoscopic aspects of laser-induced desorption and ablation, R.F. Haglund, Jr.

96-98 (1996) 1

Photoelectron emission microscopy

Photoemission spectromicroscopy and free electron laser spectroscopy of surfaces and interfaces, G. Margaritondo and Y. Hwu

92 (1996) 273

Photoelectron spectroscopy

Photoelectron spectroscopic investigations of thin Fe_xSi_{100-x} films, R. Kilper, St. Teichert, Th. Franke, P. Häussler, H.-G. Boyen, A. Cossy-Favre and P. Oelhafen

91 (1995) 93

Process optimization of copper MOCVD using modeling experimental design, M.-J. Mouche, J.-L. Mermet, F. Pires, E. Richard, J. Torres, J. Palleau and F. Braud

91 (1995) 129

Sputtering of tantalum-based diffusion barriers in Si/Cu metallization: effects of gas pressure and composition, M. Stavrev, C. Wenzel, A. Möller and K. Drescher

91 (1995) 257

Aspects of TiN and Ti deposition in an ECR plasma enhanced CVD process, A. Weber, R. Nikulski, C.-P. Klages, M.E. Gross, R.M. Charatan, R.L. Opilan and W.L. Brown

91 (1995) 314

Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on MgO(001), H. Qiu, T. Ohnuchi, H. Nakai and M. Hashimoto

92 (1996) 47

XPS studies on SiC thin layers formed by ion implantation with a metal vapor vacuum arc ion source, H. Yan, R.W.M. Kwok and S.P. Wong

92 (1996) 61

Adsorption of H₂S on GaP(001) surface and passivation effects studied by AES, LEED and XPS, Y. Fukuda, N. Sanada, M. Kuroda and Y. Suzuki

92 (1996) 212

AES and SRUPS studies on surface passivation of GaAs by (NH₄)₂S₂ sulfurization techniques, J.T. Hsieh and H.L. Hwang

92 (1996) 222

- XPS study of the reaction of the Si(100) surface with a C_2H_4 beam, T. Takagaki, Y. Igari, T. Takaoka and I. Kusunoki 92 (1996) 287
- XPS, AES and LEED studies of Cu deposited on $Cr_2O_3(0001)$ surfaces, Q. Guo, L. Gui, P.J. Møller and K. Binau 92 (1996) 513
- Surface fluorination of electrophotographic photoreceptors by plasma treatment for contact charging with a wet polymer roller, M. Satoh, S. Matsumoto, T. Higashiguchi, M. Matsuda, T. Muranoi, I. Kikuma, Y. Momose and M. Takeuchi 92 (1996) 635
- Electrocatalytic activities of proton-exchanged layered oxides for the anodic oxidation on the solid oxide fuel cell, K. Sato, S. Nomura and Y. Inoue 92 (1996) 639
- Carbon nitride - prospects for ultimate performance of superhard materials, S.A. Uglov, V.E. Shub, A.A. Beloglazov and V.I. Konov 92 (1996) 656
- An XPS and FTIR study of SO_2 adsorption on SnO_2 surfaces, F. Berger, E. Beche, R. Berjoan, D. Klein and A. Chambaudet 93 (1996) 9
- The adsorption and condensation of $Hg(CH_3)_2$ on Pt(111) at 95 and 310 K: an UPS study, A. Cassuto 93 (1996) 17
- Characterisation of the spinels $M_xCo_{1-x}Fe_2O_4$ ($M = Mn, Fe$ or Ni) using X-ray photoelectron spectroscopy, G.C. Allen and K.R. Hallam 93 (1996) 25
- X-ray photoelectron spectroscopy studies of a nitroxyl free radical, V.S. Sastri, M. Elboujdaini, J.R. Perumareddi and J.R. Brown 93 (1996) 31
- Ruthenium and sulphide passivation of GaAs, S.T. Ali, S. Ghosh and D.N. Bose 93 (1996) 37
- An investigation of the Cu/ZnO/Zn system: evidence for the formation of Cu-Zn alloys by the inward diffusion of Cu, K.R. Harikumar, A.K. Santra and C.N.R. Rao 93 (1996) 135
- XPS study of as-prepared and reduced molybdenum oxides, J.-G. Choi and L.T. Thompson 93 (1996) 143
- A study of galena (PbS) surfaces under controlled potential in pH 4.6 solution by synchrotron radiation excited photoelectron spectroscopy, I. Kartio, K. Laajalehto, T. Kaurila and E. Suoninen 93 (1996) 167
- Work function variations and oxygen conduction in a $Pt[ZrO_2(Y_2O_3)]Pt$ solid electrolyte cell, N.G. Torkelsen and S. Raasen 93 (1996) 199
- Studies of 1T TiS_2 by STM, AFM and XPS: the mechanism of hydrolysis in air, H. Martinez, C. Auriel, D. Gonbeau, M. Loudet and G. Pfister-Guilouzo 93 (1996) 231
- Ion beam studies of porphyrin adsorption on and leaching of soda lime glass, C.H.M. Marée, T.J. Savenije, T.J. Schaafsma and F.H.P.M. Habraken 93 (1996) 291
- CO_2 plasma treatment of tin oxides, H.N. Wanka, G. Bilger and M.B. Schubert 93 (1996) 339
- LEED and XPS studies of the $ZrO/W(100)$ surface, H. Satoh, H. Nakane and H. Adachi 94/95 (1996) 247
- Low-fluence excimer laser irradiation-induced defect formation in indium-tin oxide films, T. Szörényi, L.D. Laude, I. Bertóti, Zs. Geretovszky and Z. Kántor 96-98 (1996) 363
- Laser-induced formation of visible light emitting silicon, D. Dimova-Malinovska, M. Tzolov, N. Malinowski, Ts. Marinova and V. Krastev 96-98 (1996) 457
- Cleaning of copper traces on circuit boards with excimer laser radiation, D.A. Wesner, M. Mertin, F. Lupp and E.W. Kreutz 96-98 (1996) 479
- CCl_4 -assisted CF_4 etching of silicon in a microwave-assisted LDE (laser dry etching)-process, W. Pflöging, D.A. Wesner and E.W. Kreutz 96-98 (1996) 496
- Chemical surface modification of fluorocarbon polymers by excimer laser processing, H. Niino and A. Yabe 96-98 (1996) 550
- Etching and functionalization of a fluorocarbon polymer by UV laser treatment, C. Girardeaux, Y. Idrissi, J.J. Pireaux and R. Caudano 96-98 (1996) 586
- Deposition of fluoropolymer thin films containing semiconductor microcrystallites by VUV laser ablation, T. Fujii, S. Inoue and F. Kannari 96-98 (1996) 621
- Electrical and optical characteristics of organic thin films fabricated by laser ablation, T. Fujii, H. Shima, N. Matsumoto and F. Kannari 96-98 (1996) 625
- Excimer laser ablating preparation of $Ba_2NaNb_5O_{15}$ thin films on $KTiOPO_4$ substrate and its guide wave property, J.M. Liu, Z.G. Liu, S.N. Zhu, Y.Y. Zhu and N.B. Ming 96-98 (1996) 819
- Pulsed laser deposition of electroceramic thin films, M. Mertin, D. Offenberg, C.W. An, D.A. Wesner and E.W. Kreutz 96-98 (1996) 842
- Pulsed laser deposition of nasicon thin films, R. Izquierdo, F. Hanus, Th. Lang, D. Ivanov, M. Meunier, L. Laude, J.F. Currie and A. Yelon 96-98 (1996) 855
- Laser reactive ablation deposition of silicon carbide films, G. Leggieri, A. Luches, M. Martino, A. Perrone, R. Alexandrescu, A. Barborica, E. Gyorgy, I.N. Mihailescu, G. Majni and P. Mengucci 96-98 (1996) 866

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- XPS and AFM characterization of a vanadium oxide film on TiO₂(100) surface, G. Chiarello, R. Barberi, A. Amoddeo, L.S. Caputi and E. Colavita 99 (1996) 15
- Surface composition of CVD-grown α -SiC layers - an XPS and LEED study, H. Behner and R. Rupp 99 (1996) 27
- Surface and interface analysis of GaSb/GaAs semiconductor materials, K. Li, J. Lin, A.T.S. Wee, K.L. Tan, Z.C. Feng and J.B. Webb 99 (1996) 59
- Application and properties of sub-monomolecular layers of silicon dioxide deposited under mild conditions, D.M. Knotter 99 (1996) 99
- Interface chemistry and electric characterisation of nickel metallisation on 6H-SiC, Ts. Marinova, V. Krastev, C. Hallin, R. Yakimova and E. Janzén 99 (1996) 119
- X-ray photoelectron spectroscopy of Cr/COOCH₃ interfaces on self-assembled monolayers of 16-mercaptohexadecanoate, D.R. Jung and A.W. Czanderma 99 (1996) 161
- X-ray photoelectron diffraction investigation of Ge segregation and film morphology during first stage heteroepitaxy of Si on Ge(001), D. Aubel, L. Kubler, J.L. Bischoff, L. Simon and D. Bolmont 99 (1996) 169
- ¹⁸O-exchange with the substrate during ¹⁸O oxidation of Cu particles supported on ¹⁶O-oxidised Si(100), R. van Wijk, C.H.M. Marée, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 99 (1996) 197
- Influence of oxygen on the mass diffusion of Ag on Cu(110): a laterally resolved photoemission study, U. Kürpick, G. Meister and A. Goldmann 99 (1996) 221
- CuCl growth on the reconstructed surface of (0001) haematite, Q. Guo, L. Gui and N. Wu 99 (1996) 229
- Adsorption and decomposition of hexamethyldisiloxane on platinum: an XPS, UPS and TDS study, L. Colin, A. Cassuto, J.J. Ehrhardt, M.F. Ruiz-Lopez and D. Jamois 99 (1996) 245
- Large area synthesis of thin alumina films by laser ablation, B. Hirschauer, S. Söderholm, J. Paul and A.S. Flodström 99 (1996) 285
- XPS study of carbon/inconel bilayers as a function of substrate bias, M.S. Aouadi, P.C. Wong and K.A.R. Mitchell 99 (1996) 319
- The nature of the surface acidity of anodised titanium: an XPS study using 1,2-diaminoethane, J. Marsh, L. Minel, M.G. Barthés-Labrousse and D. Gorse 99 (1996) 335
- Preparation of thin silver films on mica studied by XRD and AFM, J.-D. Grunwaldt, F. Atamny, U. Göbel and A. Baiker 99 (1996) 353
- On the application of XPS to ceria films grown by MOCVD using a fluorinated precursor, D. Chadwick, J. McAleese, K. Senkiw and B.C.H. Steele 99 (1996) 417
- Quantitative XPS: non-destructive analysis of surface nano-structures, S. Tougaard 100/101 (1996) 1
- Auger electron peaks of Cu in XPS, M. Jo and A. Tanaka 100/101 (1996) 11
- The influence of elastic scattering on the concentration dependence of the photoelectron line intensity, I.S. Tilinin, A. Jablonski and B. Lesiak-Orlowska 100/101 (1996) 20
- Comparison of AES chemical shifts with XPS chemical shifts, T. Sekine, N. Ikeo and Y. Nagasawa 100/101 (1996) 30
- Simultaneous determination of composition and thickness of thin iron-oxide films from XPS Fe 2p spectra, P.C.J. Graat and M.A.J. Somers 100/101 (1996) 36
- A general procedure for extracting quantitative depth information from take-off-angle-resolved XPS and AES, W.H. Gries 100/101 (1996) 41
- XPS depth profiling by changing incident X-ray energy, H. Shimada, N. Matsubayashi, M. Imamura, T. Sato and A. Nishijima 100/101 (1996) 56
- UPS studies of conducting polymers: dopant effect on conjugated polymer systems sensitive to conductivity, S. Takemura, Y. Kitagawa, H. Kato and Y. Nakajima 100/101 (1996) 107
- Surface characterization of cell adhesion controlled polymer modified by ion bombardment, A. Nakao, M. Kaibara, M. Iwaki, Y. Suzuki and M. Kusakabe 100/101 (1996) 112
- Ion induced alteration at Pb-Sn alloy surface investigated by Auger electron spectroscopy and X-ray photoelectron spectroscopy, M. Kudo, A. Ishijima and T. Morohashi 100/101 (1996) 134
- Influence of ion-implantation on native oxidation of Si in a clean-room atmosphere, F. Yano, A. Hiraoaka, T. Itoga, H. Kojima, K. Kanehori and Y. Mitsui 100/101 (1996) 138
- Luminescent properties of an anodically oxidized P-doped silicon wafer, M. Iwaso and T. Arakawa 100/101 (1996) 147
- The surface and interface reaction of metal thin film on sapphire substrate, H.J. Kang, C.H. Kim, N.S. Park and M.W. Kim 100/101 (1996) 160
- Adsorption and thermal decomposition of diethyltellurium on GaAs(100), S.I.

- Gheysa, M. Nishio, T. Urisu and H. Ogawa 100/101 (1996) 211
- Behavior of zirconium on ZrO/W(100) surface, H. Satoh, H. Nakane and H. Adachi 100/101 (1996) 216
- Investigation of characteristics of carbon materials with various structures modified by plasmas using plasma diagnostics and material-surface analysis, M. Katoh, Y. Izumi, H. Kimura, T. Ohte, A. Kojima and S. Ohtani 100/101 (1996) 226
- Charge-up and charge compensation on monochromatized X-ray photoelectron spectroscopic measurements of alumina and glass, H. Tomizuka and A. Ayame 100/101 (1996) 243
- Simulation of geometrical aberration and beam shape of scanning X-ray probe, H. Iwai, R. Oiwa, P.E. Larson and M. Kudo 100/101 (1996) 283
- Preferential sputtering and surface segregation of CuZr alloys, H.J. Kang, C.H. Kim, N.S. Park, D.J. O'Connor and R. MacDonald 100/101 (1996) 329
- Decomposition of triethylindium (TEI) on GaP(001) surface studied by TPD, XPS and RHEED, J. Murata, T. Takeuchi, Y. Suzuki, N. Sanada and Y. Fukuda 100/101 (1996) 417
- Initial stage of oxidation of Si(100) surfaces in dry oxygen, K. Inanaga, T. Nakahata, T. Furukawa and K. Ono 100/101 (1996) 421
- High purity ozone oxidation on hydrogen passivated silicon surface, A. Kurokawa and S. Ichimura 100/101 (1996) 436
- Growth kinetics of thermal oxidation process on Si(100) by real time ultraviolet photoelectron spectroscopy, Y. Enta, Y. Takegawa, M. Suemitsu and N. Miyamoto 100/101 (1996) 449
- Initial stages of oxidation of hydrogen-terminated Si surface stored in air, T. Miura, M. Niwano, D. Shoji and N. Miyamoto 100/101 (1996) 454
- Co overlayer formation process on Si(100)2 × 1 studied by SR-PES, T. Jikimoto, C. Heck, K. Komoku, M. Hirai, M. Kusaka and M. Iwami 100/101 (1996) 513
- Behavior of ultrathin layers of Co on Si and Ge systems, K. Prabhakaran and T. Ogino 100/101 (1996) 518
- Valence band structure of metal silicides modified by argon ion implantation, S. Yamauchi, Y. Hasebe, H. Ohshima, T. Hattori, M. Hirai, M. Kusaka and M. Iwami 100/101 (1996) 522
- Annealing behavior of phosphorus in native oxide films on heavily phosphorus doped silicon, W.B. Ying, Y. Mizokawa, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto 100/101 (1996) 556
- Phosphorus redistribution in the surface region of heavily phosphorus doped silicon, Y. Mizokawa, W.B. Ying, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto 100/101 (1996) 561
- Photoluminescence enhancement of (NH₄)₂S_x passivated InP surface by rapid thermal annealing, W.D. Chen, X.Q. Li, L.H. Duan, X.L. Xie and Y.D. Cui 100/101 (1996) 592
- Surface barriers formation mechanism of the chemically etched CdTe(111) polar surfaces and gold interfaces, T. Takeuchi, T. Kore-eda and A. Ebina 100/101 (1996) 596
- XPS analysis of chemically etched II-VI semiconductor surfaces, A. Kita, M. Ozawa and C.D. Gutleben 100/101 (1996) 652
- ### Photoemission
- Growth and reactivity of evaporated platinum films on Cu(111): a study by AES, RHEED and adsorption of carbon monoxide and xenon, J. Fusy, J. Menucourt, M. Alnot, C. Huguet and J.J. Ehrhardt 93 (1996) 211
- Laser-induced emission of neutral atoms and molecules from electron-irradiated NaNO₃, J.T. Dickinson, J.J. Shin and S.C. Langford 96-98 (1996) 326
- ### Photoexcitation
- Laser ablation of sodium nitrate: NO desorption following excitation of the $\pi-\pi^*$ band of the nitrate anion, W.P. Hess, K.A.H. German, R.A. Bradley and M.I. McCarthy 96-98 (1996) 321
- ### Photon emission
- Spatially and temporally resolved emission intensities and number densities in low temperature laser-induced plasmas in vacuum and in ambient gases, R.A. Al-Wazzan, J.M. Hendron and T. Morrow 96-98 (1996) 170
- ### Plasma processing
- Patterning of copper for multilevel metalization: reactive ion etching and chemical-mechanical polishing, C. Steinbrüchel 91 (1995) 139

- Effects of the biasing frequency on RIE of Cu in a Cl_2 -based discharge, A. Bertz, T. Werner, N. Hille and T. Gessner 91 (1995) 147
- Barrier behaviour of plasma deposited silicon oxide and nitride against Cu diffusion, M. Vogt and K. Drescher 91 (1995) 303
- Aspects of TiN and Ti deposition in an ECR plasma enhanced CVD process, A. Weber, R. Nikulski, C.-P. Klages, M.E. Gross, R.M. Charatan, R.L. Opilan and W.L. Brown 91 (1995) 314
- Very low temperature polycrystalline silicon films with very large grains deposited for thin film transistor applications, K.C. Wang, T.R. Yew and H.L. Hwang 92 (1996) 99
- Textured diamond growth by microwave plasma chemical vapor deposition, Y. Liou 92 (1996) 115
- Ultra-thin gate dielectrics grown by low-temperature processes for applications to ULSI devices, H.-L. Hwang, P.-C. Chen and K.Y.J. Hsu 92 (1996) 180
- Refractive index behavior of boron-doped silica films by plasma-enhanced chemical vapor deposition, R.H. Hornig, F. Chen, D.S. Wu and T.Y. Lin 92 (1996) 387
- Surface fluorination of electrophotographic photoreceptors by plasma treatment for contact charging with a wet polymer roller, M. Satoh, S. Matsumoto, T. Higashiguchi, M. Matsuda, T. Muranoi, I. Kikuma, Y. Momose and M. Takeuchi 92 (1996) 635
- Internal surface interactions in the plasma treatment of fine bore fluoropolymer tubings, L. Mascia and Z. Zhang 93 (1996) 1
- The etching of natural alpha-recoil tracks in mica with an argon RF-plasma discharge and their imaging via atomic force microscopy, N.M.D. Brown and Z.H. Liu 93 (1996) 89
- Plasma anodic oxidation of semiinsulating GaAs, E. Pinčík, K. Gmucová, J. Bartoš, M. Kučera, M. Jergel and R. Brunner 93 (1996) 119
- CO_2 plasma treatment of tin oxides, H.N. Wanka, G. Bilger and M.B. Schubert 93 (1996) 339
- Laser plasma threshold of metals, S. Petzoldt, J. Reif and E. Matthias 96-98 (1996) 199
- Optical and particle properties of PLD vapour/plasmas of ceramics, M. Alunovic, H. Stamm, M. Aden and E.W. Kreutz 96-98 (1996) 222
- Spectroscopic study of the microwave plasma enhanced pulsed laser deposition for $\text{Y}_1\text{Ba}_2\text{Cu}_3\text{O}_{7-x}$ superconducting thin films, B.C. Chung, C.H. Tsai, S.S. Hsu, C.S. Huang, T.Y. Tseng and I.N. Lin 96-98 (1996) 233
- X-ray generation for medical applications from a laser-produced plasma, M. Grätz, C. Tillman, I. Mercer and S. Svanberg 96-98 (1996) 443
- VUV ablation of polymers by emission from gas-puff Z-pinch plasmas, H. Deno, S. Sugiyama, Y. Kakudate, M. Yoshida and S. Fujiwara 96-98 (1996) 563
- Mirror-smooth $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ superconducting films deposited by plasma-enhanced pulsed laser deposition technique, C.S. Huang, T.Y. Tseng, B.C. Chung, C.H. Tsai, H.F. Cheng and I.N. Lin 96-98 (1996) 735
- Heating effects on modifying carbon surface by reactive plasma, Y. Izumi, M. Katoh, T. Ohte, S. Ohtani, A. Kojima and N. Saitoh 100/101 (1996) 179
- Investigation of characteristics of carbon materials with various structures modified by plasmas using plasma diagnostics and material-surface analysis, M. Katoh, Y. Izumi, H. Kimura, T. Ohte, A. Kojima and S. Ohtani 100/101 (1996) 226
- Si epitaxial growth at low temperatures using remote plasma process, A. Yoshida, K. Utsumi and A. Ganjoo 100/101 (1996) 491
- Low temperature etching of Si and PR in high density plasmas, M. Puech and Ph. Maquin 100/101 (1996) 579
- Deep trench etching in silicon with fluorine containing plasmas, R.D. Mansano, P. Verdonck and H.S. Maciel 100/101 (1996) 583
- Microwave plasma assisted LCVD growth and characterization of GaN, B. Zhou, X. Li, T.L. Tansley and K.S.A. Butcher 100/101 (1996) 643
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- Metallurgical and electrical investigation of $\text{Pt}_5\text{Ni}_{95}$ /silicon interactions, F. Corni, C. Nobili, G. Ottaviani, R. Tonini, B. Grignaffini Gregorio and G. Queirolo 91 (1995) 107
- Growth mechanism of Ni on Pt(110) at low temperature, C.S. Shern, J.S. Tsay and T. Fu 92 (1996) 74
- The adsorption and condensation of $\text{Hg}(\text{CH}_3)_2$ on Pt(111) at 95 and 310 K: an UPS study, A. Cassuto 93 (1996) 17
- Work function variations and oxygen conduction in a $\text{Pt}[\text{ZrO}_2(\text{Y}_2\text{O}_3)]\text{Pt}$ solid electrolyte cell, N.G. Torkelsen and S. Raasen 93 (1996) 199
- Growth and reactivity of evaporated platinum films on Cu(111): a study by AES,

- RHEED and adsorption of carbon monoxide and xenon, J. Fusy, J. Menau-court, M. Alnot, C. Huguet and J.J. Ehrhardt 93 (1996) 211
- Oscillatory behavior in the catalytic reduction of NO and NO₂ with hydrogen on Pt field emitter tips, C. Voss and N. Kruse 94/95 (1996) 186
- Digitizing chemical oscillations: analyzing experimental data of the CO oxidation on a Pt-tip, M.C. Reckzühl, V. Gorodetskii and J.H. Block 94/95 (1996) 194
- The segregation behaviour of a Pt₉₀Rh₁₀ alloy studied with a three-dimensional atom-probe, W. Athenstaedt and M. Leisch 94/95 (1996) 403
- New STM image structures in the confined regions of the Pt(001) surface, T.T. Tsong, C.S. Chang, W.B. Su and K.L. Shih 94/95 (1996) 472
- Modelling of the particle size distribution function in the nucleation and early stages of thin film growth, M. Tomellini 99 (1996) 67
- Dissociative chemisorption of methane on clean and oxygen precovered Pt(111), M. Valden, N. Xiang, J. Pere and M. Pessa 99 (1996) 83
- Interrupted-temperature programmed desorption of hydrogen over silica-supported platinum catalysts: the distribution of activation energy of desorption and the phenomena of spillover and reverse spillover of hydrogen, M. Arai, M. Fukushima and Y. Nishiyama 99 (1996) 145
- High resolution electron microscopy characterization of small Pt-Pd/SiO₂ particles in oxide-reducing cycles, A. Vázquez and F. Pedraza 99 (1996) 213
- Adsorption and decomposition of hexamethyldisiloxane on platinum: an XPS, UPS and TDS study, L. Colin, A. Cassuto, J.J. Ehrhardt, M.F. Ruiz-Lopez and D. Jamois 99 (1996) 245
- Hydrogen adsorption on the Pt(111)($\sqrt{3} \times \sqrt{3}$)R30°-Sn surface alloy studied by high resolution core level photoelectron spectroscopy, E. Janin, M. Björkqvist, T.M. Grehk, M. Göthelid, C.-M. Pradier, U.O. Karlsson and A. Rosengren 99 (1996) 371
- Enhanced Raman scattering from copper phthalocyanine on Pt by use of a Weierstrass prism, M. Futamata, E. Keim, A. Bruckbauer, D. Schumacher and A. Otto 100/101 (1996) 60
- Surface structure analysis of dispersed metal sites on single crystal metal oxides by means of polarization-dependent total reflection fluorescent EXAFS, W.-J. Chun, K. Asakura and Y. Iwasawa 100/101 (1996) 143
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- Study of biochemical reactions in thin organic films by means of evanescent optical wave, T.I. Ksenevich, A.A. Beloglazov, P.I. Nikitin, N.A. Kalabina and S.Yu. Zaitsev 92 (1996) 426
- Simulation of polymer film and surface behaviour in a space environment, V.E. Skurat, E.A. Barbashev, Yu.I. Dorofeev, A.P. Nikiforov, M.M. Gorelova and A.I. Pertsyn 92 (1996) 441
- An electrochemical impedance spectroscopy study of thin polymeric films, R. Borkowska, M. Siekierski and J. Przyłuski 92 (1996) 447
- Internal surface interactions in the plasma treatment of fine bore fluoropolymer tubings, L. Mascia and Z. Zhang 93 (1996) 1
- Cross-sectional TEM investigations of plasmapolymer-metal composite films, W. Grünewald, A. Heilmann and C. Reinhardt 93 (1996) 157
- Excimer laser ablation of polymers and glasses for grating fabrication, P.E. Dyer, R.J. Farley, R. Giedl and D.M. Karnakis 96-98 (1996) 537
- Chemical surface modification of fluorocarbon polymers by excimer laser processing, H. Niino and A. Yabe 96-98 (1996) 550
- Excimer laser-induced surface modifications of biocompatible polymer blends, P. Viville, S. Beauvois, G. Lambin, R. Lazzaroni, J.L. Brédas, K. Kolev and L. Laude 96-98 (1996) 558
- VUV ablation of polymers by emission from gas-puff Z-pinch plasmas, H. Deno, S. Sugiyama, Y. Kakudate, M. Yoshida and S. Fujiwara 96-98 (1996) 563
- Laser implantation of fluorescent molecules into polymer films, H. Fukumura, Y. Kohji and H. Masuhara 96-98 (1996) 569
- Surface chemical reaction of polymer film with reactive intermediates produced by laser ablation of azido compound, H. Niino and A. Yabe 96-98 (1996) 572
- Etching and functionalization of a fluorocarbon polymer by UV laser treatment, C. Girardeaux, Y. Idrissi, J.J. Pireaux and R. Caudano 96-98 (1996) 586
- Excimer laser ablation of low and high absorption index polymers, P.E. Dyer, D.M. Karnakis, P.H. Key and J.P. Tait 96-98 (1996) 596

- Single pulse threshold and transmission behaviour of a triazeno-polymer during pulsed UV-laser irradiation, T. Lippert, L.S. Bennett, T. Nakamura, H. Niino and A. Yabe 96-98 (1996) 601
- High sensitivity quadrupole mass spectrometry of neutrals sputtered by UV-laser ablation of polymers, S. Lazare, W. Guan and D. Drilhole 96-98 (1996) 605
- Formation of the surface structure of polyethylene-terephthalate (PET) due to ArF excimer laser ablation, B. Hopp, M. Csete, K. Révész, J. Vinkó and Zs. Bor 96-98 (1996) 611
- Pulsed laser ablation and deposition of fluorocarbon polymers, M.G. Norton, W. Jiang, J.T. Dickinson and K.W. Hipps 96-98 (1996) 617
- Deposition of fluoropolymer thin films containing semiconductor microcrystallites by VUV laser ablation, T. Fujii, S. Inoue and F. Kannari 96-98 (1996) 621
- Surface study of cross-linking gradients in photopolymers by acoustic microscopy, F. Augereau, B. Cros and J.P. Marco 99 (1996) 293
- UPS studies of conducting polymers: dopant effect on conjugated polymer systems sensitive to conductivity, S. Takemura, Y. Kitagawa, H. Kato and Y. Nakajima 100/101 (1996) 107
- Surface characterization of cell adhesion controlled polymer modified by ion bombardment, A. Nakao, M. Kaibara, M. Iwaki, Y. Suzuki and M. Kusakabe 100/101 (1996) 112
- Photoresist characteristics of polyurea films prepared by vapor deposition polymerization. Depolymerization of polyurea, M. Iijima, M. Sato and Y. Takahashi 100/101 (1996) 120
- Molecular orientation of polyimide films determined by an optical retardation method, K. Sakamoto, R. Arafune, S. Ushioda, Y. Suzuki and S. Morokawa 100/101 (1996) 124
- Pulsed laser ablation*
- Angular resolved EPMA analysis of thin films prepared by pulsed laser ablation of $\text{CdWO}_4(010)$, K. Tanaka, N. Yokota, N. Shirai, Q. Zhuang and R. Nakata 100/101 (1996) 264
- Pulsed laser deposition*
- Modeling of dynamical processes in laser ablation, J.N. Leboeuf, K.R. Chen, J.M. Donato, D.B. Geohegan, C.L. Liu, A.A. Puretzky and R.F. Wood 96-98 (1996) 14
- Material removal and plasmadynamics during pulsed laser deposition by excimer and CO_2 laser radiation, M. Aden and E.W. Kreutz 96-98 (1996) 39
- Analytical description of the film thickness distribution obtained by the pulsed laser ablation of a monoatomic target: application to silicon and germanium, F. Antoni, C. Fuchs and E. Fogarassy 96-98 (1996) 50
- Calculations and experiments of material removal and kinetic energy during pulsed laser ablation of metals, S. Fährler and H.-U. Krebs 96-98 (1996) 61
- Modeling of laser induced plasma, spectroscopic and time of flight experiments in pulsed laser deposition, G. Granse, S. Völlmar, A. Lenk, A. Rupp and K. Rohr 96-98 (1996) 97
- Plasma parameters in pulsed laser-plasma deposition of thin films, S. Metev, M. Ozegowski, G. Sepold and S. Burmester 96-98 (1996) 122
- Electromagnetic diagnostics during pulsed laser deposition, A.V. Kabashin, W. Marine, P.I. Nikitin and M. Sentis 96-98 (1996) 139
- Optical and particle properties of PLD vapour/plasmas of ceramics, M. Alunovic, H. Stamm, M. Aden and E.W. Kreutz 96-98 (1996) 222
- Spectroscopic study of the microwave plasma enhanced pulsed laser deposition for $\text{Y}_2\text{Ba}_2\text{Cu}_3\text{O}_{7-x}$ superconducting thin films, B.C. Chung, C.H. Tsai, S.S. Hsu, C.S. Huang, T.Y. Tseng and I.N. Lin 96-98 (1996) 233
- Surface chemical reaction of polymer film with reactive intermediates produced by laser ablation of azido compound, H. Niino and A. Yabe 96-98 (1996) 572
- Pulsed laser ablation and deposition of fluorocarbon polymers, M.G. Norton, W. Jiang, J.T. Dickinson and K.W. Hipps 96-98 (1996) 617
- Deposition of fluoropolymer thin films containing semiconductor microcrystallites by VUV laser ablation, T. Fujii, S. Inoue and F. Kannari 96-98 (1996) 621
- Electrical and optical characteristics of organic thin films fabricated by laser ablation, T. Fujii, H. Shima, N. Matsumoto and F. Kannari 96-98 (1996) 625
- Thin film growth by the pulsed laser assisted deposition technique, C. Belouet 96-98 (1996) 630
- Scale-up of pulsed laser deposition (PLD) for 4"-wafer coating, M. Panzner, R. Dietsch, Th. Holz, H. Mai and S. Völlmar 96-98 (1996) 643
- Ultrathin film deposition by pulsed laser ablation using crossed beams, A.A. Gorbunov, W. Pompe, A. Sewing, S.V. Gaponov, A.D. Akhsakhlyan, I.G. Zabrodin, I.A. Kas'kov, E.B. Klyenkov,

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- Off-axis excimer laser deposition of Ta_2O_5 thin films, N. Inoue, S. Kashiwabara, S. Toshima and R. Fujimoto 96-98 (1996) 656
- Aspects of particulate production from metals exposed to pulsed laser radiation, I. Weaver and C.L.S. Lewis 96-98 (1996) 663
- Classification of particulates on pulsed-laser deposited Y-Ba-Cu-O films, S. Proyer, E. Stangl, M. Borz and D. Bäuerle 96-98 (1996) 668
- Formation of artificially-layered high-temperature superconductors using pulsed-laser deposition, D.P. Norton, B.C. Chakoumakos, D.H. Lowndes and J.D. Budai 96-98 (1996) 672
- Stoichiometric transfer of complex oxides by pulsed laser deposition, B. Dam, J.H. Rector, J. Johansson, S. Kars and R. Griessen 96-98 (1996) 679
- Improved properties of Pulsed Laser Deposited YBaCuO on NdGaO_3 using CeO_2 template layers, D.H.A. Blank, A.J.H.M. Rijnders, F.J.G. Roesthuis, G. den Ouden and H. Rogalla 96-98 (1996) 685
- The importance of gas scattering processes on the stoichiometry deviations of laser deposited films, J. Gonzalo, C.N. Afonso, J. Perrière and R. Gómez San Roman 96-98 (1996) 693
- Critical thickness of YBaCuO (123) strained thin films and superlattices grown by pulsed laser deposition, A. Abert, J.P. Contour, A. Défossez, D. Ravelosona, W. Schwegle and P. Ziemann 96-98 (1996) 703
- Laser deposition of $\text{YBa}_2\text{Cu}_3\text{O}_7$ films on $\text{MgO}(100)$ at 100 mm target-substrate distance and oxygen pressures below 0.1 mbar, F. Goerke, A. Thoms and U. Merkt 96-98 (1996) 708
- Anisotropic resistivity in pulsed-laser deposited $\text{Bi}_2\text{Sr}_2\text{CaCu}_2\text{O}_{8+\delta}$ films, S.T. Li, A. Ritzer, S. Proyer, E. Stangl, D. Bäuerle and N. Reschauer 96-98 (1996) 713
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- Ion-assisted pulsed-laser deposition for the fabrication of Y-Ba-Cu-O multilayer structures using oriented intermediate layers of YSZ and CeO_2 , R.P. Reade and R.E. Russo 96-98 (1996) 726
- Synthesis of RE-Ba-Sr-Cu-O by pulsed-laser deposition, E. Stangl, S. Proyer, B. Hellebrand and D. Bäuerle 96-98 (1996) 731
- Mirror-smooth $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ superconducting films deposited by plasma-enhanced pulsed laser deposition technique, C.S. Huang, T.Y. Tseng, B.C. Chung, C.H. Tsai, H.F. Cheng and I.N. Lin 96-98 (1996) 735
- Growth, structuring and characterisation of all-oxide thin film devices prepared by pulsed laser deposition, J.F.M. Cillessen, R.M. Wolf, J.B. Giesbers, P.W.M. Blom, K.-O. Grosse-Holz and E. Pastoor 96-98 (1996) 744
- Deposition of optical coatings by pulsed laser ablation, G. Reisse, S. Weissmantel, B. Keiper and U. Broulik 96-98 (1996) 752
- Rare-earth doped glass waveguides prepared by pulsed laser deposition, C.N. Afonso, J.M. Ballesteros, J. Gonzalo, G.C. Righini and S. Pelli 96-98 (1996) 760
- Preparation of SiO_xN_y films by reactive KrF laser ablation, K. Maruyama, Y. Aoki, M. Matsumoto, Y. Hiroshima and H. Ohta 96-98 (1996) 764
- Kinetic energy distributions of ions ejected during laser ablation of lead zirconate titanate and their correlation to deposition of ferroelectric thin films, G.C. Tyrrell, T.H. York, L.G. Coccia and I.W. Boyd 96-98 (1996) 769
- Epitaxial ferroelectric PZT and BST thin films by pulsed UV laser deposition, C. Champeaux, P. Marchet and A. Catherinot 96-98 (1996) 775
- Growth and characterization of PLZT films, M.J.M. Gomes, E. de Matos Gomes, P.L.Q. Mantas and J.L. Baptista 96-98 (1996) 779
- Electrical characterization of semiconducting La doped SrTiO_3 thin films prepared by pulsed laser deposition, K.-O. Grosse-Holz, J.F.M. Cillessen and R. Waser 96-98 (1996) 784
- Pulsed laser deposition of sillenite films intended for photorefractive damage free waveguides, J.E. Alfonso, M.J. Martín, J. Mendiola, K. Polgár and C. Zakdo 96-98 (1996) 791
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- Ferrimagnetic thin films prepared by pulsed laser deposition, M. Guyot, A. Lias, R. Krishnan, M. Porte, P. Rougier and V. Cagan 96-98 (1996) 802
- Pulsed laser deposition of high quality ITO thin films, F. Hanus, A. Jadin and L.D. Laude 96-98 (1996) 807

- Pulsed-laser deposited ZnO for device applications, S.L. King, J.G.E. Gardeniers and I.W. Boyd 96-98 (1996) 811
- $\text{Pb}_{1-x}\text{Ca}_x\text{TiO}_3$ thin films prepared by laser ablation of ceramic targets, M.J. Martín, C. Zaldo and J. Mendiola 96-98 (1996) 823
- Characterization of ZnO thin films deposited by laser ablation in reactive atmosphere, P. Verardi, M. Dinescu and A. Andrei 96-98 (1996) 827
- An experimental study and modeling of the thickness distribution in pulsed laser deposited ferroelectric thin films, M. Tyunina, K. Sreenivas, C. Bjormander, J. Wittborn and K.V. Rao 96-98 (1996) 831
- Preparation of TiO_2 thin films by pulsed laser deposition for waveguiding applications, C. Garapon, C. Champeaux, J. Mugnier, G. Panczer, P. Marchet, A. Catherinot and B. Jacquier 96-98 (1996) 836
- Pulsed laser deposition of electroceramic thin films, M. Mertin, D. Offenberg, C.W. An, D.A. Wesner and E.W. Kreutz 96-98 (1996) 842
- Pulsed laser deposition of nasicon thin films, R. Izquierdo, F. Hanus, Th. Lang, D. Ivanov, M. Meunier, L. Laude, J.F. Currie and A. Yelon 96-98 (1996) 855
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- Structural and optical characteristics of pulsed laser deposited ZnSe epilayers, A. Chergui, J.L. Deiss, J.B. Grun, J.L. Loison, M. Robino and R. Beserman 96-98 (1996) 874
- Deposition of HgCdTe epitaxial layers on anisotropically etched silicon surfaces by laser evaporation, T.Ya. Gorbach, M. Kuzma, E. Sheregii, P.S. Smertenko, S.V. Svechnikov and G. Wisz 96-98 (1996) 881
- Pulsed Laser Deposition of permanent magnetic $\text{Nd}_2\text{Fe}_{14}\text{B}$ thin films, A.J.M. Geurtsen, J.C.S. Kools, L. de Wit and J.C. Lodder 96-98 (1996) 887
- Large area synthesis of thin alumina films by laser ablation, B. Hirschauer, S. Söderholm, J. Paul and A.S. Flodström 99 (1996) 285
- Line shape study of Ba ions in laser produced plasmas, R.A. Al-Wazzan, J.M. Hendron and T. Morrow 99 (1996) 345

Quantum effects

- A method to tune the island size and improve the uniformity for the in situ formation of InGaAs quantum dots on GaAs, S.-Z. Chang, T.-C. Chang and S.-C. Lee 92 (1996) 70
- High quality quantum dots fabricated by molecular beam epitaxy, C.-P. Lee and D.-C. Liu 92 (1996) 519
- Self-organized growth of InAs/GaAs quantum boxes, J.M. Moison, L. Leprince, F. Barthe, F. Houzay, N. Lebourché, J.M. Gérard and J.Y. Marzin 92 (1996) 526
- Voltage-tunable far-infrared photodetector with a very large tuning range, Y. Huang and C. Lien 92 (1996) 537
- Photoreflectance study of GaAs/ $\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}$ resonant asymmetric double quantum wells with Si δ -doping in side barriers, C.R. Lu, S.K. Du, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 543
- Stimulated blue emission processes in $\text{Zn}_{1-x}\text{Cd}_x\text{Se}/\text{ZnSe}$ multi-quantum wells, J.Y. Jen, T. Tsutsumi, I. Souma, Y. Oka, J.R. Anderson and M. Gorska 92 (1996) 547
- Diffusion phenomena in MBE grown Si/SiGe single quantum wells studied by PL and TEM measurements, H.P. Zeindl, S. Nilsson and E. Bugiel 92 (1996) 552
- Theory of room temperature quantized resistance steps in electroformed metal-a-Si:H-metal structures, J. Hajto, B. McAuley, A.J. Snell, G.H.W. Milburn and A.E. Owen 92 (1996) 579
- Field emission from the surface quantum well of silicon, Q.-A. Huang 93 (1996) 77
- Determination of the subband carrier densities in a strained GaAs/ $\text{In}_{0.15}\text{Ga}_{0.85}\text{As}/\text{Al}_{0.22}\text{Ga}_{0.78}\text{As}$ single quantum well using photoluminescence, T.W. Kim, M. Jung and D.U. Lee 93 (1996) 131
- Photoreflectance analysis of MQWs in intermediate electric field regime, M. Geddo, S. Di Lernia and Chen Chen-Jia 93 (1996) 267

Quartz

- Multiwavelength irradiation effect in fused quartz ablation using vacuum-ultraviolet Raman laser, K. Sugioaka, S. Wada, Y. Ohnuma, A. Nakamura, H. Tashiro and K. Toyoda 96-98 (1996) 347

Raman scattering

- Raman study of tetragonal tungsten disilicide, O. Chaix-Pluchery, F. Genet, G. Lucazeau and R. Madar 91 (1995) 68
- Low temperature growth of diamond-like films by cathodic arc plasma deposition, P.-L. Chen, M.-Y. Tsai and J.-S. Kao 92 (1996) 30
- Characterization of low temperature GaAs grown by molecular beam epitaxy, W.C. Lee, T.M. Hsu, J.-I. Chyi, G.S. Lee, W.-H. Li and K.C. Lee 92 (1996) 66
- Very low temperature polycrystalline silicon films with very large grains deposited for thin film transistor applications, K.C. Wang, T.R. Yew and H.L. Hwang 92 (1996) 99
- Textured diamond growth by microwave plasma chemical vapor deposition, Y. Liou 92 (1996) 115
- Pulsed-laser deposition of "diamond-like" carbon coating-on $\text{YBa}_2\text{Cu}_3\text{O}_7$ high- T_c superconductor films, A.L. Karuzskii, N.N. Melnik, V.N. Murzin, V.S. Nozdrin, A.V. Perestoronin, N.A. Volchkov and B.G. Zhurkin 92 (1996) 457
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- Multiwavelength irradiation effect in fused quartz ablation using vacuum-ultraviolet Raman laser, K. Sugioka, S. Wada, Y. Ohnuma, A. Nakamura, H. Tashiro and K. Toyoda 96-98 (1996) 347
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- Preparation of TiO_2 thin films by pulsed laser deposition for waveguiding applications, C. Garapon, C. Champeaux, J. Mugnier, G. Panczer, P. Marchet, A. Catherinot and B. Jacquier 96-98 (1996) 836
- Pulsed laser deposition of electroceramic thin films, M. Mertin, D. Offenber, C.W. An, D.A. Wesner and E.W. Kreutz 96-98 (1996) 842
- XPS depth profiling by changing incident X-ray energy, H. Shimada, N. Matsubayashi, M. Imamura, T. Sato and A. Nishijima 100/101 (1996) 56
- Enhanced Raman scattering from copper phthalocyanine on Pt by use of a Weier-

strass prism, M. Futamata, E. Keim, A. Bruckbauer, D. Schumacher and A. Otto 100/101 (1996) 60

Rare earth metals

- Rare-earth doped glass waveguides prepared by pulsed laser deposition, C.N. Afonso, J.M. Ballesteros, J. Gonzalo, G.C. Righini and S. Pelli 96-98 (1996) 760

Rhenium

- Some physical properties of $\text{ReSi}_{1.75}$ single crystals, U. Gottlieb, M. Affronte, F. Nava, O. Laborde, A. Sulpice and R. Madar 91 (1995) 82
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- Surface diffusion and surface atomic roughness on $\text{Ir}(001)$ surface and terraces, C.L. Chen, T.T. Tsong and T.E. Mitchell 94/95 (1996) 224

Rhodium

- Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO . Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
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- NLSDA calculations for H_3 on Rh_5 including high electric fields: Could linear H_3 be stable on Rh-tips?, M.C. Reckzügel and J.H. Block 94/95 (1996) 212
- The segregation behaviour of a $\text{Pt}_{90}\text{Rh}_{10}$ alloy studied with a three-dimensional atom-probe, W. Athenstaedt and M. Leisch 94/95 (1996) 403
- CO adsorption and CO oxidation on $\text{Rh}(100)$, A. Baraldi, L. Gregoratti, G. Comelli, V.R. Dhanak, M. Kiskinova and R. Rosei 99 (1996) 1

Ruthenium

- Ruthenium and sulphide passivation of GaAs, S.T. Ali, S. Ghosh and D.N. Bose 93 (1996) 37

Ru-Cu/ZSM5 catalysts: Characterization by FT-IR spectroscopy, C. Crisafulli, S. Scirè, S. Minicò, R. Maggiore and S. Galvagno

99 (1996) 401

Scanning tunneling microscopy

High-temperature STM for atomic processes on semiconductor surfaces, M. Iwatsuki, T. Sato and Y. Yamamoto

92 (1996) 321

Oxygen etching of the Si(100)-(2 × 1) surface, Y. Wei, Y. Hong and I.S.T. Tsong

92 (1996) 491

Scanning tunneling microscopy observations of recorded organic thin films, Q. Chen, D. Gu, F. Gan, L. Xu and M. Li

93 (1996) 151

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93 (1996) 231

New STM image structures in the confined regions of the Pt(001) surface, T.T. Tsong, C.S. Chang, W.B. Su and K.L. Shih

94/95 (1996) 472

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STM observation of rapidly cooled Si(111) vicinal surfaces, F. Katsuki and K. Kamei

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Scanning tunneling microscopy of charge transfer on the Si(111)7 × 7 surface, D. Jeon, T. Hashizume and T. Sakurai

94/95 (1996) 493

Ultrathin film deposition by pulsed laser ablation using crossed beams, A.A. Gorbunov, W. Pompe, A. Sewing, S.V. Gaponov, A.D. Akhsakhlyan, I.G. Zabrodin, I.A. Kas'kov, E.B. Klyenkov, A.P. Morozov, N.N. Salaschenko, R. Dietsch, H. Mai and S. Völlmar

96-98 (1996) 649

Improved properties of Pulsed Laser Deposited YBaCuO on NdGaO₃ using CeO₂ template layers, D.H.A. Blank, A.J.H.M. Rijnders, F.J.G. Roesthuis, G. den Ouden and H. Rogalla

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99 (1996) 91

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100/101 (1996) 370

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100/101 (1996) 425

STM analysis of wet-chemically prepared H-Si(001) surface, Y. Morita and H. Tokumoto

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Schottky barrier

Electrical characterization of conductive and non-conductive barrier layers for Cu-metallization, C. Ahrens, D. Depta, F. Schithelm and S. Wilhelm

91 (1995) 285

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91 (1995) 342

The ohmic contact to the silicon Schottky barrier using vanadium silicide and gold or silver metallization, A.D. Remenyuk and N.M. Schmidt

91 (1995) 352

Ultra accurate measurements of interface parameters with free-electron laser, C. Coluzza

92 (1996) 267

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92 (1996) 362

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100/101 (1996) 526

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100/101 (1996) 596

Secondary ion mass spectrometry

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91 (1995) 257

Barrier behaviour of plasma deposited silicon oxide and nitride against Cu diffusion, M. Vogt and K. Drescher

91 (1995) 303

Selective deposition of tungsten on ITM-CoSi₂, J.D. Kähler, D. Depta and R. Ferretti

91 (1995) 339

Structural characterization of BaTiO₃ films by sol-gel method using mono-substituting chelating agent, W.-K. Kuo, J.-P. Wang and Y.-C. Ling

92 (1996) 155

Surfactant modified growth of CuInSe₂ thin films, B.-H. Tseng, G.-W. Chang and G.-L. Gu

92 (1996) 227

- Reliability study of sub-micron titanium silicide contacts, C.C. Lin, W.S. Chen, H.L. Hwang, K.Y.J. Hsu, H.K. Liou and K.N. Tu 92 (1996) 660
- Chemical surface modification of fluorocarbon polymers by excimer laser processing, H. Niino and A. Yabe 96-98 (1996) 550
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- Surface and interface analysis of GaSb/GaAs semiconductor materials, K. Li, J. Lin, A.T.S. Wee, K.L. Tan, Z.C. Feng and J.B. Webb 99 (1996) 59
- Application and properties of sub-monomolecular layers of silicon dioxide deposited under mild conditions, D.M. Knotter 99 (1996) 99
- Time-of-flight SIMS study of Bi-Mo selective oxidation catalysts, L.T. Weng, P. Bertrand, O. Tirions and M. Devillers 99 (1996) 185
- High depth resolution depth profiling of metal films using SIMS and sample rotation, D.E. Sykes, A. Chew, J. Hems and K. Stribley 100/101 (1996) 77
- Secondary ion emission from Langmuir-Blodgett (LB) films investigated by time-of-flight secondary ion mass spectrometry, M. Kudo, S. Yamada, S. Yoshida, T. Watanabe and T. Hoshi 100/101 (1996) 129
- Surface oxygen and electrical resistance of $\text{YBa}_2\text{Cu}_3\text{O}_8$, S. Saito, M. Ishihara, T. Tani, T. Maeda, N. Watanabe, I. Rittaporn and N. Koshizuka 100/101 (1996) 260
- Molecular beam epitaxy of $\text{GaAs}/\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{In}_y\text{Ga}_{1-y}\text{As}$ heterostructures for opto-electronic devices: control of growth parameters, K. Köhler 100/101 (1996) 383
- Comparison of MOCVD and MBE semiconductor superlattices for the evaluation of depth resolution in AES and SIMS, M. Furuya, M. Soga and H. Takano 100/101 (1996) 508
- Microstructure studies of PdGe/Ge ohmic contacts to n-type GaAs formed by rapid thermal annealing, W.D. Chen, X.L. Xie, Y.D. Cui, C.H. Chen and C.C. Hsu 100/101 (1996) 530
- Annealing behavior of phosphorus in native oxide films on heavily phosphorus doped silicon, W.B. Ying, Y. Mizokawa, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto 100/101 (1996) 556
- Phosphorus redistribution in the surface region of heavily phosphorus doped silicon, Y. Mizokawa, W.B. Ying, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto 100/101 (1996) 561
- Selective epitaxial Si based layers and TiSi_2 deposition by integrated chemical vapor deposition, J.L. Regolini, J. Margail, S. Bodnar, D. Maury and C. Morin 100/101 (1996) 566
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- Epitaxial growth of $\text{ZnSe}_{1-x}\text{Te}_x$ by the VPE method and its photoluminescence, K. Mochizuki, H. Oguri, T. Kyotani and M. Isshiki 92 (1996) 79
- Growth of ZnSe thin films by radical assisted MOCVD method, T. Aoki, M. Morita, S. Wickramanayaka, Y. Nakanishi and Y. Hatanaka 92 (1996) 132
- Surfactant modified growth of CuInSe_2 thin films, B.-H. Tseng, G.-W. Chang and G.-L. Gu 92 (1996) 227
- Diffusion length measurements on electrodeposited CuInSe_2 cells, S.N. Qiu, C.X. Qiu and I. Shih 92 (1996) 306
- Band lineup modification by Ge interlayer deposition at II-VI/III-V semiconductor heterojunctions, P. Rodríguez-Hernández, M. González-Díaz, M. Fuentes-Cabrera, A. Mujica and A. Muñoz 92 (1996) 408
- Interface of $\text{CuIn}_{1-x}\text{Ga}_x\text{Se}_2/\text{GaAs}$ heterostructure, B.-H. Tseng, S.-B. Lin, G.-L. Gu and H.-Z. Hsu 92 (1996) 412
- Stimulated blue emission processes in $\text{Zn}_{1-x}\text{Cd}_x\text{Se}/\text{ZnSe}$ multi-quantum wells, J.Y. Jen, T. Tsutsumi, I. Souma, Y. Oka, J.R. Anderson and M. Gorska 92 (1996) 547
- Thin film photovoltaics, H.W. Schock 92 (1996) 606
- Preparation of blue-emitting $\text{SrGa}_2\text{Se}_4:\text{Ce}$ thin films by multi-source deposition, Y. Nakanishi, F. Shiba, K. Sowa, H. Tatsuoka, H. Kuwabara, T. Nakamura and Y. Hatanaka 100/101 (1996) 639
- XPS analysis of chemically etched II-VI semiconductor surfaces, A. Kita, M. Ozawa and C.D. Gutleben 100/101 (1996) 652
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- Patterning of copper for multilevel metalization: reactive ion etching and chemical-mechanical polishing, C. Steinbrüchel 91 (1995) 139
- Stress in Al, AlSiCu, and AlPd films on oxidized Si substrates, G.J. Leusink, J.P. Lokker, M.J.C. van den Homberg, J.F. Jongste, T.G.M. Oosterlaken, G.C.A.M. Janssen and S. Radelaar 91 (1995) 215

- Model calculations on a bipolar transistor emitter interconnection with different contact shapes, K. Weide, J. Ullmann and W. Hasse 91 (1995) 234
- Growth rate modeling for selective tungsten LPCVD, H. Wolf, R. Streiter, S.E. Schulz and T. Gessner 91 (1995) 332
- Advanced metallization technology for 256M DRAM, P. Kücher, H. Aochi, J. Gambino, T. Licata, T. Matsuda, S. Nguyen, M. Okazaki, H. Palm and M. Ronay 91 (1995) 359
- Inter-metal dielectric planarization process for 0.35 μm multilevel interconnection devices, M. Bacchetta, C. Zaccherini and L. Zanotti 91 (1995) 367
- Deposition of titanium nitride/tungsten layers for application in vertically integrated circuits technology, G. Ruhl, B. Fröschle, P. Ramm, A. Intemann and W. Pamler 91 (1995) 382
- Theory of dipole generation at cleaved semiconductor surfaces, B. Chen and D. Haneman 92 (1996) 345
- Schottky barrier formation for passivated semiconductor surfaces, R. Saiz-Pardo, R. Rincón and F. Flores 92 (1996) 362
- Chemical trends of barrier heights in metal-semiconductor contacts: on the theory of the slope parameter, W. Mönch 92 (1996) 367
- Semiconductor bond rupture phenomena and surface properties, D. Haneman, N.S. McAlpine, E. Busch and C. Kaalund 92 (1996) 484
- Noise characteristics of an infrared hot-electron transistor, C.H. Kuan 92 (1996) 532
- Novel light quantum and nuclear particle detectors based on the avalanche metal-resistivity layer-semiconductor structure, Z.Y. Sadygov, I.M. Zheleznykh and T.A. Kirillova 92 (1996) 575
- Laser beam application to thin film transistors, T. Sameshima 96-98 (1996) 352
- Electrical characterization of semiconducting La doped SrTiO_3 thin films prepared by pulsed laser deposition, K.-O. Grosse-Holz, J.F.M. Cillessen and R. Waser 96-98 (1996) 784
- Surface and interface analysis of GaSb/GaAs semiconductor materials, K. Li, J. Lin, A.T.S. Wee, K.L. Tan, Z.C. Feng and J.B. Webb 99 (1996) 59
- Real-time analysis of III-V-semiconductor epitaxial growth, W. Richter and J.-T. Zettler 100/101 (1996) 465
- Synthesis of metastable group-IV alloy semiconductors by ion implantation and ion-beam-induced epitaxial crystallization, N. Kobayashi, M. Hasegawa, N. Hayashi, H. Katsumata, Y. Makita, H. Shibata and S. Uekusa 100/101 (1996) 498
- Technology development strategies for the 21st century, M.T. Bohr 100/101 (1996) 534
- A theoretical analysis of temperature dependence on hydrogenated amorphous silicon thin-film transistors with the consideration of resistance of the a-Si:H film layer as a function of temperature, B.-Y. Chen, J.-R. Chen, F.-L. Jenq and C.-S. Hong 100/101 (1996) 601
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- Growth rate modeling for selective tungsten LPCVD, H. Wolf, R. Streiter, S.E. Schulz and T. Gessner 91 (1995) 332
- ### Silica
- Post cleaning of chemical mechanical polishing process, C.-W. Liu, B.-T. Dai and C.-F. Yeh 92 (1996) 176
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- Ti/Co bilayers in silicide technology: electrical evaluation, A. Lauwers, Q.F. Wang, B. Deweerdt and K. Maex 91 (1995) 12
- Improved thermal stability of cobalt silicide formed by ion beam assisted deposition on polysilicon, S. Ravesi, F. La Via, V. Raineri and C. Spinella 91 (1995) 19
- Experimental identification of the optical phonon of CoSi_2 in the infrared, S. Bocelli, G. Guizzetti, F. Marabelli, G. Thungström and C.S. Petersson 91 (1995) 30
- Comparison of CoSi_2 interconnection lines on crystalline and noncrystalline silicon fabricated by writing focused ion beam implantation, J. Teichert, L. Bischoff, E. Hesse, P. Schneider, D. Panknin, T. Gessner, B. Löbner and N. Zichner 91 (1995) 44
- Beam induced phase transformations and self annealing in as-implanted iron silicides, G. Crecelius, K. Radermacher, Ch. Dieker and S. Mesters 91 (1995) 50
- Ni silicides formation and properties in RF sputtered $\text{Ni}_{100-x}\text{Si}_x$ thin films, A. Belu-Marian, M.D. Serbanescu, R. Manaila and A. Devenyi 91 (1995) 63
- Raman study of tetragonal tungsten disilicide, O. Chaix-Pluchery, F. Genet, G. Lucazeau and R. Madar 91 (1995) 68

- Cubic metastable FeSi_{1-x} epitaxially grown on Si and MgO substrates, S. Degroote, A. Vantomme, J. Dekoster and G. Langouche 91 (1995) 72
- Formation of CoSi_2 on strained $\text{Si}_{0.8}\text{Ge}_{0.2}$ using a sacrificial Si layer, R.A. Donaton, S. Kolodinski, M. Caymax, Ph.J. Roussel, H. Bender, B. Brijs and K. Maex 91 (1995) 77
- Some physical properties of $\text{ReSi}_{1.75}$ single crystals, U. Gottlieb, M. Affronte, F. Nava, O. Laborde, A. Sulpice and R. Madar 91 (1995) 82
- Electrical and optical properties of thin $\beta\text{-FeSi}_2$ films on Al_2O_3 substrates, K. Herz and M. Powalla 91 (1995) 87
- Angular dependence of the magnetoresistance of TiSi_2 single crystals, M. Affronte, O. Laborde, U. Gottlieb, O. Thomas and R. Madar 91 (1995) 98
- Phonon dispersion relations of metallic NiSi_2 and CoSi_2 by semi-empirical tight-binding calculation, S. Sanguinetti, C. Calegari and L. Miglio 91 (1995) 103
- Some particular features of the condensation process, structure and properties of thin metal films caused by self-ion bombardment, I.V. Gusev, A.A. Mohnjuk, V.I. Chapljuk and V.P. Belevsky 91 (1995) 182
- Ternary amorphous metallic thin films as diffusion barriers for Cu metallization, M.-A. Nicolet 91 (1995) 269
- Aspects of TiN and Ti deposition in an ECR plasma enhanced CVD process, A. Weber, R. Nikulski, C.-P. Klages, M.E. Gross, R.M. Charatan, R.L. Opilan and W.L. Brown 91 (1995) 314
- Evaluation of selective tungsten plugs on TiN, W and AlSi by analytical and electrical measurements, S.E. Schulz, B. Hintze, W. Grünwald, O. Fiedler and T. Gesaner 91 (1995) 326
- Selective deposition of tungsten on ITM- CoSi_2 , J.D. Kähler, D. Depta and R. Ferretti 91 (1995) 339
- The ohmic contact to the silicon Schottky barrier using vanadium silicide and gold or silver metallization, A.D. Remenyuk and N.M. Schmidt 91 (1995) 352
- On the formation of silicides on poly runners with topography by a two-step sili-cidation process, F. Jonckx, R. Verbeeck, B. Dewerdts and K. Maex 91 (1995) 378
- Reliability study of sub-micron titanium silicide contacts, C.C. Lin, W.S. Chen, H.L. Hwang, K.Y.J. Hsu, H.K. Liou and K.N. Tu 92 (1996) 660
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- Valence band structure of metal silicides modified by argon ion implantation, S. Yamauchi, Y. Hasebe, H. Ohshima, T. Hattori, M. Hirai, M. Kusaka and M. Iwami 100/101 (1996) 522
- Selective epitaxial Si based layers and TiSi_2 deposition by integrated chemical vapor deposition, J.L. Regolini, J. Margail, S. Bodnar, D. Maury and C. Morin 100/101 (1996) 566
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- Epitaxy of $\text{CoSi}_2/\text{Si}(100)$: from Co/Ti/Si(100) to reactive deposition epitaxy, A. Vantomme, S. Degroote, J. Dekoster and G. Langouche 91 (1995) 24
- The modelling routes for the chemical vapour deposition process: application to $\text{Si}_{1-x}\text{Ge}_x$ deposition, M. Pons, C. Bernard, H. Rouch and R. Madar 91 (1995) 34
- Electrical and optical properties of thin $\text{Fe}_{1-x}\text{Co}_x\text{Si}_2$ films, St. Teichert, R. Kilper, Th. Franke, J. Erben, P. Häussler, W. Henrion, H. Lange and D. Panknin 91 (1995) 56
- Cubic metastable FeSi_{1-x} epitaxially grown on Si and MgO substrates, S. Degroote, A. Vantomme, J. Dekoster and G. Langouche 91 (1995) 72
- Formation of CoSi_2 on strained $\text{Si}_{0.8}\text{Ge}_{0.2}$ using a sacrificial Si layer, R.A. Donaton, S. Kolodinski, M. Caymax, Ph.J. Roussel, H. Bender, B. Brijs and K. Maex 91 (1995) 77
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- Metallurgical and electrical investigation of $\text{Pt}_5\text{Ni}_{95}$ /silicon interactions, F. Corni, C. Nobili, G. Ottaviani, R. Tonini, B. Grignaffini Gregorio and G. Queirolo 91 (1995) 107
- Advanced copper interconnections for silicon CMOS technologies, J. Torres 91 (1995) 112
- Stress in Al, AlSiCu, and AlVPd films on oxidized Si substrates, G.J. Leusink, J.P. Lokker, M.J.C. van den Homberg, J.F. Jongste, T.G.M. Oosterlaken, G.C.A.M. Janssen and S. Radelaar 91 (1995) 215
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- W/Si Schottky diodes: effect of sputtering deposition conditions on the barrier height, M. Mamor, E. Dufour-Gergam, L. Finkman, G. Tremblay, F. Meyer and K. Bouziane 91 (1995) 342
- Electrical characteristics of aluminum contacts to porous silicon, S.P. Zimin, V.S. Kuznetsov and A.V. Prokashnikov 91 (1995) 355
- Stability of BaTiO₃ thin films on Si, L.H. Chang and W.A. Anderson 92 (1996) 52
- Study of Ag thin films deposited on porous silicon, T.F. Young, J.F. Liu, C.C. Wu, G.H. Fu and C.S. Chen 92 (1996) 57
- Effects of substrate cleaning and film thickness on the epitaxial growth of ultrahigh vacuum deposited Cu thin films on (001)Si, C.S. Liu and L.J. Chen 92 (1996) 84
- Very low temperature polycrystalline silicon films with very large grains deposited for thin film transistor applications, K.C. Wang, T.R. Yew and H.L. Hwang 92 (1996) 99
- Disordered Si/SiGe superlattices grown by ultrahigh vacuum chemical vapor deposition, T.-C. Chang, W.-K. Yeh, C.-Y. Chang, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 119
- Characteristics of PECVD GaN thin films, C.H. Lee and C.T. Chen 92 (1996) 124
- Ge deposition from digermane on the Si(100)-(2 × 1) surface, H.-C. Cho 92 (1996) 128
- Growth of the thin film Cd-Si-As system by metalorganic chemical vapor deposition, H. Kayama, Y. Noda and Y. Furukawa 92 (1996) 142
- The electrical and optical characteristics of GaAs on Si by modified flow rate modulation epitaxy, M.K. Lee, C.C. Hu, and C.Z. Hwang 92 (1996) 159
- The properties of SiO₂ films using direct photo-chemical vapor deposition on strained SiGe layers, C.T. Lin, S.J. Chang, D.K. Nayak and Y. Shiraki 92 (1996) 193
- Porous silicon studied by SiL₂₃ soft X-ray emission, R.S. Crisp, D. Haneman and R. Sabet-Darini 92 (1996) 198
- Application of irradiation-then-nitridation to improve the radiation hardness in MOS gate dielectrics, K.-C. Lee and J.-G. Hwu 92 (1996) 204
- In situ X-ray reflectivity measurement of thin film growth during vacuum deposition, C.-H. Lee and S.-Y. Tseng 92 (1996) 282
- XPS study of the reaction of the Si(100) surface with a C₂H₄ beam, T. Takagaki, Y. Igari, T. Takaoka and I. Kusunoki 92 (1996) 287
- Electron paramagnetic resonance measurements on porous silicon, T. Nakamura, K. Sasaki, K. Hayashi, H. Mimura and J. Kobayashi 92 (1996) 291
- Ellipsometric study of thermal and laser annealed amorphous and microcrystalline silicon films, A.H. Jayatissa, M. Suzuki, Y. Nakanishi and Y. Hatanaka 92 (1996) 300
- Interface phase transition as observed in ultra thin FeSi₂ epilayers, J. Derrien, I. Berbezier, A. Ronda and J.Y. Natoli 92 (1996) 311
- High-temperature STM for atomic processes on semiconductor surfaces, M. Iwatsuki, T. Sato and Y. Yamamoto 92 (1996) 321
- Interdiffusion and reactions in the Cu/TiN/Si thin film system, Y.S. Gong, J.-C. Lin and C. Lee 92 (1996) 335
- The determination of the average compositions of amorphous interlayers in the V/Si system using a buried ultrathin oxide layer and a capping Mo layer to define the reference planes for interdiffusion, J.H. Lin and L.J. Chen 92 (1996) 340
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- Schottky barrier formation for passivated semiconductor surfaces, R. Saiz-Pardo, R. Rincón and F. Flores 92 (1996) 362
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- Refractive index behavior of boron-doped silica films by plasma-enhanced chemical vapor deposition, R.H. Hornig, F. Chen, D.S. Wu and T.Y. Lin 92 (1996) 387
- PL properties of porous Si anodized with various light illuminations, H. Mimura, T. Matsumoto and Y. Kanemitsu 92 (1996) 396
- Surface charge transfer in plastically deformed Si, B. Pohoryles and A. Morawski 92 (1996) 417
- In situ radiotracer method for study of adsorption on semiconductor single crystal surfaces, M. Szklarczyk 92 (1996) 431
- Oxygen etching of the Si(100)-(2 × 1) surface, Y. Wei, Y. Hong and I.S.T. Tsong 92 (1996) 491
- First-principles calculations of Ga adatom structures for Ge(111) and Si(111) surfaces, C. Cheng and K. Kunc 92 (1996) 496
- Structural evolution and atomic structure of

- ultrahigh vacuum deposited Au thin films on silicon at low temperatures, C.R. Chen and L.J. Chen 92 (1996) 507
- Diffusion phenomena in MBE grown Si/SiGe single quantum wells studied by PL and TEM measurements, H.P. Zeindl, S. Nilsson and E. Bugiel 92 (1996) 552
- Dopant activation and strain relaxation in P-implanted metastable pseudomorphic $\text{Ge}_{0.12}\text{Si}_{0.88}$ grown on Si(100), D.Y.C. Lie, N.D. Theodore and J.H. Song 92 (1996) 557
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- Thin film photovoltaics, H.W. Schock 92 (1996) 606
- Correlation between light emission and dangling bonds in porous silicon, M. Shimazaki, Y. Show, M. Iwase, T. Izumi, T. Ichinohe, S. Nozaki and H. Morisaki 92 (1996) 617
- Formation of bottom oxides in porous silicon films by anodic oxidation, C.H. Lee, C.C. Yeh, C.H. Lee and K.Y.J. Hsu 92 (1996) 621
- Tungsten absorber on silicon membrane, D.C. Li, C.S. Yoo and C.Y. Sun 92 (1996) 665
- A new method for the detection of hydrogen spillover, M. Holmberg and I. Lundström 93 (1996) 67
- Field emission from the surface quantum well of silicon, Q.-A. Huang 93 (1996) 77
- Microstructural properties of laser synthesized Si/C/N nanoparticles, R. Giorgi, S. Turtù, G. Zappa, E. Borsella, S. Botti, M.C. Cesile and S. Martelli 93 (1996) 101
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- Ellipsometric studies of the oxidation kinetics of Cu particles supported on oxidised Si(100), R. van Wijk, O.L.J. Gijzeman and J.W. Geus 93 (1996) 237
- Gas-phase room-temperature oxidation of (100) silicon, G.F. Cerofolini, G. La Bruna and L. Meda 93 (1996) 255
- Modelling of the field emission microtriode with emitter covered with porous silicon, D. Nicolaescu, V. Filip and P.R. Wilshaw 94/95 (1996) 79
- Field emission characteristics of polycrystalline and single-crystalline diamond grown on Si tips, E.I. Givargizov, V.V. Zhirnov, A.N. Stepanova, P.S. Plekhanov and R.I. Kozlov 94/95 (1996) 117
- Diamond coated Si and Mo field emitters: diamond thickness effect, V.V. Zhirnov, W.B. Choi, J.J. Cuomo and J.J. Hren 94/95 (1996) 123
- Field emission properties of Au-Si eutectic, V.V. Zhirnov, L. Bormatova, E.I. Givargizov, P.S. Plekhanov, U.T. Son, A.V. Galdetsky and B.A. Belyavsky 94/95 (1996) 144
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- STM observation of rapidly cooled Si(111) vicinal surfaces, F. Katsuki and K. Kamei 94/95 (1996) 485
- Scanning tunneling microscopy of charge transfer on the Si(111) 7×7 surface, D. Jeon, T. Hashizume and T. Sakurai 94/95 (1996) 493
- Analytical description of the film thickness distribution obtained by the pulsed laser ablation of a monoatomic target: application to silicon and germanium, F. Antoni, C. Fuchs and E. Fogarassy 96-98 (1996) 50
- Electromagnetic diagnostics during pulsed laser deposition, A.V. Kabashin, W. Marine, P.I. Nikitin and M. Sentis 96-98 (1996) 139
- Temperature measurements during laser ablation of Si into He, Ar and O_2 , H.C. Le, R.W. Dreyfus, W. Marine, M. Sentis and I.A. Movtchan 96-98 (1996) 164
- Dynamics of silicon plume generated by laser ablation and its chemical reaction, T. Makimura and K. Murakami 96-98 (1996) 242
- Optical spectroscopy of emission from Si-SiO_x nanoclusters formed by laser ablation, I.A. Movtchan, W. Marine, R.W. Dreyfus, H.C. Le, M. Sentis and M. Autric 96-98 (1996) 251
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- Single shot excimer laser annealing of amorphous silicon for AMLCD, P. Boher, J.L. Stehle, M. Stehle and B. Godard 96-98 (1996) 376
- Photon-induced dry etching of Si(100) in the VUV, U. Streller, B. Li, A. Krabbe and N. Schwentner 96-98 (1996) 448
- Laser-induced formation of visible light emitting silicon, D. Dimova-Malinovska, M. Tzolov, N. Malinowski, Ts. Marinova and V. Krastev 96-98 (1996) 457

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- Sampling depth of total electron and fluorescence measurements in Si L- and K-edge absorption spectroscopy, M. Kasrai, W.N. Lennard, R.W. Brunner, G.M. Bancroft, J.A. Bardwell and K.H. Tan 99 (1996) 303
- Determination of the interface region in multilayer Si/Mo by Auger depth profile and factor analysis, T. Morohashi, T. Hoshi, H. Nikaido and M. Kudo 100/101 (1996) 84
- Damage profiling of Ar⁺ sputtered Si(100) surface by medium energy ion scattering spectroscopy, J.C. Lee, C.S. Jeong, H.J. Kang, H.K. Kim and D.W. Moon 100/101 (1996) 97
- Influence of ion-implantation on native oxidation of Si in a clean-room atmosphere, F. Yano, A. Hiraoka, T. Itoga, H. Kojima, K. Kanehori and Y. Mitsui 100/101 (1996) 138
- Luminescent properties of an anodically oxidized P-doped silicon wafer, M. Iwase and T. Arakawa 100/101 (1996) 147
- Structural fluctuation of SiO₂ network at the interface with Si, Y. Sugita, S. Watanabe, N. Awaji and S. Komiya 100/101 (1996) 268
- Ultrahigh vacuum system for atomic-scale planarization of 6 inch Si(001) substrate, K. Idota, M. Niwa and I. Sumita 100/101 (1996) 311
- Dissociative scattering of low-energy SiF₃⁺ and SiF⁺ ions (5-200 eV) on Cu(100) surface, H. Yamamoto, Y. Baba and T.A. Sasaki 100/101 (1996) 333
- CBE-grown high-quality GaAs on Si substrate, H. Uchida, M. Adachi, H. Nishikawa, T. Egawa, T. Jimbo and M. Umeno 100/101 (1996) 399
- Infrared external reflection spectroscopy of self-assembled monolayer films on Si substrate with a buried metal layer (BML) structure, Y. Kobayashi and T. Ogino 100/101 (1996) 407
- Initial stage of oxidation of Si(100) surfaces in dry oxygen, K. Inanaga, T. Nakahata, T. Furukawa and K. Ono 100/101 (1996) 421
- Atomically flat, ultra thin-SiO₂/Si(001) interface formation by UHV heating, M. Niwa, K. Okada and R. Sinclair 100/101 (1996) 425
- Initial oxidation of Si(311) surfaces studied by high-resolution electron energy loss spectroscopy, H. Ikeda, T. Yamada, K. Hotta, S. Zaima and Y. Yasuda 100/101 (1996) 431
- High purity ozone oxidation on hydrogen passivated silicon surface, A. Kurokawa and S. Ichimura 100/101 (1996) 436
- STM analysis of wet-chemically prepared H-Si(001) surface, Y. Morita and H. Tokumoto 100/101 (1996) 440
- Oxygen adsorption on hydrogen-adsorbed Si(111)7×7 observed by second harmonic generation (SHG), K. Nakamura, S. Ichimura and H. Shimizu 100/101 (1996) 444
- Growth kinetics of thermal oxidation process on Si(100) by real time ultraviolet photoelectron spectroscopy, Y. Enta, Y. Takegawa, M. Sumitsu and N. Miyamoto 100/101 (1996) 449
- Initial stages of oxidation of hydrogen-terminated Si surface stored in air, T. Miura, M. Niwano, D. Shoji and N. Miyamoto 100/101 (1996) 454
- Doping dependence of second harmonic generation from native oxide/Si(111)

- interfaces, H. Hirayama, K. Watanabe and M. Kawada 100/101 (1996) 460
- Epitaxial growth of GaAs on HF-treated Si substrates, Y. Uchida, J. Minemura, Y. Yazawa and T. Warabisako 100/101 (1996) 478
- GaAs-based LED on Si substrate with GaAs islands active region by droplet-epitaxy, Y. Hasegawa, T. Egawa, T. Jimbo and M. Umeno 100/101 (1996) 482
- Novel method of strain-relaxed $\text{Si}_{1-x}\text{Ge}_x$ growth on Si(100) by MBE, H. Iwano, K. Yoshikawa, A. Kojima, K. Hayashi, S. Zaima and Y. Yasuda 100/101 (1996) 487
- Si epitaxial growth at low temperatures using remote plasma process, A. Yoshida, K. Utsumi and A. Ganjoo 100/101 (1996) 491
- Synthesis of metastable group-IV alloy semiconductors by ion implantation and ion-beam-induced epitaxial crystallization, N. Kobayashi, M. Hasegawa, N. Hayashi, H. Katsumata, Y. Makita, H. Shibata and S. Uekusa 100/101 (1996) 498
- Atomic structure analysis of the interfaces in Si/Ge superlattices, K. Sumitomo, T. Nishioka and T. Ogino 100/101 (1996) 503
- Co overlayer formation process on Si(100) 2×1 studied by SR-PES, T. Jikimoto, C. Heck, K. Komoku, M. Hirai, M. Kusaka and M. Iwami 100/101 (1996) 513
- Behavior of ultrathin layers of Co on Si and Ge systems, K. Prabhakaran and T. Ogino 100/101 (1996) 518
- Electrical properties of metal/ $\text{Si}_{1-x}\text{Ge}_x$ /Si(100) heterojunctions, H. Shinoda, M. Kosaka, J. Kojima, H. Ikeda, S. Zaima and Y. Yasuda 100/101 (1996) 526
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- Phosphorus redistribution in the surface region of heavily phosphorus doped silicon, Y. Mizokawa, W.B. Ying, Y.B. Yu, Y. Kamiura, M. Iida and K. Kawamoto 100/101 (1996) 561
- Selective epitaxial Si based layers and TiSi_2 deposition by integrated chemical vapor deposition, J.L. Regolini, J. Margail, S. Bodnar, D. Maury and C. Morin 100/101 (1996) 566
- In-situ IR and mass spectroscopic study of the $\text{Al}(\text{CH}_3)_2\text{H}/\text{a-Si:H}$ reaction processes, T. Wadayama, Y. Maiwa, H. Shibata and A. Hatta 100/101 (1996) 575
- Low temperature etching of Si and PR in high density plasmas, M. Puech and Ph. Maquin 100/101 (1996) 579
- Deep trench etching in silicon with fluorine containing plasmas, R.D. Mansano, P. Verdonck and H.S. Maciel 100/101 (1996) 583
- A theoretical analysis of temperature dependence on hydrogenated amorphous silicon thin-film transistors with the consideration of resistance of the a-Si:H film layer as a function of temperature, B.-Y. Chen, J.-R. Chen, F.-L. Jenq and C.-S. Hong 100/101 (1996) 601
- Infrared study of chemistry of Si surfaces in etching solution, M. Niwano, T. Miura, R. Tajima and N. Miyamoto 100/101 (1996) 607
- Characterization of MOCVD-grown GaAs on Si by spectroscopic ellipsometry, G. Yu, T. Soga, T. Jimbo and M. Umeno 100/101 (1996) 617
- ZnSe crystal growth by radical assisted MOCVD, Y. Hatanaka, T. Aoki, M. Morita and Y. Nakanishi 100/101 (1996) 621
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- Ohmic contacts to p-type 6H-silicon carbide, O. Nennewitz, L. Spiess and V. Breternitz 91 (1995) 347
- XPS studies on SiC thin layers formed by ion implantation with a metal vapor vacuum arc ion source, H. Yan, R.W.M. Kwok and S.P. Wong 92 (1996) 61
- Excimer laser-induced hydrodynamical effects and surface modifications on silicon carbide, G. Nicolas and M. Autric 96-98 (1996) 296
- Excimer laser induced thermal evaporation and ablation of silicon carbide, R. Reitano, P. Baeri and N. Marino 96-98 (1996) 302
- Laser reactive ablation deposition of silicon carbide films, G. Leggieri, A. Luches, M. Martino, A. Perrone, R. Alexandrescu, A. Barborica, E. Gyorgy, I.N. Mihailescu, G. Majni and P. Mengucci 96-98 (1996) 866
- Surface composition of CVD-grown α -SiC layers—an XPS and LEED study, H. Behner and R. Rupp 99 (1996) 27
- Interface chemistry and electric characterisation of nickel metallisation on 6H-SiC, Ts. Marinova, V. Krastev, C. Hallin, R. Yakimova and E. Janzén 99 (1996) 119
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- LPCVD $\text{Re}_2\text{Si}_3\text{N}_4$ diffusion barriers in Si/SiO₂/Cu metallizations, A.-M. Dutron, E. Blanquet, C. Bernard, A. Bachli and R. Madar 91 (1995) 277
- Barrier behaviour of plasma deposited silicon oxide and nitride against Cu diffusion, M. Vogt and K. Drescher 91 (1995) 303

- Tribochemical characterization of the lubrication film at the $\text{Si}_3\text{N}_4/\text{Si}_3\text{N}_4$ interface sliding in aqueous solutions, F. Honda and T. Saito 92 (1996) 651
- Studies of silicon-nitride (Si_3N_4) using laser ablation mass spectrometry, S.L. Wang, K.W.D. Ledingham, W.J. Jia and R.P. Singhal 93 (1996) 205
- Photoluminescence enhancement of $(\text{NH}_4)_2\text{S}_x$ passivated InP surface by rapid thermal annealing, W.D. Chen, X.Q. Li, L.H. Duan, X.L. Xie and Y.D. Cui 100/101 (1996) 592

Silicon oxide

- Ti-diffusion barrier in Cu-based metallization, F. Braud, J. Torres, J. Palleau, J.-L. Mermet and M.-J. Mouche 91 (1995) 251
- LPCVD $\text{Re}_x\text{Si}_y\text{N}_z$ diffusion barriers in $\text{Si}/\text{SiO}_2/\text{Cu}$ metallizations, A.-M. Dutron, E. Blanquet, C. Bernard, A. Bachli and R. Madar 91 (1995) 277
- Barrier behaviour of plasma deposited silicon oxide and nitride against Cu diffusion, M. Vogt and K. Drescher 91 (1995) 303
- The properties of SiO_2 films using direct photo-chemical vapor deposition on strained SiGe layers, C.T. Lin, S.J. Chang, D.K. Nayak and Y. Shiraki 92 (1996) 193
- A new method for the detection of hydrogen spillover, M. Holmberg and I. Lundström 93 (1996) 67
- Optical spectroscopy of emission from Si-SiO_x nanoclusters formed by laser ablation, I.A. Movtchan, W. Marine, R.W. Dreyfus, H.C. Le, M. Sents and M. Autric 96-98 (1996) 251
- Application and properties of sub-monomolecular layers of silicon dioxide deposited under mild conditions, D.M. Knotter 99 (1996) 99
- ^{18}O -exchange with the substrate during ^{18}O oxidation of Cu particles supported on ^{16}O -oxidised $\text{Si}(100)$, R. van Wijk, C.H.M. Marée, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 99 (1996) 197
- High resolution electron microscopy characterization of small Pt-Pd/ SiO_2 particles in oxide-reducing cycles, A. Vázquez and F. Pedraza 99 (1996) 213
- Properties of radio frequency magnetron sputtered silicon dioxide films, W.-F. Wu and B.-S. Chiou 99 (1996) 237
- Sampling depth of total electron and fluorescence measurements in Si L- and K-edge absorption spectroscopy, M. Kas-

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- Structural fluctuation of SiO_2 network at the interface with Si, Y. Sugita, S. Watanabe, N. Awaji and S. Komiya 100/101 (1996) 268
- Atomically flat, ultra thin- $\text{SiO}_2/\text{Si}(001)$ interface formation by UHV heating, M. Niwa, K. Okada and R. Sinclair 100/101 (1996) 425
- Doping dependence of second harmonic generation from native oxide/ $\text{Si}(111)$ interfaces, H. Hirayama, K. Watanabe and M. Kawada 100/101 (1996) 460

Silver

- The ohmic contact to the silicon Schottky barrier using vanadium silicide and gold or silver metallization, A.D. Remenyuk and N.M. Schmidt 91 (1995) 352
- Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
- Study of Ag thin films deposited on porous silicon, T.F. Young, J.F. Liu, C.C. Wu, G.H. Fu and C.S. Chen 92 (1996) 57
- Surfactant effect of Sb on the growth of Ag films on a sapphire substrate, T. Lewowski and P. Wiczorek 93 (1996) 85
- The chemistry and structure of $(222)\text{CdO}/\text{Ag}$ heterophase interfaces on an atomic scale, D.K. Chan, D.N. Seidman and K.L. Merkle 94/95 (1996) 409
- Atomic-scale studies of silver segregation at MgO/Cu heterophase interfaces, D.A. Shashkov and D.N. Seidman 94/95 (1996) 416
- Ablation from metals induced by visible and UV laser irradiation, W. Svendsen, J. Schou, B. Thestrup and O. Ellegaard 96-98 (1996) 518
- Influence of oxygen on the mass diffusion of Ag on $\text{Cu}(110)$: a laterally resolved photoemission study, U. Kürpick, G. Meister and A. Goldmann 99 (1996) 221
- Wettability of native silver surfaces, M.A. Osman and B.A. Keller 99 (1996) 261
- Preparation of thin silver films on mica studied by XRD and AFM, J.-D. Grunwaldt, F. Atamny, U. Göbel and A. Baiker 99 (1996) 353

Solar cells

- Influence of KCN treatment on CuInS_2 thin films, Y. Ogawa, A. Jäger-Waldau, T.H. Hua, Y. Hashimoto and K. Ito 92 (1996) 232

Sputter deposition

- Electrical and optical properties of thin $\text{Fe}_{1-x}\text{Co}_x\text{Si}_2$ films, St. Teichert, R. Kilper, Th. Franke, J. Erben, P. Häussler, W. Henrion, H. Lange and D. Panknin 91 (1995) 56
- Ni silicides formation and properties in RF sputtered $\text{Ni}_{100-x}\text{-Si}_x$ thin films, A. Belu-Marian, M.D. Serbanescu, R. Manaila and A. Devenyi 91 (1995) 63
- Formation of CoSi_2 on strained $\text{Si}_{0.8}\text{Ge}_{0.2}$ using a sacrificial Si layer, R.A. Donaton, S. Kolodinski, M. Caymax, Ph.J. Roussel, H. Bender, B. Brijs and K. Maëx 91 (1995) 77
- Metallurgical and electrical investigation of $\text{Pt}_3\text{Ni}_{95}$ /silicon interactions, F. Corni, C. Nobili, G. Ottaviani, R. Tonini, B. Grignaffini Gregorio and G. Queirolo 91 (1995) 107
- Stress in Al, AlSiCu, and AlVPd films on oxidized Si substrates, G.J. Leusink, J.P. Lokker, M.J.C. van den Homberg, J.F. Jongste, T.G.M. Oosterlaken, G.C.A.M. Janssen and S. Radelaar 91 (1995) 215
- Hillock recognition by digital image processing, M. Zaborowski, M. Adamiec and A. Barcz 91 (1995) 246
- Sputtering of tantalum-based diffusion barriers in Si/Cu metallization: effects of gas pressure and composition, M. Stavrev, C. Wenzel, A. Möller and K. Drescher 91 (1995) 257
- Co-sputtered TiB_2 as a diffusion barrier for advanced microelectronics with Cu metallization, G. Sade and J. Pelleg 91 (1995) 263
- Ternary amorphous metallic thin films as diffusion barriers for Cu metallization, M.-A. Nicolet 91 (1995) 269
- Electrical characterization of conductive and non-conductive barrier layers for Cu-metallization, C. Ahrens, D. Depta, F. Schithelm and S. Wilhelm 91 (1995) 285
- Electrical characterization of reactively sputtered TiN diffusion barrier layers for copper metallization, C. Kaufmann, J. Baumann, T. Gessner, T. Raschke, M. Rennau and N. Zichner 91 (1995) 291
- Ti nitride phases in thin films deposited by DC magnetron sputtering, R. Manaila, D. Biro, P.B. Barna, M. Adamik, F. Zavaliche, S. Craciun and A. Devenyi 91 (1995) 295
- Integration of a TiN barrier layer formed by rapid thermal annealing in a 1 μm CMOS process, K.-H. Stegemann, V. Heinig, G. Fontaine, J. Palorec and C. Beyer 91 (1995) 308
- W/Si Schottky diodes: effect of sputtering deposition conditions on the barrier height, M. Mamor, E. Dufour-Gergam, L. Finkman, G. Tremblay, F. Meyer and K. Bouziane 91 (1995) 342
- Ohmic contacts to p-type 6H-silicon carbide, O. Nennewitz, L. Spiess and V. Breternitz 91 (1995) 347
- Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
- Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on $\text{MgO}(001)$, H. Qiu, T. Ohbuchi, H. Nakai and M. Hashimoto 92 (1996) 47
- Stability of BaTiO_3 thin films on Si, L.H. Chang and W.A. Anderson 92 (1996) 52
- Interdiffusion and reactions in the Cu/TiN/Si thin film system, Y.S. Gong, J.-C. Lin and C. Lee 92 (1996) 335
- Structural and optical properties of $\text{Pd}_{1-x}\text{In}_x$ thin films, W.T. Wu, P.E. Schmid and F. Lévy 92 (1996) 391
- Coercivity of $\gamma\text{-(Fe}_{0.74}\text{Mn}_{0.15}\text{Co}_{0.11})_2\text{O}_3$ thin films by dc reactive magnetron sputtering, W.-D. Chang and T.-S. Chin 92 (1996) 475
- Properties of multilayered thin films for thermal ink-jet printing devices, D.S. Wu, M.L. Lee and T.Y. Lin 92 (1996) 626
- Carbon nitride - prospects for ultimate performance of superhard materials, S.A. Uglov, V.E. Shub, A.A. Beloglazov and V.I. Konov 92 (1996) 656
- Characterization of sputter-deposited multilayers of Ni and Zr with APFIM/TAP, T. Al-Kassab, M.-P. Macht, V. Naundorf, H. Wollenberger, S. Chambrelaud, F. Danoix and D. Blavette 94/95 (1996) 306
- Low-fluence excimer laser irradiation-induced defect formation in indium-tin oxide films, T. Szörényi, L.D. Laude, I. Bertóti, Zs. Geretovszky and Z. Kántor 96-98 (1996) 363
- Zr-silicide formation during the epitaxial growth of Y-stabilized zirconia films on Si(100) and its avoidance by ion beam assisted deposition at a reduced temperature, T. Koch and P. Ziemann 99 (1996) 51
- Properties of radio frequency magnetron sputtered silicon dioxide films, W.-F. Wu and B.-S. Chiou 99 (1996) 237
- Chemical, mechanical and electrical properties of CN_x -films produced by reactive sputtering and N^+ -implantation in carbon films, N. Laidani, A. Miotello and J. Perrière 99 (1996) 273

- XPS study of carbon/inconel bilayers as a function of substrate bias, M.S. Aouadi, P.C. Wong and K.A.R. Mitchell 99 (1996) 319
- Analysis of the sensing mechanism of tin dioxide thin film gas sensors using the change of work function in flammable gas atmosphere, B. Yea, R. Konishi, T. Osaki, S. Abe, H. Tanioka and K. Sugahara 100/101 (1996) 365
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- Comments on explosive mechanisms of laser sputtering, R. Kelly and A. Miotello 96-98 (1996) 205
- Damage profiling of Ar^+ sputtered Si(100) surface by medium energy ion scattering spectroscopy, J.C. Lee, C.S. Jeong, H.J. Kang, H.K. Kim and D.W. Moon 100/101 (1996) 97
- Processes in low-energy ion-surface collisions: preferential sputtering, defect and adatom formation, H. Gnaser 100/101 (1996) 316
- Preferential sputtering and surface segregation of CuZr alloys, H.J. Kang, C.H. Kim, N.S. Park, D.J. O'Connor and R. MacDonald 100/101 (1996) 329
- ### Steel
- An atom probe study of cementite precipitation in autotempered martensite in an Fe-Mn-C alloy, R.C. Thomson and M.K. Miller 94/95 (1996) 313
- Observation of molybdenum-nitrogen clustering in highly alloyed martensite, L. Lundin and H.-O. Andr  n 94/95 (1996) 320
- Investigation of precipitation in a new maraging stainless steel, K. Stiller, F. Danoix and A. Bostel 94/95 (1996) 326
- Microstructural influences on the decomposition of an Al-containing ferritic stainless steel, H.G. Read and H. Murakami 94/95 (1996) 334
- APFIM studies of the phase transformations in thermally aged ferritic FeCuNi alloys: comparison with aging under neutron irradiation, P.J. Pareige, K.F. Russell and M.K. Miller 94/95 (1996) 362
- Characterization of neutron-induced copper-enriched clusters in pressure vessel steel weld: an APFIM study, P. Pareige and M.K. Miller 94/95 (1996) 370
- APFIM characterization of a high phosphorus Russian RPV weld, M.K. Miller and K.F. Russell 94/95 (1996) 378
- Phase separation in the Fe-Cr-Ni system, M.K. Miller, I.M. Anderson, J. Bentley and K.F. Russell 94/95 (1996) 391
- Comparison of the rate of decomposition in Fe-45%Cr, Fe-45%Cr-5%Ni and duplex stainless steels, M.K. Miller and K.F. Russell 94/95 (1996) 398
- Effect of different surface treatments on the precipitation of boron nitride for stainless steel SUS304, Y. Suzuki, T. Homma, M. Minato and Y. Itoh 100/101 (1996) 165
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- STM study of Sr adsorption on Si(100) surface, R.Z. Bakhtizin, J. Kishimoto, T. Hashizume and T. Sakurai 94/95 (1996) 478
- NO interaction with thermally activated CaO and SrO surfaces, Y. Yanagisawa 100/101 (1996) 256
- Preparation of blue-emitting SrGa_2Se_4 :Ce thin films by multi-source deposition, Y. Nakanishi, F. Shiba, K. Sowa, H. Tatsuoka, H. Kuwabara, T. Nakamura and Y. Hatanaka 100/101 (1996) 639
- Preparation and photoluminescent characteristics of $\text{Zn}_x\text{Sr}_{1-x}\text{S}$:Ce thin films, S.T. Lee, M. Kitagawa, K. Ichino and H. Kobayashi 100/101 (1996) 656
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- Influence of KCN treatment on CuInS_2 thin films, Y. Ogawa, A. J  ger-Waldau, T.H. Hua, Y. Hashimoto and K. Ito 92 (1996) 232
- Ruthenium and sulphide passivation of GaAs, S.T. Ali, S. Ghosh and D.N. Bose 93 (1996) 37
- A study of galena (PbS) surfaces under controlled potential in pH 4.6 solution by synchrotron radiation excited photoelectron spectroscopy, I. Kartio, K. Laajalehto, T. Kaurila and E. Suoninen 93 (1996) 167
- Studies of 1T TiS_2 by STM, AFM and XPS: the mechanism of hydrolysis in air, H. Martinez, C. Auriel, D. Gonbeau, M. Loudet and G. Pfister-Guilouzo 93 (1996) 231
- Surface sulfide on (100) W: formation, stability, absolute concentration of sulfur, N.R. Gall, E.V. Rut'kov, A.Ya. Tontegode and M.M. Usufov 93 (1996) 353
- XeCl laser ablation of thin film ZnS , W.M. Cranton, P.H. Key, D. Sands, C.B. Thomas and F.X. Wagner 96-98 (1996) 501
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- Sprayed films of stannite $\text{Cu}_2\text{ZnSnS}_4$, N. Nakayama and K. Ito 92 (1996) 171

- Adsorption of H_2S on GaP(001) surface and passivation effects studied by AES, LEED and XPS, Y. Fukuda, N. Sanada, M. Kuroda and Y. Suzuki 92 (1996) 212
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- Preparation and photoluminescent characteristics of $Zn_{1-x}Sr_xS$:Ce thin films, S.T. Lee, M. Kitagawa, K. Ichino and H. Kobayashi 100/101 (1996) 656
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- High temperature SO_2 retention by CaO, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 99 (1996) 111
- Superconductors*
- Characterization of freeze-dried powders prepared by alkoxide route for YBCO superconductors, T. Tachiwaki, J. Sugimoto, T. Ito and A. Hiraki 100/101 (1996) 272
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- Electrical properties of laser deposited $YBa_2Cu_3O_{7-x}$ films on silicon wafers, F.Y. Chuang, C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin 92 (1996) 452
- Pulsed-laser deposition of "diamond-like" carbon coating on $YBa_2Cu_3O_7$ high- T_c superconductor films, A.L. Karuzskii, N.N. Melnik, V.N. Murzin, V.S. Nozdrin, A.V. Perestoronin, N.A. Volchikov and B.G. Zhurkin 92 (1996) 457
- Investigation on origin of excess noise in superconducting and normal state BiSr-CaCuO films, A.L. Li and I. Shih 92 (1996) 461
- Spectroscopic study of the microwave plasma enhanced pulsed laser deposition for $Y_1Ba_2Cu_3O_{7-x}$ superconducting thin films, B.C. Chung, C.H. Tsai, S.S. Hsu, C.S. Huang, T.Y. Tseng and I.N. Lin 96-98 (1996) 233
- Single crystal laser patterning for selective $YBa_2Cu_3O_{7-x}$ growth, R. Aguiar, F. Sánchez and M. Varela 96-98 (1996) 405
- Formation of artificially-layered high-temperature superconductors using pulsed-laser deposition, D.P. Norton, B.C. Chakoumakos, D.H. Lowndes and J.D. Budai 96-98 (1996) 672
- Stoichiometric transfer of complex oxides by pulsed laser deposition, B. Dam, J.H. Rector, J. Johansson, S. Kars and R. Griessen 96-98 (1996) 679
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- The importance of gas scattering processes on the stoichiometry deviations of laser deposited films, J. Gonzalo, C.N. Afonso, J. Perrière and R. Gómez San Roman 96-98 (1996) 693
- Critical thickness of $YBaCuO$ (123) strained thin films and superlattices grown by pulsed laser deposition, A. Abert, J.P. Contour, A. Défossez, D. Ravelosoa, W. Schwegle and P. Ziemann 96-98 (1996) 703
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- Ion-assisted pulsed-laser deposition for the fabrication of Y-Ba-Cu-O multilayer structures using oriented intermediate layers of YSZ and CeO_2 , R.P. Reade and R.E. Russo 96-98 (1996) 726
- Synthesis of RE-Ba-Sr-Cu-O by pulsed-laser deposition, E. Stangl, S. Proyer, B. Hellebrand and D. Bäuerle 96-98 (1996) 731

Mirror-smooth $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ superconducting films deposited by plasma-enhanced pulsed laser deposition technique, C.S. Huang, T.Y. Tseng, B.C. Chung, C.H. Tsai, H.F. Cheng and I.N. Lin

96-98 (1996) 735

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96-98 (1996) 739

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100/101 (1996) 260

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100/101 (1996) 347

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92 (1996) 119

Novel epitaxial growth and magnetotransport characterization of single crystal $\text{Co}(11\bar{2}0)/\text{Cr}(100)$ superlattices on Mo buffer layers, J.C.A. Huang, Y.D. Yao, Y. Liou, S.F. Lee, W.T. Yang, C.P. Chang, S.Y. Liao and C.H. Lee

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92 (1996) 566

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96-98 (1996) 672

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96-98 (1996) 703

Atomic structure analysis of the interfaces in Si/Ge superlattices, K. Sumitomo, T. Nishioka and T. Ogino

100/101 (1996) 503

Surface composition

Novel method of strain-relaxed $\text{Si}_{1-x}\text{Ge}_x$ growth on Si(100) by MBE, H. Iwano, K. Yoshikawa, A. Kojima, K. Hayashi, S. Zaima and Y. Yasuda

100/101 (1996) 487

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Classification of particulates on pulsed-laser deposited Y-Ba-Cu-O films, S. Proyer, E. Stangl, M. Borz and D. Bäuerle

96-98 (1996) 668

Surface diffusion

Atomic jump lengths in surface diffusion: experiment and theory, D.C. Seft

94/95 (1996) 231

Surface morphology

Novel method of strain-relaxed $\text{Si}_{1-x}\text{Ge}_x$ growth on Si(100) by MBE, H. Iwano, K. Yoshikawa, A. Kojima, K. Hayashi, S. Zaima and Y. Yasuda

100/101 (1996) 487

Tantalum

Sputtering of tantalum-based diffusion barriers in Si/Cu metallization: effects of gas pressure and composition, M. Stavrev, C. Wenzel, A. Möller and K. Dreischer

91 (1995) 257

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92 (1996) 626

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94/95 (1996) 351

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96-98 (1996) 656

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99 (1996) 265

Soft X-ray emissions by highly charged ions on solid surfaces: Mo and Ta surfaces, T. Emoto, K. Komatsu, A. Ichimiya, S. Ninomiya and M. Sekiguchi

100/101 (1996) 355

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- Time-of-flight characterization of laser ablation plume from NbTe_2 target in He atmosphere, F. Grangeon, H. Sassoli, W. Marine and M. Autric 96-98 (1996) 186
- Investigation of vaporization and condensation processes of thin layers of CdHgTe from laser erosion plasma in Hg atmosphere, B.K. Kotlyarchuk, D.I. Popovych, V.K. Savchuk and V.G. Savitsky 96-98 (1996) 192
- Deposition of HgCdTe epitaxial layers on anisotropically etched silicon surfaces by laser evaporation, T.Ya. Gorbach, M. Kuźma, E. Sheregii, P.S. Smertenko, S.V. Svechnikov and G. Wisz 96-98 (1996) 881
- Water vapor effects on the TeO_2/Te thin film conductance, S. Suchara, T. Hatano and A. Nukui 100/101 (1996) 252
- Growth of high-quality ZnTe layers by MOVPE, S.I. Gheys, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 647
- XPS analysis of chemically etched II-VI semiconductor surfaces, A. Kita, M. Ozawa and C.D. Gutleben 100/101 (1996) 652

Thallium

- Thermal positive ion production from thallium chloride molecules impinging upon a tungsten surface heated in high vacua, H. Kawano, K. Ohgami and N. Serizawa 100/101 (1996) 199

Thermal desorption

- Ge deposition from digermane on the $\text{Si}(100)-(2 \times 1)$ surface, H.-C. Cho 92 (1996) 128
- Investigation of atomic deuterium (hydrogen) emission from the surface of some transition metal deuterides (hydrides), E. Nowicka, Z. Wolfram, W. Lisowski and R. Duś 93 (1996) 53
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- Temperature-programmed desorption of positive ions and neutral molecules from alkali halide layers deposited on a metal surface, H. Kawano, S. Kamidoi, H. Shimizu, K. Ushimaru and H. Asada 100/101 (1996) 174
- A modified surface of titanium and its vacuum characteristic, T. Homma, M. Minato, Y. Itoh, S. Akiya and T. Suzuki 100/101 (1996) 189
- Adsorption and thermal decomposition of diethyltellurium on $\text{GaAs}(100)$, S.I. Gheys, M. Nishio, T. Urisu and H. Ogawa 100/101 (1996) 211
- Hydrogen desorption characteristics of composite Co-TiN nanoparticles, Y. Sakka and S. Ohno 100/101 (1996) 232
- NO interaction with thermally activated CaO and SrO surfaces, Y. Yanagisawa 100/101 (1996) 256
- Decomposition of triethylindium (TEI) on $\text{GaP}(001)$ surface studied by TPD, XPS and RHEED, J. Murata, T. Takeuchi, Y. Suzuki, N. Sanada and Y. Fukuda 100/101 (1996) 417
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Thin films

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- Improved thermal stability of cobalt silicide formed by ion beam assisted deposition on polysilicon, S. Ravesi, F. La Via, V. Raineri and C. Spinella 91 (1995) 19
- Epitaxy of $\text{CoSi}_2/\text{Si}(100)$: from $\text{Co}/\text{Ti}/\text{Si}(100)$ to reactive deposition epitaxy, A. Vantomme, S. Degroote, J. Dekoster and G. Langouche 91 (1995) 24
- Electrical and optical properties of thin $\text{Fe}_{1-x}\text{Co}_x\text{Si}_2$ films, St. Teichert, R. Kilper, Th. Franke, J. Erben, P. Häussler, W. Henrion, H. Lange and D. Panknin 91 (1995) 56
- Ni silicides formation and properties in RF sputtered $\text{Ni}_{100-x}\text{Si}_x$ thin films, A. Belu-Marian, M.D. Serbanescu, R. Manaila and A. Devenyi 91 (1995) 63
- Cubic metastable FeSi_{1-x} epitaxially grown on Si and MgO substrates, S. Degroote, A. Vantomme, J. Dekoster and G. Langouche 91 (1995) 72
- Formation of CoSi_2 on strained $\text{Si}_{0.8}\text{Ge}_{0.2}$ using a sacrificial Si layer, R.A. Donaton, S. Kolodinski, M. Caymax, Ph.J. Roussel, H. Bender, B. Brijs and K. Maex 91 (1995) 77
- Electrical and optical properties of thin $\beta\text{-FeSi}_2$ films on Al_2O_3 substrates, K. Herz and M. Powalla 91 (1995) 87
- Photoelectron spectroscopic investigations of thin $\text{Fe}_x\text{Si}_{100-x}$ films, R. Kilper, St. Teichert, Th. Franke, P. Häussler, H.-G. Boyen, A. Cossy-Favre and P. Oelhafen 91 (1995) 93
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- Process optimization of copper MOCVD using modeling experimental design, M.-J. Mouche, J.-L. Mermet, F. Pires, E. Richard, J. Torres, J. Palleau and F. Braud 91 (1995) 129
- Structure and electrical properties of thin copper films deposited by MOCVD, J. Röber, C. Kaufmann and T. Gessner 91 (1995) 134
- Effects of the biasing frequency on RIE of Cu in a Cl_2 -based discharge, A. Bertz, T. Werner, N. Hille and T. Gessner 91 (1995) 147
- Investigation of the oxidation behaviour of thin film and bulk copper, M. O'Reilly, X. Jiang, J.T. Beechiner, S. Lynch, C. Ni Dheasuna, J.C. Patterson and G.M. Crean 91 (1995) 152
- Nucleation and growth of CVD-W on TiN studied by X-ray fluorescence spectrometry, M.S. Marangon, G. Queirolo and C. Savoia 91 (1995) 157
- Influence of mixed reductants on the growth rate of WF_6 -based W-CVD, J.F. Jongste, T.G.M. Oosterlaken, G.J. Leusink, C.A. van der Jeugd, G.C.A.M. Janssen and S. Radelaar 91 (1995) 162
- Cluster beams for metallization of microstructured surfaces, P. Gatz and O.F. Hagen 91 (1995) 169
- Some particular features of the condensation process, structure and properties of thin metal films caused by self-ion bombardment, I.V. Gusev, A.A. Mohnjuk, V.I. Chapljk and V.P. Belevsky 91 (1995) 182
- Precursor development for the chemical vapor deposition of aluminium, copper and palladium, A. Gräfe, R. Heinen, F. Klein, Th. Kruck, M. Scherer and M. Schober 91 (1995) 187
- Stress voiding and electromigration phenomena in aluminum alloys, S. Kordic, R.A. Augur, A.G. Dirks and R.A.M. Wolters 91 (1995) 197
- Influence of the anti reflective coating on the electromigration resistance of 0.5 μm technology metal-2 line structures, R. Stevens, A. Witvrouw, Ph.J. Roussel, K. Maex, H. Meynen and A. Cuthbertson 91 (1995) 208
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- Interaction of a void and a grain boundary under a high electric current stress employing three-dimensional molecular dynamics simulation, S. Shingubara, I. Utsumomiya and T. Takahagi 91 (1995) 220
- Electromigration resistance of TiWN/Cu/TiWN interconnections, T. Fukada, T. Mori, Y. Toyoda, M. Hasegawa, K. Namba and K. Ogata 91 (1995) 227
- Model calculations on a bipolar transistor emitter interconnection with different contact shapes, K. Weide, J. Ullmann and W. Hasse 91 (1995) 234
- The effect of ion implantation on the properties of Al films, M. Zaborowski, A. Barcz, G. Gawlik and I.W. Rangelow 91 (1995) 239

- Hillock recognition by digital image processing, M. Zaborowski, M. Adamiec and A. Barcz 91 (1995) 246
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- Sputtering of tantalum-based diffusion barriers in Si/Cu metallization: effects of gas pressure and composition, M. Stavrev, C. Wenzel, A. Möller and K. Drescher 91 (1995) 257
- Ternary amorphous metallic thin films as diffusion barriers for Cu metallization, M.-A. Nicolet 91 (1995) 269
- LPCVD $\text{Re}_2\text{Si}_2\text{N}_2$ diffusion barriers in Si/ SiO_2 /Cu metallizations, A.-M. Dutron, E. Blanquet, C. Bernard, A. Bachli and R. Madar 91 (1995) 277
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- Electrical characterization of reactively sputtered TiN diffusion barrier layers for copper metallization, C. Kaufmann, J. Baumann, T. Gessner, T. Raschke, M. Rennau and N. Zichner 91 (1995) 291
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- Integration of a TiN barrier layer formed by rapid thermal annealing in a 1 μm CMOS process, K.-H. Stegemann, V. Heinig, G. Fontaine, J. Palorec and C. Beyer 91 (1995) 308
- Aspects of TiN and Ti deposition in an ECR plasma enhanced CVD process, A. Weber, R. Nikulski, C.-P. Klages, M.E. Gross, R.M. Charatan, R.L. Opilan and W.L. Brown 91 (1995) 314
- 3D simulation of tungsten low-pressure chemical vapor deposition in contact holes, E. Bär and J. Lorenz 91 (1995) 321
- Growth rate modeling for selective tungsten LPCVD, H. Wolf, R. Streiter, S.E. Schulz and T. Gessner 91 (1995) 332
- Selective deposition of tungsten on ITM- CoSi_2 , J.D. Kähler, D. Depta and R. Ferretti 91 (1995) 339
- Ohmic contacts to p-type 6H-silicon carbide, O. Nennewitz, L. Spiess and V. Breternitz 91 (1995) 347
- Advanced metallization technology for 256M DRAM, P. Kücher, H. Aochi, J. Gambino, T. Licata, T. Matsuda, S. Nguyen, M. Okazaki, H. Palm and M. Ronay 91 (1995) 359
- Inter-metal dielectric planarization process for 0.35 μm multilevel interconnection devices, M. Bacchetta, C. Zaccherini and L. Zanotti 91 (1995) 367
- A highly reliable, low cost 0.5 μm three level tungsten metallization, M. Hain, H. Körner, B. Neureither and S. Röhl 91 (1995) 374
- Deposition of titanium nitride/tungsten layers for application in vertically integrated circuits technology, G. Ruhl, B. Fröschle, P. Ramm, A. Intemann and W. Pamler 91 (1995) 382
- Low temperature growth of diamond-like films by cathodic arc plasma deposition, P.-L. Chen, M.-Y. Tsai and J.-S. Kao 92 (1996) 30
- Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
- Diamond-like coating prepared by pulsed laser sputtering of graphite in a high-vacuum environment, I.A. Bogonin, A.L. Karuzskii, N.N. Melnik, Yu.A. Mityagin, V.N. Murzin, A.A. Orlikovsky, A.V. Perestoronin, P.P. Sverbil, S.D. Tkachenko, A.V. Tsikunov, N.A. Volchkov and B.G. Zhurkin 92 (1996) 43
- Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on $\text{MgO}(001)$, H. Qiu, T. Ohbuchi, H. Nakai and M. Hashimoto 92 (1996) 47
- Stability of BaTiO_3 thin films on Si, L.H. Chang and W.A. Anderson 92 (1996) 52
- Study of Ag thin films deposited on porous silicon, T.F. Young, J.F. Liu, C.C. Wu, G.H. Fu and C.S. Chen 92 (1996) 57
- XPS studies on SiC thin layers formed by ion implantation with a metal vapor vacuum arc ion source, H. Yan, R.W.M. Kwok and S.P. Wong 92 (1996) 61
- Growth mechanism of Ni on Pt(110) at low temperature, C.S. Shern, J.S. Tsay and T. Fu 92 (1996) 74
- Epitaxial growth of $\text{ZnSe}_x\text{Te}_{1-x}$ by the VPE method and its photoluminescence, K. Mochizuki, H. Oguri, T. Kyotani and M. Isshiki 92 (1996) 79
- Effects of substrate cleaning and film thickness on the epitaxial growth of ultrahigh vacuum deposited Cu thin films on (001)Si, C.S. Liu and L.J. Chen 92 (1996) 84
- Very low temperature polycrystalline sili-

- con films with very large grains deposited for thin film transistor applications, K.C. Wang, T.R. Yew and H.L. Hwang 92 (1996) 99
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- Textured diamond growth by microwave plasma chemical vapor deposition, Y. Liou 92 (1996) 115
- Disordered Si/SiGe superlattices grown by ultrahigh vacuum chemical vapor deposition, T.-C. Chang, W.-K. Yeh, C.-Y. Chang, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 119
- Characteristics of PECVD GaN thin films, C.H. Lee and C.T. Chen 92 (1996) 124
- Ge deposition from digermane on the Si(100)-(2 × 1) surface, H.-C. Cho 92 (1996) 128
- Growth of ZnSe thin films by radical assisted MOCVD method, T. Aoki, M. Morita, S. Wickramanayaka, Y. Nakanishi and Y. Hatanaka 92 (1996) 132
- Growth of the thin film Cd-Si-As system by metalorganic chemical vapor deposition, H. Kayama, Y. Noda and Y. Furukawa 92 (1996) 142
- Electrosynthesis of yttrium chalcogenides from a non-aqueous bath, U.K. Mohite and C.D. Lokhande 92 (1996) 151
- Structural characterization of BaTiO₃ films by sol-gel method using mono-substituting chelating agent, W.-K. Kuo, J.-P. Wang and Y.-C. Ling 92 (1996) 155
- The electrical and optical characteristics of GaAs on Si by modified flow rate modulation epitaxy, M.K. Lee, C.C. Hu, and C.Z. Hwang 92 (1996) 159
- Characteristics of spray pyrolytic ZnO thin films, C.H. Lee and L.Y. Lin 92 (1996) 163
- Fluorine doped tin oxide films from spray pyrolysis of stannous fluoride solutions, G.C. Morris and A.E. McElnea 92 (1996) 167
- Sprayed films of stannite Cu₂ZnSnS₄, N. Nakayama and K. Ito 92 (1996) 171
- The properties of SiO₂ films using direct photo-chemical vapor deposition on strained SiGe layers, C.T. Lin, S.J. Chang, D.K. Nayak and Y. Shiraki 92 (1996) 193
- Surfactant modified growth of CuInSe₂ thin films, B.-H. Tseng, G.-W. Chang and G.-L. Gu 92 (1996) 227
- Influence of KCN treatment on CuInS₂ thin films, Y. Ogawa, A. Jäger-Waldau, T.H. Hua, Y. Hashimoto and K. Ito 92 (1996) 232
- Phenomenological approach in modeling of thin film nucleation from the liquid phase, T.V. Sakalo and S.A. Kukushkin 92 (1996) 261
- In situ X-ray reflectivity measurement of thin film growth during vacuum deposition, C.-H. Lee and S.-Y. Tseng 92 (1996) 282
- Photoellipsometric studies on CdTe thin films, P.D. Paulson and V. Dutta 92 (1996) 295
- Diffusion length measurements on electrodeposited CuInSe₂ cells, S.N. Qiu, C.X. Qiu and I. Shih 92 (1996) 306
- Interface phase transition as observed in ultra thin FeSi₂ epilayers, J. Derrien, I. Berbezier, A. Ronda and J.Y. Natoli 92 (1996) 311
- Interdiffusion and reactions in the Cu/TiN/Si thin film system, Y.S. Gong, J.-C. Lin and C. Lee 92 (1996) 335
- The determination of the average compositions of amorphous interlayers in the V/Si system using a buried ultrathin oxide layer and a capping Mo layer to define the reference planes for interdiffusion, J.H. Lin and L.J. Chen 92 (1996) 340
- Coalescence of cylindrical islands on the crystal surface accompanied by correlated changes of their heights and radii, T.V. Sakalo and S.A. Kukushkin 92 (1996) 350
- Structural and electrical properties of excimer laser deposited PLZT thin films, H.-F. Cheng 92 (1996) 378
- Structural characterization of epitaxial ferromagnetic MnSb layers grown by hot-wall epitaxy, H. Tatsuoka, H. Kuwabara, M. Oshita, Y. Nakanishi, T. Nakamura and H. Fujiyasu 92 (1996) 382
- Structural and optical properties of Pd_{1-x}In_x thin films, W.T. Wu, P.E. Schmid and F. Lévy 92 (1996) 391
- The influence of residual O₂ gas in vacuum on the structural and luminescent properties of ZnF₂:Mn thin films, Y. Nakanishi, S. Naito, T. Nakamura, Y. Hatanaka and G. Shimaoka 92 (1996) 400
- Study of the internal electric fields across the interfaces in the GaAs/(Al,Ga)As microstructures, C.R. Lu, C.L. Chang, C.H. Liou, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 404
- Electrochromic behavior of amorphous cobaltphthalocyanine thin films, M. Masui, T. Ogawa and M. Takeuchi 92 (1996) 421
- Study of biochemical reactions in thin organic films by means of evanescent optical wave, T.I. Ksenovich, A.A. Beloglazov, P.I. Nikitin, N.A. Kalabina and S.Yu. Zaitsev 92 (1996) 426
- Simulation of polymer film and surface be-

- haviour in a space environment, V.E. Skurat, E.A. Barbashev, Yu.I. Dorofeev, A.P. Nikiforov, M.M. Gorelova and A.I. Pertsyn 92 (1996) 441
- An electrochemical impedance spectroscopy study of thin polymeric films, R. Borkowska, M. Siekierski and J. Przyhuski 92 (1996) 447
- Electrical properties of laser deposited $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ films on silicon wafers, F.Y. Chuang, C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin 92 (1996) 452
- Pulsed-laser deposition of "diamond-like" carbon coating on $\text{YBa}_2\text{Cu}_3\text{O}_7$ high- T_c superconductor films, A.L. Karuzskii, N.N. Melnik, V.N. Murzin, V.S. Nozdrin, A.V. Perestoronin, N.A. Volchkov and B.G. Zhurkin 92 (1996) 457
- Investigation on origin of excess noise in superconducting and normal state BiSr-CaCuO films, A.L. Li and I. Shih 92 (1996) 461
- Effect of substrate-film interface on magnetic properties of Mn_4N films, K.-M. Ching, W.-D. Chang and T.-S. Chin 92 (1996) 471
- Coercivity of $\gamma\text{-(Fe}_{0.74}\text{Mn}_{0.15}\text{Co}_{0.11})_2\text{O}_3$ thin films by dc reactive magnetron sputtering, W.-D. Chang and T.-S. Chin 92 (1996) 475
- Structural evolution and atomic structure of ultrahigh vacuum deposited Au thin films on silicon at low temperatures, C.R. Chen and L.J. Chen 92 (1996) 507
- XPS, AES and LEED studies of Cu deposited on $\text{Cr}_2\text{O}_3(0001)$ surfaces, Q. Guo, L. Gui, P.J. Møller and K. Binau 92 (1996) 513
- Dopant activation and strain relaxation in P-implanted metastable pseudomorphic $\text{Ge}_{0.12}\text{Si}_{0.88}$ grown on $\text{Si}(100)$, D.Y.C. Lie, N.D. Theodore and J.H. Song 92 (1996) 557
- Electroluminescence in thin films, R.H. Mauch 92 (1996) 589
- Thin film photovoltaics, H.W. Schock 92 (1996) 606
- Formation of bottom oxides in porous silicon films by anodic oxidation, C.H. Lee, C.C. Yeh, C.H. Lee and K.Y.J. Hsu 92 (1996) 621
- Properties of multilayered thin films for thermal ink-jet printing devices, D.S. Wu, M.L. Lee and T.Y. Lin 92 (1996) 626
- Solar cells from thin films prepared by periodic pulse electrodeposition, G.C. Morris and R.J. Vanderveen 92 (1996) 630
- Gas sensitive properties of copperphthalocyanine thin films, M. Masui, M. Sashihara, T. Wada and M. Takeuchi 92 (1996) 634
- Carbon nitride - prospects for ultimate performance of superhard materials, S.A. Uglov, V.E. Shub, A.A. Beloglazov and V.I. Konov 92 (1996) 656
- Tungsten absorber on silicon membrane, D.C. Li, C.S. Yoo and C.Y. Sun 92 (1996) 665
- Depth profiling of W, O and H in tungsten trioxide thin films using RBS and ERDA techniques, O. Bohnke, G. Frand, M. Fromm, J. Weber and O. Greim 93 (1996) 45
- Surfactant effect of Sb on the growth of Ag films on a sapphire substrate, T. Lewowski and P. Wiczcerek 93 (1996) 85
- Scanning tunneling microscopy observations of recorded organic thin films, Q. Chen, D. Gu, F. Gan, L. Xu and M. Li 93 (1996) 151
- Studies of silicon-nitride (Si_3N_4) using laser ablation mass spectrometry, S.L. Wang, K.W.D. Ledingham, W.J. Jia and R.P. Singhal 93 (1996) 205
- Growth and reactivity of evaporated platinum films on $\text{Cu}(111)$: a study by AES, RHEED and adsorption of carbon monoxide and xenon, J. Fusy, J. Menau-court, M. Alnot, C. Huguet and J.J. Ehrhardt 93 (1996) 211
- Relationship between organic thin film uniformity and its electroluminescence, G. Wang, Y. Ding and Y. Wei 93 (1996) 281
- Improvement of the crystallinity in PbTiO_3 films grown on indium tin oxide-coated glass by metalorganic chemical vapor deposition using the continuous cooling process, Y.S. Yoon, S.S. Yom, T.W. Kim, D.U. Lee and C.O. Kim 93 (1996) 285
- Characterization of sputter-deposited multilayers of Ni and Zr with APFIM/TAP, T. Al-Kassab, M.-P. Macht, V. Naundorf, H. Wollenberger, S. Chambréland, F. Danoix and D. Blavette 94/95 (1996) 306
- Analytical description of the film thickness distribution obtained by the pulsed laser ablation of a monoatomic target: application to silicon and germanium, F. Antoni, C. Fuchs and E. Fogarassy 96-98 (1996) 50
- Plasma parameters in pulsed laser-plasma deposition of thin films, S. Metev, M. Ozegowski, G. Sepold and S. Burmester 96-98 (1996) 122
- Investigation of vaporization and condensation processes of thin layers of CdHgTe from laser erosion plasma in Hg atmosphere, B.K. Kotlyarchuk, D.I. Popovych, V.K. Savchuk and V.G. Savitsky 96-98 (1996) 192
- Optical and particle properties of PLD vapour/plasmas of ceramics, M. Alunovic, H. Stamm, M. Aden and E.W. Kreutz 96-98 (1996) 222
- Spectroscopic study of the microwave plasma enhanced pulsed laser deposition for $\text{Y}_1\text{Ba}_2\text{Cu}_3\text{O}_{7-x}$ superconducting

- thin films, B.C. Chung, C.H. Tsai, S.S. Hsu, C.S. Huang, T.Y. Tseng and I.N. Lin 96-98 (1996) 233
- Laser patterning of thin-film electrochemical gas sensors, A. Lecours, M. Caron, P. Ciureanu, G. Turcotte, D. Ivanov, A. Yelon and J.F. Currie 96-98 (1996) 341
- Laser beam application to thin film transistors, T. Sameshima 96-98 (1996) 352
- Low-fluence excimer laser irradiation-induced defect formation in indium-tin oxide films, T. Szörényi, L.D. Laude, I. Bertóti, Zs. Geretovszky and Z. Kántor 96-98 (1996) 363
- Liquid carbon observed with reflection measurements on CVD-diamond under UV pulsed-laser irradiation, P. Tosin, W. Lüthy and H.P. Weber 96-98 (1996) 384
- Excimer laser interaction with dielectric thin films, E. Welsch, K. Ettrich, H. Blaschke and N. Kaiser 96-98 (1996) 393
- Decomposition mechanisms of thin palladium acetate film with excimer UV radiation, J.-Y. Zhang, H. Esrom and I.W. Boyd 96-98 (1996) 399
- Single crystal laser patterning for selective $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ growth, R. Aguiar, F. Sánchez and M. Varela 96-98 (1996) 405
- Picosecond UV-laser ablation of Au and Ni films, A. Rosenfeld and E.E.B. Campbell 96-98 (1996) 439
- XeCl laser ablation of thin film ZnS, W.M. Cranton, P.H. Key, D. Sands, C.B. Thomas and F.X. Wagner 96-98 (1996) 501
- Surface temperature measurements during pulsed laser action on metallic and ceramic materials, M.B. Ignatiev, I.Yu. Smurov, G. Flamant and V.N. Senchenko 96-98 (1996) 505
- Surface chemical reaction of polymer film with reactive intermediates produced by laser ablation of azido compound, H. Niino and A. Yabe 96-98 (1996) 572
- Pulsed laser ablation and deposition of fluorocarbon polymers, M.G. Norton, W. Jiang, J.T. Dickinson and K.W. Hipps 96-98 (1996) 617
- Deposition of fluoropolymer thin films containing semiconductor microcrystallites by VUV laser ablation, T. Fujii, S. Inoue and F. Kannari 96-98 (1996) 621
- Electrical and optical characteristics of organic thin films fabricated by laser ablation, T. Fujii, H. Shima, N. Matsumoto and F. Kannari 96-98 (1996) 625
- Thin film growth by the pulsed laser assisted deposition technique, C. Belouet 96-98 (1996) 630
- Scale-up of pulsed laser deposition (PLD) for 4" wafer coating, M. Panzner, R. Dietsch, Th. Holz, H. Mai and S. Völlmar 96-98 (1996) 643
- Ultrathin film deposition by pulsed laser ablation using crossed beams, A.A. Gorbunov, W. Pompe, A. Sewing, S.V. Gaponov, A.D. Akhsakhalyan, I.G. Zabrodin, I.A. Kas'kov, E.B. Klyenkov, A.P. Morozov, N.N. Salaschenko, R. Dietsch, H. Mai and S. Völlmar 96-98 (1996) 649
- Off-axis excimer laser deposition of Ta_2O_5 thin films, N. Inoue, S. Kashiwabara, S. Toshima and R. Fujimoto 96-98 (1996) 656
- Classification of particulates on pulsed-laser deposited Y-Ba-Cu-O films, S. Proyer, E. Stangl, M. Borz and D. Bäuerle 96-98 (1996) 668
- Formation of artificially-layered high-temperature superconductors using pulsed-laser deposition, D.P. Norton, B.C. Chakoumakos, D.H. Lowndes and J.D. Bulai 96-98 (1996) 672
- Stoichiometric transfer of complex oxides by pulsed laser deposition, B. Dam, J.H. Rector, J. Johansson, S. Kars and R. Griessen 96-98 (1996) 679
- Improved properties of Pulsed Laser Deposited YBaCuO on NdGaO_3 using CeO_2 template layers, D.H.A. Blank, A.J.H.M. Rijnders, F.J.G. Roesthuis, G. den Ouden and H. Rogalla 96-98 (1996) 685
- The importance of gas scattering processes on the stoichiometry deviations of laser deposited films, J. Gonzalo, C.N. Afonso, J. Perrière and R. Gómez San Roman 96-98 (1996) 693
- Laser ablation of oxides: study of the oxygen incorporation by ^{18}O isotopic tracing techniques, R. Pérez Casero, R. Gómez San Román, C. Maréchal, J.P. Enard and J. Perrière 96-98 (1996) 697
- Critical thickness of YBaCuO (123) strained thin films and superlattices grown by pulsed laser deposition, A. Abert, J.P. Contour, A. Défosses, D. Ravelosona, W. Schwegle and P. Ziemann 96-98 (1996) 703
- Laser deposition of $\text{YBa}_2\text{Cu}_3\text{O}_7$ films on $\text{MgO}(100)$ at 100 mm target-substrate distance and oxygen pressures below 0.1 mbar, F. Goerke, A. Thoms and U. Merkt 96-98 (1996) 708
- Anisotropic resistivity in pulsed-laser deposited $\text{Bi}_2\text{Sr}_2\text{CaCu}_2\text{O}_{8+x}$ films, S.T. Li, A. Ritzer, S. Proyer, E. Stangl, D. Bäuerle and N. Reschauer 96-98 (1996) 713
- Substrate size effect at off-axis laser deposition of multicomponent films, M.R. Predtechensky, O.M. Tukhto, A.N. Smal' and S.A. Vasil'eva 96-98 (1996) 717

- In-situ reflectivity measurements during pulsed-laser deposition of $\text{Bi}_2\text{Sr}_2\text{CaCu}_2\text{O}_{8-x}$, A. Ritzler, B. Falkner, S.T. Li and D. Bäuerle 96-98 (1996) 721
- Ion-assisted pulsed-laser deposition for the fabrication of Y-Ba-Cu-O multilayer structures using oriented intermediate layers of YSZ and CeO_2 , R.P. Reade and R.E. Russo 96-98 (1996) 726
- Synthesis of RE-Ba-Sr-Cu-O by pulsed-laser deposition, E. Stangl, S. Proyer, B. Hellebrand and D. Bäuerle 96-98 (1996) 731
- Mirror-smooth $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ superconducting films deposited by plasma-enhanced pulsed laser deposition technique, C.S. Huang, T.Y. Tseng, B.C. Chung, C.H. Tsai, H.F. Cheng and I.N. Lin 96-98 (1996) 735
- Growth, structuring and characterisation of all-oxide thin film devices prepared by pulsed laser deposition, J.F.M. Cillessen, R.M. Wolf, J.B. Giesbers, P.W.M. Blom, K.-O. Grosse-Holz and E. Pastoor 96-98 (1996) 744
- Deposition of optical coatings by pulsed laser ablation, G. Reisse, S. Weissmantel, B. Keiper and U. Broulik 96-98 (1996) 752
- Rare-earth doped glass waveguides prepared by pulsed laser deposition, C.N. Afonso, J.M. Ballesteros, J. Gonzalo, G.C. Righini and S. Pelli 96-98 (1996) 760
- Preparation of SiO_xN_y films by reactive KrF laser ablation, K. Maruyama, Y. Aoki, M. Matsumoto, Y. Hiroshima and H. Ohta 96-98 (1996) 764
- Kinetic energy distributions of ions ejected during laser ablation of lead zirconate titanate and their correlation to deposition of ferroelectric thin films, G.C. Tyrrell, T.H. York, L.G. Coccia and I.W. Boyd 96-98 (1996) 769
- Epitaxial ferroelectric PZT and BST thin films by pulsed UV laser deposition, C. Champeaux, P. Marchet and A. Catherinot 96-98 (1996) 775
- Growth and characterization of PLZT films, M.J.M. Gomes, E. de Matos Gomes, P.L.Q. Mantas and J.L. Baptista 96-98 (1996) 779
- Pulsed laser deposition of sillenite films intended for photorefractive damage free waveguides, J.E. Alfonso, M.J. Martín, J. Mendiola, K. Polgár and C. Zaldo 96-98 (1996) 791
- Ferrimagnetic thin films prepared by pulsed laser deposition, M. Guyot, A. Lisfi, R. Krishnan, M. Porte, P. Rougier and V. Cagan 96-98 (1996) 802
- Pulsed laser deposition of high quality ITO thin films, F. Hanus, A. Jadin and L.D. Laude 96-98 (1996) 807
- Pulsed-laser deposited ZnO for device applications, S.L. King, J.G.E. Gardeniers and I.W. Boyd 96-98 (1996) 811
- Excimer laser ablating preparation of $\text{Ba}_2\text{NaNb}_5\text{O}_{15}$ thin films on KTiOPO_4 substrate and its guide wave property, J.M. Liu, Z.G. Liu, S.N. Zhu, Y.Y. Zhu and N.B. Ming 96-98 (1996) 819
- $\text{Pb}_{1-x}\text{Ca}_x\text{TiO}_3$ thin films prepared by laser ablation of ceramic targets, M.J. Martín, C. Zaldo and J. Mendiola 96-98 (1996) 823
- Characterization of ZnO thin films deposited by laser ablation in reactive atmosphere, P. Verardi, M. Dinescu and A. Andrei 96-98 (1996) 827
- An experimental study and modeling of the thickness distribution in pulsed laser deposited ferroelectric thin films, M. Tyunina, K. Sreenivas, C. Bjormander, J. Wittborn and K.V. Rao 96-98 (1996) 831
- Pulsed laser deposition of electroceramic thin films, M. Mertin, D. Offenberg, C.W. An, D.A. Wesner and E.W. Kreutz 96-98 (1996) 842
- Excimer laser ablation and film deposition of Ti:sapphire, P.E. Dyer, S.R. Jackson, P.H. Key, W.J. Metheringham and M.J.J. Schmidt 96-98 (1996) 849
- Pulsed laser deposition of nasicon thin films, R. Izquierdo, F. Hanus, Th. Lang, D. Ivanov, M. Meunier, L. Laude, J.F. Currie and A. Yelon 96-98 (1996) 855
- Comparative diagnostics of ArF- and KrF-laser generated carbon plumes used for amorphous diamond-like carbon film deposition, A.A. Puzetky, D.B. Gehegan, G.E. Jellison Jr. and M.M. McGibbin 96-98 (1996) 859
- Carbon nitride thin films obtained by laser ablation of graphite in a nitrogen plasma, M.C. Polo, R. Aguiar, P. Serra, L. Clèries, M. Varela and J. Esteve 96-98 (1996) 870
- Deposition of HgCdTe epitaxial layers on anisotropically etched silicon surfaces by laser evaporation, T.Ya. Gorbach, M. Kuźma, E. Sheregii, P.S. Smertenko, S.V. Svechnikov and G. Wisz 96-98 (1996) 881
- Pulsed Laser Deposition of permanent magnetic $\text{Nd}_2\text{Fe}_{14}\text{B}$ thin films, A.J.M. Geurtsen, J.C.S. Kools, L. de Wit and J.C. Lodder 96-98 (1996) 887
- Surface composition of CVD-grown α -SiC layers - an XPS and LEED study, H. Behner and R. Rupp 99 (1996) 27
- Zr-silicide formation during the epitaxial growth of Y-stabilized zirconia films on

- Si(100) and its avoidance by ion beam assisted deposition at a reduced temperature, T. Koch and P. Ziemann 99 (1996) 51
- Modelling of the particle size distribution function in the nucleation and early stages of thin film growth, M. Tomellini 99 (1996) 67
- AFM and STM studies on In_2O_3 and ITO thin films deposited by atomic layer epitaxy, T. Asikainen, M. Ritala, M. Leskelä, T. Prohaska, G. Friedbacher and M. Grasserbauer 99 (1996) 91
- Application and properties of sub-mono-molecular layers of silicon dioxide deposited under mild conditions, D.M. Knotter 99 (1996) 99
- X-ray photoelectron diffraction investigation of Ge segregation and film morphology during first stage heteroepitaxy of Si on Ge(001), D. Aubel, L. Kubler, J.L. Bischoff, L. Simon and D. Bolmont 99 (1996) 169
- Properties of radio frequency magnetron sputtered silicon dioxide films, W.-F. Wu and B.-S. Chiou 99 (1996) 237
- Chemical, mechanical and electrical properties of CN_x -films produced by reactive sputtering and N^+ -implantation in carbon films, N. Laidani, A. Miotello and J. Perrière 99 (1996) 273
- Large area synthesis of thin alumina films by laser ablation, B. Hirschauer, S. Söderholm, J. Paul and A.S. Flodström 99 (1996) 285
- Photon and ion beam assisted deposition of titanium nitride, H. Wengenmair, J.W. Gerlach, U. Preckwinkel, B. Stritzker and B. Rauschenbach 99 (1996) 313
- XPS study of carbon/inconel bilayers as a function of substrate bias, M.S. Aouadi, P.C. Wong and K.A.R. Mitchell 99 (1996) 319
- Preparation of thin silver films on mica studied by XRD and AFM, J.-D. Grunwaldt, F. Atamny, U. Göbel and A. Baiker 99 (1996) 353
- Study of the chemical bonding in tungsten carbide and chromium films by application of factor analysis on AES depth profiles, F. Reniers, E. Silberberg, N. Roose and J. Vereecken 99 (1996) 379
- On the application of XPS to ceria films grown by MOCVD using a fluorinated precursor, D. Chadwick, J. McAleese, K. Senkiw and B.C.H. Steele 99 (1996) 417
- Simultaneous determination of composition and thickness of thin iron-oxide films from XPS Fe 2p spectra, P.C.J. Graat and M.A.J. Somers 100/101 (1996) 36
- High depth resolution depth profiling of metal films using SIMS and sample rotation, D.E. Sykes, A. Chew, J. Hems and K. Stribley 100/101 (1996) 77
- Structural properties of epitaxially grown perfluoro *n*-alkane thin films prepared by vapor deposition, K. Ishida, T. Horiuchi, S. Kai and K. Matsushige 100/101 (1996) 116
- Molecular orientation of polyimide films determined by an optical retardation method, K. Sakamoto, R. Arafune, S. Ushioda, Y. Suzuki and S. Morokawa 100/101 (1996) 124
- Water vapor effects on the TeO_2/Te thin film conductance, S. Suehara, T. Hatano and A. Nukui 100/101 (1996) 252
- Analysis of the sensing mechanism of tin dioxide thin film gas sensors using the change of work function in flammable gas atmosphere, B. Yea, R. Konishi, T. Osaki, S. Abe, H. Tanioka and K. Sugahara 100/101 (1996) 365
- Behavior of ultrathin layers of Co on Si and Ge systems, K. Prabhakaran and T. Ogino 100/101 (1996) 518
- High-rate deposition of high-quality Cu film with LPCVD, K. Numajiri, T. Goya, R. Tobe, O. Okada, N. Hosokawa, C. Mu, N. Cox, C. Scott and J. Yu 100/101 (1996) 541
- Low pressure MOCVD of TiN thin films, S.W. Kim, H. Jimba, A. Sekiguchi, O. Okada and N. Hosokawa 100/101 (1996) 546
- Characterization of MOCVD-grown GaAs on Si by spectroscopic ellipsometry, G. Yu, T. Soga, T. Jimbo and M. Umeno 100/101 (1996) 617
- ZnSe crystal growth by radical assisted MOCVD, Y. Hatanaka, T. Aoki, M. Morita and Y. Nakanishi 100/101 (1996) 621
- Preparation of blue-emitting $\text{SrGa}_2\text{Se}_4:\text{Ce}$ thin films by multi-source deposition, Y. Nakanishi, F. Shiba, K. Sowa, H. Tatsuoka, H. Kuwabara, T. Nakamura and Y. Hatanaka 100/101 (1996) 639
- Microwave plasma assisted LCVD growth and characterization of GaN, B. Zhou, X. Li, T.L. Tansley and K.S.A. Butcher 100/101 (1996) 643

Time of flight techniques

- Modeling of laser induced plasma, spectroscopic and time of flight experiments in pulsed laser deposition, G. Granse, S. Völlmar, A. Lenk, A. Rupp and K. Rohr 96-98 (1996) 97
- Transport of neutral atoms, monoxides and clusters in the plume produced by laser ablation of $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ in oxygen environment, A.V. Bulgakov, M.R. Predtechensky and A.P. Mayorov 96-98 (1996) 159
- Laser produced plasmas in high fluence ablation of metallic surfaces probed by

- time-of-flight mass spectrometry, S. Amoroso, A. Amodeo, V. Berardi, R. Bruzzese, N. Spinelli and R. Velotta 96-98 (1996) 175
- Time-of-flight characterization of laser ablation plume from NbTe₂ target in He atmosphere, F. Grangeon, H. Sassoli, W. Marine and M. Autric 96-98 (1996) 186
- Soft laser sputtering of the GaAlAs (100) surface, L. Vivet, B. Dubreuil, T. Gibert-Legrand and M.F. Barthe 96-98 (1996) 238
- Optical spectroscopy of emission from Si-SiO₂ nanoclusters formed by laser ablation, I.A. Movchan, W. Marine, R.W. Dreyfus, H.C. Le, M. Sentis and M. Autric 96-98 (1996) 251
- Magnetic field enhanced growth of carbon cluster ions in the laser ablation plume of graphite, F. Kokai, Y. Koga and R.B. Heimann 96-98 (1996) 261
- The role of defects in laser induced positive ion emission from ionic crystals, J.T. Dickinson, J.-J. Shin and S.C. Langford 96-98 (1996) 316
- Selection of kinetic energy of laser ablated particles, K. Kuba and T. Sugihara 96-98 (1996) 659
- ToF-SIMS analysis of adsorbate/membrane interactions. I. Adsorption of dehydroabietic acid on poly(vinylidene fluoride), P. Spevack and Y. Deslandes 99 (1996) 41
- Time-of-flight SIMS study of Bi-Mo selective oxidation catalysts, L.T. Weng, P. Bertrand, O. Tirions and M. Devillers 99 (1996) 185
- Apparatus for positron-annihilation-induced Auger electron spectroscopy with a pulsed positron beam, R. Suzuki, T. Ohdaira, T. Mikado, H. Ohgaki, M. Chiwaki and T. Yamazaki 100/101 (1996) 297
- Tin**
- Sprayed films of stannite Cu₂ZnSnS₄, N. Nakayama and K. Ito 92 (1996) 171
- Hydrogen adsorption on the Pt(111)($\sqrt{3} \times \sqrt{3}$)R30°-Sn surface alloy studied by high resolution core level photoelectron spectroscopy, E. Janin, M. Björkqvist, T.M. Grehk, M. Göthelid, C.-M. Pradier, U.O. Karlsson and A. Rosengren 99 (1996) 371
- Ion induced alteration at Pb-Sn alloy surface investigated by Auger electron spectroscopy and X-ray photoelectron spectroscopy, M. Kudo, A. Ishijima and T. Morohashi 100/101 (1996) 134
- Sn segregation to the low index surfaces of a copper single crystal, J. du Plessis and E.C. Viljoen 100/101 (1996) 222

Tin oxide

- Fluorine doped tin oxide films from spray pyrolysis of stannous fluoride solutions, G.C. Morris and A.E. McElna 92 (1996) 167
- An XPS and FTIR study of SO₂ adsorption on SnO₂ surfaces, F. Berger, E. Beche, R. Berjoan, D. Klein and A. Chahaudet 93 (1996) 9
- CO₂ plasma treatment of tin oxides, H.N. Wanka, G. Bilger and M.B. Schubert 93 (1996) 339
- Low-fluence excimer laser irradiation-induced defect formation in indium-tin oxide films, T. Szörényi, L.D. Laude, I. Bertóti, Zs. Geretovszky and Z. Kántor 96-98 (1996) 363
- Pulsed laser deposition of high quality ITO thin films, F. Hanus, A. Jadin and L.D. Laude 96-98 (1996) 807
- AFM and STM studies on In₂O₃ and ITO thin films deposited by atomic layer epitaxy, T. Asikainen, M. Ritala, M. Leskellä, T. Prohaska, G. Friedbacher and M. Grasserbauer 99 (1996) 91
- Analysis of the sensing mechanism of tin dioxide thin film gas sensors using the change of work function in flammable gas atmosphere, B. Yea, R. Konishi, T. Osaki, S. Abe, H. Tanioka and K. Sugahara 100/101 (1996) 365

Titanium

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- Epitaxy of CoSi₂/Si(100): from Co/Ti/Si(100) to reactive deposition epitaxy, A. Vantomme, S. Degroote, J. Dekoster and G. Langouche 91 (1995) 24
- Angular dependence of the magnetoresistance of TiSi₂ single crystals, M. Afronte, O. Laborde, U. Gottlieb, O. Thomas and R. Madar 91 (1995) 98
- Some particular features of the condensation process, structure and properties of thin metal films caused by self-ion bombardment, I.V. Gusev, A.A. Mohnjuk, V.I. Chapljuk and V.P. Belevsky 91 (1995) 182
- Electromigration resistance of TiWN/Cu/TiWN interconnections, T. Fukada, T. Mori, Y. Toyoda, M. Hasegawa, K. Namba and K. Ogata 91 (1995) 227
- Ti-diffusion barrier in Cu-based metallization, F. Braud, J. Torres, J. Palleau, J.-L. Mermet and M.-J. Mouche 91 (1995) 251

- Co-sputtered TiB₂ as a diffusion barrier for advanced microelectronics with Cu metallization, G. Sade and J. Pelleg 91 (1995) 263
- Aspects of TiN and Ti deposition in an ECR plasma enhanced CVD process, A. Weber, R. Nikulski, C.-P. Klages, M.E. Gross, R.M. Charatan, R.L. Opilan and W.L. Brown 91 (1995) 314
- Ohmic contacts to p-type 6H-silicon carbide, O. Nennewitz, L. Spiess and V. Breternitz 91 (1995) 347
- On the formation of silicides on poly runners with topography by a two-step sili-cidation process, F. Jonckx, R. Verbeeck, B. Dewerdts and K. Maex 91 (1995) 378
- Reliability study of sub-micron titanium silicide contacts, C.C. Lin, W.S. Chen, H.L. Hwang, K.Y.J. Hsu, H.K. Liou and K.N. Tu 92 (1996) 660
- Studies of IT TiSi₂ by STM, AFM and XPS: the mechanism of hydrolysis in air, H. Martinez, C. Auriel, D. Gonbeau, M. Loudet and G. Pfister-Guillouzo 93 (1996) 231
- Temperature effects in the early stages of titanium oxidation, I. Vaquillo, M.C.G. Passeggi, Jr. and J. Ferrón 93 (1996) 247
- Improvement of the crystallinity in PbTiO₃ films grown on indium tin oxide-coated glass by metalorganic chemical vapor deposition using the continuous cooling process, Y.S. Yoon, S.S. Yom, T.W. Kim, D.U. Lee and C.O. Kim 93 (1996) 285
- Atom probe analysis of carbonitride grains in (Ti, W, Ta, Mo)(C, N)(Co/Ni) cer-mets with different carbon content, J. Zackrisson, M. Thuvander, P. Lindahl and H.-O. André 94/95 (1996) 351
- Pb_{1-x}Ca_xTiO₃ thin films prepared by laser ablation of ceramic targets, M.J. Martín, C. Zaldo and J. Mendiola 96-98 (1996) 823
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- The surface and interface reaction of metal thin film on sapphire substrate, H.J. Kang, C.H. Kim, N.S. Park and M.W. Kim 100/101 (1996) 160
- A modified surface of titanium and its vac-uum characteristic, T. Homma, M. Mi-nato, Y. Itoh, S. Akiya and T. Suzuki 100/101 (1996) 189
- Effect of gas adsorption on the segregation behavior of substrate Cu on Ti film, M. Yoshitake and K. Yoshihara 100/101 (1996) 203
- Electrical properties of metal/Si_{1-x}Ge_x/Si(100) heterojunc-tions, H. Shinoda, M. Kosaka, J. Ko-jima, H. Ikeda, S. Zaima and Y. Yasuda 100/101 (1996) 526
- Selective epitaxial Si based layers and TiSi₂ deposition by integrated chemical vapor deposition, J.L. Regolini, J. Margail, S. Bodnar, D. Maury and C. Morin 100/101 (1996) 566
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- Effect of Nb metal ion in TiO₂ oxygen gas sensor, R.K. Sharma, M.C. Bhatnagar and G.L. Sharma 92 (1996) 647
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- Electroless copper metallisation of titanium nitride, J.C. Patterson, C. Ni Dheasuna, J. Barrett, T.R. Spalding, M. O'Reilly, X. Jiang and G.M. Crean 91 (1995) 124
- Nucleation and growth of CVD-W on TiN studied by X-ray fluorescence spectrom-etry, M.S. Marangon, G. Queirolo and C. Savoia 91 (1995) 157
- Electrical characterization of conductive and non-conductive barrier layers for Cu-metallization, C. Ahrens, D. Depta, F. Schithelm and S. Wilhelm 91 (1995) 285
- Electrical characterization of reactively sputtered TiN diffusion barrier layers for copper metallization, C. Kaufmann, J. Baumann, T. Gessner, T. Raschke, M. Rennau and N. Zichner 91 (1995) 291
- Ti nitride phases in thin films deposited by DC magnetron sputtering, R. Manaila, D. Biro, P.B. Barna, M. Adamik, F. Zavaliche, S. Craciun and A. Devenyi 91 (1995) 295
- Integration of a TiN barrier layer formed by rapid thermal annealing in a 1 µm CMOS process, K.-H. Stegemann, V. Heinig, G. Fontaine, J. Palorec and C. Beyer 91 (1995) 308
- Aspects of TiN and Ti deposition in an ECR plasma enhanced CVD process, A. Weber, R. Nikulski, C.-P. Klages, M.E. Gross, R.M. Charatan, R.L. Opilan and W.L. Brown 91 (1995) 314
- Evaluation of selective tungsten plugs on TiN, W and AlSi by analytical and elec-trical measurements, S.E. Schulz, B. Hintze, W. Grünwald, O. Fiedler and T. Gessner 91 (1995) 326
- Deposition of titanium nitride/tungsten lay-ers for application in vertically inte-grated circuits technology, G. Ruhl, B. Fröschle, P. Ramm, A. Intemann and W. Pamler 91 (1995) 382
- Interdiffusion and reactions in the Cu/TiN/Si thin film system, Y.S. Gong, J.-C. Lin and C. Lee 92 (1996) 335

- Photon and ion beam assisted deposition of titanium nitride, H. Wengenmair, J.W. Gerlach, U. Preckwinkel, B. Stritzker and B. Rauschenbach 99 (1996) 313
- Hydrogen desorption characteristics of composite Co-TiN nanoparticles, Y. Sakka and S. Ohno 100/101 (1996) 232
- Low pressure MOCVD of TiN thin films, S.W. Kim, H. Jimba, A. Sekiguchi, O. Okada and N. Hosokawa 100/101 (1996) 546

Titanium oxide

- Stability of BaTiO₃ thin films on Si, L.H. Chang and W.A. Anderson 92 (1996) 52
- Structural characterization of BaTiO₃ films by sol-gel method using mono-substituting chelating agent, W.-K. Kuo, J.-P. Wang and Y.-C. Ling 92 (1996) 155
- Formation of polycrystalline BaTi_xO_y compounds in barium implanted TiO₂, S.M.M. Ramos, B. Canut, M. Ambri, N. Bonardi, R. Brenier, M. Pitaval, P. Thevenard and M. Brunel 93 (1996) 191
- Preparation of TiO₂ thin films by pulsed laser deposition for waveguiding applications, C. Garapon, C. Champeaux, J. Mugnier, G. Panczer, P. Marchet, A. Catherinot and B. Jacquier 96-98 (1996) 836
- XPS and AFM characterization of a vanadium oxide film on TiO₂(100) surface, G. Chiarello, R. Barberi, A. Amoddeo, L.S. Caputi and E. Colavita 99 (1996) 15
- AES study of electron beam induced damage on TiO₂ surfaces, A.J.M. Mens and O.L.J. Gijzeman 99 (1996) 133
- FTIR study of adsorption of CO, NO and C₂H₄ and reaction of CO + H₂ on the well-dispersed FeOx/γ-Al₂O₃ and FeOx/TiO₂(a) catalysts, W. Ji, Y. Chen, S. Shen, S. Li and H. Wang 99 (1996) 151

Transition metals

- Electrocatalytic activities of proton-exchanged layered oxides for the anodic oxidation on the solid oxide fuel cell, K. Sato, S. Nomura and Y. Inoue 92 (1996) 639
- Investigation of atomic deuterium (hydrogen) emission from the surface of some transition metal deuterides (hydrides), E. Nowicka, Z. Wolfram, W. Lisowski and R. Duř 93 (1996) 53

Tribology

- Tribological properties of smooth diamond films, S.M. Pimenov, A.A. Smolin, E.D. Obraztsova, V.I. Konov, U. Bögli, A. Blatter, E.N. Loubnin, M. Maillat, A. Leijala, J. Burger and H.E. Hintermann 92 (1996) 106

Tungsten

- Raman study of tetragonal tungsten disilicide, O. Chaix-Pluchery, F. Genet, G. Lucazeau and R. Madar 91 (1995) 68
- Nucleation and growth of CVD-W on TiN studied by X-ray fluorescence spectrometry, M.S. Marangon, G. Queirolo and C. Savoia 91 (1995) 157
- Influence of mixed reductants on the growth rate of WF₆-based W-CVD, J.F. Jongste, T.G.M. Oosterlaken, G.J. Leusink, C.A. van der Jeugd, G.C.A.M. Janssen and S. Radelaar 91 (1995) 162
- 3D simulation of tungsten low-pressure chemical vapor deposition in contact holes, E. Bär and J. Lorenz 91 (1995) 321
- Evaluation of selective tungsten plugs on TiN, W and AlSi by analytical and electrical measurements, S.E. Schulz, B. Hintze, W. Grünwald, O. Fiedler and T. Gessner 91 (1995) 326
- Growth rate modeling for selective tungsten LPCVD, H. Wolf, R. Streiter, S.E. Schulz and T. Gessner 91 (1995) 332
- Selective deposition of tungsten on ITM-CoSi₂, J.D. Köhler, D. Depta and R. Ferretti 91 (1995) 339
- W/Si Schottky diodes: effect of sputtering deposition conditions on the barrier height, M. Mamor, E. Dufour-Gergam, L. Finkman, G. Tremblay, F. Meyer and K. Bouziane 91 (1995) 342
- A highly reliable, low cost 0.5 μm three level tungsten metallization, M. Hain, H. Körner, B. Neureither and S. Röhl 91 (1995) 374
- Deposition of titanium nitride/tungsten layers for application in vertically integrated circuits technology, G. Ruhl, B. Fröschle, P. Ramm, A. Intemann and W. Pamler 91 (1995) 382
- Tungsten absorber on silicon membrane, D.C. Li, C.S. Yoo and C.Y. Sun 92 (1996) 665
- Depth profiling of W, O and H in tungsten trioxide thin films using RBS and ERDA techniques, O. Bohnke, G. Frand, M. Fromm, J. Weber and O. Greim 93 (1996) 45

- Surface sulfide on (100) W: formation, stability, absolute concentration of sulfur, N.R. Gall, E.V. Rut'kov, A.Ya. Tontegode and M.M. Usufov 93 (1996) 353
- Control of formation sites for liquid-Li cones on a W(100) tip by means of the remolding method, K. Hata, F. Nakayama, Y. Saito and A. Ohshita 94/95 (1996) 156
- Adsorption studies of cobalt on tungsten (110), (100) and (111) planes by probe-hole field emission microscopy, R.B. Sharma, A.D. Adsool, N. Pradeep and D.S. Joag 94/95 (1996) 177
- Study of CO surface diffusion on CO/W(111) by analysis of CO⁺ field ion rate fluctuations, Yu. Suchorski, J. Bęben, V.K. Medvedev and J.H. Block 94/95 (1996) 207
- Noble-gas-like mechanism of localized field ionization of nitrogen as detected by field ion appearance energy spectroscopy, Yu. Suchorski, V.K. Medvedev and J.H. Block 94/95 (1996) 217
- Atomic jump lengths in surface diffusion: experiment and theory, D.C. Senft 94/95 (1996) 231
- LEED and XPS studies of the ZrO/W(100) surface, H. Satoh, H. Nakane and H. Adachi 94/95 (1996) 247
- Atom probe analysis of carbonitride grains in (Ti, W, Ta, Mo)C, N(Co/Ni) cermets with different carbon content, J. Zackrisson, M. Thuvander, P. Lindahl and H.-O. Andrén 94/95 (1996) 351
- Field ion microscopy study of the interactions between self interstitials and impurities in metals, A.L. Suvorov and D.E. Dolin 94/95 (1996) 384
- In situ surface cleaning of pure and implanted tungsten photocathodes by pulsed laser irradiation, M. Afif, J.P. Girardeau-Montaut, C. Tomas, M. Romand, M. Charbonnier, N.S. Prakash, A. Perez, G. Marest and J.M. Frigerio 96-98 (1996) 469
- Study of the chemical bonding in tungsten carbide and chromium films by application of factor analysis on AES depth profiles, F. Reniers, E. Silberberg, N. Roose and J. Vereecken 99 (1996) 379
- Thermal positive ion production from gallium chloride molecules impinging upon a tungsten surface heated in high vacua, H. Kawano, K. Ohgami and N. Serizawa 100/101 (1996) 199
- Behavior of zirconium on ZrO/W(100) surface, H. Satoh, H. Nakane and H. Adachi 100/101 (1996) 216
- Angular resolved EPMA analysis of thin films prepared by pulsed laser ablation of CdWO₄(010), K. Tanaka, N. Yokota, N. Shirai, Q. Zhuang and R. Nakata 100/101 (1996) 264

Tunneling

- Magnetostochastic resonance as a new method for investigations of surface and thin film magnetism, A.N. Grigorenko and P.I. Nikitin 92 (1996) 466
- Local field and potential barrier in tunneling processes, M.M. Mollicone, L.C.O. Dacal and C.M.C. de Castilho 94/95 (1996) 68

Vanadium

- Stress in Al, AlSiCu, and AlVPd films on oxidized Si substrates, G.J. Leusink, J.P. Lokker, M.J.C. van den Homberg, J.F. Jongste, T.G.M. Oosterlaken, G.C.A.M. Janssen and S. Radelaar 91 (1995) 215
- The ohmic contact to the silicon Schottky barrier using vanadium silicide and gold or silver metallization, A.D. Remenyuk and N.M. Schmidt 91 (1995) 352
- The determination of the average compositions of amorphous interlayers in the V/Si system using a buried ultrathin oxide layer and a capping Mo layer to define the reference planes for interdiffusion, J.H. Lin and L.J. Chen 92 (1996) 340
- XPS and AFM characterization of a vanadium oxide film on TiO₂(100) surface, G. Chiarello, R. Barberi, A. Amodeo, L.S. Caputi and E. Colavita 99 (1996) 15

Water

- A theoretical analysis of the molecular and dissociative adsorption of H₂O on GaAs(110), R. Rincón, F.J. García-Vidal and F. Flores 92 (1996) 216
- Water vapor effects on the TeO₂/Te thin film conductance, S. Suchara, T. Hatano and A. Nukui 100/101 (1996) 252

Work function

- LEED and XPS studies of the ZrO/W(100) surface, H. Satoh, H. Nakane and H. Adachi 94/95 (1996) 247
- Quantitative relationship between the work function and transfer ratio of a potassium-adsorbed MIM cathode, T. Kusunoki and M. Suzuki 100/101 (1996) 207

Xenon

- Angular distribution of particles sputtered from GaAs by Ar⁺ and Xe⁺ ion bom-

bardment, T. Aoyama, M. Tanemura and F. Okuyama

100/101 (1996) 351

X-ray absorption

EXAFS measurements on the structure of Mo/Si multilayers produced using ion bombardment and increased deposition temperature, H.-J. Voorma, G.E. van Dorssen, E. Louis, N.B. Koster, A.D. Smith, M.D. Roper and F. Bijkerk

93 (1996) 221

Dynamics of silicon plume generated by laser ablation and its chemical reaction, T. Makimura and K. Murakami

96-98 (1996) 242

Sampling depth of total electron and fluorescence measurements in Si L- and K-edge absorption spectroscopy, M. Kasrai, W.N. Lennard, R.W. Brunner, G.M. Bancroft, J.A. Bardwell and K.H. Tan

99 (1996) 303

Surface structure analysis of dispersed metal sites on single crystal metal oxides by means of polarization-dependent total-reflection fluorescent EXAFS, W.-J. Chun, K. Asakura and Y. Iwasawa

100/101 (1996) 143

X-ray diffraction

Epitaxy of $\text{CoSi}_2/\text{Si}(100)$: from Co/Ti/Si(100) to reactive deposition epitaxy, A. Vantomme, S. Degroote, J. Dekoster and G. Langouche

91 (1995) 24

Ni silicides formation and properties in RF sputtered $\text{Ni}_{100-x}\text{Si}_x$ thin films, A. Belu-Marian, M.D. Serbanescu, R. Manaila and A. Devenyi

91 (1995) 63

Cubic metastable FeSi_{1-x} epitaxially grown on Si and MgO substrates, S. Degroote, A. Vantomme, J. Dekoster and G. Langouche

91 (1995) 72

Formation of CoSi_2 on strained $\text{Si}_{0.8}\text{Ge}_{0.2}$ using a sacrificial Si layer, R.A. Donaton, S. Kolodinski, M. Caymax, Ph.J. Roussel, H. Bender, B. Brijs and K. Maex

91 (1995) 77

Metallurgical and electrical investigation of $\text{Pt}_5\text{Ni}_{95}$ /silicon interactions, F. Corni, C. Nobili, G. Ottaviani, R. Tonini, B. Grignaffini Gregorio and G. Queirolo

91 (1995) 107

Investigation of the oxidation behaviour of thin film and bulk copper, M. O'Reilly, X. Jiang, J.T. Beechinor, S. Lynch, C. Ni Dheasuna, J.C. Patterson and G.M. Crean

91 (1995) 152

Some particular features of the condensation process, structure and properties of thin metal films caused by self-ion bom-

bardment, I.V. Gusev, A.A. Mohnjak, V.I. Chapjuk and V.P. Belevsky

91 (1995) 182

Ti nitride phases in thin films deposited by DC magnetron sputtering, R. Manaila, D. Biro, P.B. Barna, M. Adamik, F. Zavaliche, S. Craciun and A. Devenyi

91 (1995) 295

W/Si Schottky diodes: effect of sputtering deposition conditions on the barrier height, M. Mamor, E. Dufour-Gergam, L. Finkman, G. Tremblay, F. Meyer and K. Bouziane

91 (1995) 342

Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Siazay

92 (1996) 35

Effects of substrate cleaning and film thickness on the epitaxial growth of ultrahigh vacuum deposited Cu thin films on (001)Si, C.S. Liu and L.J. Chen

92 (1996) 84

Textured diamond growth by microwave plasma chemical vapor deposition, Y. Liou

92 (1996) 115

Disordered Si/SiGe superlattices grown by ultrahigh vacuum chemical vapor deposition, T.-C. Chang, W.-K. Yeh, C.-Y. Chang, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei

92 (1996) 119

Growth of ZnSe thin films by radical assisted MOCVD method, T. Aoki, M. Morita, S. Wickramanayaka, Y. Nakanishi and Y. Hatanaka

92 (1996) 132

Growth of the thin film Cd-Si-As system by metalorganic chemical vapor deposition, H. Kayama, Y. Noda and Y. Furukawa

92 (1996) 142

Electrosynthesis of yttrium chalcogenides from a non-aqueous bath, U.K. Mohite and C.D. Lokhande

92 (1996) 151

Characteristics of spray pyrolytic ZnO thin films, C.H. Lee and L.Y. Lin

92 (1996) 163

Sprayed films of stannite $\text{Cu}_2\text{ZnSnS}_4$, N. Nakayama and K. Ito

92 (1996) 171

Interdiffusion and reactions in the Cu/TiN/Si thin film system, Y.S. Gong, J.-C. Lin and C. Lee

92 (1996) 335

Structural characterization of epitaxial ferromagnetic MnSb layers grown by hot-wall epitaxy, H. Tatsuoka, H. Kuwabara, M. Oshita, Y. Nakanishi, T. Nakamura and H. Fujiyasu

92 (1996) 382

Structural and optical properties of $\text{Pd}_{1-x}\text{In}_x$ thin films, W.T. Wu, P.E. Schmid and F. Lévy

92 (1996) 391

The influence of residual O_2 gas in vacuum on the structural and luminescent properties of $\text{ZnF}_2:\text{Mn}$ thin films, Y. Nakan-

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- Effect of substrate-film interface on magnetic properties of Mn_4N films, K.-M. Ching, W.-D. Chang and T.-S. Chin 92 (1996) 471
- Coercivity of $\gamma\text{-(Fe}_{0.74}\text{Mn}_{0.15}\text{Co}_{0.11})_2\text{O}_3$ thin films by dc reactive magnetron sputtering, W.-D. Chang and T.-S. Chin 92 (1996) 475
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- Light emission from the porous boron δ -doped Si superlattice, T.-C. Chang, W.-K. Yeh, M.-Y. Hsu, C.-Y. Chang, C.-P. Lee, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 571
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- Formation of polycrystalline BaTi_2O_7 compounds in barium implanted TiO_2 , S.M.M. Ramos, B. Canut, M. Ambri, N. Bonardi, R. Brenier, M. Pitaval, P. Thevenard and M. Brunel 93 (1996) 191
- Surface phases analysis by grazing incidence of X-rays in a Bragg-Brentano diffractometer, S. Battaglia 93 (1996) 349
- Laser cleaning in art restoration, I. Gobernado-Mitre, J. Medina, B. Calvo, A.C. Prieto, L.A. Leal, B. Pérez, F. Marcos and A.M. de Frutos 96-98 (1996) 474
- Electrical and optical characteristics of organic thin films fabricated by laser ablation, T. Fujii, H. Shima, N. Matsumoto and F. Kannari 96-98 (1996) 625
- Off-axis excimer laser deposition of Ta_2O_5 thin films, N. Inoue, S. Kashiwabara, S. Toshima and R. Fujimoto 96-98 (1996) 656
- Formation of artificially-layered high-temperature superconductors using pulsed-laser deposition, D.P. Norton, B.C. Chakoumakos, D.H. Lowndes and J.D. Budai 96-98 (1996) 672
- Improved properties of Pulsed Laser Deposited YBaCuO on NdGaO_3 using CeO_2 template layers, D.H.A. Blank, A.J.H.M. Rijnders, F.J.G. Roesthuis, G. den Ouden and H. Rogalla 96-98 (1996) 685
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- Anisotropic resistivity in pulsed-laser deposited $\text{Bi}_2\text{Sr}_2\text{CaCu}_2\text{O}_{8+\delta}$ films, S.T. Li, A. Ritzer, S. Proyer, E. Stangl, D. Bäuerle and N. Reschauer 96-98 (1996) 713
- Synthesis of RE-Ba-Sr-Cu-O by pulsed-laser deposition, E. Stangl, S. Proyer, B. Hellebrand and D. Bäuerle 96-98 (1996) 731
- Mirror-smooth $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ superconducting films deposited by plasma-enhanced pulsed laser deposition technique, C.S. Huang, T.Y. Tseng, B.C. Chung, C.H. Tsai, H.F. Cheng and I.N. Lin 96-98 (1996) 735
- Reactive laser deposition of high quality YBaCuO and ErBaCuO films, D. Berling, A. Del Vecchio, S. Acquaviva, D. Bolmont, G. Leggieri, B. Loegel, M. Luisa De Giorgi, A. Luches, A. Mehdaoui and L. Tapfer 96-98 (1996) 739
- Kinetic energy distributions of ions ejected during laser ablation of lead zirconate titanate and their correlation to deposition of ferroelectric thin films, G.C. Tyrrell, T.H. York, L.G. Coccia and I.W. Boyd 96-98 (1996) 769
- Epitaxial ferroelectric PZT and BST thin films by pulsed UV laser deposition, C. Champeaux, P. Marchet and A. Catherinot 96-98 (1996) 775
- Growth and characterization of PLZT films, M.J.M. Gomes, E. de Matos Gomes, P.L.Q. Mantas and J.L. Baptista 96-98 (1996) 779
- Electrical characterization of semiconducting La doped SrTiO_3 thin films prepared by pulsed laser deposition, K.-O. Grosse-Holz, J.F.M. Cillessen and R. Waser 96-98 (1996) 784
- Pulsed laser deposition of novel materials for thin film solid oxide fuel cell applications: $\text{Ce}_{0.9}\text{Gd}_{0.1}\text{O}_{1.95}$, $\text{La}_{0.7}\text{Sr}_{0.3}\text{CoO}_x$ and $\text{La}_{0.7}\text{Sr}_{0.3}\text{Co}_{0.2}\text{Fe}_{0.8}\text{O}_x$, L.G. Coccia, G.C. Tyrrell, J.A. Kilner, D. Waller, R.J. Chater and I.W. Boyd 96-98 (1996) 795
- Ferrimagnetic thin films prepared by pulsed laser deposition, M. Guyot, A. Lisfi, R. Krishnan, M. Porte, P. Rougier and V. Cagan 96-98 (1996) 802
- Pulsed laser deposition of high quality ITO thin films, F. Hanus, A. Jadin and L.D. Laude 96-98 (1996) 807
- Pulsed-laser deposited ZnO for device applications, S.L. King, J.G.E. Gardeniers and I.W. Boyd 96-98 (1996) 811
- Excimer laser ablating preparation of $\text{Ba}_2\text{NaNb}_5\text{O}_{15}$ thin films on KTiOPO_4 substrate and its guide wave property, J.M. Liu, Z.G. Liu, S.N. Zhu, Y.Y. Zhu and N.B. Ming 96-98 (1996) 819

- Pb_{1-x}Ca_xTiO₃ thin films prepared by laser ablation of ceramic targets, M.J. Martín, C. Zaldo and J. Mendiola 96-98 (1996) 823
- Preparation of TiO₂ thin films by pulsed laser deposition for waveguiding applications, C. Garapon, C. Champeaux, J. Mugnier, G. Panczer, P. Marchet, A. Catherinot and B. Jacquier 96-98 (1996) 836
- Pulsed laser deposition of electroceramic thin films, M. Mertin, D. Offenber, C.W. An, D.A. Wesner and E.W. Kreutz 96-98 (1996) 842
- Laser reactive ablation deposition of silicon carbide films, G. Leggieri, A. Luches, M. Martino, A. Perrone, R. Alexandrescu, A. Barborica, E. Gyorgy, I.N. Mihailescu, G. Majni and P. Mengucci 96-98 (1996) 866
- Pulsed Laser Deposition of permanent magnetic Nd₂Fe₁₄B thin films, A.J.M. Geurtsen, J.C.S. Kools, L. de Wit and J.C. Lodder 96-98 (1996) 887
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- X-ray photoelectron diffraction investigation of Ge segregation and film morphology during first stage heteroepitaxy of Si on Ge(001), D. Aubel, L. Kubler, J.L. Bischoff, L. Simon and D. Bolmont 99 (1996) 169
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- Photon and ion beam assisted deposition of titanium nitride, H. Wengenmair, J.W. Gerlach, U. Preckwinkel, B. Stritzker and B. Rauschenbach 99 (1996) 313
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- Preparation of thin silver films on mica studied by XRD and AFM, J.-D. Grunwaldt, F. Atamny, U. Göbel and A. Bäker 99 (1996) 353
- Structural properties of epitaxially grown perfluoro *n*-alkane thin films prepared by vapor deposition, K. Ishida, T. Horiuchi, S. Kai and K. Matsushige 100/101 (1996) 116
- Novel method of strain-relaxed Si_{1-x}Ge_x growth on Si(100) by MBE, H. Iwano, K. Yoshikawa, A. Kojima, K. Hayashi, S. Zaima and Y. Yasuda 100/101 (1996) 487
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- ZnSe crystal growth by radical assisted MOCVD, Y. Hatanaka, T. Aoki, M. Morita and Y. Nakanishi 100/101 (1996) 621
- Preparation of blue-emitting SrGa₂Se₄:Ce thin films by multi-source deposition, Y. Nakanishi, F. Shiba, K. Sowa, H. Tatsuoka, H. Kuwabara, T. Nakamura and Y. Hatanaka 100/101 (1996) 639
- Preparation and photoluminescent characteristics of Zn,Sr_{1-x}S:Ce thin films, S.T. Lee, M. Kitagawa, K. Ichino and H. Kobayashi 100/101 (1996) 656
- ### X-ray emission
- Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
- Porous silicon studied by Si L₂₃ soft X-ray emission, R.S. Crisp, D. Haneman and R. Sabet-Dariani 92 (1996) 198
- Tribochemical characterization of the lubrication film at the Si₃N₄/Si₃N₄ interface sliding in aqueous solutions, F. Honda and T. Saito 92 (1996) 651
- X-ray generation for medical applications from a laser-produced plasma, M. Grätz, C. Tillman, I. Mercer and S. Svanberg 96-98 (1996) 443
- Soft X-ray emissions by highly charged ions on solid surfaces: Mo and Ta surfaces, T. Emoto, K. Komatsu, A. Ichimiya, S. Ninomiya and M. Sekiguchi 100/101 (1996) 355
- ### X-ray fluorescence
- Nucleation and growth of CVD-W on TiN studied by X-ray fluorescence spectrometry, M.S. Marangon, G. Queirolo and C. Savoia 91 (1995) 157
- ### X-ray scattering
- In situ X-ray reflectivity measurement of thin film growth during vacuum deposition, C.-H. Lee and S.-Y. Tseng 92 (1996) 282

Investigation of the solid surface structural inhomogeneities by the 'combined' small-angle X-ray scattering and Hg porosimetry methods, L.I. Skatkov, P.G. Cheremskoy, V.P. Gomofov and B.I. Bayrachny

99 (1996) 367

X-ray spectroscopy

Characterization of low temperature GaAs grown by molecular beam epitaxy, W.C. Lee, T.M. Hsu, J.-I. Chyi, G.S. Lee, W.-H. Li and K.C. Lee

92 (1996) 66

Depth-dependent non-destructive analysis of thin overlayers using total-reflection-angle X-ray spectroscopy, N. Shibata, S. Okubo and K. Yonemitsu

100/101 (1996) 69

A nondestructive analysis technique for residual thin films in deep-submicron contact holes, K. Ninomiya, T. Kure, Y. Sudo, K. Kuroda and H. Todokoro

100/101 (1996) 551

Yttrium

Electrosynthesis of yttrium chalcogenides from a non-aqueous bath, U.K. Mohite and C.D. Lokhande

92 (1996) 151

Electrical properties of laser deposited $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ films on silicon wafers, F.Y. Chuang, C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin

92 (1996) 452

Work function variations and oxygen conduction in a $\text{Pt}(\text{ZrO}_2(\text{Y}_2\text{O}_3))\text{Pt}$ solid electrolyte cell, N.G. Torkelsen and S. Raaen

93 (1996) 199

Zr-silicide formation during the epitaxial growth of Y-stabilized zirconia films on Si(100) and its avoidance by ion beam assisted deposition at a reduced temperature, T. Koch and P. Ziemann

99 (1996) 51

Zinc

Epitaxial growth of $\text{ZnSe}_x\text{Te}_{1-x}$ by the VPE method and its photoluminescence, K. Mochizuki, H. Oguri, T. Kyotani and M. Isshiki

92 (1996) 79

Growth of ZnSe thin films by radical assisted MOCVD method, T. Aoki, M. Morita, S. Wickramanayaka, Y. Nakanishi and Y. Hatanaka

92 (1996) 132

Growth of Zn δ -doped $\text{Al}_x\text{Ga}_{1-x}\text{As}$ ($x = 0-0.65$) by low pressure metal organic vapour phase epitaxy, G. Li and C. Jagadish

92 (1996) 138

Sprayed films of stannite $\text{Cu}_2\text{ZnSnS}_4$, N. Nakayama and K. Ito

92 (1996) 171

The influence of residual O_2 gas in vacuum on the structural and luminescent properties of $\text{ZnF}_2\text{:Mn}$ thin films, Y. Nakanishi, S. Naito, T. Nakamura, Y. Hatanaka and G. Shimaoka

92 (1996) 400

Band lineup modification by Ge interlayer deposition at II-VI/III-V semiconductor heterojunctions, P. Rodríguez-Hernández, M. González-Díaz, M. Fuentes-Cabrera, A. Mujica and A. Muñoz

92 (1996) 408

Stimulated blue emission processes in $\text{Zn}_{1-x}\text{Cd}_x\text{Se/ZnSe}$ multi-quantum wells, J.Y. Jen, T. Tsutsumi, I. Souma, Y. Oka, J.R. Anderson and M. Gorska

92 (1996) 547

An investigation of the Cu/ZnO/Zn system: evidence for the formation of Cu-Zn alloys by the inward diffusion of Cu, K.R. Harikumar, A.K. Santra and C.N.R. Rao

93 (1996) 135

Preferential vaporization and plasma shielding during nano-second laser ablation, X. Mao, W.-T. Chan, M. Caetano, M.A. Shannon and R.E. Russo

96-98 (1996) 126

XeCl laser ablation of thin film ZnS, W.M. Cranton, P.H. Key, D. Sands, C.B. Thomas and F.X. Wagner

96-98 (1996) 501

Study of the composition and morphology of initial stages of corrosion products formed on Zn plates exposed to the atmosphere of southeast Mexico, P. Quintana, L. Veleza, W. Cauch, R. Pomes and J.L. Peña

99 (1996) 325

Growth of high-quality ZnTe layers by MOVPE, S.I. Gheyas, S. Hirano, M. Nishio and H. Ogawa

100/101 (1996) 647

Preparation and photoluminescent characteristics of $\text{Zn}_{1-x}\text{Sr}_x\text{S:Ce}$ thin films, S.T. Lee, M. Kitagawa, K. Ichino and H. Kobayashi

100/101 (1996) 656

XPS analysis of chemically etched II-VI semiconductor surfaces, A. Kita, M. Ozawa and C.D. Gutleben

100/101 (1996) 652

Zinc oxide

Characteristics of spray pyrolytic ZnO thin films, C.H. Lee and L.Y. Lin

92 (1996) 163

Pulsed-laser deposited ZnO for device applications, S.L. King, J.G.E. Gardeniers and I.W. Boyd

96-98 (1996) 811

Characterization of ZnO thin films deposited by laser ablation in reactive atmosphere, P. Verardi, M. Dinescu and A. Andrei

96-98 (1996) 827

Zinc selenide

- Structural and optical characteristics of pulsed laser deposited ZnSe epilayers, A. Chergui, J.L. Deiss, J.B. Grun, J.L. Loison, M. Robino and R. Beserman 96-98 (1996) 874
- ZnSe crystal growth by radical assisted MOCVD, Y. Hatanaka, T. Aoki, M. Morita and Y. Nakanishi 100/101 (1996) 621
- Correlation between cathodoluminescence and structural defects in ZnS/GaAs(100) and ZnSe/GaAs(100) studied by transmission electron microscopy, T. Mitsui, N. Yamamoto, J. Yoshino, T. Tadokoro, S. Ohta, K. Yanashima and K. Inoue 100/101 (1996) 625

Zinc telluride

- Aluminum doping of ZnTe grown by MOVPE, S.I. Gheyas, S. Hirano, M. Nishio and H. Ogawa 100/101 (1996) 634

Zirconium

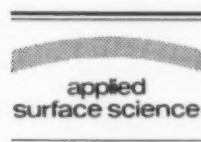
- Work function variations and oxygen conduction in a Pt(ZrO₂(Y₂O₃))Pt solid electrolyte cell, N.G. Torkelsen and S. Raaen 93 (1996) 199

- Pulsed field desorption mass spectrometric study of the oxidation of hydrogen-doped Ni₁Zr, T.R. Hess, D.L. Cocke, G. Abend and J.H. Block 94/95 (1996) 238
- LEED and XPS studies of the ZrO/W(100) surface, H. Satoh, H. Nakane and H. Adachi 94/95 (1996) 247
- Characterization of sputter-deposited multilayers of Ni and Zr with APFIM/TAP, T. Al-Kassab, M.-P. Macht, V. Naundorf, H. Wollenberger, S. Chambrelaud, F. Danoix and D. Blavette 94/95 (1996) 306
- Zr-silicide formation during the epitaxial growth of Y-stabilized zirconia films on Si(100) and its avoidance by ion beam assisted deposition at a reduced temperature, T. Koch and P. Ziemann 99 (1996) 51
- The surface and interface reaction of metal thin film on sapphire substrate, H.J. Kang, C.H. Kim, N.S. Park and M.W. Kim 100/101 (1996) 160
- Behavior of zirconium on ZrO/W(100) surface, H. Satoh, H. Nakane and H. Adachi 100/101 (1996) 216
- Preferential sputtering and surface segregation of CuZr alloys, H.J. Kang, C.H. Kim, N.S. Park, D.J. O'Connor and R. MacDonald 100/101 (1996) 329
- Electrical properties of metal/Si_{1-x}Ge_x/Si(100) heterojunctions, H. Shinoda, M. Kosaka, J. Kojima, H. Ikeda, S. Zaima and Y. Yasuda 100/101 (1996) 526



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Applied Surface Science MI 91-101 (1995) 134-136



List of terms used in the subject index

- | | |
|-----------------------------|-----------------------------------|
| Ablation | Cobalt |
| Acoustic effects | Computer simulations |
| Alkali halides | Copper |
| Alkali metals | Corrosion |
| Alloys | |
| Aluminium | Depth profiling |
| Aluminium oxide | Deuterium |
| Ammonia | Diamond |
| Amorphous materials | Doping effects |
| Annealing | |
| Antimony | Electrical properties |
| Arc evaporation | Electron diffraction |
| Argon | Electron emission |
| Arsenic | Electron energy loss spectroscopy |
| Atomic force microscopy | Electron microscopy |
| Atomic probe analysis | Electron spin resonance |
| Auger electron spectroscopy | Electron stimulated desorption |
| | Ellipsometry |
| Barium | Emission |
| Bismuth | Epitaxy |
| Borides | Etching |
| Boron | Evaporation |
| Boron nitride | |
| | Field desorption |
| Cadmium | Field effect |
| Cadmium sulphide | Field electron microscopy |
| Cadmium telluride | Field emission |
| Calcium | Field emission microscopy |
| Calcium fluoride | Field ion microscopy |
| Carbides | Field ionisation |
| Carbon | Fluorescence |
| Carbon monoxide | Fullerenes |
| Catalysis | |
| Ceramics | Gallium |
| Cerium | Gallium antimonide |
| Chalcogenides | Gallium arsenide |
| Chemical vapour deposition | Gallium phosphide |
| Chromium | Gallium selenide |
| Clusters | |

- Germanium
Glass
Gold
Graphite

Hafnium
Halides
Hall effect
Halogenides
Halogens
Heterostructures
Hydrocarbons
Hydrogen

Indium
Indium arsenide
Indium phosphide
Infrared spectroscopy
Interfaces
Ion bombardment
Ion implantation
Ion scattering
Iron

Langmuir-Blodgett structures
Laser processing
Lead
Low energy electron diffraction
Luminescence

Magnesium
Magnesium oxide
Magnetic measurements
Magnetic structures
Manganese
Mass spectroscopy
Mercury
Metal-oxide-semiconductor structure (MOS)
Metals
Metal-semiconductor interfaces
Methane
Mica
Molecular beam epitaxy
Molecular dynamics
Molybdenum
Monte Carlo simulations
Mössbauer spectroscopy
Multilayers

Nickel
Niobium
Nitric oxide
Nitrides
Nitrogen
Nitrogen dioxide
Nitrous oxide
Noble gases
Nuclear reaction analysis

Optical properties
Organic substances
Organometallic vapour deposition
Oxidation
Oxides
Oxygen
Oxynitrides
Ozone

Palladium
Phase transitions
Phosphorus
Photochemistry
Photoconductivity
Photodesorption
Photoelectron emission microscopy
Photoelectron spectroscopy
Photoemission
Photoexcitation
Photon emission
Plasma processing
Platinum
Polymers
Pulsed laser ablation
Pulsed laser deposition

Quantum effects
Quartz

Raman scattering
Rare earth metals
Rhenium
Rhodium
Ruthenium

Scanning tunneling microscopy
Schottky barrier
Secondary ion mass spectrometry

- Selenium
- Semiconductors
- Silane
- Silica
- Silicides
- Silicon
- Silicon carbide
- Silicon nitride
- Silicon oxide
- Silver
- Solar cells
- Sputter deposition
- Sputtering
- Steel
- Strontium
- Sulphides
- Sulphur
- Sulphur dioxide
- Superconductors
- Superconductivity
- Superlattices
- Surface composition
- Surface conductivity
- surface diffusion
- Surface morphology
- Tantalum
- Tellurium
- Thallium
- Thermal desorption
- Thin films
- Time of flight techniques
- Tin
- Tin oxide
- Titanium
- Titanium dioxide
- Titanium nitride
- Titanium oxide
- Transition metals
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MASTER INDEX

Volumes 91-101

Author index	1
Subject index	39
List of terms used in the subject index	134



0169-4332(1996)91/101;1-E

